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Norbain House, Boulton Road, Reading, Berkshire, RG2 0LT Tel: (0734) 866766, Telex: 847203

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INTRODUCTION

Silicon General is committed to innovative excellence in the manufacture of integrated circuits. A unique combination of design and processing skills developed over the past ten years results in the continual generation of leadership solid state products.

All Silicon.General devices are processed in the finest facilities available in strict accordance with the requirements of MIL-STD-883 level B and a complete range of screening and testing capabilities to higher levels is available.

This book describes Silicon General's complete line of products and includes information which will allow you to both specify and apply these products. Also included is a section describing our quality and reliability program.

If you need more information on these products or on other applications, please contact the nearest Silicon General representative listed in the back of this product catalog.







Product Selector Guide

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117A/217A/317A
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138A/238A/338A 723/723C
723/723C
1532/2532/3532
Negative Adjustable
104/204/304
137/237/337
137HV/237HV/337HV
Dual Tracking Adjustable
1502/2502/3502
Dual Tracking
1501A/2501A/3501A
1568/1468
4501
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*SG238 *SG239 SG250 SG301A	UA239 UA301A	LM239 LM250	LM239 LM250 LM301A	LM239 LM301A	
SG304 SG305 SG305A	UA305 UA305AC	LM304 LM305	LM304 LM305 LM305A	Lincont	
SG307 *SG309 *SG310 SG311 SG317 SG320-05 SG320-08 SG320-12	UA309 UA311 UA317 UA7905 UA7908 UA7912	LM309 LM310 LM311 LM317 MC7905 MC7908 MC7912	LM307 LM309 LM310 LM311 LM317 LM320-05 LM320-12	LM307 LM311 LM317 UA7905 UA7908 UA7912	
SG320-15 SG320-18 SG323 SG324 SG333	UA7915 SH323 UA324 SH333	MC7915 MC7918 LM323 LM324 LM333	LM7912 LM320-15 LM323 LM324 LM333	UA7915 UA7918 LM324	
SG337 SG338 SG340-05	UA7805	LM337 LM340-05	LM337 LM338 LM7805	LM337 LM340-05 TL780-05C	
SG340-06	UA7806	MC7806 LM340-06 MC7808		UA7806 LM340-06 UA7808	
SG340-08 SG340-12	UA7808 UA7812	LM340-08 MC7812 LM340-12	LM7812 LM340-12	LM340-08 UA7812 LM340-12	
SG340-15	UA7815	MC7815 LM340-15	LM7815 LM340-15	TL780-12C UA7815 LM340-15 TL780-15C	
SG340-18 SG340-20 SG340-24	UA7818 UA7824	MC7818 LM340-18 MC78M20 MC7824 LM340-24		UA7818 LM340-18 UA78M20 UA7824 LM340-24	
SG350		LM350	LM350		

						
Silicon General	Fairchild	Motorola	National	Texas Inst.	Sprague	
*SG555	UA555	MC1455 MC1555	LM555	NE555 SE555		
*SG556	UA556	MC3456 MC3556	LM556	NE556 SE556		
SG723	UA723	MC1723	LM723	UA723		
*SG733	UA733	MC1733 MC1741	LM733 LM741	UA733 UA741		
SG741 *SG741S	UA741	MC1741 MC1741S	LIV1741	04/41		
*SG747	UA747	MC1747	LM747	UA747		
SG1436		MC1436	LM1436			
*SG1458	UA1458	MC1458	LM458			
SG1468 *SG1488	UA1488	MC1468 MC1488	DS1488	MC1488 SN55188		
*SG1489	MC1489	DS1489	SN55189	SN75189		
SG1489A	UA1489A	MC1489A	DS1489A	SN55189A SN75189A		
SG1495 SG1496		MC1495 MC1496 MC1596	LM1496 LM1596			
SG1503		MC1503	LM1524	SG1524		
SG1524 SG1525A		SG1525A	LIVI 1024	001024		
SG1526		SG1526			UL58126	
SG1527A SG1536 *SG1558	UA1558	SG1527A MC1536 MC1588	LM1536 LM1558	MC1558		
SG 1568 SG 1595 SG 1596	UA796	MC1568 MC1595 MC1596	LM1596			
SG2001				ULN2001	ULN2001	
SG2002				ULN2002	ULS2001 ULN2002 ULS2002	
SG2003		1		ULN2003	ULN2003 ULS2003	
SG2004				ULN2004	ULN2004 ULS2004	
SG2021					ULN2021 ULS2021	
SG2022					ULN2022 ULS2022	
SG2023					ULN2023 ULS2023 ULN2024	
SG2024 SG2064W				ULN2064	ULS2024 ULS2024 ULN2064	
SG2065W				ULN2065	ULS2064 ULN2065	
SG2066W				ULN2066	ULS2065 ULN2066	
SG2067W				ULN2067	ULS2066 ULN2067	
SG2068W				ULN2069	ULS2067 ULN2068 ULS2068	
SG2069W				ULN2069	ULN2069 ULS2069	
SG2070W					ULN2070 ULS2070	
SG2071W					ULN2071 ULS2071	
SG2074W		ULN2074		ULN2074 ULN2075	ULN2074 ULS2074 ULN2075	
SG2075W SG2076W				ULN2075	ULS2075 ULS2075	
SG2077W					ULS2076 ULN2077	
SG2524			LM2524	SG2524	ULS2077	
SG2525A SG2526 SG2527A *SG3059 *SG3079		SG2525 SG2526 SG2527A CA3059 CA3079			ULN8126	
*SG3146		MC3423	LM3146	MC3423		
SG3423 SG3503		MC3423 MC1503	1	100423		
SG3523 SG3524 SG3525A		MC3523 SG3525A	LM3524	MC3523 SG3524 SG3525A		
				<u> </u>		

Silicon General	Fairchild	Motorola	National	Texas Inst.	Sprague
SG3526		SG3526			ULN8126
SG3527A		SG3527A		SG3527A	
SG3821	UA3086	MC3386	LM3086		ULN2046
					ULN2086
SG3822		CA3054			ULN2054A
SG3851				SN75466	ULN2001
				ULN2001	ULS2001
SG4250			LM4250		
*SG6118					UDN6118
0.07005	114 7005	1107007		-	ULN6118
SG7805 SG7805A	UA7805 UA7805A	MC7805	LM7805		
SG7805A	UA7805A	MC7806		UA7806	
SG7808	UA7808	MC7808		UA7808	
SG7812	UA7812	MC7808 MC7812	LM7812	UA7806	
SG7815	UA7815	MC7815	LM7812	UA7812	
SG7818	UA7818	MC7818	LINITOIS	UA7815	
SG7824	UA7824	MC7824		UA7824	
SG7905	UA7905	MC7905	LM7905	UA7905	
SG7908	UA7908	MC7908	Lini ooo	UA7908	
SG7912	UA7912	MC7912	LM7912	UA7912	
SG7915	UA7915	MC7915	LM7915	UA7915	
			LM320-15		
SG7918		MC7918		UA7918	
SG55236				SN55236	
SG55325		MC55325	DS55325	SN55325	
SG75325		MC75325	DS75325	SN75325	
SG55326				SN55326	

Silicon General	Fairchild	Motorola	National	Texas Inst.	Sprague
SG75326				SN75326	
SG55327				SN55327	
SG75327				SN75327	
SG55450	55450			SN55450	
SG75450	75450	MC75450	DS75450	SN75450	
SG55460				SN55460	
SG75460				SN75460	
*SG55451			DS55451	SN55451	
*SG75451	7541A	MC75451	DS75451	SN75451	
*SG55461			DS55461	SN55461	
*SG75461	75461	MC75461	DS75461	SN75461	
*SG55452	55452		DS55452	SN55452	
*SG75452	75452	MC75452	DS75452	SN75452	
*SG55462			DS55462	SN55462	
*SG75462	75462	MC75462	DS75462	SN75462	
		MC75402			
*SG55453	55453		DS55453	SN55453	
*SG75453	75453		DS75453	SN75453	
*SG55463			DS55463	SN55463	
*SG75463		MC75463	DS75463	SN75463	
*SG55454			DS55454	SN55454	
*SG75454		MC75454	DS75454	SN75454	
*SG55464			DS55464	SN55464	
*SG75464			SG75464	SN75464	
*SG55470	55470	MC55470	DS55470	SN55470	
*SG75470	75470	MC75470	DS75470	SN75470	•
*SG55471	55471	MC55471	DS55471	SN55471	
*SG75471	75471	MC75471	DS75471	SN75471	

*Not Recommended for New Design

Silicon General	Unitrode	Silicon General	Unitrode
SM600	PIC600	SM635A	PIC7528
SM601	PIC600	SM636A	PIC7529
SM602	PIC602	SM637A	PIC7530
SM610	PIC610	SM645A	PIC7531
SM611	PIC611	SM646A	PIC7532
SM612	PIC612	SM647A	PIC7533
SM625	PIC625	SM655A	PIC7534
SM626	PIC626	SM656A	PIC7535
SM627	PIC627	SM657A	PIC7536
SM635	PIC635	SM600B	PIC7501
SM636	PIC636	SM601B	PIC7502
SM637	PIC637	SM602B	PIC7503
SM645	PIC645	SM610B	PIC7504
SM646	PIC646	SM611B	PIC7505
SM647	PIC647	SM612B	PIC7506
SM655	PIC655	SM625B	PIC7507
SM656	PIC656	SM626B	PIC7508
SM657	PIC657	SM627B	PIC7509
SM600A	PIC7519	SM635B	PIC7510
SM601A	PIC7520	SM636B	PIC7511
SM602A	PIC7521	SM637B	PIC7512
SM610A	PIC7522	SM645B	PIC7513
SM611A	PIC7523	SM646B	PIC7514
SM612A	PIC7524	SM647B	PIC7515
SM625A	PIC7525	SM655B	PIC7516
SM626A	PIC7526	SM656B	PIC7517
SM627A	PIC7527	SM657B	PIC7518

PACKAG	E SUFFIXES	Silicon General	MSC	Signatics	Fairchild	Motorola	TI	RCA	AMD	Reytheon	Sprague
	Plastic DIF 8-Lead 14, 16 and 18 Lead	M . N	N	V A B	T P	P	P	E	PC PC	N DN DP MP	M A
b≞ ĭ₩	TO 220	Р	T	U	ษ	т	кс				т
	Low Temperature Glass Hermetic Flat Pack	F	*		F	F	*		FM		L
4	TO-66 3 Lead 5 Lead 9 Lead	R				Ŗ				R TK	
Į∎	Giass/Metai Fiat-Pack	F	F	۵	F	F	F	ĸ	F	J F Q	
Ē	TO-5, TO-39, TO 96, TO-99, TO-100 and TO-101	т	н	т к L D18	н	G	L	s. v1	н	т	D K
	Ceramic DIP 8-Less Ceramic DIP 14, 16 and 18 Less	,		F	D	U	L			DC DD	R
40	TO 3 (Steel)	ĸ	к					ĸ		×	
\odot	(Aluminum)		ĸc	DA	ĸ	ĸ	к			LK	
THE REAL PROPERTY AND IN THE REAL PROPERTY AND INTERPORTY.	SIP -	s									w
	L dadiess Package	L			L		FC	LH	L		
 mmmi	Batwing	w					NE				8
6											

Processing and Assembly Flow

The following outline describes the standard production processing procedures used exclusively at Silicon General to insure that all hermetically sealed products are manufactured in full conformance to the requirements of MIL-STD-883, Class B as a minimum.



Post-Assembly Screening Procedures

Silicon General manufactures products to the three standard levels of quality assurance processing outlined below. In addition, the company's unique flexibility allows ready accommodations to special customer requirements. The following screening procedures are in full compliance to MIL-M-38510 and all methods are as detailed in MIL-STD-883, Methods 5004 and 5005.

	MIL-STD-883, CL/		MIL-STD-883, CL		STANDARD PROL	DUCT
SCREEN	METHOD	REQMT	METHOD	REQMT	METHOD	REOMT
Wafer Lot Acceptance	5007	Sample				
Non-Destructive Bond Pull	2023	100%				
Internal Visual Pre-Cap	2010, Condition A	100%	2010, Condition B	100%	2010, Condition B	100%
High Temperature Storage	1008, Condition C 24 Hours @ 150°C	100%	1008, Condition C 24 Hours @ 150°C	100%	1008, Condition C 24 Hours @ 150°C	100%
Temperature	1010. Condition C	100%	1010, Condition C	100%	1010. Condition C	100%
Cycling	10 Cycles, -65°C to +150°C	100 /0	10 Cycles, -65°C to +150°C		10 Cycles, -65°C to + 150°C	100 /0
Constant	2001, Condition E	100%	2001, Condition E	100%	2001, Condition E	100%
Acceleration	30,000 g, Y ₁ orientation		30,000 g, Y ₁ orientation		30,000 g, Y1 orientation	
Particle Impact	2020 Test Condition					
Noise Detection (PIND)	A					
Hermeticity a) Fine Leak	1014, Condition B 5 x 10 ⁸ atm-cc/sec	100%	1014, Condition B 5 x 10 ⁻⁸ atm-cc/sec	100%	1014, Condition B 5 x 10 ⁻⁷ atm-cc/sec	Sample
b) Gross Leak	1014, Condition C2	100%	1014, Condition C2	100%	1014, Condition C2	Sample
Pre-Burn-in	Per Applicable Pro-	100%	Per Applicable	100%		
Electrical	curement Document		Procurement			
Test	Unit Serialization as required		Document			
Burn-in Test	1015, Dynamic	100%	1015, Static or	100%		
	240 Hours @ 125° C		Dynamic			
	(Note: An additional		168 Hours @ 125° C			
	72 Hours HTRB					
	burn-in and interim					
	electrical test as required)					
Final Electrical	Per Applicable		Per Applicable		Per Applicable	
Test	Procurement		Procurement		Procurement	
	Document		Document		Document	
a) DC @ 25°C		100%		100%		100%
b) DC @ Max		100%		100%		
and Min Rated						
Temperature c) Dynamic @ 25°C		100%		100%		
d) Functional @ 25°C		100%		100%		100%
Hermeticity	1014, Condition B	100%				
a) Fine Leak	5 x 10 ⁻⁸ , atm-cc/sec					
b) Gross Leak	1014, Condition C2	100%				
Radiographic	Method 2012	100%				
External Visual	Method 2009	100%	Method 2009	100%	Method 2009	100%
Quality Confor- mance Testing	5005		5005			
Group A	DC, AC Parameters	+25°C +125°C 55°C	DC, AC Parameters	+25°C +125°C -55°C	DC Parameters	+25°C
Groups B, C*, D	5005 Paragraph	3.5	5005 Paragraph	3.5		
	5005 Faidyiapii	0.0	1 5005 Falagraph	0.0	1	

*Class B only.

MIL-M-38510 Qualification and

The following Group B, C and D tests are performed on a periodic basis or when specified by the customer. This testing is in full compliance to MIL-M-38510 as detailed in MIL-STD-883, Method 5005, and although Class B quality level is shown below, other Class levels are also available.



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Quality Conformance Inspection



★★★★ FIVE-STAR PROGRAM

FOR PLASTIC INTEGRATED CIRCUITS

The increased reliability of a 5 Star device will help you eliminate the high cost of circuit failure — an expense which can include the price of assembly rework, system downtime, service calls and customer goodwill. Costs that can range from \$35 to \$350 are not uncommon.

Silicon General's 5 Star Program removes marginal devices before shipment at a relatively low cost to you. This extra screening is done during the last stage of production and results in the highest levels of performance reliability, insuring customer satisfaction.

QUALITY IS a product's degree of conformance to its specified parameters. It pertains to the probability of defective units exisiting in a given lot when received by the user. Although zero percent defective is a goal, there will usually be some percentage of defective units in any lot of mass produced items. The number of defec- tive units received by the user is a functiuon of the outgoing inspection criteria used by the supplier.	
	RELIABILITY IS a measurement of how well an initially good device will perform over time to its specified characteristics. Semiconductor failures primarily occur duing the early life phase of operation. After this phase, a low failure rate can be expected until the wear-out phase is even- tually reached. Overall system reliability is improved if these early life failures are removed prior to system use.

TEST PROCEDURES $\star \star \star \star \star$

- STABILIZATION BAKE. This is a process designed to stabilize electrical drift and accelerate chemical degradation such as surface contamination. It is a four hour bake at +175°C without electrical stress applied (similar to MIL-STD-883, Method 1008).
- TEMPERATURE CYCLE. This is a screening process designed to mechanically stress the integrated circuit by alternately heating and cooling it. Potential failures are: bond failure, cracked packages or chips, etc. This process consists of ten cycles with ten minutes of dwell at -65C and at +150°C (air/air), with a maximum transfer time of five minutes (MIL-STD-883, Method 1010, condition C).
- BURN-IN. The burn-in is performed specifically to screen out marginal devices, those with inherent defects, or defects resulting from manufacturing deviations which can cause time or stress-dependent failures. Without this conditioning, marginal circuits which initially meet all specifications could result in early lifetime failures under normal operating conditions. The test is conducted 100% under electrical stress conditions (similar to MIL-STD-883, method 1015) such as:

Type of Device	Electrical Stress
Bipolar Interface	Steady State Reverse Bias
Linear Devices	Steady State Forward Bias

 QUALITY CONTROL AUDIT. A product's outgoing quality level from the manufacturer determines the probability of a user receiving defective units. Sampling procedures for 5 Star Integraded Circuits assures a tighterthan-normal outgoing quality level.

OUTLINE OF 5 STAR PROCEDURE

Silicon General Processing Flow Pre-Conditioned Plastic Assembly

Wafer Fabrication

Elecrical Test Wafer Probe

Plastic Assembly & Processing

100% Dice Visual Inspection MIL-STD-883, Method 2010

100% Premold Visual Inspection MIL-STD-883, Method 2010

Stabilization Bake

Temperature Cycle

MIL-STD-883, Method 1010 (10 Cycles -65 to +150°C)

Electrical Test 100% D.C. +25°C/Temperature Extremes Burn-in 100% at 125°C Or Equivalent Electrical Test 100% D.C., 25°C/Temperature Extremes PDA = 5%Exceeds PDA = 5%Re-Burn in 100%. 125°C Electrical Test 100% D.C. $+25^{\circ}$ C. PDA =2%MEETS PDA = 2%Quality Control Visual/Mechanical Electrical D.C., A.C. @+25°C LTPD = 3, (SS = 76, Acc = 0) SHIP

PROBABILITY OF FAILURE AS A FUNCTION OF TIME



RELATIVE FAILURE RATE vs. TIME

ORDERING INFORMATION:

All processed Silicon General Integrated Circuits are branded with the Silicon General 5-Star Trademark. The 5-Star identifies parts subject to the screening program for extra reliability. Devices processed in the 5-Star Burn-in Program are specified by adding the suffix ''5 S'' to the end of the part number. For example, to order SG3524 with this processing, specify SG3524N5S.

NOTE: The 5-Star Program is available on selected products. Please contact Silicon General or its local representatives to discuss your specific product interests.

VOLTAGE REGULATORS

Positive Adjustable Regulators Negative Adjustable Regulators 3-Terminal, Adjustable Regulators 3-Terminal, Fixed Positive Regulators 3-Terminal, Fixed Negative Regulators 3-Terminal, 3-Amp Regulators Precision Negative Regulators Dual Polarity Tracking Regulators Adjustable Dual Polarity Regulators

SG LINEAR VOLTAGE REGULATORS

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AMPS	TYPE	P/N	PACKAGE	VOLTAGE
5.0	POS. ADJ.	SG138	TO-3 (K)	+1.2 to +32
3.0	POS. FIXED POS. ADJ.	SG123 SG153 SG150	TO-3(K)	+5 +5, 12, 15 +1.2 to +33
		SG109		+5
	POS. FIXED	SG140		+5, 6, 8, 12, 15,
		SG7800		18, 20, 24
1.5	POS. ADJ.	SG117	ТО-3 (К)	+1.2 to +37
1.5	F03. ADJ.	SG117HV	TO-66 (R) TO-220 (P)	+1.2 to +57
		SG120		-5, 5.2, 8, 12,
	NEG. FIXED	SG7900A		15, 18, 20
		SG137		-1.2 to -37
	NEG. ADJ.	SG137HV		-1.2 to -47
	L			
	POS. FIXED	SG109 SG140		+5
	POS. FIXED	SG7800		+5, 6, 8, 12, 15,
	POS. ADJ.	SG117		18, 20, 24 +1.2 to +37
0.5		SG117HV	TO-39 (T)	+1.2 to +57
		SC120		
	NEG. FIXED	SG7900		15, 18, 20
	NEG. ADJ.	SG137		-1.2 to -37
	NEG. ADJ.	SG137HV		-1.2 to -47
0.2	DUAL TRACK	SG1501	TO-100 (T) DIP (J,N)	±15
0.15	POS. ADJ.	SG723	TO-96 (T) DIP (J)	+2 to +37
	DUAL TRACK ADJ.	SG1502	DIP (J)	+10 to ±28
0.1	POS. ADJ.	SG1532	TO-96 (T) DIP(J)	+2 to+38
	DUAL TRACK	SG1568/	TO-100 (T)	
		1468	DIP (J) TO-66 (R)	±15
0.025	NEG. ADJ.	SG104	TO-100 (T)	-0.015 TO -40
0.020	POS. ADJ.	SG105	TO-99 (T) DIP (Y)	+4.5 TO +40
0.010	PRECISION REFERENCE	SG1503	TO-39 (T) DIP (Y)	+ 2.5V

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

SG104/204/304

Negative Voltage Regulators

This circuit is a negative voltage regulator designed for both linear and switching applications. It is a complement of the SG 100/200/300, SG 105/205/305 and SG 723/723C intended for systems requiring regulated negative voltages having a common ground with the unregulated supply. With an input voltage rating of up to 50V, this device will deliver load currents to 25mA. Adding external transistors will increase the current capability to greater than 10 amps and further improve regulation.

- Output voltage adjustable from 15mV to 40V
- 1mV regulation no load to full load
- 0.01%/V line regulation
- 1% maximum temperature variation

PARAMETERS*	104	204	304	UNITS	
Operating Temperature Range	-55 to +125	-25 to +85	0 to +70	°C	
Package Types		т			
Input Voltage Range	-50 to	-8	40 to8	v	
Output Voltage Range	-40 to	-0.015	-30 to -0.035	v	
Input/Output Differential In = 20 mA ¹	2.0 to 5	0	2.0 to 40	v	
Load Regulation ² $0 \le I_0 \le 20$ mA, R _{sc} = 15 Ω		5mV			
Line Regulation 3 Vout $\leq -5V$ $\Delta V_{in} = 0.1 V_{in}$	0.1			%	
Ripple Feed thru C ₁₉ = $10\mu f$, f = $120Hz$, $-7V \le V_{in} \le -15V$	1.0		1.0	mV/V	
Output Voltage Scale Factor R ₂₃ = 2.4kΩ	1.8 to 2.2		1.8 to 2.2	V/kΩ	
Temperature Stability Vo ≤ -1V	1.0		1.0	%	
Output Noise Voltage C ₁₉ = 0μ F BW = 10Hz to 10KHz V ₀ $\leq -5V$	0.007 (typ)		0.007 (typ)	%	
Standby Current Drain $V_0 = 0$, $I_1 = 5 \text{ mA}$	2.5		2.5	mA	
Long Term Stability Vo < -1V	1.0		1.0	%	

*Parameters apply at junction temperatures equal to or less than operating temperature range unless otherwise specified. The line and load regulation specifications are for constant junction temperature. Temperature drift effects must be taken into account separately when the unit is operating under conditions of high dissipation.

¹With I_0 = 5 mA, min differential is 0.5V. With external transistors differential is increased, in the worst case, by approx. 1V.

²Output current and load regulation can be improved with external transistors. Improvement factor will be approx, equal to the composite current gain of added transistors.

³With zero output, the dc line regulation is determined from the ripple rejection. Hence, with output voltages between 0 volts and -5 volts, a dc output variation, determined from the ripple rejection, must be added to find the worst-case line regulation.



SG104/204/304 Chip (See T-package diagram for pad functions)

CONNECTION DIAGRAM







Silicon General LINEAR INTEGRATED CIRCUITS

Positive Voltage Regulators

This circuit is a positive voltage regulator designed for both linear and switching applications. Inherent component tracking of the monolithic integrated circuit process provides a high degree of stability and accuracy in addition to fast response to both line and load transients. With an input voltage rating of up to 50V, this device will deliver load currents of 20mA (45mA with 305A). Adding external transistors will increase the current capability to greater than 10 amps and further improve regulation.

SG105/205/305/305A

- . Output voltage adjustable from 4.5 to 40V
- Load regulation better than 0.01%/mA
- Line regulation better than 0.06%/V
- Ripple rejection of 0.01%/V
- 1.0% maximum temperature variation .

PARAMETERS*	105	205	305	305A	UNITS	
Operating Temperature Range	-55 to +125	-25 to +85	0 to +70	0 to 70	°C	
Package Types	T, J, Y	T, J, Y	, M, N	т	-	
Input Voltage Range	8.5	to 50	8.0 to 40	8.5 to 50	V	
Output Voltage Range	4.5	to 40	4.5 to 30	4.5 to 40	v	
Input/Output Differential	3.0	to 30	3.0 to 30	3.0 to 30	v	
Load Regulation	0.1	2,3	0.1 ^{2,3}	2.0 ^{2,3}	%	
$V_{in} - V_{out} \le 5V$			0.06			
Line Regulation $V_{in} - V_{out} > 5V$			0.03	%/V		
Ripple Feed thru Cref = 10µf, f = 120Hz	0.01		0.01	0.003 (typ)	%/V	
Temperature Stability	1.0		1.0	1.0	%	
Output Noise Voltage						
(10 Hz < f < 10 KHz, C _{ref} = 0)	0.005 (typ)		0.005 (typ)	0.005 (typ)	%	
Feedback Sense Voltage	1.7	(typ)	1.7 (typ)	1.55 to 1.85	v	
Standby Current Drain	2.0		2.0	2.0	mA	
Minimum Load Current	0	0		0	mA	
Long Term Stability	1.0		1.0	1.0	%	

*Parameters apply at junction temperatures equal to or less than operating temperature range, and for a divider impedance seen by the feedback terminal of $2V\Omega$, unless otherwise specified.

 1 I $_{L}$ < 12mA, Rsc = 0 Ω . Output current and load regulation can be improved with external transistors. Improvement factors will be approx. equal to the composite current gain of added transistors.

²Applies for constant junction temperature. Temperature drift effects must be taken into account separately when the unit is operating under conditions of high dissipation.

³Same as Note 1, except Rsc = 10Ω .





Basic Regulator Circuit

CONNECTION DIAGRAMS







SG 105/205/305 Chip (See T-Pa diagram for pad functions).

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

5 Volt Fixed Voltage Regulators

The SG 109 series is a completely self-contained 5V regulator. Designed to provide local regulation at currents up to 1 amp for digital logic cards, this device is available in two commonly used transistor packages – the solid header TO-5 and the TO-3 power package.

A major feature of the SG109's design is its built-in protective features which make it essentially blowout proof. These consist of both current limiting to control the peak currents and thermal shutdown to protect against excessive power dissipation. With the only added component being the possible need for an input bypass capacitor, this regulator becomes extremely easy to apply.

Fully compatible with TTL and DTL

- Output current in excess of 1 amp
- Internal thermal overload protection
- No additional external components

PARAMETERS ¹	109	209	309	UNITS	
Operating Temperature Range	-55 to +150	-25 to +150	0 to +125	°C	
Package Types	Т, К		т, к	-	
Output Voltage	4.9 to 5	4.8 to 5.2	V		
Line Regulation 7V < Vin < 25V		50			
Load Regulation 5mA < Iout < 0.5A (1.5A for TO-3)	TO-5: 5	mV			
Total Output Voltage Tolerance ²		v			
Quiescent Current Vin < 25V		mA			
Ripple Rejection 10 Hz < f < 10kHz		dB			
Output Noise Voltage 10Hz ≤ f ≤ 100kHz	40 (typ)				
Output Impedance 10Hz ≤ f ≤ 10kHz	0.1 (typ)				
Long Term Stability	10				

¹ Unless otherwise specified, $T_j = 25^{\circ}C$, $V_{in} = 10$ Volts, and $I_{out} = 0.1A$.

 2 7V \leq V_{in} \leq 25V, 5mA \leq I_{out} \leq 1.0A (0.2A for TO-5), P \leq 20W (2W for TO-5), Δ T_j max.

Timax = -55°C to +150°C for the SG109

= -25°C to +150°C for the SG209

 $= 0^{\circ}$ C to $+125^{\circ}$ C for the SG309



Fixed 5V Regulator



• REQUIRED IF REGULATOR IS AN APPRECIABLE DISTANCE FROM POWER SUPPLY FILTER.

† ALTHOUGH NO OUTPUT CAPACITOR IS NEEDED FOR STABILITY IT DOES IMPROVE TRANSIENT RESPONSE.



SG109/209/309 Chip





SILICON GENEPAL

LINEAR INTEGRATED CIRCUITS

SG117A / SG217A / SG317A SG117 / SG217 / SG317

1.5 - AMP Three Terminal Adjustable Voltage Regulator

DESCRIPTION

The SG117A Series are 3-terminal positive adjustable voltage regulators which offer improved performance over earlier devices. A major feature of the SG117A is the output voltage tolerance is guaranteed at a maximum of \pm 1%, allowing an overall power supply tolerance to be better than 3% using inexpensive 1% resistors. Line and load regulation performance has been improved as well. Additionally, the SG117A reference voltage is guaranteed not to exceed 2% when operating over the full load, line and power dissipation conditions. The SG117A adjustable regulators offer an improved solution for all positive voltage regulator requirements with load currents up to 1.5 amps.

Regulator with Reference



ABSOLUTE MAXIMUM RATINGS

SG217A/SG217 - 25 °C to 150 °C SG317A/SG317 0 °C to 150 °C Storage Temperature Range SG117A/117 - 65 °C to 150 °C SG217A/SG217 - 65 °C to 150 °C SG317A/SG317 0 °C to 150 °C Lead Temperature (Soldering, 10 sec.) ... 300 °C

ADJUST ORDER PART NO. SG117AR SG217AR SG217AR SG217R SG217R SG217R SG217R

FEATURES

- 1% Output Voltage Tolerance
- 0.01%/V Line Regulation
- 0.3% Load Regulation
- Min. 1.5 Output Current

APPLICATIONS

Wide Range Power Supplies

Constant Current Supplies

Voltage Programmable Supplies

Output Voltage Error



PACKAGE ORDER INFORMATION



ELECTRICAL CHARACTERISTICS (See Note 1)

SYMBOL	PARAMETER	CONDITIONS		MIN	G117A/SG217A TYP	MAX	MIN	SG117/SG217 TYP	MAX	UNIT
REF	Reference Voltage	IOUT = 10mA TJ = 25°		1.238	1.250	1.262				V
		3V ≤(VIN - VOUT) ≤ 40V 10mA ≤ IOUT ≤ Imax, ≤ Pmax	•	1.225	1.250	1.270	1.20	1.25	1.30	V
VOUT	Line Regulation	3V ≤ (VIN - VOUT) ≤ 40V, (See Note 2)			0.005	0.01		0.01	0.02	%N
MIN	-		•		0.01	0.02		0.02	0.05	%N
VOUT Win	Load Regulation	10mA ≤ IQUT ≤ I _{max} (See Note 2) VO ≤ 5V VO ≥ 5V			5 0.1	15 0.3		5 0.1	15 0.3	mV %
	-	V0 ≤ 5V V0 ≥ 5V	:		20 0.3	50 1		20 0.3	50 1	mV %
	Thermal Regulation	TA = 25°C, 20msec Pulse			0.002	0.02		0.03	0.07	%M
	Ripple Rejection	Vo = 10V, f = 120Hz CADJ = 0			65			65		dB
		CADJ = 1µF	•	66	80		66	80		dB
ADJ	Adjust Pin Current				50	100		50	100	μA
ADJ	Adjust Pin Current Change	$10mA \le IOUT \le Imax$ 2.5V \le (VIN - VOUT) \le 40V	•		0.2	5		0.2	5	μΑ
min	Minimum Load Current	(VIN - VOUT)= 40V	•		3.5	5		3.5	5	mA
	Current Limit	(VIN – VOUT) ≤ 15V K Package T Package	:	1.5 0.5	2.2 0.8		1.5 0.5	2.2 0.8		A
		(VIN - VOUT) = 40V, TJ = 25 °C K Package T Package	:	0.3 0.15	0.4 0.2		0.3 0.15	0.4 0.2		Â
AVOUT Temp	Temperature Stability	0°C ≤ TJ ≤ 125°C			1	2		1		%
VOUT Time	Long Term Stability	T _A = 125 °C	1		0.3	1		0.3	• 1	%
	RMS Output Noise (% of VOUT)	$T_A = 25 ^{\circ}C$, 10Hz $\leq f \leq 10$ kHz			0.001			0.001		%
€	Thermal Resistance Junction to Case	T Package K Package			12 2.3	15 3		12 2.3	15 3	CN CN
SYMBOL		CONDITIONS		MIN	SG317A TYP	MAX	MIN	SG317 TYP	MAX	UNI
VREF	Reference Voltage	IOUT = 10mA TJ = 25°		1.238	1.250	1.262				V
		$3V \le (VIN - VOUT) \le 40V$ $10mA \le IOUT \le Imax, P \le Pmax$	•	1.225	1.250	1.270	1.20	1.25	1.30	V V
AVOUT		3V ≤ (VIN - VOUT) ≤ 40V, (See Note 2)			0.005	0.01		0.01	0.04	%/
	Line Regulation									%/
	Line Regulation		•		0.01	0.02		0.02	0.07	
	Line Regulation	10ma ≤ IOUT ≤ I _{max} (See Note 2) VO ≤ 5V VO ≥ 5V	•		5 0.1	0.02 25 0.5		0.02 5 0.1	25 0.5	%
		VO ≥ 5V VO ≤ 5V	· ·		5	25		5 0.1 20 0.3	25 0.5 70 1.5	% m' %
		VO ≥ 5V			5 0.1 20	25 0.5 50		5 0.1 20	25 0.5 70	% m' %
	Load Regulation	VO ≥ 5V VO ≥ 5V TA = 25 °C, 20msec Pulse VO = 10V, f = 120Hz			5 0.1 20 0.3 0.002	25 0.5 50 1		5 0.1 20 0.3 0.03	25 0.5 70 1.5	% m\ %
	Load Regulation Thermal Regulation			66	5 0.1 20 0.3	25 0.5 50 1	66	5 0.1 20 0.3	25 0.5 70 1.5	m) % %/ %/
	Load Regulation Thermal Regulation Ripple Rejection	VO ≥ 5V VO ≥ 5V TA = 25 °C, 20msec Pulse VO = 10V, f = 120Hz		66	5 0.1 20 0.3 0.002 65	25 0.5 50 1	66	5 0.1 20 0.3 0.03 65	25 0.5 70 1.5	% m\ %/
	Load Regulation Thermal Regulation	$VO \ge 5V$ $VO \ge 5V$ $TA = 25^{\circ}C, 20msec Puise$ $VO = 10V, f = 120Hz$ $CADJ = 0$ $CADJ = 1\mu F$		66	5 0.1 20 0.3 0.002 65 80	25 0.5 50 1 0.02	66	5 0.1 20 0.3 0.03 65 80	25 0.5 70 1.5 0.07	% ۳۱ % // // dl dl لاس
ΔVOUT ΔVOUT ΔVIN ΔVIN	Load Regulation Thermal Regulation Ripple Rejection Adjust Pin Current Adjust Pin Current Change	$\begin{array}{l} VO \leq 5V \\ VO \leq 5V \\ VO \geq 5V \\ TA = 25^{\circ}C, 20msec Pulse \\ VO = 10V, I = 120Hz \\ CADJ = 0 \\ CADJ = 1 \mu F \\ \hline \\ 10mA \leq IOUT \leq I_{max} \\ 25V \leq (VIN - VOUT) \leq 40V \\ \end{array}$:	66	5 0.1 20 0.3 0.002 65 80 50	25 0.5 50 1 0.02 100	66	5 0.1 20 0.3 0.03 65 80 50	25 0.5 70 1.5 0.07	% ۳۱ % ۱۵ اله لابر
ΔVOUT ΔVOUT ΔVIN ΔVIN	Load Regulation Thermal Regulation Ripple Rejection Adjust Pin Current	VO ≤ 5V VO ≤ 5V VO ≥ 5V TA = 25°C, 20msec Puise VO = 10V, I = 120Hz CADJ = 0 CADJ = 1 μ F 10mA ≤ IOUT ≤ Imax 25V ≤(VIN - VOUT) ≤ 40V (VIN - VOUT) ≤ 40V (VIN - VOUT) ≤ 15V K, R, & P Package	•		5 0.1 20 0.3 0.002 65 80 50 0.2 3.5 2.2	25 0.5 50 1 0.02 100 5	1.5	5 0.1 20 0.3 0.03 85 80 50 0.2 3.5 2.2	25 0.5 70 1.5 0.07 100 5	% ۳ %/ الم الم الم سر سر
ΔVOUT ΔVOUT ΔVIN ΔVIN	Load Regulation Thermal Regulation Ripple Rejection Adjust Pin Current Adjust Pin Current Change Minimum Load Current	$\begin{array}{c} VO \leq 5V \\ VO \leq 5V \\ VO \geq 5V \\ VO \geq 5V \\ VO = 10V, f = 120Hz \\ CADJ = 0 \\ CADJ = 1\mu F \\ \hline \\ 10mA \leq IOUT \leq Imax \\ 2.5V \leq (VIN - VOUT) \leq 40V \\ (VIN - VOUT) \leq 40V \\ (VIN - VOUT) \leq 15V \\ K, R, & P Package \\ T Package \\ VIN - VOUT) \leq 40V = 25^{\circ}C \\ K, R, & e Package \\ \hline \end{array}$	•	66 1.5 0.5 0.15 .075	5 0.1 20 0.3 0.002 65 80 50 0.2 3.5	25 0.5 50 1 0.02 100 5		5 0.1 20 0.3 0.03 65 80 50 0.2 3.5 2.2 0.8 0.4	25 0.5 70 1.5 0.07 100 5	% ۳۱ ۱۵ ۵۱ ۵۱ ۵۱ ۵۱ ۵۱ ۵۹ ۹۹
ADJ ADJ AJADJ Min Min AVOUT	Load Regulation Thermal Regulation Ripple Rejection Adjust Pin Current Adjust Pin Current Change Minimum Load Current	$\begin{array}{c} VO \leq 5V \\ VO \leq 5V \\ VO \geq 5V \\ VO \geq 5V \\ VO = 10V, f = 120Hz \\ CADJ = 0 \\ CADJ = 1\muF \\ \hline \\ 10mA \leq IQUT \leq Imax \\ 25V \leq (VIN - VOUT) \leq 40V \\ (VIN - VOUT) = 40V \\ (VIN - VOUT) \leq 15V \\ K, R, & P Package \\ I Package \\ T Package \\ \end{array}$	•	1.5 0.5	5 0.1 20 0.3 0.002 65 80 50 0.2 3.5 2.2 0.8 0.4	25 0.5 50 1 0.02 100 5	1.5 0.5 0.15	5 0.1 20 0.3 0.03 65 80 50 0.2 3.5 2.2 0.8 0.4	25 0.5 70 1.5 0.07 100 5	% % س/ س/ م/ س/ س/ س/ س/ س/ س/ س/ س/ س/ س/ س/ س/ % // // % // //
AVOUT AVOUT AJADJ AJADJ Imin AVOUT ATemp AVOUT	Load Regulation Thermal Regulation Ripple Rejection Adjust Pin Current Adjust Pin Current Change Minimum Load Current Current Limit	$\begin{array}{l} VO \leq 5V \\ VO \leq 5V \\ VO \geq 5V \\ VO \geq 5V \\ VO = 10V, f = 120Hz \\ CADJ = 0 \\ CADJ = 1\muF \\ \hline \\ 10mA \leq IOUT \leq Imax \\ 25V \leq (VIN - VOUT) \leq 40V \\ (VIN - VOUT) \leq 40V \\ (VIN - VOUT) \leq 15V \\ K, R, & PPackage \\ T Package \\ \hline \\ (VIN - VOUT) \leq 10V = 25^{\circ}C \\ K, R, & PPackage \\ \hline \\ T Package \\ \hline \\ Vactor \\ A = 25^{\circ}C \\ K = 25^{\circ$	•	1.5 0.5	5 0.1 20 0.3 0.002 65 80 50 0.2 3.5 2.2 0.8 0.4 0.2	25 0.5 50 1 0.02 100 5 10	1.5 0.5 0.15	5 0.1 20 0.3 0.03 65 80 50 0.2 3.5 2.2 0.8 0.8 0.4 0.2	25 0.5 70 1.5 0.07 100 5	% % % 41 طا س س س م 8 8 8 8 9
	Load Regulation Thermal Regulation Ripple Rejection Adjust Pin Current Adjust Pin Current Change Minimum Load Current Current Limit Temperature Stability	$ \begin{array}{l} VO \leq 5V \\ VO \leq 5V \\ VO \geq 5V \\ VO = 10V, f = 120Hz \\ CADJ = 0 \\ \hline \\ CADJ = 0 \\ \hline \\ CADJ = 1\mu F \\ \hline \\ \hline \\ 10mA \leq IOUT \leq Imax \\ 2.5V \leq (VIN - VOUT) \leq 40V \\ \hline \\ (VIN - VOUT) = 40V \\ \hline \\ (VIN - VOUT) \leq 40V \\ \hline \\ (VIN - VOUT) \leq 15V \\ K, R, & P Package \\ \hline T Ackage \\ \hline $	•	1.5 0.5	5 0.1 20 0.3 0.002 65 80 50 0.2 3.5 2.2 0.8 0.4 0.2 1	25 0.5 50 1 0.02 100 5 10 2	1.5 0.5 0.15	5 0.1 20 0.3 0.03 85 80 50 0.2 3.5 2.2 0.8 0.4 0.2 1	25 0.5 70 1.5 0.07 100 5 10	% m) % %/

The • denotes the specifications which apply over the full operating temperature range.

Note 1: Unless otherwise specified, these specifications apply for VIN - VOUT; and IOUT = 0.1A for the TO-39 and IOUT = 0.5A for the TO-3 and TO-220 packages. Although power dissipation is internally limited, these specifications are applicable for power dissipations of 2W for the TO-39, and 20W for the TO-3 and TO-220. IMAX is 15A for the TO-3 and TO-220 packages and 0.5A for the TO-39.

Note 2: Regulation is measured at constant junction temperature, using pulse testing with a low duty cycle. Changes in output voltage due to heating effects are covered under the specification for thermal regulation.





APPLICATION INFORMATION GENERAL

The SG117A develops a 1.25V reference voltage between the output and the adjustable terminal (see Figure 1). By placing a resistor, R_1 , between these two terminals, a constant current is caused to flow through R_1 and down through R_2 to set the overall output voltage. Normally this current is the specified minimum load current of 5mA or 10mA.



Figure 1

Because I_{ADJ} is very small and constant when compared with the current through R_1 , It represents a small error and can usually be ignored.

It is easily seen from the above equation, that even if the resistors were of exact value, the accuracy of the output is limited by the accuracy of V_{REF}. Earlier adjustable regulators had a reference tolerance of $\pm 4\%$. This tolerance is dangerously close to the $\pm 5\%$ supply tolerance required in many logic and analog systems. Further, many 1% resistors can drift 0.01%/°C adding another 1% to the output voltage tolerance.

For example, using 2% resistors and $\pm 4\%$ tolerance for V_{REF}, calculations will show that the expected range of a 5V regulator design would be 4.66V \leq V_{OUT} \leq 5.36V or approximately $\pm 7\%$. If the same example were used for a 15V regulator, the expected tolerance would be $\pm 8\%$. With these results most applications require some method of trimming, usually a trim pot. This solution is both expensive and not conducive to volume production.

One of the enhancements of Silicon General's adjustable regulators over existing devices is tightened initial tolerance. This allows relatively inexpensive 1% or 2% film resistors to be used for R_1 and R_2 while setting output voltage within an accepatble tolerance range.

With a guaranteed 1% reference, a 5V power supply design, using $\pm 2\%$ resistors, would have a worse case manufacturing tolerance of $\pm 4\%$. If 1% resistors were used, the tolerance would drop to $\pm 2.5\%$. A plot of the worst case output voltage tolerance as a function of resistor tolerance is shown on the front page.

For convenience, a table of standard 1% resistor values is shown below.

Table of 1/2 % and 1% Standard Resistance

Values							
1.00	1.47	2.15	3.16	4.64	6.81		
1.02	1.50	2.21	3.24	4.75	6.98		
1.05	1.54	2.26	3.32	4.87	7.15		
1.07	1.58	2.32	3.40	4.99	7.32		
1.10	1.62	2.37	3.48	5.11	7.50		
1.13	1.65	2.43	3.57	5.23	7.68		
1.15	1.69	2.49	3.65	5.36	7.87		
1.18	1.74	2.55	3.74	5.49	8.06		
1.21	1.78	2.61	3.83	5.62	8.25		
1.24	1.82	2.67	3.92	5.76	8.45		
1.27	1.87	2.74	4.02	5.90	8.66		
1.30	1.91	2.80	4.12	6.04	8.87		
1.33	1.96	2.87	4.22	6.19	9.09		
1.37	2.00	2.94	4.32	6.34	9.31		
1.40	2.05	3.01	4.42	6.49	9.53		
1.43	2.10	3.09	4.53	6.65	9.76		

Standard Resistance Values are obtained from the Decade Table by multiplying by multiples of 10. As an example, 1.21 can represent 1.21Ω , 12.1Ω , $1.21K\Omega$, etc.



Connections for Best Load Regulation Figure 2

TYPICAL APPLICATIONS

SG317A



Bypass Capacitors: Input bypassing using a 1μ F tantalum or 25μ F electrolytic is recommended when the input filter capacitors are more than 5 inches from the device. Improved ripple rejection (80 dB) can be accomplished by adding a 10μ F capacitor from the adjust pin to ground. For improved AC transient response and to prevent the possibility of oscillation due to unknown reactive load, a 1μ F capacitor is also recommended at the output. Because of their low impedance at high frequencies, the best type of capacitor to use is solid tantalum.







*C1 Improves Ripple Rejection. Xc should be small compared to R2.

Load Regulation: Because the SG117A is a three-terminal device, it is not possible to provide true remote load sensing. Load regulation will be limited by the resistance of the wire connecting the regulator to the load. For the data sheet specification, regulation is measured at the bottom of the package. Negative side sensing is a true Kelvin connection, with the bottom of the output divider returned to the negative side of the load. Although it may not be immediately obvious. best load regulation is obtained when the top of the divider is connected directly to the case, not to the load. This is illustrated in Figure 2. If R1 were connected to the load, the effective resistance between the regulator and the load would be

$$R_P \times \left(\frac{R2 + R1}{R1}\right) R_P = Parasitic Line Resistance.$$

Connected as shown, R_p is not multiplied by the divider ratio. R_p is about 0.004 Ω per foot using 16 gauge wire. This translates to 4mV/ft. at 1A load current, so it is important to keep the positive lead between regulator and load as short as possible.

5V Regulator with Shut Down



21V Programming Supply for UV PROM/EEROM



1



1

SILICON GENEPAL

SG117HV / SG217HV / SG317HV

1.5-Amp Positive Adjustable Voltage Regulator

DESCRIPTION

1

The SG117HV/SG217HV/SG317HV positive adjustable regulators will deliver up to 1.5 Amps output current over an output voltage range of 1.2V to 57V. Silicon General has made significant improvements in these regulators compared to previous devices, such as better line and load regulation, and a maximum output voltage error of 1%.

Every effort has been made to make these devices easy to use and difficult to damage. Internal current and power limiting coupled with true thermal limiting prevents device damage due to overloads or shorts, even if the regulator is not fastened to a heat sink.

The SG117HV family of products are ideal complements to the SG137HV adjustable positive regulators.

FEATURES

- Output Adjustable from 1.2V to 57V
- 0.01%/V Line Regulation
- 0.1% Load Regulation
- Min. 1.5 Output Current

APPLICATIONS

Wide Range Power Supplies Constant Current Supplies Voltage Programmable Supplies



Temperature Stability Curve



ABSOLUTE MAXIMUM RATINGS

Power Dissipation Internally Limited Input to Output Voltage Differential 60V Operating Junction Temperature Range

SG117HV
SG217HV – 25 °C to 150 °C
SG317HV 0°C to 125°C
Storage Temperature Range 65 °C to 150 °C
Lead Temperature (Soldering, 10 sec.) 300 °C

PACKAGE/ORDER INFORMATION



SG117HV/SG217HV/SG317HV

1

					7HV/SG21			SG317HV		
SYMBOL	PARAMETER	CONDITIONS		MIN	ΤΥΡ	MAX	MIN	TYP	MAX	UNITS
V _{REF}	Reference Voltage	$\begin{array}{l} 3V \leq (V_{IN} - V_{OUT}) \leq 60V \\ 10mA \leq I_{OUT} \leq I_{MAX}, \leq P_{MAX} \end{array}$	•	1.20	1.25	1.30	1.20	1.25	1.30	V
ΔV _{OUT}	Line Regulation	$3V \leq (V_{IN} - V_{OUT}) \leq 60V$			0.01	0.02		0.01	0.04	%/V
ΔV _{IN}		$T_A = 25$ °C. (See Note 2)	٠		0.02	0.05		0.02	0.07	%/V
ΔV _{OUT} ΔV _{IN}	Load Regulation	$\begin{array}{l} 10mA \leq I_{OUT} \leq I_{MAX} (\text{See Note 2}) \\ V_O \leq 5V \\ V_Q \geq 5V \end{array}$			5 0.1	15 0.3		5 0.1	25 0.5	mV %
		$V_O \le 5V$ $V_O \ge 5V$	•		20 0.3	50 1		20 0.3	70 1.5	mV %
	Thermal Regulation	T _A = 25 °C, 20msec Pulse	Γ		0.03	0.07		0.04	0.07	%W
	Ripple Rejection	$V_0 = 10V, f = 120Hz$ $C_{ADJ} = 0$	•		65			65		dB
		$C_{ADJ} = 1\mu F$	•	66	80		66	80		dB
I _{ADJ}	Adjust Pin Current		•		50	100		50	100	μA
ΔI _{ADJ}	Adjust Pin Current Change	$\begin{array}{l} 10mA \leq I_{OUT} \leq I_{MAX} \\ 2.5V \leq (V_{IN} - V_{OUT}) \leq 60V \end{array}$	•	-	0.2	5		0.2	5	μA
I _{MIN}	Minimum Load Current	$(V_{\rm IN} - V_{\rm OUT}) = 60V$	•		3.5	7		3.5	12	mA
	Current Limit	(V _{IN} − V _{OUT}) ≤ 15V K Package T Package	•	1.5 0.5	2.2 0.8		1.5 0.5	2.2 0.8		A
		(V _{IN} - V _{OUT}) = 60V K Package T Package	•		0.1 0.03			0.1 0.03		A A
∆V _{ouī} ∆Temp	Temperature Stability	$0^{\circ}C \leq T_{J} \leq 125^{\circ}C$			1			1		%
ΔV _{OUT} ΔTime	Long Term Stability	T _A = 125 °C			0.3	1		0.3	1	%
en	RMS Output Noise (% of V _{OUT})	$TA = 25^{\circ}C, 10Hz \le f \le 10kHz$			0.003			0.003		%
θ _{jc}	Thermal Resistance Junction to Case	T Package K Package			12 2.3	15 3		12 2.3	15 3	C/W C/W

The • denotes the specifications which apply over the full operating temperature range.

Note 1: Unless otherwise specified, these specifications apply for VIN – V_{OUT}; and I_{OUT} = 0.1A for the TO-39 and I_{OUT} = 0.5A for the TO-3 package. Although power dissipation is internally limited, these specifications are applicable for power dissipations of 2W for the TO-39, and 20W for the TO-3. I_{MAX} is 1.5A for the TO-3 package and 0.5A for the TO-39.

Note 2: Regulation is measured at constant junction temperature, using pulse testing with a low duty cycle. Changes in output voltage due to heating effects are covered under the specification for thermal regulation. Note 3: Selected devices with tightened reference voltages are available.

TYPICAL PERFORMANCE CHARACTERISTICS



Silicon General

LINEAR INTEGRATED CIRCUITS

SG123A / SG223A / SG323A SG123 / SG223 / SG323

5 VOLT---3-AMP POSITIVE REGULATOR

DESCRIPTION

The SG123A family is an improved version of the popular LM123 5 Volt, 3 Amp Regulator line. These new devices offer maximum initial output voltage tolerance of 1% and maintain a maximum tolerance of 3% over worst case operating conditions. Line and load regulation are also improved by a factor of 2. These tightened specifications ease design and application problems since safety margins are improved. Also, error budgets in other parts of the system can be expanded, and output voltages at the end of long supply runs can be more accurately calculated.

SG323A/SG323

SG123A/SG123..... - 65 °C to 150 °C

SG223A/SG223 - 65 °C to 150 °C

SG323A/SG323 - 65 °C to 150 °C Lead Temperature (Soldering, 10 sec.) . . 300 °C

Storage Temperature Range

FEATURES

- 1% Initial Tolerance of Output Voltage
- 3 Amp Output Current
- 30 Watt
- Full Internal Overload Protection

APPLICATIONS

- Local 5V Regulators
- On Card Regulation
- Lab Supplies
- Instrumentation Supplies



0°C to 125°C

Worst Case Output Voltage

PACKAGE / ORDER INFORMATION



SG123A / SG223A / SG323A SG123 / SG223 / SG323

SYMBOL	PARAMETER	CONDITIONS		SG MIN	123A/SG22 TYP	3A MAX	S MIN	G123/SG2 TYP	23 MAX	11.11-
	Output Voltage									UNITS
TUOT	Output voltage	$\frac{T_{J} = 25^{\circ}C, V_{IN} = 7.5V, I_{OUT} = 0}{7.5V, I_{OUT} = 0}$	┣	4.95	5.0	5.05	4.7	5.0	5.3	V
		$7.5V \le V_{IN} \le 15V$, $T_{MIN} \le T_J \le T_{MAX}$ $0 \le I_{OUT} \le 3A$, $P \le 30W$	•	4.85	5.0	5.15	4.6		5.4	v
SV _{OUT} SV _{IN}	Line Regulation	$T_j = 25 \text{ °C}, 7.5 \text{V} \leq \text{V}_{IN} \leq 15 \text{V}$ (See Note 1)			5	10		5	25	mV
ΔV _{OUT} ΔΙουτ	Load Regulation	$T_J = 25 ^{\circ}C, V_{IN} = 7.5V$ $0 \le I_{OUT} \le 3A$ (See Note 1)			25	50		25	100	mV
0	Quiescent Current	$7.5V \le V_{IN} \le 15V, 0 \le I_{OUT} \le 3A$	•		12	20		12	20	mA
∋n	Output Noise Voltage	$T_{\rm J} = 25 ^{\circ}{\rm C}, 10{\rm Hz} \le f \le 100{\rm kHz}$			40			40		μV _{rms}
sc	Short Circuit Current Limit	$T_J = 25 °C,$ $V_{IN} = 15V$ $V_{IN} = 7.5V$			3 4	4.5 6		3 4	4.5 5	A
	Long Term Stability of Output Voltage					35			35	mV
9JC	Thermal Resistance Junction to Case	K Package			1.8	2.5		1.8		•c/w
SYMBOL	PARAMETER	CONDITIONS		MIN	SG323A TYP	мах	MIN	SG323 TYP	MAX	UNITS
Vout	Output Voltage	$T_J = 25 ^{\circ}C, V_{IN} = 7.5V, I_{OUT} = 0$		4.95	5.0	5.05	4.8	5.0	5.2	V
		$7.5V \le V_{IN} \le 15V$, $T_{MIN} \le T_J \le T_{MAX}$ $0 \le I_{OUT} \le 3A$, $P \le 30W$ (Note 2)	•	4.85	5.0	5.15	4.75	5.0	5.25	v
ΔV _{OUT} ΔV _{IN}	Line Regulation	$T_j = 25 \text{°C}, 7.5 \text{V} \leq \text{V}_{IN} \leq 15 \text{V}$ (See Note 1)			5	10		5	25	mV
ΔV _{OUT} Δlout	Load Regulation	T _J = 25 °C, V _{IN} = 7.5V 0 ≤ I _{OUT} ≤ 3A (See Note1)			25	50		25	100	mV
la	Quiescent Current	$7.5V \leq V_{IN} \leq 15V, 0 \leq I_{OUT} \leq 3A$	•		12	20		12	20	mA
∋ <u>n</u>	Output Noise Voltage	$T_{J} = 25 ^{\circ}C, 10Hz \le f \le 100kHz$			40			40		μVrms
lsc	Short Circuit Current Limit	$T_J = 25 °C,$ $V_{IN} = 15V$ $V_{IN} = 7.5V$			3 4	4.5 6		3 4	4.5 5	A
	Long Term Stability of Output Voltage					35			35	mV
9 _{JC}	Thermal Resistance				1.8	2.5		1.8		°CM

Note 1: Load and line regulation are tested with pulsed low duty cycle techniques where pulse width \leq 1msec and duty cycle \leq 5%.

$\begin{array}{r} -25\,^{\circ}{\rm C}\,\, {\rm for}\,\, {\rm SG223A\,/\,SG223\,\, and\,\, 0\,\,^{\circ}{\rm C}\,\, for\,\, {\rm SG323A\,/\,SG323A\,/\,SG323A\,/\,SG323A\,/\,SG123A\,/\,SG123A\,/\,SG123A\,/\,SG3223A\,/\,SG322A\,/\,SG322A\,/\,SG324\,/\,SG3224\,/\,SG324\,/\,SG324\,/\,SG324\,/\,SG32$

Dropout Voltage

TYPICAL PERFORMANCE CHARACTERISTICS





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SG123A / SG223A / SG323A SG123 / SG223 / SG323

APPLICATIONS INFORMATION

Bypass Capacitors: The SG123A does not require an output capacitor for resistive loads. For almost all applications, however, a 1μ F or larger solid tantalum capacitor should be used at the output within 2" of the regulator to improve the output impedance at high frequencies. For applications where very low high frequency impedance is required, a 10μ F solid tantalum output capacitor is recommended. Total output capacitance either local or distributed may be increased without limit.

A 2μ F or larger solid tantalum capacitor or a 25μ F aluminum capacitor, must be used at the input if the regulator is more than 4" away from the large rectifier capacitor.

Avoiding Ground Loops: For best regulation, the ground pin of the SG123A should be tied directly to the load point as shown. This prevents excess drop in load voltage caused by load current flowing through the ground return lead. This is essentially a Kelvin connection for the low side of the regulator. A Kelvin connection cannot be made for the high output of regulator because only three pins are available on the package. Therefore, every attempt should be made to minimize the resistance between the output pin of the regulator and the load. #18 gauge hookup wire has a resistance of 0.006 ohms per foot. This translates to 0.36% change in load voltage at full load current. The SG123A is specified at 1% maximum load regulation, so one foot of wire represents a significant loss of regulation. If connectors are used, careful consideration must be given to contact resistance, especially if the connector is subjected to nasty ambients, vibration, or multiple insertions.

Raw Supply: Transformer, diode, and capacitor selection for the raw supply to the SG123A is very important because of the conflicting requirements for reliability, efficiency, and resistance to "brown-out" conditions. High secondary voltage on the transformer will cause unnecessarily high power dissipation in the regulator. Too low a secondary voltage will cause the regulator output to drop out of regulation with only a small reduction in AC mains voltage. The following formula gives a good starting point for transformer selection. This formula assumes a center tapped transformer, using two recifier diodes.





SG123A / SG223A / SG323A SG123 / SG223 / SG323

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APPLICATIONS INFORMATION

$$\begin{split} & \text{Example: } I_{\text{OUT}} = 2.5\text{A}, \, V_{\text{OUT}} = 5\text{V} \\ & \text{Assume: } V_{\text{DO}} = 2.5\text{V}, \, V_{\text{RECT}} = 1.1\text{V}, \, \text{C} = 8,000 \mu\text{F} \\ & V_{\text{NOM}} = 115\text{V}, \, V_{\text{LOW}} = 0.88\text{V} \\ & \text{V}_{\text{RIP}} = \frac{(5.3 \times 10^{-3})(2.5)}{2(8 \times 10^{-3})} = 0.83\text{V} \\ & \text{V}_{\text{RMS}} = \left(\frac{5 + 2.5 + 1.1 + 0.83}{\sqrt{2}}\right) \left(\frac{115}{05}\right) (1.1) \\ & = 8.03 \, \text{V}_{\text{RMS}} \\ & \text{V}_{\text{RMS}} = \left(\frac{V_{\text{OUT}} + V_{\text{DO}} + V_{\text{RECT}} + V_{\text{RIP}}}{\sqrt{2}}\right) \left(\frac{V_{\text{NOM}}}{V_{\text{LOW}}}\right) \, (1.1^*) \\ & \text{I}_{\text{RMS}} = (I_{\text{OUT}}) \, (1.2) \end{split}$$

The filter capacitor should be at least $2000 \,\mu$ F per amp of load current to minimize capacitor heating and ripple voltage. The diodes should be rated at 5-6 amps even though their average current is only 1.5A at full rated load current. The reason for this is that although the average current is 1.5A, the RMS current is typically twice this value. In addition, the diode must withstand very high surge currents during power turn-on. This surge can be 10-20 times the DC rating of the supply, depending on capacitor size and wiring resistance and induction.

TYPICAL APPLICATIONS



INPUT CROWBAR

- † Q2 and D1 must withstand large surge currents until the 5A fuse blows. Peak surge current is limited only by the fuse, wiring, and filter cap resistance.
- ††Trip point is approximately 7.3V.



- * The 6.4V Zener is internal to the SG123A.
- **Q1 must be able to withstand continuous currents of 5A if additional system shutdown is not used.

Silicon General

LINEAR INTEGRATED CIRCUITS

SG137A/SG237A/SG337A SG137/SG237/SG337

1.5 - AMP NEGATIVE ADJUSTABLE REGULATOR

DESCRIPTION

The SG137A/SG337A negative adjustable regulators will deliver up to 1.5 Amps output current over an output voltage range of -1.2V to -37V. Silicon General has made significant improvements in these regulators compared to previous devices, such as better line and load regulation, and a maximum output voltage error of 1%.

Every effort has been made to make these devices easy to use and difficult to damage. Internal current and power limiting coupled with true thermal limiting prevents device damage due to overloads or shorts, even if the regulator is not fastened to a heat sink.

The SG137A family of products are ideal complements to the SG117A adjustable positive regulators.

FEATURES

- -1% initial voltage tolerance
- - 0.01%ly line regulation
- 0.5% load regulation
- 0.02% Iw thermal regulation

APPLICATIONS

- · Adjustable Power Supplies
- System Power Supplies
- Precision Voltage/Current Regulators
- · On-Card Regulators





ABSOLUTE MAXIMUM RATINGS

Power Dissipation Input to Output Voltage Differ Operating Junction Temperat SG137A/SG137 SG237A/SG237 SG337A/SG337 Storage Temperature Range Lead Temperature (Soldering,	ential
	PART NO. SG137AR SG137R SG237AR SG237R SG337AR SG337R SG337R



SG137A/SG237A/SG337A SG137/SG237/SG337

ELECTRICAL CHARACTERISTICS (See Note 1)

SYMBOL	PARAMETER	CONDITIONS		MIN	G137A/SG237 TYP	MAX	MIN	SG137/SG23 TYP	MAX	UNITS
VREF	Reference Voltage	VIN - VOUT = 5V, IOUT = 10mA, T] = 25℃		- 1.238	- 1.250	- 1.262	- 1.225	- 1.250	- 1.275	v
		$3V \le VIN - VOUT \le 40V$ $10mA \le IOUT \le IMAX P \le PMAX$	1.	- 1.220	- 1.250	- 1.280	- 1.200	- 1.250	- 1.300	v
	Load Regulation	10m3 10UT ≤ 1MAX (See Note 2.8.3) Tj = 25°C, VOUT ≤ 5V Tj = 25°C, VOUT ≤ 5V VOUT ≤ 5V VOUT ≤ 5V		- 1.220	5 0.1 10 0.2	25 0.5 50 1.0	- 1.200	15 0.3 20 0.3	25 0.5 50 1.0	mV % mV %
	Line Regulation	$3V \ge V_{IN} - V_{OUT} \le 40V,$ (See Note 2)-IOUT $\le I_{MAX}$ (See Note 2 & 3) T _I = 25 °C			0.005	0.01		0.01	0.02	%N
	Ripple Rejection	VOUT = -10V, f = 120hZ CADJ = 0 CADJ = 10 μ F	:	60 70	66 80		66	60 77		dB dB
	Thermal Regulation	Tj = 25°C, 10msec Pulse			0.002	0.02		0.002	0.02	%/W
ADJ	Adjust Pin Current				65	100		65	100	µA
	Adjust Pin Current Change	10mA ≤ IOUT ≤ IMAX 3V ≤ VIN - VOUT ≤ 40V	•		0.2 1.0	2 5		0.5 2	5 5	μΑ μΑ
	Minimum Load Current	VIN ~ VOUT ≤ 40V VIN ~ VOUT ≤ 10V	:		2.5 1.2	5 3		2.5 1.2	5.0 3.0	mA mA
	Current Limit	VIN - VOUT ≤ 15V, K and P Package T Package VIN - VOUT ≤ 40V, K and P Package	:	1.5 0.5 0.24	2.2 0.8 0.4	3.2 1.5 1.0	1.5 0.5 0.24	2.2 0.8 0.4		Â
	Temperature Stability	Tj = 25 °C T Package	-	0.15	0.25	0.5	0.15	0.25		A %
	Long Term Stability	T _A = 125 °C, 1000 Hours		,	0.3	1.0		0.3	1.0	%
AVTime	RMS Output Noise	$T_A = 25^{\circ}C$, 10 Hz > f < 10kHz			0.003			0.003	1.0	%
	(% of VOUT)									
θIC	Thermal Resistance Junction to Case	T Package K Package			12 2.3	15 3.0		12 2.3	15 3.0	*C/W *C/W
SYMBOL	PARAMETER	CONDITIONS		MIN	SG337A TYP	MAX	MIN	SG337 TYP	MAX	UNITS
VREF	Reference Voltage	$ V_{IN} - V_{OUT} = 5V, I_{OUT} = 10mA,$ T _j = 25°C		- 1.238	- 1.250	- 1.262	- 1.213	- 1.250	- 1.287	v
		3V ≤ VIN - VOUT ≤40V 10mA ≤ IOUT ≤ IMAX P ≤ PMAX	•	- 1.220	- 1.250	- 1.280	- 1.200	- 1.250	- 1.300	v
	Load Regulation	10mA ≤ IOUT ≤ IMAX (See Note 2 & 3) Tj = 25°C, VOUT ≤ 5V Tj = 25°C, VOUT ≤ 5V VOUT ≤ 5V VOUT ≤ 5V			5 0.1 10 0.2	25 0.5 50 1.0		15 0.3 20 0.3	50 1.0 70 1.5	mV % mV %
	Line Regulation	$3V \ge V N - VOUT \le 40V$, (See Note 2)- OUT $\le MAX $ (See Note 2 & 3) T _j = 25 °C			0.005	0.01		0.01	0.04	%N
	Ripple Rejection	VOUT = -10V, f = 120hZ CADJ = 0 CADJ = 10 μ F	:	60 70	66 80		66	60 77		dB dB
	Thermal Regulation	Tj = 25°C, 10msec Pulse			0.002	0.02		0.003	0.04	%W
ADJ	Adjust Pin Current				65	100		65	100	μA
∆IADJ	Adjust Pin Current Change	$10mA \le IOUT \le IMAX$ $3V \le VIN - VOUT \le 40V$	ŀ		0.2 1.0	2 5		0.5 2	5	μΑ μΑ
	Minimum Load Current	VIN - VOUT ≤ 40V VIN - VOUT ≤ 10V	:		2.5 1.2	5 3		2.5 1	10 6	mA mA
ISC	Current Limit	VIN – VOUT ≤ 15V, K and P Package T Package VIN – VOUT ≤ 40V, K and P Package	:	1.5 0.5	2.2 0.8	3.5 1.5	1.5 0.5	2.2 0.8		A
		K and P Package Tj = 25°C T Package		0.24 0.15	0.5 0.25	1.0 0.5	0.15 0.10	0.4 0.17		Â
	Temperature Stability				0.6	1.5		0.6		%
	Long Term Stability	T _A = 125 °C, 1000 Hours			0.3	1.0		0.3	1.0	%
9n	RMS Output Noise (% of VOUT)	$T_A = 25 ^{\circ}C$, 10 Hz $\leq f \leq 10$ kHz			0.003			0.003		%
ЭIC	Thermal Resistance Junction to Case	T Package K Package P Package			12 2.3 4	15 3.0 5		12 2.3 4	15 3.0	*C/W *C/W *C/W

The • denotes the specifications which apply over the full operating temperature range.

Note 1: Unless otherwise indicated, these specifications apply: $|V_N - V_{OUT}| = 5V$; and $I_{OUT} = 0.1A$ for the T package, $I_{OUT} = 0.5A$ for the K and P packages. Power dissipation up to 2W for the T package and 20W for the K and P packages. Imax = 1.5A for the K and P packages, and 0.5 for the T package.

Note 2: Testing is done using a pulsed low duty cycle technique. See thermal regulation specifications for output changes due to heating effects. Load regulation is measured on the output pin at a point %" below the base of the K and T package and at the junction of the wide and narrow portion of the lead on the P package.

Note 3: Load Regulation for the SG337AP is the same as for SG337P.

SG137A/SG237A/SG337A SG137/SG237/SG337



APPLICATION INFORMATION

Output Voltage: The output voltage is determined by two external resistors, $R_1 \& R_2$ (see Figure 1). The exact formula for the output voltage is:

$$V_{OUT} = V_{Ref} \left(1 + \frac{R_2}{R_1} \right) + I_{ADJ}(R_2)$$

Where: V_{Ref} = Reference Voltage, I_{ADJ} = Adjustment Pin Current. In most applications, the second term is small enough to be ignored, typically about 0.5% of V_{OUT} . In more critical applications, the exact formula should be used, with I_{ADJ} equal to 65 μ a. Solving for R₂ yields:

$$R_{2} = \frac{V_{OUT} - V_{Ref}}{\frac{V_{Ref}}{R_{1}} - I_{ADJ}}$$

Smaller values of R₁ and R₂ will reduce the influence of I_{ADJ} on the output voltage, but the no-load currrent drain on the regulator will be increased. Typical values for R₁ are between 100 Ω and 300 Ω , giving 12.5 mA and 4.2mA no-load current respectively. There is an additional consideration in selecting R₁, the minimum load current specification of the regulator. The operating current of the SG137A flows from input to output. If this current is not absorbed by the load, the output of the regulator will rise above the regulated value. The current drawn by R₁ and R₂ is normally high enough to absorb the current, but care must be taken in no-load situations where R₁ and R₂ have high values. The maximum value for the operating current, which must be absorbed, is 5mA for the SG137A. If input-output voltage differential is less than 10V, the operating current that must be absorbed drops to 3mA.



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SG137A/SG237A/SG337A SG137/SG237/SG337

TYPICAL APPLICATION

the output stability, load regulation, line regulation, thermal regulation, temperature drift, long term drift, and noise, can be improved by a factor of 6.6 over the standard regulator configuration. This assumes a zener whose drift and noise is considerably better than the regulator itself. The LM329B has 20 PPM/°C maximum drift and about 10 times lower noise than the regulator.

In the application shown below, regulators #2 to "N" will track regulator #1 to within ± 24 mV initially, and to ± 60 mV over all load, line, and • temperature conditions. If any regulator output is shorted to ground, all other outputs will drop to - 2V. Load regulation of regulators 2 to "N" will be improved by V_{OUT}1.5V compared to a standard regulator, so regulator #1 should be the one which has the lowest load current.

High Stability Regulator



Dual Tracking Supply \pm 1.25V to \pm 20V







Multiple Tracking Regulators


Silicon General

LINEAR INTEGRATED CIRCUITS

SG137HV/SG237HV/SG337HV

1.5 - AMP NEGATIVE ADJUSTABLE REGULATOR

DESCRIPTION

The SG137HV/SG237HV/SG337HV negative adjustable regulators will deliver up to 1.5 Amps output current over an output voltage range of -1.2V to -47V. Silicon General has made significant improvements in these regulators compared to previous devices, such as better line and load regulation, and a maximum output voltage error of 1%.

Every effort has been made to make these devices easy to use and difficult to damage. Internal current and power limiting coupled with true thermal limiting prevents device damage due to overloads or shorts, even if the regulator is not fastened to a heat sink.

The SG137HV family of products are ideal complements to the SG117HV adjustable positive regulators.

FEATURES

- Output adjustable from -1.2V to -47V
- 0.01%/V line regulation
- 0.5% load regulation
- 0.002% thermal regulation

APPLICATIONS

- Adjustable Power Supplies
- System Power Supplies
- Precision Voltage/Current Regulators
- On-Card Regulators



TEMPERATURE STABILITY CURVE



ABSOLUTE MAXIMUM RATINGS

Power Dissipation Internally Limited Input to Output Voltage Differential 50V Operating Junction Temperature Range

SG137HV – 55 °C to 150 °C
SG237HV – 25 °C to 150 °C
SG337HV 0°C to 125°C
Storage Temperature Range65 °C to 150 °C
Lead Temperature (Soldering, 10 sec.) 300 °C

PACKAGE ORDER INFORMATION



SG137HV/SG237HV/SG337HV

SYMBOL	PARAMETER	CONDITIONS		SG13 MIN	7HV/SG2 TYP	37HV MAX	MIN	SG337HV TYP	MAX	UNITS
VREF	Reference Voltage	$ V_{IN} - V_{OUT} = 5V. I_{OUT} = 10mA,$ T _J = 25 °C (Note 3)		- 1.225	- 1.250	- 1.275	- 1.213	-1.250	-1.287	v
		$3V \le V_{IN} - V_{OUT} \le 50V$ $10mA \le I_{OUT} \le I_{MAX}P \le P_{MAX}$	•	- 1.200	- 1.250	- 1.300	-1.200	- 1.250	- 1.300	v
ΔV _{OUT} ΔI _{OUT}	Load Regulation	$\begin{array}{l} 10mA \leq I_{OUT} \leq I_{MAX} \text{ (See Note 2)} \\ V_{OUT} \leq 5V \\ V_{OUT} \geq 5V \end{array}$	•		20 0.3	50 1.0		20 0.3	70 1.5	mV %
ΔV _{OUT} ΔV _{IN}	Line Regulation	$3V \le V_{IN} - V_{OUT} \le 50V$ (See Note 2)			0.02	0.05		0.02	0.07	%/V
	Ripple Rejection	$V_{OUT} = -10V, f = 120Hz$ $C_{ADJ} = 0$ $C_{ADJ} = 10\mu F$	•	66	60 77		66	60 77		dB dB
	Thermal Regulation	T _J = 25 °C, 10msec Pulse			0.002	0.02	1	0.003	0.04	%/W
ADJ	Adjust Pin Current		•		65	100		65	100	μΑ
ΔI _{ADJ}	Adjust Pin Current Change	$\begin{array}{l} 10mA \leq I_{OUT} \leq I_{MAX} T_A = 25^{\circ}\text{C} \\ 2.5V \leq V_{IN} - V_{OUT} \leq 50V \end{array}$			2 3	5 6		2 3	5 6	μΑ μΑ
	Minimum Load Current		:		2.5 1.2	5 3		2.5 1.5	10 6	mA mA
lsc	Current Limit	V _{IN} - V _{OUT} ≤ 13V K Package T Package V _{IN} - V _{OUT} ≤ 50V K Package	•	1.5 0.5 0.2	2.2 0.8 0.4	3.2 1.6 0.8	1.5 0.5 0.1	2.2 0.8 0.4	3.5 1.8 0.8	A A A
		T Package T _J = 25 °C		0.1	0.17	0.5	0.05	0.4	0.5	Â
ΔV _{OUT} ΔV _{TEMP}	Temperature Stability				0.6	1.5		0.6		%
ΔV _{OUT} ΔVτime	Long Term Stability	T _A = 125 °C, 1000 Hours			0.3	1.0		0.3	1.0	%
en	RMS Output Noise (% of V _{OUT})	$T_A = 25 ^{\circ}C$, $10Hz \le f \ge 10kHz$			0.003			0.003		%
θ _{JC}	Thermal Resistance Junction to Case	T Package K Package			12 2.3	15 3.0		12 2.3	15 3.0	°C/W °C/W

The • denotes the specifications which apply over the full operating temperature range.

Note 1: Unless otherwise indicated, these specifications apply: $|V_{IN} - V_{OUT}| = 5V$; and $I_{OUT} = 0.1A$ for the T package, $l_{OUT} = 0.5A$ for the K package. Power dissipation up to 2W for the T package and 20W for the K package. $l_{MAX} = 1.5A$ for the K package and 0.5 for the T package.

Note 2: Testing is done using a pulsed low duty cycle technique. See thermal regulation specifications for output changes due to heating effects. Load regulation is measured on the output pin at a point 1/8-" below the base of the K and T package.

Note 3: Selected devices with tightened reference voltages available.



INPUT-OUTPUT DIFFERENTIAL



TYPICAL PERFORMANCE CHARACTERISTICS



Minimum Load Current



SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

SG138A/SG238A/SG338A SG138/SG238/SG338

5 AMP POSITIVE ADJUSTABLE VOLTAGE REGULATOR

DESCRIPTION

The SG138A series of adjustable regulators provide 5 amps output current over an output voltage range of 1.2 volts to 32 volts. The internal voltage reference is trimmed to less than 1%, enabling a very tight output voltage. In addition to excellent line and load regulation, with full overload protection, the SG138A incorporates new current limiting circuitry allowing large transient load currents to be handled for short periods. Transient load currents of up to 12 amps can be supplied without limiting, eliminating the need for a large output capacitor.

The SG138A is an improved version of the popular LM138 with improved circuit design and advanced process techniques to provide superior performance and reliability.

The graph below shows the significant improvement in output voltage tolerance achieved by using the SG138A or SG338A.

FEATURES

- 1% Initial Tolerance
- 0.3% Load Regulation
- 5 Amp output Current
- 12 Amp Transient Output Current

APPLICATIONS

- High Power Linear Regulator
- Battery Chargers
- Power Driver
- Constant Current Regulator





Output Voltage Error



ABSOLUTE MAXIMUM RATINGS

Power Dissipation Internally Limited
Input to output Voltage Differential
Operating Junction Temperature Range
SG138A/138 – 55°C to 150°C
SG238A/238 25°C to 150°C
SG338A/338
Storage Temperature Range – 65°C to 150°C
Lead Temperature (Soldering, 10 sec.)300°C

PACKAGE/ORDER INFORMATION



ELECTRICAL CHARACTERISTICS (See Note 1)

SYMBOL	PARAMETER				38A/SG2	38A	SG	138/SG2	38	
		CONDITIONS		MIN	TYP	MAX	Min	TYP	MAX	UNITS
VREF	Reference Voltage	$I_{OUT} = 10 \text{mA} \text{ T}_{A} = 25^{\circ}\text{C}$		1.238	1.250	1.262				
		$\begin{array}{l} 3V \leqslant (V_{\text{IN}} - V_{\text{OUT}}) \leqslant 35V \\ 10 \text{mA} \leqslant I_{\text{OUT}} \leqslant 5\text{A}, P \leqslant 50W \end{array}$	•	1.225	1.250	1.270	1. 19	1.24	1.29	1
<u>The Art</u>	Line Regulation	$3V \leq (V_{IN} - V_{OUT}) \leq 35V$, (See								
		Note 2) $T_A = 25^{\circ}C$	•		0.005 0.02	0.01 0.04		0.005 0.02	0.01 0.04	%/' %/'
<u>דוס</u> עב דוסוב	Load Regulation	$ \begin{array}{l} 10mA \leqslant I_{0UT} \leqslant 5A, (\text{See Note 2}) \\ T_A = 25^\circ\text{C} \\ V_{0UT} \leqslant 5V \end{array} $						E	4.5	
		$V_{OUT} \ge 5V$ $V_{OUT} \ge 5V$			5 0.1	15 0.3		5 0.1	15 0.3	m\ %
		V _{OUT} ≤ 5V V _{OUT} ≥ 5V	•		20 0.3	30 0.6		20 0.3	30 0.6	m\ %
	Thermal Regulation	$T_A = 25^{\circ}C$, 20msec Pulse			0.002	.01		0.002	0.01	%/V
	Ripple Rejection	$V_{0UT} = 10V, f = 120Hz$ $C_{ADJ} = 0$ $C_{ADJ} = 10\mu F$	•	60	60 75		60	60 75		dE
IADJ	Adjust Pin Current		•		45	100		45	100	μA
^{LDJ}	Adjust Pin Current Change	$\begin{array}{l} 10mA \leqslant I_{OUT} \leqslant 5A, \\ 3V \leqslant (V_{IN}-V_{OUT}) \leqslant 35V \end{array}$	•		0.2	5		0.2	5	μA
	Minimum Load Current	$(V_{IN} - V_{OUT}) = 35V$	•		3.5	5		3.5	5	m/
Isc	Current Limit	$(V_{IN} - V_{OUT}) \le 10V$ DC 0.5ms peak	•	5 7	8 12		5 7	8 12		A A
		$(V_{IN} - V_{OUT}) = 30V, T_i = 25^{\circ}C$,		1			1		A
<u>Temp</u> ک	Temperature Stability		•		1	2		1		%
{Time} کد	Long Term Stability	$T{A} = 125^{\circ}C$, 1000 Hours			0.3	1		0.3	1	%
en	RMS Output Noise (% of Vout)	$T_A = 25^{\circ}C$, $10Hz \le f \le 10kHz$			0.001			0.003		%
Θις	Thermal Resistance Junction to Case	K Package				1			1	°C/W

ELECTRICAL CHARACTERISTICS (See Note 1)

SYMBOL	PARAMETER	CONDITIONS		MIN	SG338A TYP	MAX	MIN	SG338 Typ	MAX	UNITS
VREF	Reference Voltage	$I_{OUT} = 10 \text{mA}$ $T_j = 25^{\circ}\text{C}$	Τ	1.238	1.250	1.262				V
		$3V \leq (V_{IN} - V_{OUT}) \leq 35V$ 10mA $\leq l_{OUT} \leq 5A, P \leq 50W$	•	1.225	1.250	1.270	1. 19	1.24	1.29	v
ΔV _{OUT} ΔV _{IN}	Line Regulation	$3V \le (V_{IN} - V_{OUT}) \le 35V$, (See Note 2) $T_A = 25^{\circ}C$	•		0.005 0.02	0.01 0.04		0.005 0.02	0.03 0.06	%/\ %/\
ΔV _{OUT} Δί _{ουτ}	Load Regulation	ulation $ \begin{array}{c} 10mA < I_{OUT} < 5A, (See Note 2) \\ T_A = 25^\circ C \\ V_{OUT} < 5V \\ V_{OUT} > 5V \end{array} $			5 0.1	15 0.3		5 0.1	25 0.5	mV %
		$V_{OUT} \le 5V$ $V_{OUT} \ge 5V$	•		20 0.3	30 0.6		20 0.3	50 1	mV %
	Thermal Regulation	T _A = 25°C, 20msec pulse			0.002	.02		0.002	0.02	%/W
	Ripple Rejection	$V_{OUT} = 10V, f = 120Hz$ $C_{ADJ} = 0$ $C_{ADJ} = 10\mu F$	•	60	60 75		60	60 75		dB dB
IADJ	Adjust Pin Current		٠		45	100		45	100	μA
ΔI _{ADJ}	Adjust Pin Current Change	$\begin{array}{l} 10\text{mA} \leqslant I_{\text{OUT}} \leqslant 5\text{A}, \\ 3\text{V} \leqslant (\text{V}_{\text{IN}} - \text{V}_{\text{OUT}}) \leqslant 35\text{V} \end{array}$			0.2	5		0.2	5	μA
	Minimum Load Current	$(V_{IN} - V_{OUT}) = 35V$	•		3.5	10		3.5	10	mA
Isc	Current Limit	$(V_{IN} - V_{OUT}) \le 10V$ DC 0.5ms peak	•	5 7	8 12		5 7	8 12		A
		$(V_{IN} - V_{OUT}) = 30V, T_i = 25^{\circ}C$			1	2		1		A
∆V _{OUT} ∆Temp	Temperature Stability		•		1	2		1		%
∆V _{out} ∆Time	Long Term Stability	$T_{A} = 125^{\circ}C, 1000 \text{ Hours}$			0.3	1		0.3	1	%
e _n	RMS Output Noise (% of V _{OUT})	$T_A = 25^{\circ}C$, $10Hz \le f \le 10kHz$	T		0.001			0.003		*
θ _{JC}	Thermal Resistance Junction to Case	K Package			,	1			1	°C/W

The ${\ensuremath{\bullet}}$ denotes the specifications which apply over the full operating temperature range.

Note 1: Unless otherwise specified, these specifications apply: $V_{IN} - V_{OUT} = 5V$ and $I_{OUT} = 2.5A$. These specifications are applicable for power dissipations up to 50W.

Note 2: See thermal regulation specifications for changes in output voltage due to heating effects. Load and line regulation are measured at a constant junction temperature by low duty cycle pulse testing.





APPLICATIONS INFORMATION

General

The SG138A develops a 1.25V reference voltage between the output and the adjustable terminal (see Figure 1). By placing a resistor, R1, between these two terminals, a constant current is caused to flow through R1 and down through R2 to set the overall output voltage. Normally this current is the specified minimum load current of 5mA or 10mA. Because IADJ is very small and constant when compared with the current through R1, it represents a small error and can usually be ignored. It is easily seen from the output voltage equation, that even if the resistors were of exact value, the accuracy of the output is limited by the accuracy of VREF Earlier adjustable regulators had a reference tolerance of ±4% which is dangerously close to the ±5% supply many logic and analog tolerance required in systems. Further, even 1% resistors can drift 0.01%/°C, adding additional error to the output voltage tolerance.



Figure 1

For example, using 2% resistors and $\pm 4\%$ tolerance for V_{REF}, calculations will show that the expected range of a 5V regulator design would be $4.66V \le V_{OUT} \le 5.36V$ or approximately $\pm 7\%$. If the same example were used for a 15V regulator, the expected tolerance would be $\pm 8\%$. With these results most applications required some method of trimming, usually a trim pot. This solution is both expensive and not conducive to volume production.

One of the enhancements of Silicon General's adjustable regulators over existing devices is the tightened initial tolerance of V_{REF} . This allows relatively inexpensive 1% or 2% film resistors to be used to R1 and R2 to set the output voltage within an acceptable tolerance.

With a guaranteed 1% reference, a 5V power supply design, using $\pm 2\%$ resistors, would have a worst case manufacturing tolerance of $\pm 4\%$. If 1% resistors are used, the tolerance will drop to $\pm 2.5\%$. A plot of the worst case output voltage tolerance as a function of resistor tolerance is shown on the front page.

For convenience, a table of standard 1% resistor values is shown below.

1.00	1.47	2.15	3.16	4.64	6.81	I
1.02	1.50	2.21	3.24	4.75	6.98	
1.05	1.54	2.26	3.32	4.87	7.15	
1.07	1.58	2.32	3.40	4.99	7.32	
1.10	1.62	2.37	3.48	5.11	7.50	
1.13	1.65	2.43	3.57	5.23	7.68	
1.15	1.69	2.49	3.65	5.36	7.87	ł
1.18	1.74	2.55	3.74	5.49	8.06	
1.21	1.78	2.61	3.83	5.62	8.25	
1.24	1.82	2.67	3.92	5.76	8.45	
1.27	1.87	2.74	4.02	5.90	8.66	
1.30	1.91	2.80	4.12	6.04	8.87	
1.33	1.96	2.87	4.22	6.19	9.09	
1.37	2.00	2.94	4.32	6.34	9.31	
1.40	2.05	3.01	4.42	6.49	9.53	
1.43	2.10	3.09	4.53	6.65	9.76	

Table of 1/2% and 1% Standard Resistance Values

Standard Resistance Values are obtained from the Decade Table by multiplying by multiples of 10. As an example, 1.21 can represent 1.21 Ω , 12.1 Ω

Bypass Capacitors

Input bypassing using a 1μ F tantalum or 25μ F electrolytic is recommended when the input filter capacitors are more than 5 inches from the device. Improved ripple rejection (80 dB) can be accomplished by adding a 10μ F capacitor from the adjust pin to ground. Increasing the size of the capacitor to 20μ F will help ripple rejection at low output voltage since the reactance of this capacitor should be small compared to the voltage setting resistor, R2. For improved AC transient response and to prevent the possibility of oscillation due to unknown reactive load, a 1μ F capacitor is also recommended at the output. Because of their low impedance at high frequencies, the best type of capacitor to use is solid tantalum.

Protection Diodes

The SG138A/338A do not require a protection diode from the adjustment terminal to the output (see figure 2). Improved internal circuitry eliminates the need for this diode when the adjustment pin is bypassed with a capacitor to improve ripple rejection.



If a very large output capacitor is used, such as a 100μ F shown in figure 2, the regulator could be damaged or destroyed if the input is accidentally shorted to ground or crowbarred, due to the output capacitor discharging into the output terminal of the regulator. To prevent this, a diode D1 as shown, is recommended to safely discharge the capacitor.

Load Regulation

Because the SG138A is a three-terminal device, it is not possible to provide true remote load sensing. Load regulation will be limited by the resistance of the wire connecting the regulator to the load. The data sheet specification for load regulation is measured at the bottom of the package. Negative side sensing is a true Kelvin connection, with the bottom of the output divider returned to the negative side of the load. Although it may not be immediately obvious, best load regulation is obtained when the top of the resistor divider, (R1), is connected *directly* to the case *not to the load*. This is illustrated in *Figure 3*. If R1 were connected to the

load, the effective resistance between the regulator and the load would be

$$R_p \times \left(\frac{R2 + R1}{R1}\right)$$
, R_p = Parasitic Line Resistance.

Connected as shown, R_p is not multiplied by the divider ratio. R_p is about 0.004Ω per foot using 16 gauge wire. This translates to 4mV/ft at 1A load current, so it is important to keep the positive lead between regulator and load as short as possible, and use large wire or PC board traces.



Connections For Best Load Regulation

Figure 3.

TYPICAL APPLICATIONS 5V Regulator With Shut Down 1.2V-25V Adjustable Regulator **Improving Ripple Rejection** SG338A SG338A SG338A 5٧ Vout‡ Vour Vou ٧n Vou R1 240 AD. Ş R1 AD. ٨D 121Ω 1% 1210 1% C1* C2† 1 ... 1µF 14 R2 3650 5 10 1% 2N3904 **36**5Ω TTL Needed if device is far from 1% * C1 IMPROVES RIPPLE REJECTION XC SHOULD capacitor BE SMALL COMPARED TO R2 † Optional—improves transient Ť response $\neq V_{OUT} = 1.25V \left(1 + \frac{R2}{R1} \right)$ Temperature Compensated Lead Acid **Battery Charger Remote Sensing** SG338A SG338A Ro (MAX DROP 300mV) OUTPUT 54 ٧. ► Vour 3 AMP **243**Ω 10k * ٧in **25** Ω 50 O SG301A - 12 V R 2N3906 1kΩ 2k * 1210 -11-50k ' 365 \ 100pF 41 RET 255 Ť RETURN



Silicon General

LINEAR INTEGRATED CIRCUITS

SG150A / SG250A / SG350A SG150 / SG250 / SG350

3-AMP POSITIVE ADJUSTABLE REGULATOR

DESCRIPTION

1

The SG150/150A series are adjustable 3-terminal positive voltage regulators capable of supplying in excess of 3A over a 1.2V to 33V output range. They are exceptionally easy to use and require only 2 external resistors to set the output voltage. The SG150/150A series offers full overload protection available only in IC's. Included on the chip are current limit, thermal overload protection and safe operating area protection.

Since the regulator is "floating" and sees only the inputto-output differential voltage, supplies of several hundred volts can be regulated as long as the maximum input to output differential is not exceeded.

Supplies needing electronic shutdown can be achieved by clamping the adjustment terminal to ground, which programs the output to 1.2V where most loads draw little current. Reference voltage, which is trimmed to be within $\pm 1\%$ at room temperature, is guaranteed to be within $\pm 2\%$ over all operating conditions for the "A" version and $\pm 4\%$ for the standard version. They are packaged in standard steel TO-3 transistor packages.

TYPICAL APPLICATIONS



ABSOLUTE MAXIMUM RATINGS Internally limited **Power Dissipation** Input-Output Voltage Differential 35V Operating Junction Temperature Range SG150/150A - 55°C to + 150°C - 25°C to + 150°C SG250/250A 0°C to + 125°C SG350/350A - 65°C to + 150°C Storage Temperature 300°C Lead Temperature (Soldering, 10 seconds)

FEATURES

- Trimmed ± 1% reference voltage
- Adjustable output down to 1.2V
- Guaranteed 3A output current
- Line Regulation typically 0.1%
- · Guaranteed thermal regulation
- · Current limit constant with temperature
- 86 dB ripple rejection
- Standard 3-lead transistor package



Output Voltage Error



PACKAGE/ORDER INFORMATION



SYMBOL	PARAMETER	CONDITIONS		SG [.] MIN	150A/SG2	50A MAX	MIN	SG150 TYP	MAX	
VREF	Reference Voltage	$I_{OUT} = 10 \text{mA}, T_J = 25 ^{\circ}\text{C},$		1.238	1.250	1.262				V
		$3V \le (V_{IN} - V_{OUT}) \le 35V$ $10mA \le IOUT \le 3A, P \le 30W$	•	1.225	1.250	1.270	1.20	1.25	1.30	V
<u>ΔV_{OUT}</u> ΔV _{IN}	Line Regulation	3V ≤(V _{IN} − V _{OUT})≤ 35V, (See Note 2)			0.005 0.02	0.01 0.05		0.005 0.02	0.01	%/V %/V
ΔV _{OUT} ΔI _{OUT}	Load Regulation	$10mA \le I_{OUT} \le 3A$, (See Note 2) T _A = 25°C, V _{OUT} ≤ 5V			5	15		5	15	mV
		Vout ≥ 5V Vout ≤ 5V	•		<u>0.1</u>	0.3 50		0.1	0.3	% mV
	Thermal Regulation	$V_{OUT} \ge 5V$ T _A = 25 °C, 20msec Pulse	<u>+</u>		0.3	1 0.01		0.3	1 0.01	%
	Ripple Rejection	$V_{OUT} = 10V, f = 120Hz$ $C_{ADJ} = 0$ $C_{ADJ} = 10\mu F$	•	66	65 86	0.01	66	65 86	0.01	%/W dB dB
IADJ	Adjust Pin Current		•		50	100		50	100	μA
ΔI _{ADJ}	Adjust Pin Current Change	$\begin{array}{l} 10\text{mA} \leq \text{I}_{\text{L}} \leq 3\text{A} \\ 3\text{V} \leq (\text{V}_{\text{IN}} - \text{V}_{\text{OUT}}) \leq 35\text{V} \end{array}$			0.2	5		0.2	5	μΑ
	Minimum Load Current	$(V_{IN} - V_{OUT}) = 35V$	•		3.5	5		3.5	5	mA
	Current Limit	$(V_{IN} - V_{OUT}) \le 10V$ $(V_{IN} - V_{OUT}) = 30V$	•	3 0.3	4.5 1		3 0.3	4.5 1		A
ΔV _{OUT} ΔTEMP	Temperature Stability	– 55 °C ≤ T _J ≤+ 150 °C	•		1	2		1		%
ΔV _{OUT} ΔTIME	Long Term Stability	T _A = 125 °C			0.3	1		0.3	1	%
e _n	RMS Output Noise (% of V _{OUT})	$T_A = 25$ °C, 10Hz $\leq f \leq 10$ kHz			0.001			0.001		%
θ _{JC}	Thermal Resistance Junction to Case	K Package				1.5		* 9.4	1.5	•c/w
SYMBOL	PARAMETER	CONDITIONS		MIN	SG350A TYP	MAX	MIN	SG350 TYP	MAX	UNITS
VREF	Reference Voltage	$I_{OUT} = 10 \text{mA}, T_{J} = 25 ^{\circ}\text{C},$		1.238	1.250	1.262				V
		$3V \le (V_{IN} - V_{OUT}) \le 35V$ $10mA \le IOUT \le 3A, P \le 30W$	•	1.225	1.250	1.270	1.20	1.25	1.30	V
ΔV _{OUT} ΔV _{IN}	Line Regulation	$3V \leq (V_{IN} - V_{OUT}) \leq 35V$, (See Note 2) T _A = 25 °C			0.005 0.02	0.01 0.05		0.005 0.02	0.03 0.07	%/V %/V
ΔVουτ ΔΙουτ	Load Regulation	$\begin{array}{l} 10mA \leq I_{OUT} \leq 3A, (\text{See Note 2}) \\ T_A = 25^\circ\text{C}, \\ V_{OUT} \leq 5V \\ V_{OUT} \geq 5V \end{array}$			5 0.1	15 0.3		5 0.1	25 0.5	mV %
		Vou⊤ ≤ 5V Vou⊤ ≥ 5V	:		15 0.3	50 1		20 0.3	70 1,5	mV %
	Thermal Regulation	T _A = 25 °C, 20msec Pulse			0.002	0.01		0.002	0.03	%M
	Ripple Rejection	$V_{OUT} = 10V, f = 120Hz$ $C_{ADJ} = 0$ $C_{ADJ} = 10\mu F$	•	66	65 86		66	65 86		dB
ADJ	Adjust Pin Current			00	50	100	00	50	100	dB µA
ΔI _{ADJ}	Adjust Pin Current Change	$10mA \le I_{OUT} \le 3A$ $3V \le (V_{IN} - V_{OUT}) \le 35V$			0.2	5		0.2	5	μΑ
	Minimum Load Current	$(V_{IN} - V_{OUT}) \le 35V$	•		3.5	10		3.5	10	mA
	Current Limit	$(V_{IN} - V_{OUT}) \le 10V$ $(V_{IN} - V_{OUT}) = 30V, T_J = 25 ^{\circ}C$:	3 0.25	4.5 1		3 0.25	4.5		A
ΔV _{OUT} ΔΤΕΜΡ	Temperature Stability		•		1	2		1		%
ΔV _{OUT}	Long Term Stability	T _A = 125 °C			0.3	1		0.3	1	%
ידואו⊂ ו		-	}		0.001			0.001		
<u>∆`тіме</u> ∋n	RMS Output Noise (% of V _{OUT})	$T_A = 25 ^{\circ}C$, 10Hz $\leq f \leq 10$ kHz			0.001			0.001		%

The ${\mbox{ \bullet}}$ denotes the specifications which apply over the full operating temperature range.

temperature range. **Note** 1: Unless otherwise specified, these specifications apply for V_{IN} – Vour = 5V and lour = 1.5A. These specifications are applicable for power dissipations up to 30W for the K package and up to 25W for the T package. Power dissipation is guaranteed at these values up to 15 Volts input-output

differential. Above 15 Volts input-output differential power dissipation is limited by device internal protections circuitry. **Note 2:** Regulation is measured at a constant Tj. Changes in output due to heating must be taken into account separately. Pulse testing with low duty cycle is used.

APPLICATIONS INFORMATION

General

The SG150A develops a 1.25V reference voltage between the output and the adjustable terminal (see Figure 1). By placing a resistor, R1, between these two terminals, a constant current is caused to flow through R1 and down through R2 to set the overall output voltage. Normally this current is the specified minimum load current of 5mA or 10mA.



Basic Adjustable Regulator Figure 1

Because I_{ADJ} is a very small and constant when compared with the current through R1, it represents a small error and can usually be ignored. It is easily seen from the above equation, that even if the resistors were of exact value, the accuracy of the output is limited by the accuracy of V_{REF}. Earlier adjustable regulators had a reference tolerance of $\pm 4\%$ which is dangerously close to the $\pm 5\%$ supply tolerance required in many logic and analog systems. Further, even 1% resistors can drift 0.01%/°C, adding additional error to the output voltage tolerance.



Bypass Capacitors

Input bypassing using a 1μ F tantalum or 25μ F electrolytic is recommended when the input filter capacitors are more than 5 inches from the device. Improved ripple rejection (80 dB) can be accomplished by adding a 10µF capacitor from the adjust pin to ground. Increasing the size of the capacitor to 20µF will help ripple rejection at low output voltage since the reactance of this capacitor should be small compared to the voltage setting resistor, R2. For improved AC transient response and to prevent the possibility of oscillation due to unknown reactive load, a 1µF capacitor is also recommended at the output. Because of their low impedance at high frequencies, the best type of capacitor to use is solid tantalum.

Load Regulation

Because the SG150A is a three-terminal device, it is not possible to provide true remote load sensing. Load regulation will be limited by the resistance of the wire connecting the regulator to the load. The data sheet specification for load regulation is measured at the bottom of the package. Negative side sensing is a true Kelvin connection, with the bottom of the output divider returned to the negative side of the load. Although it may not be immediately obvious, best load regulation is obtained when the top of the resistor divider (R1) is connected directly to the case, not the load. This is illustrated in Figure 2. If R1 were connected to the load, the effective resistance between the regulator and the load would be

$$R_p \times \left(\frac{R2 + R1}{R1}\right)$$
, $R_p = Parasitic Line Resistance$.

Connected as shown, R_p is not multiplied by the divider ratio. R_p is about 0.004 Ω per foot using 16 gauge wire. This translates to 4mV/ft at a 1A load current, so it is important to keep the positive lead between regulator and load as short as possible, and use large wire or PC board traces.

SG150A / SG250A / SG350A SG150 / SG250 / SG350



SILICON GENEPAL

ADVANCED DATA SG153/SG253/SG353

Performance data described herein represent design goals. Final design specifications are subject to change.

HIGH CURRENT FIXED VOLTAGE REGULATORS

DESCRIPTION

The SG153 family of fixed-voltage, three-terminal regulators are designed to supply load currents in excess of three amps over a wide range of operating conditions. Requiring nothing more than a small output capacitor, these regulators feature output voltages internally trimmed to greater than $\pm 2\%$ accuracy. In addition to excellent line regulation, a voltage-boost circuit provides positive load regulation (increasing output voltage with increasing load current) to help correct for line losses.

All protective features of thermal shutdown, current limiting, and safe-area control have been designed into these units with added reliability offered by a hard-solder eutectic die attach and an hermetically sealed TO-3 power package.

FEATURES

- Load current in excess of 3A
- Output voltage trimmed to ±2%
- · Complete self-contained protective features
- Correction for line resistance
- · Eliminates external voltage setting resistors
- · Hermetically sealed steel power package
- · Available with 5, 12, and 15 volt outputs



ELECTRICAL CHARACTERISTICS (See Note 1)

V _{in} unless otherwise sp	pecified (Note 1)		10V			19V —					25V			
PARAMETER	TEST CONDITIONS		G253-05	SG35			G253-12			SG153/S		SG35		UNITS
		MIN	MAX	MIN	MAX	Min	MAX	MIN	MAX	MIN	MAX	MIN	MAX	01110
VOUT	$I_0 = 1A, 25^{\circ}C$ $V_{IN} = (V_{OUT} + 2.5V) \text{ to } 30V$ $I_0 = 5\text{mA} \text{ to } 3A, P \le 30W$	4.9 4.8	5.1 5.2	4.8 4.4	5.2 5.4	11.8 11.6			12.5 12.75	14.8 14.6		14.4 14.15	15.6 15.85	v v
Load Regulation (Note 2)	5mA-1A 5mA-3A I ₀ , 25°C 500mA-1.5A		20 30 20		30 50 30		50 80 50		80 130 80		60 100 60		100 150 100	mV mV mV
Line Reg. Range	(Note 2)		7V ≤ VN	≤ 25V		14	1.5V ≤ \	IN ≤ 30	V	1	7.5V < 1	/N ≤ 30'	V	
Line Regulation	$I_0 = 1A, 25^{\circ}C$		50		75		50	ľ	100		50		100	mV
Line Reg. Range	(Note 2)		8V ≤ VN	≤ 12V	2V 16V ≤ V		16V ≤ Vi	≤ V _{IN} ≤ 22V		20V ≤ V _N ≤ 26V				
Line Regulation	$I_0 = 1A, 25^{\circ}C$		25		50		30		60		30		60	mν
Quiescent Current	$I_0 = 1A, 25^{\circ}C$		9		12		9		12		9		12	mA
Quiescent Current Change	$\begin{array}{llllllllllllllllllllllllllllllllllll$		500 1.0		500 1.5		500 1.0		500 1.5		500 1.0		1.5	μA mA mA mA
I ₀ — Peak	25°C V _{IN} = 35V, 25°C	3 60	6	3 60	6	3 600	6	3 600	6	3 600	6	3 600	6	A mA
Io, Short Circuit	$V_0 = V_{IN} = 35V, 25^{\circ}C$		100		100		100		100		100		100	mA
Ripple Rejection at $I_0 = 100 \text{mA}$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	51		41		46		41		46		41		dB dB dB

Note 1: Unless otherwise specified, these specifications apply: $-55^{\circ}C \leq T_J \leq +150^{\circ}C$ for the SG153; $-25^{\circ}C \leq T_J \leq +150^{\circ}C$ for the SG253, and $0^{\circ}C \leq T_J \leq +125^{\circ}C$ for the SG353 and $0_{UIT} = 1.0A$. Although power dissipation is internally limited, these specifications are applicable for power dissipations up to 30W.

Note 2: Regulation is measured at constant junction temperature. Changes in output voltage due to heating effects must be taken into account separately. Pulse testing with low duty cycle is used. LINEAR INTEGRATED CIRCUITS

ilicon General

SG723/723C

General-Purpose Positive Regulator

This regulator is designed for use with either positive or negative supplies as a series, shunt, switching, or floating regulator with currents up to 150mA. Higher current requirements may be accommodated through the use of external NPN or PNP power transistors.

- Positive or negative supply operation
- 0.03% line and load regulation
- Output adjustable from 2 to 37V
- Low standby current drain
- 0.002%/⁰C average temperature variation

PARAMETERS	723 ¹	723C ¹	UNITS
Operating Temperature Range	-55 to +125	0 to +70	°C
Package Types	Т*, Ј	T*, J, N	-
Input Voltage Range	9.5 to 50	9.5 to 50	v
Output Voltage Range	2.0 to 37	2.0 to 37	V
Input/Output Differential	3.0 to 38	3.0 to 38	V
Load Regulation ^{2,3}	0.15	0.2	% Vou
Line Regulation V _{in} = 12 to 40V	0.2	0.5	% V _{ou}
Ripple Rejection C _{ref} = 5µF; f = 50Hz to 10KHz	86 (typ)	86 (typ)	dB
Reference Voltage	6.95 - 7.35	6.80 - 7.50	V
Temperature Stability	0.015	0.015	%/ºC
Output Noise Voltage C _{ref} = 0; BW = 100Hz to 10KHz	20 (typ)	20 (typ)	μV rm:
Standby Current Drain	3.5	4.0	mA
Minimum Load Current	0	0	mA
Long Term Stability	0.1 (typ)	0,1 (typ)	%/khr

¹Parameters apply at $T_A = +25^{\circ}C$, except temperature stability is over temperature ranges.

² Applies for constant junction temperature. Temperature drift effects must be taken into account separately when the unit is operating under conditions of high dissipation.

 ${}^{3}I_{L} = 1 \text{ to 50 mA}.$

*T-package is TO-96 (can height: 240" max., 230" min.)



SG723/723C Chip (See T-package for pad functions) Note: V_Z (Pin X) is available only in J or N-Package



High Current Regulator External NPN Transistor it_ = 1A

CONNECTION DIAGRAMS







Basic High Voltage Regulator Vout = 7 to 37 volts



Basic Low Voltage Regulator Vout = 2 to 7 volts

ilicon General LINEAR INTEGRATED CIRCUITS

SG1501A/2501A/3501A/4501

Dual-Polarity Tracking Regulators

SG1501A dual tracking regulators are factory set to provide balanced \pm 15V outputs, but a single external adjustment can be used to change both outputs, simultaneously. Line regulation of 20 mV and load regulation of 30 mV is guaranteed, and stability, over temperature, is 1% or less. Provision is made for adjustable current limiting and operation in excess of 2 amps is feasible with external transistors.

In the SG1501A, a buit-in sensing circuit monitors junction temperature and shuts down the regulator above 170°C eliminating the need for concern about power dissipation under short circuit conditions. The SG1501A series also offers superior input/output voltage range and current handling capability (refer to table of specifications.).

- Thermal shutdown protection
- ±35V inputs
- Output current to 200mA
- Output adjustable from ±10V to ±23V

PARAMETERS ¹	1501A	2501A	3501A	4501	UNITS
Operating Temperature Range	-55 to +125	0 to +70	0 to +70	0 to +70	°C
Package Types	T, J		T, J, N		-
Output Voltage	±14.8/1	5.2	±14.5/15.5	±14.25/15.75	v
Input Voltage	±35		±30	±30	v
Input/Output Differential	2		2	2	V
Output Voltage Balance	150		300	300	mV
Line Regulation (Vin = 17 to Vmax) ⁵	20		20	20	mV
Load Regulation (IL = 0 to 50mA) ⁵	30		30	30	mV
Output Voltage Range	10 to 23	3	10 to 23	10 to 23	V
Input Voltage Range (8V _{out})	10 to 35		10 to 30	12 to 30 ⁴	v
Ripple Rejection (f = 120Hz)	75 (typ)	75 (typ)	75 (typ)	dB
Temperature Stability	1.0		1.0	1.0	%
Short Circuit Current Limit ²	60 (typ))	60 (typ)	60 (typ)	mA
Output Noise Voltage ³	50 (typ)	50 (typ)	50 (typ)	μVrms
Positive Standby Current	4		4	4	mA
Negative Standby Current	5		5	5	mA
Long Term Stability	0.1 (typ)		0.1 (typ)	0.1 (typ)	%/khr
Output Current	200		200	100	mA
Thermal Shutdown Protection	yes		yes	yes	

¹All specifications apply to both positive and negative sides of the regulator, either singly or together. Unless otherwise specified $T_A = +25^{\circ}$ C, $V_{in} = 20V$, $V_{out} = 15V$, $i_L = 0$, Rsc = 0Ω , C1 = C2 = 0.01 mfd, C3 = C4 = 1.0 mfd, voltage adjust pin open 2 Rsc = 10 Ω ⁴10∨ out put

³BW = 100Hz to 10kHz

⁵Over temperature range



SG1501A/2501A/3501A Chip (See T-package diagr for pad functions) Note: Balance Adjust (Pin X) is available only on D or N package.)



CONNECTION DIAGRAMS



POS. OUTPUT POS. SENSE

Silicon General

LINEAR INTEGRATED CIRCUITS

SG1502/2502/3502

Adjustable Dual-Polarity Tracking Regulators

This circuit is identical to the SG1501 series of dual polarity tracking regulators except that the internal voltage setting resistors are not included and the current limit inputs have been disconnected from the pass transistors. While this circuit does require external divider resistors, maximum versatility is offered in adjusting the output voltage levels, and additional current-limit inputs ease the application of foldback current limiting. In all other respects, this circuit performs as the SG1501.

- · Positive and negative output voltages independently adjustable from 10 to 28V
- Output currents to 100mA
- Line and load regulation of 0.1%
- 1% maximum temperature variation
- Standby current drain only 4mA
- · Internal thermal shutdown protection

PARAMETERS*	1502	2502	3502	UNITS	
Operating Temperature Range	-55 to +125	0 to +70	0 to +70	°C	
Package Types	J, N		J, N	-	
Input Voltage Range	±12/	30	±12/25	v	
Output Voltage Range	±10/	28	±10/23	v	
Input/Output Differential	2	2			
Line Regulation $(\Delta V_{in} = 10V)^5$	0V) ⁵ 0.2 0.2			% V _{out}	
Load Regulation (IL = 0 to 50mA) ⁵	0.3	0.3	% V _{out}		
Temperature Stability	1.0	1.0		% V _{out}	
Current Limit Sense Voltage	0.6 (0.6 (typ)		v	
Reference Voltage	6.3/6	6.6	6.2/6.8	V	
Ripple Rejection f = 120Hz	75 (t	yp)	75 (typ)	dB	
Output Noise Voltage ²	50 (t	50 (typ)		μVrms	
Positive Standby Current ³	4		4	mA	
Negative Standby Current ³	5	5	mA		
Long Term Stability	0.1 (0.1 (typ)	%/khr		

 1 All specifications apply to both positive and negative sides of the regulator either singly or together. Unle $T_A = +25^{\circ}C$, $V_{in} = +20V$, $V_{out} = +15V$, $I_L = 0$, $R_{sc} = 0\Omega$, C1 = C2 = 0.01 mfd, C3 = C4 = 1.0 mfd.

³Divider 1 = 0.5mA ²BW = 100Hz to 10kHz

⁴1502 not available in plastic

⁵Over temperature range

CONNECTION DIAGRAM





See Applications Notes for additional information

BASIC REGULATOR CIRCUIT



NEGATIVE VO - 6.5 × (R1 × R2) , POSITIVE VO - R3 NEGATIVE VO

For best temperature performance, the parallel impedance of R1 and R2 should be 6.3 K ohm while that of R3 and R4 should be 10 K. Increasing the value of C1 and C2 will reduce the frequency response while transient response may be improved by increasing C3 and C4. For very low-noise applications, a 4.7 mfd capacitor for Cref may be added. Rsc is selected such that a sense voltage of 0.6 volts (at Tj = 25°C) is developed at the maximum load current desired.

SILICON GANAPAL

SG1532 / SG2532 / SG3532

PRECISION GENERAL-PURPOSE REGULATOR

DESCRIPTION

This monolithic integrated circuit is a versatile, generalpurpose voltage regulator designed as a substantially improved replacement for the popular SG723 device. The SG1532 series regulators retain all the versatility of the SG723 but have the added benefits of operation with input voltages as low as 4.5 volts and as high as 50 volts; a low noise, low voltage reference; temperature compensated, low threshold current limiting; and protective circuits which include thermal shutdown and independent current limiting of both the reference and output voltages. Also included is a separate remote shutdown terminal and - in the dual-in-line package - open collector outputs for low input-output differential applications.

These devices are available in both hermetic 14-pin cerdip DIL and 10-pin TO-96 packages. In the T-package, these units are interchangeable with the LAS-1000 and LAS-1100 regulators. The SG1532 is rated for operation over the temperature range of -55°C to +125°C while the SG2532 and SG3532 are intended for industrial applications of 0°C to +70°C.

FEATURES:

- Input voltage range of 4.5 to 50 volts
- 2.5 volt low noise reference
- Independent shutdown terminal
- Improved line and load regulation
- 80 mV current limit sense voltage
- Fully protected including thermal shutdown
- Useful output current to 150 mA

ABSOLUTE MAXIMUM RATINGS:

Input Voltage SG1532/2532 SG3532	50 Volts 40 Volts
Output Current	250 mA
Reference Current	25 mA
Zener current (J-package only)	100 mA
Storage Temperature Range	-65°C to +150°C
Power Dissipation T-Package (TO-96) Derate Above 25 ⁰ C	800 mW 6.4 mW/ºC
J-Package (TO-116) Derate Above 25 ⁰ C	1000 mW 8 mW/ºC
Operating Temperature Range SG1532 SG2532 and SG3532	-55°C to +125°C 0°C to +70°C





CONNECTION DIAGRAMS

ELECTRICAL CHARACTERISTICS (See Notes 1 & 2)

		SG1	532/2	532	S	G353	2	
PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
Input Voltage	T _A = 25°C	4.5	-	50	4.5	-	40	Volts
Input Voltage	Over Temperature Range	4.7	-	50	4.7	—	40	Volts
Output Voltage		2.0	-	38	2.0	-	38	Volts
Max Output Current	RSC = 0, VO = 0, TA = 25°C		175	250	1	175	250	mA
Min (VIN – VO)	IO = 100 mA, TA = 25°C	1	1.7	2.0	—	1.7	2.0	Volts
Reference Voltage	T _A = 25°C	2.40	2.50	2.60	2.40	2.50	2.60	Volts
Reference Voltage	Over Temperature Range	2.35	1	2.65	2.35	_	2.65	Volts
Temperature Stability		-	.005	.015	_	.005	.015	%/ºC
Ref Short Ckt Current	VREF = 0, TA = 25°C	-	15	25	-	15	25	mA
Line Regulation	8V ≤ V _{IN} ≤ 40V	-	.005	.01	-	.005	.02	%/V
Line Regulation	8V ≤ V _{IN} ≤ 20V, I _O = 25 mA		.01	.02	-	.01	.03	%/V
Load Regulation	1 mA ≤ IQ ≤ 25 mA	-	.002	.004	-	.002	.004	%/mA
Load Regulation	1 mA ≤ IO ≤ 100 mA	_	.002	.005	-	.002	.005	%/mA
Current Limit Sense Voltage	R _{SC} = 100Ω, V _O = 0	.06	.08	.10	.06	.08	.10	Volts
Shutdown Voltage Threshold		.40	.70	1.0	.40	.70	1.0	Volts
Shutdown Source Current	VO ≈ high	100	200	300	100	200	300	μA
Zener Voltage	J-Package only	6.0	6.4	7.0	6.0	6.4	7.0	Volts
Standby Current	VIN = 40V		2.5	3.5	-	2.5	3.5	mA
Error Amplifier Offset Voltage		_	2.0	10		2.0	15	mV
Error Amplifier Input Bias Current		-	4	15	_	4	20	μA
Open Loop Gain	T _A = 25°C	66	68	72	60	68	72	dB
Ripple Rejection	f = 120Hz, TA = 25°C	-	66	-	-	66	-	dB
Output Noise	10Hz ≤ f ≤ 100kHz, TA = 25°C	-	50		-	50	-	μVrms
Long Term Stability	VIN = 30V, TA = 125°C	-	0.3	1.0		0.3	1.0	%/kHr
Thermal Shutdown		-	175			175		٥C

Note 1: Unless otherwise specified, $V_{IN} = 10V$, $V_O = 5V$, $I_O = 1$ mA, $T_A =$ specified operating range.

Note 2: All regulation specifications are measured at constant junction temperature using low duty-cycle pulse test.



SG1532 / SG2532 / SG3532



SG1532 / SG2532 / SG3532



APPLICATIONS



Licon General LINEAR INTEGRATED CIRCUITS

Dual-Polarity Tracking Regulators

SG1568/1468 is a dual polarity tracking regulator designed to provide balanced positive and negative output voltages at currents to 100mA. The device is set internally for ±15V outputs but a single external adjustment can be used to change both outputs simultaneously from 14.5 to 20 volts. Input voltages up to ±30 volts can be used and there is provision for adjustable current limiting.

- Outputs balanced to within 1% (SG1568)
- Line and load regulation of 0.06%
- 1% maximum output variation due to temperature changes
- Standby current drain of 3.0mA
- Remote sensing provisions

PARAMETERS*	SG 1568	SG 1468	UNIT
Operating Temperature Range	-55 to +125	0 to +75	°C
Package Types	T,J	T, J, N	-
Peak Load Current	10	D	mA
Storage Junction Temp Range	65 to ·	+175	°C
Output Voltage	14.8/15.2	14.5/15.5	v
Input Voltage	30	30	V
Input-Output Voltage Differential	2.0	2.0	V
Output Voltage Balance	±150	±300	mV
Line Regulation Voltage			
(V _{in} = 18V to 30V)	10	10	
$(T_{low}^{1} \text{ to } T_{high}^{2})$	20	20	mV
Load Regulation Voltage			
(IL = 0 to 50 mA, TJ = constant)	10	10	1
$(T_A = T_{low} \text{ to } T_{high})$	30	30	mV
Output Voltage Range	14.5/20	14.5/20	V
Ripple Rejection (f = 120Hz)	75 (typ)	75 (typ)	dB
Output Voltage Temperature Stability			
(Tlow to Thigh)	1.0	1.0	%
Short-Circuit Current Limit			
(R _{SC} = 10 ohms)	60 (typ)	60 (typ)	mA
Output Noise Voltage	· · · · · · · · · ·		
(BW = 100Hz - 10kHz)	100 (typ)	100 (typ)	μV(rms)
Positive Standby Current			
(V _{in} = +30V)	4.0	4.0	mA
Negative Standby Current			
(V _{in} = -30V)	3.0	3.0	mA
Long-Term Stability	0.2 (typ)	0.2 (typ)	%/k Hr



CONNECTION DIAGRAMS

SG1568/1468









SG1568/1468 Chip (See diagram for pad functions)

(VCC = +20V, VEE = -20V, C1 = C2 = 1500 pF, C3 = C4 = 1.0 μ F, R_{SC}⁺ = R_{SC}⁻ = 4.0 Ω , $I_L^+ = I_L^- = 0$, $T_C = +25^{\circ}C$ unless otherwise noted.)

T_{low} = 0°C for 1468

= --55°C for 1568

²T_{high} = +75^oC for 1468 = +125^oC for 1568

Basic 50 mA Regulator



C1 and C2 should be located as close to the device as possible. A 0.1μ F ceramic capacitor may be required on the input lines if the device is located an appreciable distance from the rectifier filter capacitors.

C3 and C4 may be increased to improve load transient response and to reduce the output noise voltage. At low temperature operation it may be essary to bypass C4 with a 0.1µF ceramic disc capacitor.

±1.5 Amp Regulate (Short Circuit Protected, with Proper Heatsinking)



See Applications Notes for additional information.

SILICON GENERAL LINEAR INTEGRATED CIRCUITS

SG7800A/7800AC/7800/7800C/140/240/340

Three Terminal Positive Regulators

DESCRIPTION

The SG7800A/7800/140 series of positive regulators offer self contained, fixed-voltage capability with up to 1.5 amps of load current and input voltages up to 50 volts. (SG7800A series only)

These units feature a unique on-chip trimming system to set the output voltages to within $\pm 1.5\%$ of nominal on the SG7800A series, $\pm 2.0\%$ on the SG140/240 series, and $\pm 4.0\%$ on the SG7800/340 series. The SG7800A versions also offer much improved line and load regulation characteristics.

All protective features of thermal shutdown, current limiting, and safe-area control have been designed into these units and since these regulators require only a small output capacitor for satisfactory performance, ease of application is assured.

Although designed as fixed-voltage regulators, the output voltage can be increased through the use of a simple voltage divider. The low quiescent drain current of the device insures good regulation when this method is used.

Product is available in hermetically sealed TO-3, TO-39 and TO-66 power packages as well as the plastic TO-220 package.



GROUND P-Package TO-220 OUTPUT 3 FRONT VIEW Ç Q $^{(2)}$ INPUT OUTPUT - Input ന - Output _ Ground GROUND - Ground Tab INPUT С T-Package R-Package TO-39 TO-64 TO-3

FEATURES

- Output voltage set internally to ±1.5% on SG7800A
- · Input voltage range to 50 volts max. on SG7800A
- Two volt input-output differential
- · Excellent line and load regulation
- Foldback current limiting
- Thermal overload protection
- Voltages available 5V, 6V, 8V, 12V, 15V, 18V, 20V, 24V

ABSOLUTE MAXIMUM RATINGS

Device Output Voltage	Input Voitage (operating)	7800A Series Input Voltage (transient)*	Input Voltage (Output shorted to ground)
5V	35V	50V	35V
6V	35V	50V	35V
8V	35V	50V	35V
12V	35V	50V	35V
15V	35V	50V	35V
18V	35V	50V	35V
20V	35V	50V	35V
24V	40V	50V	35V
	*see not	e next page	

Operating Junction Temperature Range

SG7800A/7800/140	-55°C to +150°C
SG240	0°C to +150°C
SG7800AC/7800C/340	0°C to +125°C
torage Temperature Range	-65°C to +150°C
unleal Damas/Thomas Observation	

Typical Power/Thermal Characteristics

C:

Package	K (TO-3)	R(TO-66)	P (TO-220)	T (TO-30
25°C Case Rated Power	20W	15W	15W	2W
25°C Ambient Rated Power	4.3W	3.0W	2.0W	1.0W
Design Current	1.5A	1.5A	1.0A	0.5A
Therm. Res. θJC (°C/W) θJA (°C/W)	3.0 35	5.0 40	3.0 60	15 120





Note: Operation at high input voltages is dependent upon load current. When load current is less than 5 mA, output will rise out of regulation as input-output differential increases beyond 30 volts. Note also from curve above, that maximum load current is reduced at high voltages. The 50 volt input rating of the SG7800A series refers to ability to withstand high line or transient conditions without damage. Since the regulator's maximum current capability is reduced, the output may fall out of regulation at high input voltages under nominal loading.

60

APPLICATIONS









CIRCUIT FOR INCREASING OUTPUT VOLTAGE



ADJUSTABLE OUTPUT REGULATOR, 7 to 30 VOLTS



К, В, Т К, R, Т
-55°C to -55°C to +150°C 150°C
TYP MAX MIN
5.08 4.8
5 25
2 12
15 50
5 25
5 25
5.15 4.75
4 6
7
0.8
0.5
1.8
5
1.0
2.1
0.7
-0.5
70
40
20
175

Three Terminal Positive Regulators

Pos. 5.0 Volts

6. Short circuit protection is only assured to $V_{IN} = 35V$. 5. At T_J = -55° C, minimum (V_{IN} - VO) = 2.5V.

testing.

4. All regulation tests are made at constant junction temperature with low duty-cycle

3. Unless otherwise specified. VIN = 10V and I_O = 500mA for K,R,P-Pkg; I_O = 100mA for T-Pkg.

1. Minimum load current for full line regulation is 5mA. 2. Maximum test current for T-Pkg is 500mA.

SG7805C K, P, R, T

SG340-05(309)

SG7805AC

SG7805(109)

SG140-05

SG7805A

DEVICE PART NUMBERS PACKAGE STYLES (P/N SUFFIX)

		0	DEVICE PART NUMBERS	s	SG7806A	4	SG	SG140-06		SG7	SG7806		SG7806A	N6A	S	SG340-06	90	Š	SG7806C	0	
		PACKAG	PACKAGE STYLES (P/N SUFFIX)		К, Я, Т			K,R,T		K,R,T	۲.		K,P,R,T	۲.		K, P, R, T	F	¥	K,P,R,T		
ō	ERATING	LUNCTION (Unless of	OPERATING JUNCTION TEMPERATURE RANGE (Unless otherwise specified below)	1	-55°C to +150°C	•	l i f	-55°C to 150°C		-55° 150	-55°C to 150°C		0°C to 125°C	20		0° C to 125° C		0 -	0° C to 125° C		
PARAMETERS	RS	TEST CONE	CONDITIONS (See notes below)	NW		TYP MAX	NIW	TYP N	MAXM	T VIM	TYP MAX	AX MIN	N TYP	MAX	NW	ТҮР	MAX	NW	Δ¥Ρ	MAX	UNITS
Output Voltage	lge	T _J = 25°C		5.9		6.1	5.75		6.25 5.	5.75	ن ه	6.25 5.9	6	6.1	5.75		6.25	5,75	T	6.25	>
		L order	V _{IN} = 8 to 25V		9	8		9	8	ľ	9	8	9	8		9	8		12	120	Ę
LINE REGUIATION	tion	0.62 = LI	•		3	15		3	30		3	30	3	30		3	30		9	99	È
	P,R,K		IO = 5mA to 1.5A		20	60		20	8	~	20	09	8	8		20	80		6	120	È
Regulation	Pkg	TJ = 25°C	IO = 250 to 750mA		6	8		9	30		6 3	8	9	8		9	30		12	8	È
	T-Pkg		$I_{O} = 5mA$ to 500mA		6	30		9	30	-	6 3	30	9	8		9	30		12	60	> E
Total Output	1	K-Pkg: IO	K-Pkg: I _O = 5 to 1.0A, P 20W															_			
Voltage Tolerance	erance	R,P-Pkg: I _C	R,P-Pkg: I _O = 5 to 1000mA, P ≤ 15W	5.82		6.18	5.7		6.3 5.	5.65	ý	6.35 5.82	2	6.18	5.7		6.3	5.7		6.3	>
	>	T-Pkg: IO	T-Pkg: I _O = 5 to 500mA, P ≤ 2W					-+	\neg			-									
Contract Creating	100221	T _J = 25°C			4	6		4	6		4	6	4	9		4	8		4	8	٩W
Curescent C		Over Temp	Over Temperature Range			7			7		-	7		2			8.5			8.5	٩W
Quiescent Current	urrent	With line: V	line: V _{IN} = 8 to 25V			0.8			0.8		0	0.8		1.0			1.0			1.3	٩w
Change		With load:	load: 1 ₀ = 5 to 1000mA			0.5			0.5		0	0.5		0.5			0.5			0.5	٩u
Dropout Voltage	tage	T - 36° C	K,R,P-Pkg: IO = 1A		2			2		5	2	_	2			2			2		>
4VO = 100mV	۲ د		T-Pkg: I _O = 500mA		1.8			1.8		1.8	8		1.8			1.8			1.8		•
Peak Output		עי= 35°C			2.5			2.5		5	2.5	_	2.5			2.5			2.5	_	۲
Current		0 07 - [1	T-Pkg		1.0			1.0		1.0	0		1.0			1.0			1.0		۲
Short Circuit	t	ד - יזניר ד	K,R,P-Pkg		2.0			2.0		2.0	•		2.0			2.0			2.0	-	۲
Current			T-Pkg		0.6			0.6		0.6	9		0.6			0.6			9.6		۲
Temperature Coefficient		lo = 5mA			-0.5			-0.5		-0.5	5.		-0.5			-0.5			-0:5		∧°C ∕°
Ripple Rejection	tion	τ _J = 25° C,	25° C, f = 120Hz, Δ V _{IN} = 10V		68			68		68	8		68			68			68		đB
Output Noise Voltage	æ	T _J = 25°C,	25° C, f = 10Hz to 100 kHz		45			45		45			45			45			45		vr ™s
Long Term Stability	Stability	1000 hrs. at T _J	t T_J = 125°C		24			24		24	+		24			24			24 24		۶
Thermal Shutdown	utdown	l _O = 5mA			175			175		175	5		175			175			175		ပ္
NOTES:																					
1. Minimum lo	ad curren	t for full line r	1. Minimum load current for full line regulation is 5mA.							4. All i	egula	tion te	4. All regulation tests are made at constant junction temperature with low duty-cycle	nade al	const	antjun	ction t	Smpera	aturew	/ith lov	/ duty-
2. Maximum te	est current	2. Maximum test current for T-Pkg is 500mA.	500m A.							testing.	ing.										•

Three Terminal Positive Regulators

Pos. 6.0 Volts

6. Short circuit protection is only assured to $V_{IN} = 35V$. 5. At $T_J = -55^{\circ}$ C, minimum (V_{IN} - VO) = 2.5V.

3. Unless otherwise specified, VIN = 11V and I_O = 500mA for K,R,P-Pkg: I_O = 100mA for T-Pkg.

KIT KIT <th></th> <th></th> <th>DEVICE PART NUMBERS</th> <th>00</th> <th>SG7808A</th> <th></th> <th>Ċ.</th> <th>SG140-08</th> <th>_</th> <th>SG7808</th> <th>ROB</th> <th>_</th> <th>CG7808AC</th> <th>U V B</th> <th></th> <th>01000</th> <th>ę</th> <th>Ċ</th> <th></th> <th></th> <th></th>			DEVICE PART NUMBERS	00	SG7808A		Ċ.	SG140-08	_	SG7808	ROB	_	CG7808AC	U V B		01000	ę	Ċ			
						+	3		╉	3		╉					ş	"	12/808	5	
		PACKAG	E STYLES (P/N SUFFIX)	¥	н, н		¥	н,	_	Х, К,	F		K, P, R	F		K, P, R,	Т	¥	, P. R. T		
METERS TEST COMDITIONS (See noteo below) Mini TYP Max Mini TYP </th <th>OPERATIN</th> <th>G JUNCTION (Unless of</th> <th>TEMPERATURE RANGE therwise specified below)</th> <th>-55 +1</th> <th>°C to</th> <th></th> <th>-55 15</th> <th>0°C 0°C</th> <th></th> <th>-55° (</th> <th>e o</th> <th></th> <th>0°C 125°</th> <th>è o</th> <th></th> <th>0°C to 125°C</th> <th></th> <th>0.</th> <th>0° C to 125° C</th> <th></th> <th></th>	OPERATIN	G JUNCTION (Unless of	TEMPERATURE RANGE therwise specified below)	-55 +1	°C to		-55 15	0°C 0°C		-55° (e o		0°C 125°	è o		0°C to 125°C		0.	0° C to 125° C		
$ \begin{array}{l l l l l l l l l l l l l l l l l l l $	PARAMETERS	TEST CONE	ITIONS (See notes below)						-				-		_			NIW		_	UNITS
Image: light of the set of the	Output Voltage	TJ = 25°C		7.88	~		2	®.	+	-	8.3	1	Ļ	8.12			8.3	7.7	Ī	8.3	>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	lion Bootin	T - 750 C	V _{IN} = 10.5 to 25V			ę				8	8		8	8		8	80		16	160	Ę
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	спле медиканоп	רי ני	$V_{IN} = 11$ to 17V			R	-			4	6		4	\$		4	4		80	8	È
$ \begin{array}{ $			I_0 = 5mA to 1.5A			2				24		·	24	8		24	8		\$	160	È
$ \begin{array}{ $	lation L	- 11				8		-	-	8	4	-	80	\$		80	40		16	8	Ę
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	-		IO = 5mA to 500mA			35	-	-		æ	4		80	4		8	40		16	8	Ę
$ \frac{\mathrm{R.P-Frig: 10}}{\mathrm{T.Prig: 10} = 5 \text{ to 500mA, } \mathbf{P} \leq 13W}{\mathrm{T.Prig: 10} = 5 \text{ to 500mA, } \mathbf{P} \geq 2W} \ 7.6 \ 8.24 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.4 \ 7.6 \ 8.5 \ 8.6 \ 7.6 \ 8.5 \ $	Total Output	K-Pkg: IO	= 5 to 1.0A, P 20W			-	-	-	-												
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Voltage Tolerance	R, P-Pkg: I _O		7.76	80	24	9	œ	_		8.4			8.24	7.6		8.4	7.6		8.4	>
$ \begin{array}{l l l l l l l l l l l l l l l l l l l $	V _{IN} = 11.5 to 23V	T-Pkg: Io =	= 5 to 500mA; P≤2W			-			_		<u> </u>			<u></u>							
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Outpost O	T _J = 25°C				9	-			4	9		4	9		4	8		4	8	₹ E
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		Over Temp	erature Range			~	-		L	ļ	~			~			8.5			8.5	٩w
With load: $ _{O} = 5 \text{ to 1000mA}$ 0.5 0.5	Quiescent Current	With line: V	IN = 11.5 to 25V			8.		ö		L	0.8	ļ		0.1			1.0			0.1	₹ E
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Change	With load: I	O = 5 to 1000mA		0	.5		ö	5		0.5			0.5			0.5			0.5	¥ E
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Dropout Voltage	T.= 25°C	K,R,P-Pkg: ł _O = 1A		2			2		2			2			2			~	\square	:
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	4VO = 100mV) 23 [-	T-Pkg: I _O = 500mA	-	8.		+	8.		1.8			1.8			1.8			1.8		>
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Peak Output	11	K,R,P-Pkg	~	Ŀ.		2	5		2.5			2.5			2.5			2.5		<
	Current		T-Pkg	-	0.		1	0		1.0			1.0			1.0			1.0		<
'J $= 0.6$ 0.6 0.6	Short Circuit	- 18	K,R,P-Pkg	-	8.		-	8		1.8			1.8			1.8			1.8		<
$I_O = 5mA$ -0.6 <	Current		T-Pkg	0	9.		•	9		0.6			0.6			0.6			0.6		<
$T_J = 25^{\circ}C_t t = 120hz$, $\Delta V_{IN} = 10V$ 68 68	Temperature Coefficient	IO = 5mA		T	9.6		<u> </u>	9.6		9.0 			-0.6			-0.6			-0.6		≥ °
T J = 25°C, f = 10Hz to 100 kHz 52 52 52 52 52 1000 hrs. at T J = 125°C 32 32 32 32 32 100 brs. at T J = 125°C 175 175 175 175 175	Ripple Rejection	T_J = 25°C,	$f = 120Hz, \Delta V_{IN} = 10V$	_	38		-	88		68			89			68			89		89
1000 hrs. at T _j = 125°C 32	Output Noise Voltage	TJ = 25°C,	f = 10Hz to 100 kHz		5		2	2		52			52			52			52	<u> </u>	v ™
lo = 5mA 175 175 175 1765 175	Long Term Stability	1000 hrs. at	T _J = 125°C	.,	2			2		32			32			32			32		ž
	Thermal Shutdown	l _O = 5mA		1	75		-	75		175			175			1765			175		ပ့

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Three Terminal Positive Regulators

Pos. 8.0 Volts

- 1. Minimum load current for full line regulation is 5mA.
 - 2. Maximum test current for T-Pkg is 500mA.
- 3. Unless otherwise specified, VIN = 14V and I_O = 500mA for K,R,P-Pkg; I_O = 100mA for T-Pkg.

5. At T_J = -55° C, minimum (V_{IN} - V_O) = 2.5V.

4. All regulation tests are made at constant junction temperature with low duty-cycle

testing.

6. Short circuit protection is only assured to $V_{IN} = 35V$.

$ \begin{array}{ $			DEVICE PART NUMBERS	Ľ	SG7812A		S	SG140-12	┢	SG7812	812	-	SG7812AC	2AC	Ĺ	SG340-12	12	s	SG7812C	U)	
		PACKAG	GE STYLES (P/N SUFFIX)		K,R,T			ς,R,Τ		, Y	۲.		K,P,R	Ľ,		K,P,R,	F	¥	, P, R, T		
	OPERATING	3 JUNCTION (Unless o	I TEMPERATURE RANGE otherwise specified below)		-55°C +150°(20	Ĩ	55°C to 150°C		-55° 150	0 to 0 to		0° C 125°	စ္စပ္		0°C t	• 0		0° C to 125° C		
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	DARAMETERS	TEST CON	DITIONS (See notes below)	-		MAX		TYP M						A MA		_			-	MAX	UNITS
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Output Voltage	T = 25°C		-		12.2	_		-	5.	<u>⊨</u>	-	8	12.2	-		12.5	-		12.5	>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		2			12	8			ର	<u>۲</u>	 	2	12			₽	120		24	240	Ę
	Line Regulation	T _J = 25°C	-		6	8			8	9		0	9	8		9	8		12	120	È
Piton TJ = 25°C Io = 25°C Io = 25° to 750mA 10 40 10 60 Dutput T-Pkg: IO = 5 to 10A, P 20W 10 40 10 60 Dutput R-Pkg: IO = 5 to 10A, P 20W 11.7 12.3 11.4 12.6 11 6 = 70erance R-Pkg: IO = 5 to 500mA, P ≤ 15W 11.7 12.3 11.4 12.6 11 15.5 to 27V T-Pkg: IO = 5 to 500mA, P ≤ 15W 11.7 12.3 11.4 12.6 7 15.5 to 27V T-Pkg: IO = 5 to 500mA, P ≤ 15W 11.7 7 20 <td< td=""><td>ARA</td><td></td><td>I_O = 5mA to 1.5A</td><td> </td><td>58</td><td>120</td><td></td><td></td><td>20</td><td>21</td><td></td><td>30</td><td>28</td><td></td><td></td><td>28</td><td>120</td><td></td><td>8</td><td>240</td><td>۶ ۲</td></td<>	ARA		I_O = 5mA to 1.5A	 	58	120			20	21		30	28			28	120		8	240	۶ ۲
T-Pkg IO 40 10 40 10 60 Output K-Pkg: IO = 5 to 1.0A, P< 20W 11.7 12.3 11.4 12.6 11 Es to 22V K-Pkg: IO = 5 to 1.0A, P< 20W 11.7 12.3 11.4 12.6 11 Es to 22V K-Pkg: IO = 5 to 1000mA, P $\leq 15W$ 11.7 12.3 11.4 12.6 1 Eent Current With line: VIN = 15 to 30V 0.8 0.6 0.8 0.8 0.8 Current With load: IO = 5 to 1000mA 1.8 7 7 7 7 Cent Current With load: IO = 5 to 1000mA 0.8 0.8 0.8 0.8 0.8 Cent Current With load: IO = 5 to 1000mA 1.8 7 7 7 7 Cent Current With load: IO = 5 to 1000mA 1.8 2.0 0.5 2.0 0.5 Current With load: IO = 500mA 1.7 2.0 0.5 2.0 0.5 7 Current TJ = 25°C K.R.P-Pkg <		T ₁ = 25°C			₽	4		╞	8	F		0	9			<u>0</u>	8		24	120	۶
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	<u> </u>)	IO = 5mA to 500mA		₽	4			8	Ŧ		0	10			10	8		24	120	È
$\label{eq:relation} \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Total Outout	K-Pkg: IO	4 11 1																		
DS 10 2/V T-pkg: I_0 = 5 to 500mA, P $\ge 2W$ A 6 4 6 ent Current $T_J = 25^{\circ}C$ A 6 4 6 6 4 6 ent Current With line: V _{IN} = 15 to 30V 0.8 0.8 0.8 0.8 0.8 0.8 ent Current With line: V _{IN} = 15 to 30V 0.8 0.8 0.8 0.5 0.5 0.5 ent Current With line: V _{IN} = 15 to 30V 0.8 0.8 0.8 0.8 0.8 0.8 0.8 0.8 0.8 0.8 0.5	Voltage Tolerance	R,P-Pkg: I	0 = 5 to 1000mA, P ≤ 15W			12.3	11.4	<u>~</u>	2.6 11	4	12	.6 11.		12.3			12.6	11.4		12.6	>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	V _{IN} =15.5 to 27V	T-Pkg: IO	= 5 to 500mA, P≤2W						+	+	-	+									
Current cent Current Over Temperature Range 7 7 7 7 cent Current With line: $V_{ N} = 15 to 30V$ 0.8 0.8 <td></td> <td>TJ = 25°C</td> <td></td> <td></td> <td>4</td> <td>9</td> <td></td> <td></td> <td>9</td> <td>4</td> <td></td> <td></td> <td>4</td> <td>9</td> <td>_</td> <td>4</td> <td>8</td> <td></td> <td>4</td> <td>8</td> <td>٩u</td>		TJ = 25°C			4	9			9	4			4	9	_	4	8		4	8	٩u
cent Current With line: $V_{ N} = 15 \text{ to } 30V$ 0.8 0.8 0.8 ge With load: $1_{O} = 5$ to 1000mA 0.5 0.5 0.5 0.5 ut Voltage $T_{J} = 25^{\circ} C$ $K, R, P-Pkg: 1O = 1A$ 2.0 2.0 2.0 i 100mV $T_{J} = 25^{\circ} C$ $K, R, P-Pkg: 1O = 500mA$ 1.8 1.8 1.8 Dutput $T_{J} = 25^{\circ} C$ $K, R, P-Pkg$ 2.5 2.5 2.5 Dutput $T_{J} = 25^{\circ} C$ $K, R, P-Pkg$ 1.0 1.0 1.0 Dutput $T_{J} = 25^{\circ} C$ $K, R, P-Pkg$ 0.5 2.5 2.5 2.5 Entruit $T_{J} = 25^{\circ} C$ $T-Pkg$ 0.5 0.5 2.6 5.5 Entruit $T_{J} = 25^{\circ} C, t = 120Hz, \Delta V_{ N} = 10V$ 6.5 6.5 7.5 2.5 5.6 5.7 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5	Quiescent Current	Over Tem	perature Range			7			7		2			2			8.5			8.5	₹ E
ge With load: $1O = 5$ to 1000mA 0.5 0.	Quiescent Current	With line:	V _{IN} = 15 to 30V			0.8		<u> </u>	8		ö	8		1.0			1.0			1.0	٩u
ut Voltage $T_{J} = 25^{\circ}C$ $K_{1}R_{1}P_{2}P_{3}(0 = 1A)$ 2.0 2.0 1.8 2.0 1.8 1.0 2.5 1.0 2.5 1.0 1.0 2.5 1.0 2.5 1.0 2.5 1.0 2.5 1.0 2.5 1.0 2.5 1.0 2.5 1.5 2	Change		IO = 5 to 1000mA			0.5			÷.		0	5		0.5			0.5			0.5	Am
	Dropout Voltage				2.0			2.0		5	0		2.0			2.0			2.0		Λ
Dutput T_J = 25°C K,R,P-Pkg 2.5	4V _O = 100mV	0,92 = ¹			1.8			1.8		+	8		1.8			1.8			1.8		•
ant $T_J = 25^{\circ}C$ T-pkg 1.0 1.0 1.0 1.0 Circuit $T_J = 25^{\circ}C$ K.R.P-Pkg 1.55 1.5 1.55 <th< td=""><td>Peak Output</td><td></td><td>+−−</td><td></td><td>2.5</td><td></td><td></td><td>2.5</td><td></td><td>5</td><td>5</td><td></td><td>2.5</td><td></td><td></td><td>2.5</td><td></td><td></td><td>2.5</td><td></td><td>۲</td></th<>	Peak Output		+−−		2.5			2.5		5	5		2.5			2.5			2.5		۲
Circuit T_J = 25°C K.R.PPkg 1.5	Current	T _J = 25°C		ļ	0;F			1.0		1.	0		1.0			1.0			1.0		۲
ent $T_{J} = 25^{\circ}C$ $T_{-}Pkg$ 0.5 0.5 0.5 0.5 ficient $I_{O} = 5mA$ -0.8 <	Short Circuit		+	L	1.5			1.5	\vdash	1.	5		1.5			1.5			1.5		۲
reature ficient $I_O = 5mA$ -0.8 -0.8 -0.8 ficient $T_J = 25^{\circ}$ C, $f = 120$ Hz, $\Delta V_{IN} = 10V$ 65 65 65 t Holection $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 t Noise $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 ge $T_J = 25^{\circ}$ C, $f = 10$ Hz to 100 kHz 75 75 75 f and the stability 1000 hrs. at $T_J = 125^{\circ}$ C 48 98 175 $hal ShutdownI_J = 5mA175175175$	Current	T _J = 25°C			0.5			0.5		Ö	5		0.5			0.5			0.5		۲
Rejection T_J = 25°C, f = 120Hz, $\Delta V_{\rm IN} = 10V$ 65 61 65 65 75 75 75 75 71 75 75 75 75 75 75 75 75 75 75 75 75 75 <	Temperature Coefficient	l_0 = 5mA			-0.8			-0.8			8		-0 -			-0.8			-0.8		≥ C E °
t Noise T_J = 25° C. f = 10Hz to 100 kHz 75 75 75 ge Term Stability 1000 hrs. at T_J = 125° C 48	Ripple Rejection		0, f = 120Hz, ΔV _{IN} = 10V		65			65		۳ 	<u>ب</u>		8	_		65			65		đđ
Term Stability 1000 hrs. at T _J = 125°C 48 48 Nal Shutdown IO = 5mA 175 175	Output Noise Voltage	T _J = 25°C	0, f = 10Hz to 100 kHz	·	75			75			<u> </u>		75			75			75		З Ę
al Shutdown I _O = 5mA 175 175 175 175 175 175 175 175 175 175	Long Term Stability	1000 hrs. a	at T_J = 125°C		48	 		48		4			48			48			84		È
num load current for full line regulation is 5mA.	Thermal Shutdown	l _O = 5mA			175			175		12	5		175			175			175		ပ္
	NOTES:																				
	 Minimum load curren 	of for full line	e regulation is 5mA.							4. All	regula	ation te	ists are	madea	atcons	tantju	nction	tempe	rature	withlo	w duty-

Three Terminal Positive Regulators

Pos. 12 Volts

2. Maximum test current for T-Pkg is 500mA.

3. Unless otherwise specified, VIN = 19V and IO = 500mA for K,R,P-Pkg; IO = 100mA for T-Pkg.

5. At T_J = -55° C, minimum (V_{IN} - VO) = 2.5V.

6. Short circuit protection is only assured to $V_{IN} = 35V$.

$ \ \ \ \ \ \ \ \ \ \ \ \ \ $			DEVICE PART NUMBERS	SG	SG7815A		SG1	SG140-15	⊢	SG7815	315	Ś	SG7815AC	AC	Š	SG340-15	5	SG	SG7815C		
	-	PACKAG	ie STYLES (P/N SUFFIX)		ς, R, Τ		×	Ъ,Т		Т. Т.	τ		К,Р,Я	-		КР.	L	Ŷ	Р.Я.Т		
	OPERATING	3 JUNCTION (Unless o	TEMPERATURE RANGE therwise specified below)	Ŷ÷	5°C t		- 1 27 ₹2	5°C to		-55°	9 0 9		0° C 125°	9.0		0° C tc 125° C		0.	0° C to 125° C		
$ \begin{array}{ $	PARAMETERS	TEST CON	DITIONS (See notes below)									_				_	MAX	NIM			UNITS
Hegalation T _J = 2 ^s C Vm = 17.5 to 30V 15 75 15 150 15 150 15	Output Voltage	T = 25°C		14.8			4.4	=		4	15.0	-		15.2	-		15.6	14.4		15.6	>
			>		5	75		+	20	12	+		15	150		15	150		ŝ	8 8	کم ع
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	Line Regulation	11	1			ą		┼──	5	80	-		80	75		8	75		15	150	2
			IO = 5mA to 1.5A		R	8	-	t –	20	×			8	150		8	150		<u>5</u>	300	È
	a tion	H	1		12	3			5	12	-	-	12	75		12	75		ß	150	Ę
	·		IO = 5mA to 500mA		12	50	-		5	12			12	75		12	75		90	150	کر عر
$ \frac{R_{\rm IP} {\rm Prgc} (J_{\rm C} = 5 \text{to} \text{toromA}, P \leq 5 \text{W}}{\rm T. Prgc} 4 \text{G} 15 1 14.3 15.7 14.2 15.5 15.0 15.7 14.2 15.5 15.0 15.7 14.2 15.5 15.0 15.7 14.2 15.7 15.$	Total Output	K-Pkg: IO	= 5 to 1.0A, P					_	-												
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Voltage Tolerance	R,P-Pkg: I _C	н	14.6			4.3	~		ej.	15.			15.4			15.7	14.3		15.7	>
$ \begin{array}{l lllllllllllllllllllllllllllllllllll$	V _{IN} = 18.5 to 30V	T-Pkg: IO	5 to					,													
					4	9				4			4	9		4	8		4	8	٩w
$ \begin{array}{ $	Curent Current	Over Temp	erature Range			2			~		~		1.4	2			8.5			8.5	¥
$ \begin{array}{ $	Quiescent Current	With line: \	/IN = 18.5 to 30V			0.8		0	80	_	0.8			1.0			1.0			1.0	٩W
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Change	With load:	l _O = 5 to 1000mA			0.5		0	5		0.5			0.5			0.5			0.5	٩W
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Dropout Voltage		<u> </u>		~			2		2	-		8			2			2		>
	ΔV _O = 100mV	þ	<u> </u>		1.8			1.8		÷	80		1.8			1.8			1.8		>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Peak Output				2.2			2.2		2	8		2.2			2.2			2.2		A
	Current	1			0.9		-	6.0		ö	6		6.0			0.9			6.0		A
	Short Circuit	1	-		1.3			1.3			3		1.3			1.3			1.3		۲
$I_O = 5mA$ -1.0 <	Current	E.			0.4			0.4		ö	4		0.4			0.4			0.4		•
$T_J = 25^{\circ}C. f = 120Hz. \Delta V_{IN} = 10V$ 64	Temperature Coefficient	- 11			-1.0			1.0		-	0		-1.0			-1.0			1.0		∧ ° °
$T_J = 25^{\circ}$ C, $f = 10Hz$ to 100 kHz 90 <t< td=""><td>Ripple Rejection</td><td>H</td><td>$f = 120Hz, \Delta V_{IN} = 10V$</td><td></td><td>64</td><td></td><td></td><td>64</td><td></td><td>é</td><td>4</td><td></td><td>64</td><td></td><td></td><td>64</td><td></td><td></td><td>64</td><td></td><td>6B</td></t<>	Ripple Rejection	H	$f = 120Hz, \Delta V_{IN} = 10V$		64			64		é	4		64			64			64		6B
\prime 1000 hrs. at T _J = 125°C 60 60 60 60 60 60 75 <t< td=""><td>Output Noise Voltage</td><td>H</td><td>f = 10Hz to 100 kHz</td><td></td><td>06</td><td></td><td></td><td>06</td><td></td><td>5</td><td></td><td></td><td>6</td><td></td><td></td><td>66</td><td></td><td></td><td>8</td><td></td><td>rms</td></t<>	Output Noise Voltage	H	f = 10Hz to 100 kHz		06			06		5			6			66			8		rms
10 = 5mA 175 175 175 175 175 175 175 175 175 175	Long Term Stability	1000 hrs. a	t T_J = 125°C		60			60		9	0		99			8			8		۶ ۲
	Thermal Shutdown	H			175			175		2 1	5		175			175			175		°

Three Terminal Positive Regulators

Pos. 15 Volts

1. Minimum load current for full line regulation is 5mA.

2. Maximum test current for T-Pkg is 500mA.

3. Unless otherwise specified. VIN = 23V and IO = 500mA for K,R,P-Pkg. IO = 100mA for T-Pkg.

6. Short circuit protection is only assured to $V_{IN} = 35V$. 5. At $T_J = -55^{\circ}$ C, minimum (V_{IN} - VO) = 2.5V.

4. All regulation tests are made at constant junction temperature with low duty-cycle

testing.

-		1	Г	ø							_		Т															
				UNITS	>	۲ ۲	È	۲ ۲	۲ ۲	È		>		ĕ	A E	٩	۹u	>	•	۷	۲	۷	۷	≥ O E €	₿	v sr sr	۲ ۳	ပိ
ູ		0.0		MAX	18.7	360	180	360	180	180		18.9			8.5	1.0	0.5											
2010/02	K,P,R,T	0° C to 125° C		ΥP		40	8	120	40	4				4				2.0	1.8	2.2	6.0	1.0	0.3	-1.2	62	110	72	175
"	Ť			NiN	17.3							17.1																
8	F			MAX	18.7	180	8	180	6	ଛ		18.9		80	8.5	1.0	0.5											
SG340-18	K,P,R,T	0° C to 125° C		түр		20	₽	4	15	15				4				2.0	1.8	5.2	0.9	1.0	0.3	-1.2	62	110	72	175
"				MIM	17.3							17.1		_														
AC		• •		MAX	18.3	180	8	180	8	8		18.5		٥	7	1.0	0.5			 								
SG7818AC	K,P,R,T	0° C to 125° C		түр		20	₽	40	15	15				4				2.0	1.8	2.2	6.0	1.0	0.3	-1.2	62	110	72	175
ō	_		║	NIN	17.7							17.5	╡							_	L							
SG7818		ی ₽		MAX	18.7	180	8	180	8	8		18.9		9	2	0.8	0.5											
	К, Я, Т	-55°C to 150°C		түр		8	9	6	15	15				4				2.0	1.8	2.2	6.0	1.0	0.3	-1.2	62	110	72	175
				NIN	17.3							17.1	_															
-18		₽0		MAX	18.7	180	8	180	8	8		18.9		g	2	0.8	0.5											
SG140-18	K,R,T	-55°C to 150°C		ΤYΡ		8	9	4	15	15			_	4				2.0	1.8	2.2	0.9	1.0	0.3	-1.2	62	110	72	175
			Щ	NIW	17.3							17.1	_							-							<u> </u>	Ц
8A		ی⊈		MAX	18.3	8	45	120	99	8		18.5	_	9 	~	0.8	0.5	-						- 01				
SG7818A	K,R,T	-55°C to +150°C		ΤYΡ		8	8	4	15	15				4				2.0	1.8	2.2	0.9	1.0	0.3	-1.2	62	110	22	175
				NIW	17.7				ļ	ļ		17.5	_							L							-	
DEVICE PART NUMBERS	PACKAGE STYLES (P/N SUFFIX)	JNCTION TEMPERATURE RANGE (Unless otherwise specified below)		TEST CONDITIONS (See notes below)		$V_{IN} = 21 \text{ to } 33V$	$V_{\rm IN} = 24$ to 30V	1 _O = 5mA to 1.5A	I = 250 to 750mA	IO = 5mA to 500mA	= 5 to 1.0A, P 20W		= 5 to 500mA, P≤2W		Over Temperature Range	With line: $V_{IN} = 22$ to 33V	With load: I _O = 5 to 1000mA	K,R,P-Pkg: IO = 1A		K,R,P-Pkg	T-Pkg	K,R,P-Pkg			r _J = 25°C, f = 120Hz, ΔV _{IN} = 10V	$f_{J} = 25^{\circ} C$, $f = 10Hz$ to 100 kHz	t T _J = 125°C	
٥	PACKAG	UNCTION (Unless of		TEST COND	T _J = 25°C	,	T _J = 25°C		T = 25°C	5	K-Pkg: Io	R,P-Pkg: I _O	T-Pkg: 10 =	T_J = 25°C	Over Temp	With line: V	With load: I		T_J = 25°C		T _J = 25°C		T _J = 25°C	1 ₀ = 5mA	T_J = 25°C.	T _J = 25°C,	1000 hrs. at T _J	l _O = 5mA
		OPERATING JU		TERS	oltage		ulation	Рак	Pkg	-		Voltage Tolerance	A CC C1	-	Quiescent Current	Ouiescent Current		Voltage	100mV	tia		cuit		ture ent	ejection	loise	Long Term Stability	Thermal Shutdown
				PARAMETERS	Output Voltage		Line Regulation		Load	Regulation	trat. O latot	Voltage Toleranc	77 = NIA		Quiescen	Ouiescen	Change	Dropout /	4VO = 100mV	Daak Outnut	Current	Short Circuit	Current	Temperature Coefficient	Ripple Rejection	Output Noise Voltage	Long Ter	Thermal

4. All regulation tests are made at constant junction temperature with low duty-cycle testing. S. At T_J = -55° C, minimum (VIN – VO) = 2.5V.

6. Short circuit protection is only assured to $V_{IN} = 35V$.

Maximum test current for T-Pkg is 500mA.
 Allow and the solution of t

1. Minimum load current for full line regulation is 5mA.

3. Unless otherwise specified, VIN = $27V\,\text{and}$ IO = 500mA for K,R,P-Pkg; IO = 100mA for T-Pkg.

Pos. 18 Volts

Three Terminal Positive Regulators

	J	DEVICE PART NUMBERS	š	SG7820A		SG	SG140-20		SG7820	920	s	SG7820AC	AC	S	SG340-20	20	S	SG7820C	υ	
	PACKAG	ACKAGE STYLES (P/N SUFFIX)		К, Р, Т		¥	K,R,T		K,R,T	۲.		K,P,R,T	_		K,P,R,T	F	¥	K,P,R,T		
OPERATING JUN	3 JUNCTION (Unless of	UNCTION TEMPERATURE RANGE (Unless otherwise specified below)	Ϋ+	-55°C to +150°C		Ϋ́	55°C to 150°C		-55°C to 150°C	e o		0° C to 125° C			0° C to 125° C			0° C to 125° C		
PARAMETERS	TEST COND	TEST CONDITIONS (See notes below)	NIW	μ	MAX	NIW	TYP M	MAX MI	MIN TYP	P MAX	MIN	٩۲	MAX	NW	Түр	MAX	NIM	٩۲	MAX	UNITS
Output Voltage	T _J = 25°C		19.7		20.3	19.2	X	20.8 19	19.2	20.8	19.7		20.3	19.2		20.8	19.2		20.8	>
	U 830 - F	$V_{IN} = 23 \text{ to } 35V$		52	100		22 2(200	8	200		52	200		22	200		44	400	È
Line Regulation	ר	V _{IN} = 26 to 32V		12	50		12 1(100	12	100		12	100		12	100		24	200	È
		IO = 5mA to 1.5A		45	140		45 2(200	45	200		45	200		45	200		150	400	È
Load Pkg Regulation	T _J = 25°C	I _O = 250 to 750mA		20	70		20 1(100	20	100		20	100		20	100		50	200	È
T-Pkg		IO = 5mA to 500mA		20	70	-	20 10	100	8	100		20	100		20	100		50	200	۶
Total Output	K-Pkg: I _{O ⁼}	= 5 to 1.0A, P 20W		-																
Voltage Tolerance	R,P-Pkg: I _O	= 5 to 1000mA, P ≤ 15W	19.4		20.6 1	19.0	Ň	21.0 19	19.0	21.0	19.4		20.6	19.0		21.0	19.0		21.0	>
$V_{IN} = 24$ to 35V	T-Pkg: Io =	= 5 to 500mA, P≤2W																		
	T_J = 25°C			4	9	 	4	9	4	9		4	9		4	8		4	8	٩u
	Over Temp	Over Temperature Range			7			7		7			7			8.5			8.5	٩u
Quiescent Current	With line: V	With line: $V_{IN} = 24$ to $35V$			0.8		0	8.		0.8			1.0			1.0			1.0	₽
Change	With load:	With load: I _O = 5 to 1000mA			0.5		0	0.5		0.5			0.5			0.5			0.5	A E
Dropout Voltage	U 900 - F	K,R,P-Pkg: IO = 1A		2.0			2.0		2.0			2.0			2.0			2.0		3
ΔV _O = 100mV	0 cz - [1	T-Pkg: I _O = 500mA		1.8			1.8		1.8	_		1.8			1.8			1.8		>
Peak Output	T . = 36° C	K,R,P-Pkg		2.2		Η	2.2	\mid	2.2			2.2			2.2			2.2		۷
Current		T-Pkg		0.9			0.9		0.9			0.9			0.9			0.9		۲
Short Circuit	1 - 36°C	K,R,P-Pkg		0.9			0.9		0.9			0.9			0.9			0.9		۲
Current	2 c2 - [-	T-Pkg		0.2			0.2		0.2			0.2			0.2			0.2		۷
Temperature Coefficient	lO = 5mA			-1.3			-1.3		-1.3			-1.3			-1.3			-1.3		> C 2 €
Ripple Rejection	T _J = 25°C,	= 25° C, f = 120Hz, ΔV _{IN} = 10V		60			60		60			99			60			60		Вb
Output Noise Voltage	T_J = 25° C,	T _J = 25°C, f = 10Hz to 100 kHz		140			140		140			140			140			140		V≓ sm sm
Long Term Stability	1000 hrs. at	1000 hrs. at T _J = 125°C		80			80		80			80			80			80		۶
Thermal Shutdown	1 _O = 5mA			175			175		175	5		175			175			175		ပ

Three Terminal Positive Regulators

Pos. 20 Volts

1. Minimum load current for full line regulation is 5mA.

2. Maximum test current for T-Pkg is 500mA.

3. Unless otherwise specified. VIN = 29V and I_O = 500mA for K,R,P-Pkg; I_O = 100mA for T-Pkg.

5. At $T_J = -55^{\circ}$ C, minimum (V_{IN} - VO) = 2.5V.

testing.

4. All regulation tests are made at constant junction temperature with low duty-cycle

6. Short circuit protection is only assured to $V_{IN} = 35V$.

				UNITS	>	ک ۲	ž	۲ ۲	۲ ۲	> E		>	T	٩u	٩	٩u	٩u	>	>	۲	A	۲	۲	≥ C E °	ąp	μV ms	۲ ۳	ပံ
			-	MAX	25.0	480	240	480	240	240		25.2		80	8.5	1.0	0.5			_								
0+20100	К,Р,Я,Т	0° C to 125° C		Ł		50	28	180	70	5				4				2.0	1.8	2.2	0.9	0.7	0.2	-1.5	56	170	96	175
ñ	¥	0-	ľ	NW	23.0							22.8																
4	-		Γ	MAX	25.0	240	120	240	120	120		25.2		8	8.5	1.0	0.5											
SG340-24	K,P,R,T	0° C to 125° C		TγP		25	14	50	25	25				4				2.0	1.8	2.2	0.9	0.7	0.2	-1.5	26	170	96	175
ũ	-	_	_	NW	23.0							22.8																
Ş	L_			MAX	24.4	240	120	240	120	120		24.7		9	2	1.0	0.5											
SG7824AC	K,P,R,T	0° C to 125° C	-	TΥΡ		25	4	50	25	25				4				2.0	1.8	2.2	0.9	0.7	0.2	-1.5	56	170	8	175
š				Ň	23.6				<u> </u>			23.3	4															
SG7824 K B T	L .	₽۵		MAX	25.0	240	120	240	120	120		25.2		9	2	0.8	0.5										 	
	K, R, T	-55°C to 150°C		TΥΡ		25	14	50	25	25				4				2.0	1.8	2.2	0.9	0.7	0.2	-1.5	56	170	8	175
				MIN	23.0							22.8	_															
-24		۵ م		MAX	25.0	240	120	240	120	120		25.2		9	2	0.8	0.5											
SG140-24	K,R,T	-55°C to 150°C		TYP		25	4	50	25	25			_	4				2.0	1.8	2.2	0.9	0.7	0.2	-1.5	56	170	8	175
0)				(MIN	23.0							22.8	$ \rightarrow$						-		_							
4A	-	20		MAX	24.4	120	99	160	8	8		24.7	_	9	2	0.8	0.5			-	-	-		Ω.				
SG7824A	K,R,T	-55°C to +150°C		I TYP		25	4	20	25	25				4	<u> </u>			2.0	1.8	2.2	6.0	0.7	0.2	1	29	170	8	175
	ļ	ļ	╢	NIN	23.6		-		<u> </u>			33.3	_			-				-	-						_	
DEVICE PART NUMBERS	PACKAGE STYLES (P/N SUFFIX)	INCTION TEMPERATURE RANGE (Unless otherwise specified below)		TEST CONDITIONS (See notes below)		$V_{IN} = 27$ to 38V	$V_{IN} = 30 \text{ to } 36V$	I = 5mA to 1.5A	I = 250 to 750mA	IO = 5mA to 500mA	= 5 to 1.0A, P 20W) = 5 to 1000mA, P ≤ 15W	= 5 to 500mA, P≤2W		ver Temperature Range	/ _{IN} = 28 to 38V	I _O = 5 to 1000mA	K,R,P-Pkg: 10 = 1A	_	K.R.P-Pkg		K,R,P-Pkg	T-Pkg		f = 120Hz, ΔV _{IN} = 10V	[_J = 25°C, f = 10Hz to 100 kHz	t T_J = 125°C	
	PACKAG	JUNCTION (Unless of		TEST COND	T_] = 25°C		T _J = 25°C		T = 25°C	7	K-Pkg: IO	R,P-Pkg: 10	T-Pkg: Io =	T _{.1} = 25°C	Over Temp	With line: V _{IN}	With load: IO		T _J = 25°C		T _J = 25°C		T _J = 25°C	l _O = 5mA	Τ _J = 25°C, f	T _J = 25°C,	1000 hrs. at T _J	l _O = 5mA
		OPERATING JU		3S	e		tion	a X	Pkg	T-Pkg		rance	38V		urrent	urrent		tace	2						tion	e e	Stability	utdown
		ð		PARAMETERS	Output Voltage		Line Regulation		Load	Hegulation	Total Output	Voltage Tolerance	$V_{IN} = 28 \text{ to } 38V$		Quiescent Current	Ouiescent Current	Change	Dropout Volt	4VO = 100mV	Boak Output	Current	Short Circuit	Current	Temperature Coefficient	Ripple Rejection	Output Noise Voltage	Long Term Stability	Thermal Shutdown

Three Terminal Positive Regulators

Pos. 24 Volts

4. All regulation tests are made at constant junction temperature with low duty-cycle

testing.

1. Minimum load current for full line regulation is 5mA.

2. Maximum test current for T-Pkg is 500mA.

5. At $T_J = -55^{\circ}C$, minimum (V_{IN} - VO) = 2.5V. 3. Unless otherwise specified, VIN = 33V and I_O = 500mA for K,R,P-Pkg; I_O = 100mA for T-Pkg.

6. Short circuit protection is only assured to $V_{IN} = 40V$

Silicon General

SG7900A / 7900AC SG120/220/320 SG7900/7900C

LINEAR INTEGRATED CIRCUITS

THREE TERMINAL NEGATIVE REGULATORS

DESCRIPTION

The SG7900A/7900/120/220/320 series of negative regulators offer self-contained, fixed-voltage capability with up to 1.5 amps of load current. With a variety of output voltages and four package options this regulator series is an optimum complement to the SG7800A/7800/140/240/340 line of three terminal regulators.

These units feature a unique band gap reference which allows the SG7900A series to be specified with an output voltage tolerance of ±1.5%. The SG7900A versions also offer much improved line regulation characteristics.

All protective features of thermal shutdown, current limiting, and safe-area control have been designed into these units and since these regulators require only a single output capacitor (7900 series) or a capacitor and 5 mA minimum load (SG120 series) for satisfactory performance, ease of application is assured.

Although designed as fixed-voltage regulators, the output voltage can be increased through the use of a simple voltage divider. The low guescent drain current of the device insures good regulation when this method is used, especially for the SG120 series.

These devices are available in hermetically sealed TO-3. TO-39 and TO-66 power packages as well as the plastic comercial power TO-220 package.

Silicon General specializes in testing parts for unique customer requirements. If certain parameters are required for your application, contact factory for testing to your specification.

FEATURES

- · Output voltages set internally to ±1.5% (SG7900A)
- Output current to 1.5 amp
- Excellent line and load regulation
- Foldback current limiting
- Thermal overload protection
- Voltages available -5 V, -5.2V, -8V, -12V, -15V, -18V, -20V
- Contact factory for other voltage options.



ABSOLUTE MAXIMUM RATINGS

Device Output Voltage -5V -5.2V	input Voitage – 35V	Input-Output Differential 25V 25V	Storage Ten Lead Tampe Power/The	rature (So	Idering, 10		
-8 V	- 35V - 35V	30V	Package	K (TO-3)	R (TO-66)	P (TO-220)	T (TO-39)
-12V	- 35V	30V	25° C Case Rated Power	20W	15W	15W	2W
- 15V - 18V - 20V	- 40V - 40V - 40V	30V 30V 35V	25° C Ambient Rated Power	4.3W	3.0W	2.0W	1.0W
Operating Junction T	emperature Ran	ge	Design Current	1.5A	1.5A	1.0A	0.5A
		55° C to +150° C 0° C to +150° C 0° C to +125° C	i'herm. Res θJC (°C/₩) θJA (°C/₩)	3.0 35	5.0 40	3.0 60	15 120

APPLICATIONS

Fixed Output Regulator



 C1 is required only if regulator is separated from rectifier filter.
 Both C1 and C2 should be low ES R types such as solid tantatum. If aluminum electrolitics are used, at least 10 times values shown should be selected
 If large output capacities are used, the regulators must be protected from NOTE: 1. 2. momentary input shorts. A high current diode from output to input will suffice



SG7900A/7900AC SGSG120/220/320 SG7900/7900C


SG7900A/7900AC SGSG120/220/320 SG7900/7900C



$ \ \ \ \ \ \ \ \ \ \ \ \ \ $			Ō	DEVICE PART NUMBERS	Š	SG7905A		SG	SG120-05		SG	SG7905	Ļ	SG7905AC	5AC	<u> </u>	SG320-05	65		SG7905C	U2	
			PACKAGI	E STYLES (P/N SUFFIX)		K,R,T			ζ,R,T		¥	R,T		K,P,	R,T		K,P,R	Ŀ		K,P,R,	-	
i TEST CONDITIONS (See notee below) (MIN TYP MAX MIN	ō	PERATIN	IG JUNCTION 1 (Unless oth	FEMPERATURE RANGE erwise specified below)	I	55°C 1 150°C		i i	55°C to 50°C		- 55 75	မ ပူပူ	· .	28 28	ခင်		0°C 1 125 (<u>ع</u> د		0°C t	0.0	
$ \left(\begin{array}{cccccccccccccccccccccccccccccccccccc$	PARAMETERS	s	TEST COND	TIONS (See notes below)	NIW	٩	-		TYP N			VP M		1 1	P MA		TYP	MA		4	MAX	
$ \ \ \ \ \ \ \ \ \ \ \ \ \ $	Output Voltag	e	T _J = 25°C		-492	-5.0				+			52 -45					1				>
$ \begin{array}{ $	Line Regulatic	5		= -7 to		5	25	-		52			0	5			P			e	<u>6</u>	۶
PRA $10 = 5m \ to 15A$ 15 75 16 <td>(Note 7)</td> <td></td> <td></td> <td>11</td> <td></td> <td>3</td> <td>15</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td>2</td> <td>۳ ۳</td> <td><u> </u></td> <td></td> <td> </td> <td> </td> <td></td> <td>-</td> <td>50</td> <td>کر ۲</td>	(Note 7)			11		3	15						2	۳ ۳	<u> </u>		 			-	50	کر ۲
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		P,R,K		11		15	75			75	-	· ·	8	₩ ,			33	 		15	100	È
FPR $i = 5 \text{ mat} \text{ to 500m}$ $i = 2 \text{ mat} to $		Pkg.	11	- 11		15	25				-		2	5						S	50	ž
KR.P.Prig. Io 5 to to to to the set of the set		T-Pkg.		- 18		5	40			20		-	Q	5			8			15	<u>6</u>	È
$ \frac{20}{10} \overline{Ty} \overline{Ty} \overline{Y} = 5 \ co \ co \ math math math math math math math math$	Total Output Voltage Tolera	Ince	K,R,P-Pkg: I P ≤ 15W	5 to 1000mA,	-4.85	1	5.15	-4.8		22	470	 	30-45		- 51	15-47		-22	5 - 47		-525	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	$V_{IN} = -8 \text{ to}$	- 20/	T-Pkg: lo =	5 to 500mA, P ≤																		
Over Tamperature Range I 20<	Oniescent Cur	rant	TJ = 25°C			-	2			5	-			-	2		-	~		-	2	٩m
$ \begin{array}{ $			Over Tempe	rature Range			2.0			0		101	5	 	2.0	-		2.0			e	٩m
	Quiescent Cur	rrent	With line: V _i	- 0			1.3		3	0.4					1.3			0.4			1.3	ЧW
	Change		With load: I	- 11			0.5		3	4		0	2		0.5			0.4			0.5	٩u
	Dropout Volta	<u>e</u>	. II	K,R,P-Pkg.: Io = 1A			2.0			0.9	1.		0				÷			÷	2.0	>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	4Vo = 100mV			T-Pkg: lo = 100mA			2.0			0.0	, '		0	-			1.1			1.1	2.0	•
	Peak Output		II	K,R,RPkg.:	1.5			_		-				-						2.1	3.3	A
	Current			T-Pkg:	0.5	1.0	_	5	1.0	0		0	0.5			0.5			0.5	1.0		۲
n T PPkg: 0.7	Short Circuit			K,R,RPkg.:		2.1		-	2.1	_	5	-		5.			2.1			2.1		۷
Dn TJ=25°C, f = 120Hz, ΔVN = 10V 54 60 54 50 55 60 54 50 125 125 50	Current			T-Pkg:		0.7		-	0.7		ö	7		0.7			0.7			0.7		۲
T _J = 25°C, f = 10Hz to 100 kHz 25 80 156 25 80 125 150 125 billty 1000 hrs at T _J = 125°C 20 5 50 20 </td <td>Ripple Rejecti</td> <td>u</td> <td>TJ=25°C, f</td> <td>= 120Hz, ΔVIN = 10V</td> <td>2</td> <td>8</td> <td></td> <td></td> <td>80</td> <td>u)</td> <td></td> <td>0</td> <td>54</td> <td>90</td> <td></td> <td>54</td> <td>8</td> <td></td> <td>54</td> <td>8</td> <td></td> <td>đB</td>	Ripple Rejecti	u	TJ=25°C, f	= 120Hz, ΔVIN = 10V	2	8			80	u)		0	54	90		54	8		54	8		đB
1000 hrs at T _J = 125°C 20 5 50 20 20 5 50 20 lo = 5mA 175 175 175 175 175 175 175 175	Output Noise Voltage		TJ = 25°C,	f = 10Hz to 100 kHz		25	80		150		Ň			4			5			125		^μ ζ sm
lo = 5mA 175 175 175 175 175 175 175 175	Long Term Sta	ability	1000 hrs at	зŧĵ		20				00	2	0		20			5	8		ຊ		È
	Thermal Shutc	uwop				175			175		17	5		¥			175			175		ပ့

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, VN = -10V and IO = 500mA for K,R,P-Package (SG7900 Series). IO = 1A for K,R,P Pkg (SG120 Series), IO = 100mA for T-Pkg. CIN = $2\mu F$, COUT = $1\mu F$.
- All regulation tests are made at constant junction temperature with low duty-cycle testing.
- 5. At T_J = -56 °C, minimum (V_{IN} V_O) = 2.5V.
- 6. Short circuit protection is only assured to $V_{IN} = -35V$.
- Line regulation @lo = 5mA = 10mV (120-05) and 20mV (320-05).

$ \begin{array}{ $		ā	DEVICE PART NUMBERS	SG!	SG7905.2A	×	SG	SG120-5.2		SG7	SG7905.2	s	SG7905.2AC	2AC		SG320-5.2	5.2	SS	SG7905.2C	0		
$ \begin{array}{ $		PACKAG	E STYLES (P/N SUFFIX)		, В, Т		×	, R, T		ΥΥ Υ	R,Т		K,P,R	ŗ,T		K,P,R,1	-		K,P,R,T			
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	OPERATIN	IG JUNCTION 1 (Unless oth	FEMPERATURE RANGE Ierwise specified below)	Ϋ́́	ဦး ဦး သို့ သို့ သို့ သို့ သို့ သို့ သို့ သို့		₩ 	5°C to 50°C		- 55 150	°C to		28	20		0°C tc 125°C			125 to 125 to			
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	PARAMETERS	TEST COND			Ч					L L	YP MA						MAX	MIN	MIN TYP MAX		UNITS	
$ T_{1} = 35^{\circ} T_{1} = 32^{\circ} T_{1} = -810 - 25^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = -31035^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = -31035^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = -310 - 15^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = -310 - 15^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = -310 - 15^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = -310 - 15^{\circ} T_{1} = 3$ $ T_{1} = 25^{\circ} T_{1} = 25^{\circ} T_{2} = 5^{\circ} T_{2} = $	Output Voltage	11			-52 -								2 - 27			1		-5.0	-52	-5.4	>	
$ \begin{array}{ $	Line Regulation		= -8 to		5	25			25				2	4		5	4		9	50	کو ع	
RR I_J = 25°C I_O = 5ma to 15A 15 75 15 75 15 75 15 75 15 75 15 75 15 75 15 75 15 75 15 75 15 75 15 75 15 75	(Note 7)				9	15		3	15				e	25		e	25		ъ			
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			н		15	75			75	-	<u> </u>		15			15	<u>1</u> 0		15	<u>6</u>	۶	
$ \frac{\text{PK}}{\text{NK}} \xrightarrow{\text{PK}} 10^{-5} \text{ Find to 500mA} = 5 \text{ 50} \text{ 5} \text{ 50} \text{ 5} \text{ 5} $		Н	П		5	30			8	<u> </u>			5	20		5	50		5	20	ž	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			0		5	50		-	20	-			5	20		ъ	20		5	8	۶	
-2V TPkg: lo = 5 to 500mA, P ≤ 2W I <	Total Output Voltage Tolerance	K,R,P-Pkg: P ≤ 15W	= 5 to 1000mA,	-5.05	<u> </u>	-5.35	5.00	1	5.40 -4	063	-2;	<u>x0 - 5.0</u>	<u>م</u>	-536	5-495		-5.45	-496		-5.45	>	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	$V_{IN} = -9 \text{ to } -21 \text{ V}$	T-Pkg: I _O =	5 to 500mA, P ≤																			
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Onjescent Current				-	2		-	2	-			-	~		-	2		-	2	MM	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		Over Tempe	nature Range⊭			2.0			2.0		2.5			2.0			2.0			30	МÅ	
	Quiescent Current	With line: V	'IN =9 to -25V			1.3).4		1.3			1.3			0.4			1.3	ЧW	
	Change	With load:	8			0.5		-	0.4		0.5			0.5			0.4			0.5	МА	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Dropout Voltage	Н	K,R,P-Pkg.: Io = 1A		÷	2.3						6-	1.1						1.1	2.3	>	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	ΔVo = 100mV		T-Pkg: I _O = 500mA		<u>-</u> :	2.3			2.3				1.1	-		1.1	2.3		1.1	2.3	•	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Peak Output	II.	K,R,Pkg.:		5.1											2.5	3.3	1.5	2.1	3.3	A	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Current		T-Pkg:		<u>0</u>	-		1.0	Ö	_	0.	0.5			0.5	1.0		0.5	1.0		۲	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	Short Circuit	H	K,R,RPkg.:		2.0			2.0		5	0.		2.0			2.0			2.0		٩	
n TJ=25°C, f = 120H2, Δ VIN = 10V 54 60 54 50 56 <td>Current</td> <td></td> <td>T-Pkg:</td> <td></td> <td>9.0</td> <td></td> <td></td> <td>0.6</td> <td></td> <td>Ö</td> <td>9.</td> <td></td> <td>0.6</td> <td></td> <td></td> <td>0.6</td> <td></td> <td></td> <td>0.6</td> <td></td> <td>٩</td>	Current		T-Pkg:		9.0			0.6		Ö	9.		0.6			0.6			0.6		٩	
T _J = 25°C, f = 10Hz to 100 kHz 25 80 150 25 80 25 80 150 <th 150<="" <="" td=""><td>Ripple Rejection</td><td>= 25 °C,</td><td>= 120Hz, ΔVIN =</td><td>54</td><td>8</td><td></td><td></td><td>60</td><td>5</td><td></td><td>0</td><td>54</td><td></td><td></td><td>54</td><td>60</td><td></td><td>54</td><td>60</td><td></td><td>dB</td></th>	<td>Ripple Rejection</td> <td>= 25 °C,</td> <td>= 120Hz, ΔVIN =</td> <td>54</td> <td>8</td> <td></td> <td></td> <td>60</td> <td>5</td> <td></td> <td>0</td> <td>54</td> <td></td> <td></td> <td>54</td> <td>60</td> <td></td> <td>54</td> <td>60</td> <td></td> <td>dB</td>	Ripple Rejection	= 25 °C,	= 120Hz, ΔVIN =	54	8			60	5		0	54			54	60		54	60		dB
1000 hrs at T _J = 125 °C 24 5 50 24 24 5	Output Noise Voltage		f = 10Hz to 100 kHz		25	80		150		2			52	80		150		25	80		× ms Lus	
	Long Term Stability	1000 hrs at	- 11 [3				ß	Ñ	4		24			5	50		24		٣٧	
lo = 5mA 175 175 175 175 175	Thermal Shutdown	lo = 5mA			175		_	175		÷	75	-	175			175			175		ပ့	

THREE TERMINAL NEGATIVE REGULATORS NEG. 5.2 VOLTS

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/220/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, VIN = -10V and Io = 500mA for K,R,P-Package (7900 Series). Io = 1A for K,R,P Pkg (120 Series), Io = 100mA for T-Pkg. CiN = $2\mu F$. Cour = $1\mu F$.
- 7. Line regulation @ lo = 5mA = 10 mV (120-5.2) and 20mV (320-5.2).

6. Short circuit protection is only assured to $V_{IN} = -35V$.

At T_J = -56°C, minimum (V_{IN} - V_O) = 2.5V.

 All regulation tests are made at constant junction temperature with low duty-cycle testing.

	ö	DEVICE PART NUMBERS	S	SG7908A		S.	SG120-08	┝	SG7908	806		SG7908AC	3AC	Ĺ	SG320-08	8	s	SG7908C	6	
	PACKAGI	PACKAGE STYLES (P/N SUFFIX)		K,R,T		×	K,R,T		K,R,T	t,T		K,P,R,T	E		K,P,R,T	⊢		K,P,R,T		
OPERATING J	IG JUNCTION 1 (Unless oth	UNCTION TEMPERATURE RANGE (Unless otherwise specified below)	Ĩ.	55°C to 150°C		1 2 2	55°C to 150°C		- 55°	55°C to 150°C		0°C to 125°C	ളാ		0°C to 125°C	00		0°C to 125°C		
PARAMETERS	TEST CONDI	TEST CONDITIONS (See notes below) MIN	NIW	TYP MAX		MIN	νP	AXM	TYP MAX MIN TYP MAX	P MA	NIW		TYP MAX	MIN		TYP MAX	NIW	TYP MAX	MAX	UNITS
Output Voltage	T _J = 25°C		-7.88	-8.0	-8.12	-7.8 -	- 8.0	-82	- 7.7 - 8	-8.0 -8.3	3 - 7.88	8 - 8.0	0 -8.12	2 - 7.7	- 8.0	-8.3	1-7.7	-8.0	-8.3	۷
Line Regulation		$V_{IN} = -10.5 \text{ to } -25V$		9	52		10	25	9	80		9	40		9	40		9	160	۲
(Note 7)	2-07 = fi	$V_{IN} = -11 \text{ to } -17V$		2	15				2	40		4	25					2	80	٨
P.R.K		I _O = 5mA to 1.5A		12	8		20 8	80	7	12 100	0	8	100		20	10		12	160	ž
Load Pkg.	TJ = 25°C	I _O = 250 to 750mA		4	40				4	40		9	50					4	8	ž
T-Pkg.		I _O = 5mA to 500mA		₽	25		10 2	25	7	10 80		10	64		9	40		₽	160	۶
Total Output	K,R,P-Pkg: Io	o = 5 to 1000mA,																		
Voltage Tolerance	P ≤ 15W		-7.76	<u> </u>	-824-	- 7.65	Í	-8.35 -	- 760	80 	8.40 - 7.76	ø	- 824	4 - 7.60	~	- 8.40	097-00		- 8.40	>
$V_{\rm IN} = -11.5$ to $-23V$	T-Pkg: I _O =	5 to 500mA, P ≤ 2W																		
Orisonant Current	TJ = 25°C			٢	2		1	2	-	5		ب	2		-	2		-	2	٩u
	Over Tempe	Over Temperature Range			2.5			2.5		2.5			2.5			2.5			2.5	МА
Quiescent Current	With line: Vi	v = -11.5 to - 25V		-	0.1			0.4		1.0			1.0			0.4			1.0	МA
Change	With load: Ic	With load: Io = 5 to 1000mA			0.5		F	0.4		0.5			0.5			0.4			0.5	٩w
Dropout Voltage	T. = 25°C	K,R,P-Pkg.: Io=1A		÷	2.3		1.1 2	2.3	1.1	1 2.3	3	1.1	2.3		1.1	2.3	_	1.1	2.3	۷
AV0 = 500mV	l	T-Pkg: Io = 500mA		1.0	2.3		1.0 2	2.3	-	1.0 2.3		<u>;</u>	2.3		- 1.0	2.3		1.0	2.3	>
Peak Output		K,R,Pkg.:	1.5	2.1	3.3	1.5	2.1 3	3.3 1	1.5 2.1	1 3.3	3 1.5	51	3.3	1.5	2.1	3.3	<u>9</u>	2:1	3.3	٩
Current		T-Pkg:	0.5	1.0		0.5	1.0		0.5 1.	1.0	0.5	0; -		0.5	P. F		0.5	<u>0</u>		A
Short Circuit		K,R,PPkg.:		1.5			1.5	-		1.5		1.5			1.5			1.5		۲
Current		T-Pkg:		0.5			0.5		ö	0.5		0.5			0.5			Ó.5		٩
Ripple Rejection	TJ=25°C, f	= 120Hz, ΔVIN = 10V	54	60		54	60		54 6	60	5	8		5	8		54	8		đB
Output Noise Voltage	TJ = 25°C, f =	f = 10Hz to 100 kHz		25	80		150		~~~	25 80		50			150			<u></u>		×π ms
Long Term Stability	1000 hrs at TJ	TJ = 125°C		32			5 5	50	3	32		8			2	8		32		Š
Thermal Shutdown	lo = 5mA			175			175		1	175		175			175			175		ပ့
																		i	I	

THREE TERMINAL NEGATIVE REGULATORS NEG. 8.0 VOLTS

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/220/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, V_{IN} = -14V and I_O = 500mA for K,R,P-Package (SG7900 Series). I_O = 1A for K,R,P Pkg (SG120 Series). I_O = 100mA for T-Pkg. G_{IN} = 2μ F, CoUT = 1μ F.
- 7. Line regulation @lo = 5mA = 10 mV (120-08) and 20mV (320-08).

6. Short circuit protection is only assured to $V_{IN} = -35V$.

5. At T_J = -55 °C, minimum (V_{IN} - V_O) = 2.5V.

 All regulation tests are made at constant junction temperature with low duty-cycle testing.

$ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$		ā	DEVICE PART NUMBERS	Š	SG7912A		SG1	SG120-12		SG7912	912	л П	SG7912AC	Q	Š	SG320-12	_	SG	SG7912C		
		PACKAG	E STYLES (P/N SUFFIX)	-	ς,R,T		¥	R,T	-	К,Я	۲.		K,P,R,1		×	,P,R,T		Ϋ́	,Я,Т	-	
iss Test conditions (see notes below, MiN Try Max Min	OPERATIN	G JUNCTION 1 (Unless oth	TEMPERATURE RANGE erwise specified below)	Ĩ	55°C to 50°C		1 37	0°C 0°C		- 55°	e vo		0°C to 125°C		0-	5°C 25°C		12	5 5 5 5		
	PARAMETERS	TEST COND	ITIONS (See notes below)		A P	_	IN I	YP M		and the second second	P MA)			MAX	NIW	٩			γP M/	NN X	IIS
$ \ \ \ \ \ \ \ \ \ \ \ \ \ $	Output Voltage	н		- 11.8	-120-	122 -	11.7 -	12.0 -	12.3 - 1	15-1	20-12	5 - 11.8	- 12.0	- 12.2	- 11.6	-120-	- 12.4 -	1.5	120 - 1		
$ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	Line Regulation		Ił		4	10			0	10			4	20		4	8				>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	(Note 7)	H	H		3	8				3			ю	16							>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$			-11		20	80			0	1			20	80		4	20				2
$ \begin{array}{ $		H	11	_		40				4			10	04							>
$ \begin{array}{ $	T-Pkg.		Ш			25	-		ي ي	¥			₽	4		ę	4				>
$ \begin{array}{ $	Total Output Voltage Tolerance	K,R,P-Pkg:I P ≤ 15W	= 5 to 1000mA,	- 11.7		123-	115	1	125 - 1	14	- 12	6 - 11.7		- 123	- 114	'-	-12.6-	11.4	ī		
	$V_{IN} = -15.5 \text{ to } -27V$	T-Pkg: lo	5 to 500mA, P ≤																		
$ \begin{array}{ $	Quinecent Curront	T _J = 25°C			1.5	е С	-			, , ,			1.5	e		1.5	<i>е</i>		┣		4
$ \begin{array}{ $		Over Tempe	irature Range			4			4		4			4			4		•		₹
$ \begin{array}{ $	Quiescent Current	With line: V _I	11			0.1			4		1.0			0. 1		0.1	0.4		-		4
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Change	With load: Ic	8 8			0.5	0		4		0.5			0.5	Π	0.1	0.4		O		Ā
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Dropout Voltage	- 11	K,R,P-Pkg.: Io = 1A			2.3	-		с.	+			÷	2.3		÷	2.3			L	<u> </u>
	ΔVO = 100mV		T-Pkg: Io = 100mA			2.3	-		3		<u> </u>		11	2.3		1.1	2.3	-			
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Peak Output	1	K,R,PPkg.:	1.5					-				2.1	3.3	1.5	2.1					-
	Current	1	T-Pkg:	0.5	1.0			0.	ö			0.5	1.0		0.5	1.0	-		0.1	-	7
$J = 25^{\circ}$ TPkg: 0.5	Short Circuit	1	K,R,PPkg.:		1.2		-	5.		7			1.2			1.5			1.2	-	7
nn T _J = 25°C, f = 120Hz, $\Delta V_{\rm IN}$ = 10V 56 60 54 60 54 60 56 60 54 60 56 60 54 60 56 60 54 60 56 60 54 60 56 60 54 60 54 60 56 60 54 60 56 60 54 60 54 60 54 60 54 60 54 60 54 60 56 50	Current	1	FPkg:		0.5			.5		ö			0.5			0.5).5		
TJ = 25°C, f = 10Hz to 100 kHz 25 80 25 80 300 400 300 bility 1000 hrs at TJ = 125°C 48 12 120 48	Ripple Rejection	TJ=25°C, f	= 120Hz, ΔVIN = 10V	56	60			80	5			54	99		56	60			08	p	ß
1000 hrs at T _J = 125 °C 48 12 120 48 48 12 120 48 <t< td=""><td>Output Noise Voltage</td><td>н</td><td>Ш</td><td></td><td>25</td><td>80</td><td>4</td><td>8</td><td></td><td>3</td><td></td><td></td><td>300</td><td></td><td></td><td>400</td><td></td><td></td><td>00</td><td>1</td><td>> %</td></t<>	Output Noise Voltage	н	Ш		25	80	4	8		3			300			400			00	1	> %
IO = 5mA 175 175 175 175 175	Long Term Stability	1000 hrs at	- 11		48				20	4			48			12	120		48	ε	2
	Thermal Shutdown	lo = 5mA			175		-	75		4			175			175		-	75		0

THREE TERMINAL NEGATIVE REGULATORS NEG. 12 VOLTS

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/220/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, VIN = -9V and IO = 500mA for K,R,P-Package. (7900 Series). IO = 1A for K,R,P Pkg (120 Series), IO = 100mA for T-Pkg. CIN = $2\mu F$, COUT = $1\mu F$.
- Line regulation @ lo = 5 mA = 10mV (120-12) and 20mV (320-12).

Short circuit protection is only assured to V_{IN} = - 35V.

At T_J = -56°C, minimum (V_{IN} - V_O) = 2.5V.

 All regulation tests are made at constant junction temperature with low duty-cycle testing.

		ā	DEVICE PART NUMBERS	S	SG7915A		SG	SG120-15		SG:	SG7915	_	SG7915AC	5AC		SG320-15	5	S	SG7915C	υ	
		PACKAG	E STYLES (P/N SUFFIX)		ς,R,Τ		×	, В, Т		K,	R,T		K,P,F	Г		K,P,R,T	┝		K,P,R,T		
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	OPERATI	NG JUNCTION 1 (Unless oth	TEMPERATURE RANGE erwise specified below)	ĩ	55°C to 50°C		15	5°C to 50°C		- 55 15(°C to		ည်းရှိ	ളറ		0°C to 125°C	0.0		0°C to 125°C		
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	PARAMETERS	TEST COND	TIONS (See notes below)	NIM	٩ ۲		NIV	٩			YP MA			MA			TYP MAX		MIN TYP MAX	MAX	UNITS
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Output Voltage	н		-148	- 15.0 -	- 15.2 -	- 14.7	-15.0 -	15.3 -	14.4 - 1	15.0 - 1	5.6 - 14	- 1 5	.0 - 15	2 - 14	6 – 15.0	0 - 15.4	- 14.4	- 15.0	- 15.6	>
$ \begin{array}{ $	Line Regulation		П		5	6		5	P	-		0	5	8		5	8		4	300	Š
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	(Note 7)	11	1		6	8					-		4	16					3	150	کم ع
HG T _J = 25°C Io = 260 to 750mA Io 40 10 25 10 26 10 40 40 40 PKG. Io = 500 to 750mA 10 25 10 25 10 25 10 40 40 40 PKG. Io = 500 to 750mA, 10 25 10 25 10 25 10 40 40 40 Propertion Fisher io = 510 to00mA, -146 -165 -165 2 4 2 4 2 4 2 4 2 4 4 2 4 4 4 4 4 Ore <temperature range<="" th=""> 1 15 3 15 3 15 3 15 3 15 3 15 3 15 14 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4</temperature>			IF.		30	80			8	-		0	8			8	8		12	300	۶
$ \frac{\text{PKg}}{\text{PKg}} \cdot \frac{1}{\text{C}} = 5 \text{ for } 1000\text{ MA}}{\text{L}} \cdot \frac{1}{\text{C}} = 5 \text{ for } 1000\text{ MA}} \cdot \frac{1}{\text{C}} = 5 \text{ for } 1000\text{ MA}} \cdot \frac{1}{\text{C}} \cdot \frac{1}{\text{C}} = 5 \text{ for } 1000\text{ MA}} \cdot \frac{1}{\text{C}} \cdot \frac{1}{C$		H	п		4	40							4	4					4	150	کم ۲
			1		5	52		₽	25	-		0	2	-		₽	\$		ę	240	Ę
$\frac{1}{300} \frac{1}{1} = 25^{\circ} C$ $\frac{1}{1} = 25^{\circ} C$	Total Output Voltage Tolerance	K,R,P-Pkg: P ≤ 15W	= 5 to 1000mA,	- 14.6	!	- 15.4 -	14.5		15.5 - 1	425	- 15	75 - 14	9	- L	4 - 14	4	- 15.6	- 15.6 - 14.25		- 15.75	>
	$V_{IN} = -18.5 \text{ to} - 30.0$	T-Pkg: Io	5 to 500mA, P ≤																		
Over Temperature Range I 4 2 4		TJ = 25°C			1.5	6		1.5	0	-			1.5			1.5	e		1.5	6	٩u
	Quiescent Current	Over Tempe	erature Range			4		2	4		4			4		~	4			4	٩w
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Quiescent Current	With line: V	IN =22 to - 33V			1.0			0.4		÷	_		1.0		0.1	0.4			1.0	٩u
	Change	With load: I	11			0.5	-		0.4		0			0.5		0.1	0.4			0.5	٩u
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Dropout Voltage	- 11	K,R,P-Pkg.: Io=1A			2.3			2.3	1				2.3		1:1	2.3		1.1	2.3	>
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	ΔVo = 100mV		T-Pkg: Io = 500mA			2.3			2.3	-			-	2.3		1.1	2.3		1.1	2.3	>
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Peak Output	1	K,R,PPkg.:	1.5	-									3.3			3.3	1.5	2.1	3.3	A
$ T_{J} = 25^{\circ}C \xrightarrow{\text{K,R,P,Pkg.:}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,Pkg.:}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,Pkg.:}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,Pkg.:}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R,P,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R}} D_{A} = 25^{\circ}C \xrightarrow{\text{K,R}}$	Current	1	T-Pkg:	0.5	0.9			0.9	0		6.	0.5			0.5			0.5	0.9		A
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Short Circuit		K,R,P.Pkg.:		1.3			1.3	_	1	.3		1.3			1.3			1.3		A
nn $T_J = 25^{\circ}$ C, $f = 120$ Hz, $\Delta V_{IN} = 10V$ 54 60 54 60 54 60 56 60 56 60 56 60 56 60 56 60 56 60 56 60 56 60 56 56 56 56 56 56 57 50 56 56 56 57 50 56 56 56 56 56 50 56 50 56 50 56 50 56 50 56 50 56 50 56 50 56 50 56 50	Current		T-Pkg:		0.4			0.4		0	.4		0.4			0.4			0.4		A
TJ = 25°C, f = 10Hz to 100 kHz 25 80 400 25 80 375 bility 1000 hrs at TJ = 125°C 60 15 150 60	Ripple Rejection	TJ=25°C, f	= 120Hz, ΔVIN = 10V	54	60		56	60	4		0	54	60		56	60		54	60		dB
1000 hrs at T _J = 125 °C 60 60 60 60 60 60 60	Output Noise Voltage	11	Ш		25	80		6 0		5			375			400			375		rms rms
	Long Term Stability	1000 hrs at	-11		60				50	9	0		60			15	150		60		٣٧
lo = 5mA 175 175 175 175	Thermal Shutdown	lo = 5mA			175			175		<u></u>	22		175			175			175		ပ့

THREE TERMINAL NEGATIVE REGULATORS NEG. 15 VOLTS

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/220/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, VN = -22V and IO = 500mA for K,R,PPackage (SG7900 Series). IO = 1A for K,R,P Pkg (SG120 Series), IO = 10mA for T-Pkg. CIN = $2\mu F$, COUT = $1\mu F$.
- All regulation tests are made at constant junction temperature with low duty-cycle testing.
- 5. At T_J = -56 °C, minimum (VIN VO) = 2.5V.
- 6. Short circuit protection is only assured to $V_{IN} = -35V$.
- 7. Line regulation @ lo = 5mA = 10mV (120-15) and 20mV (320-15).

Ŷ	-		MAX UNITS	0-18.6 V	300 mV	150 mV	360 mV	180 mV	300 mV	– 18.9 V		3 mA	4 mA	1.0 mA	0.5 mA	2.3 V	2.3 V	3.3 A	A	۲	۷	89	,, Sun Sun Sun Sun Sun Sun Sun Sun Sun Sun	Ě	
SG7918C	K,P,R,T	0°C to 125°C	ТYР	4 18.0	2	6	12	4	9			1.5				÷	1:1	2.1	0.9	1:1	0.3	8	375	2	
			NIW	6 - 17.4						9 - 17.1								1.5	0.5			54			
5-18	,T	20	MAX	0 - 18.6	8		8		\$	- 18.9		e	4	0.4	0.4	2.3	2.3	3.3							
SG320-18	K,P,R,T	0°C to 125°C	4 TYP	4 - 18.0	5		8		₽ 	5		1.5	2	0.1	<u>.</u>	11	1.1	2.1	0.9	1.1	0.3	8	400	2	
			NIW	33 - 17.4						35 - 17.1				-	-		_	3 1.5	0.5			5			Ļ
18AC	R,T	ခ္မပ္	TYP MAX	- 18.0 - 18.3	5	16	80	4	4	- 185		3	4	1:0	0.5	1 2.3	1 2.3	1 3.3	6				2		┞
SG7918AC	K,P,R,T	0°C to 125°C	MIN TY	- 17.7 - 1	5	4	30	4	₽	- 175		1.5				÷	1.1	5 2.1	5 0.9	1.1	0.3	4 60	375	2	
			MAX MI	- 18.7 - 1	180	75	180	8	120	- 18.9 - 1			4	1.0	0.5	2.3	2.3	3.3 1.5	0.5			2	8		┞
SG7918	K,R,T	55°C to 150°C	TYP M	18.0 - 1	¥ 9	3 7	12 18	4	10	<u> </u>		1.5	F	-	0	1.1 2	1.1 2	2.1 3.	0.9	1.1	0.3	8	25 8	72	
SG	Ϋ́	- 55	MIN	- 173-			-		-	- 17.1		-	-			-	-	1.5 2	0.5 0	-	0	54			╞
			MAX N	- 18.4 -	ę		80		25	- 18.6 -		е В	4	0.4	0.4	2.3	2.3	3.3 1	0			4			-
SG120-18	K,R,T	55°C to 150°C	TYP N	- 18.0 -	2		30		10	1		1.5	2	0.1 (0.1	÷	1.1	2.1 3	0.9	1.1	0.3	8	400	72	
SG	¥	1	L NIM	- 17.6 -						- 17.4				-	-			1.5	0.5			2			┢
			MAX	- 18.3 -	9	œ	8	40	25	- 18.5		e	4	1.0	0.5	2.3	2.3	3.3					80		
SG7918A	K,R,T	-55°C to 150°C	٩	- 18.0	S	e	8	4	10			1.5				÷	1.1	2.1	0.9	1.1	0.3	8	25	22	
Š		ï	MIN	- 177 -						- 175								1.5	0.5			2			F
DEVICE PART NUMBERS	PACKAGE STYLES (P/N SUFFIX)	UNCTION TEMPERATURE RANGE (Unless otherwise specified below)	TEST CONDITIONS (See notes below) MIN TYP		$V_{IN} = -21 \text{ to } -33 \text{ V}$	$V_{IN} = -24 \text{ to } -30V$	$I_O = 5mA \text{ to } 1.5A$	l _O = 250 to 750mA	I _O = 5mA to 500mA	$I_0 = 5$ to 1000mA,	: 5 to 500mA, P ≤ 2W		Over Temperature Range	$/_{\rm IN} = -18.5 \text{ to } -30 \text{ V}$	lo = 5 to 100mA	K,R,P-Pkg.: Io = 1A	T-Pkg: lo = 500mA	K,R,PPkg.:	T-Pkg:	K,R,PPkg.	T-Pkg.	[.]=25°C, f = 120Hz, ΔVIN = 10V	f = 10Hz to 100 kHz	TJ = 125°C	
Q	PACKAG	VG JUNCTION (Unless of	TEST COND	T _J = 25°C		T _J = 25°C		TJ = 25°C		K,R,P-Pkg: I _O P ≤ 15W	T-Pkg: lo =	T _J = 25°C	Over Tempe	With line: V _{IN}	With load: Io	T ₁ = 25°C		T. = 25°C		T. = 25°C	1	TJ=25°C,1	TJ = 25°C, f	1000 hrs at TJ	
		OPERATING J	PARAMETERS	Output Voltage	Line Regulation	(Note 7)	P,R,K	Load Regulation	T-Pkg.	Total Output Voltage Tolerance	$V_{IN} = -22 \text{ to } -33V$	Culoront Current		Quiescent Current	Change	Dropout Voltage	ΔVo = 100mV	Peak Output	Current	Short Circuit	Current	Ripple Rejection	Output Noise Voltage	Long Term Stability	

THREE TERMINAL NEGATIVE REGULATORS NEG. 18 VOLTS

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/220/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, VIN = -27V and I/o = 500mA for K,R,P-Package (SG7900 Series). I/o = 1A for K,R,P Pkg (SG120 Series), I/o = 100mA for T-Pkg. CiN = $2\mu F$. CoUT = $1\mu F$.
- Line regulation @ lo = 5mA = 10mV (120-18) and 20mV (320-18).

5. At T_J = -55 °C, minimum (V_{IN} - V_O) = 2.5V. 6. Short circuit protection is only assured to V_{IN} = -35V.

 All regulation tests are made at constant junction temperature with low duty-cycle testing.

		DEVICE PART NUMBERS	S	SG7920A		SG1	SG120-20		SG7920	120	Š	SG7920AC	0	Š	SG320-20		SG	SG7920C		
	PACKAGI	PACKAGE STYLES (P/N SUFFIX)		K,R,T		Υ.	K,R,T	-	K,R,T	<u>-</u>		K,P,R,T		×	K,P,R,T		ΥΎ	K,P,R,T		
OPERATING J	VG JUNCTION 1 (Unless oth	UNCTION TEMPERATURE RANGE (Unless otherwise specified below)	Ĩ	55°C to 150°C		- 55 15(55°C to 150°C		- 22,-	55°C to 150°C		125°C			0°C 125°C		°,4	0°C to 125°C		
PARAMETERS	TEST COND	EST CONDITIONS (See notes below) MIN	-	TYP	MAX N	T NIM	TYP MAX	X MIN		TYP MAX	NIW	μ	MAX	NIW	٩Y	MAX	NIN	TYP N	MAX U	UNITS
Output Voltage	T _J = 25°C		- 19.7	-20.0 -	-20.3 -	- 19.5 2	-20.0 -18.5	3.5 - 19.2	92 - 20	-20.0 -20.8	8 – 19.7	-20.0	-20.0 -20.3		- 19.2 - 20.0	-20.8	- 19.2	-20.0 -20.8	20.8	>
Line Regulation		$V_{IN} = -23 \text{ to } -35V$		5	10		5 10	_	11	150		6	20		5	20		11 3	300	٨
(Note 7)	TJ = 25°C	$V_{IN} = -26 \text{ to } -32V$		4	8				3	75		4	16					3	150	۲ ۲
P,R,K		$I_0 = 5mA \text{ to } 1.5A$		30	80	(7)	30 80		12	200		30	80		30	80		12 4	400	۲ ۲
Load Pkg. Regulation	TJ = 25°C	l _O = 250 to 750mA		4	40				4	100		4	40					10	200	۲ ۲
T-Pkg.		I _O = 5mA to 500mA		10	25	-	10 25		10	150		10	40		10	80		10	300	Ž
Total Output Voltage Tolerance	K,R,P-Pkg: I _O P ≤ 15W	= 5 to 1000mA,	- 19.4		- 20.6	- 19.3	- 20.7	0.7 - 19.0	06	-31	- 21.0 - 19.4		- 20.6	20.6 - 19.0		- 21.0-	- 19.0	1	21.0	>
$V_{IN} = -24 \text{ to } -35V$	T-Pkg: lo =	: 5 to 500mA, P ≤ 2W																		
	T _J = 25°C			1.5	3	-	1.5 3		1.5	3		1.5	e		1.5	3		1.5	3	۳A
Guiescent Current	Over Tempe	Over Temperature Range			4		2 4			4			4	5		4			4	٩W
Quiescent Current	With line: V	With line: $V_{IN} = -24$ to $-35V$			1.0	°	0.1 0.4			1.0			1.0		0.1	0.4			1.0	шA
Change	With load: Io	lo = 5 to 1000mA			0.5	0	0.1 0.4	+		0.5			0.5		0.1	0.4		-	0.5	мA
Dropout Voltage	Tı = 25°C	K,R,P-Pkg.: lo = 1A		1:1	2.3	-	1.1 2.3		1.1	2.3		1.1	2.3		1.1	2.3		1.1	2.3	>
AV0 = 100mV		T-Pkg: Io = 500mA		; -	2.3	-	1.1 2.3		÷	2.3		÷	2.3		÷	2.3		Ţ.	2.3	>
Peak Output	T _ 26 °C	K,R,PPkg.:	1.5	2.1	3.3 1	1.5 2	2.1 3.3	1	.5 2.1	3.3	1.5	2.1	3.3	1.5	2.1	3.3	1.5	2.1	3.3	٩
Current	I	T-Pkg:	0.5	0.9	-	0.5 1	1.0	ö	5 1.0	_	0.5	1.0		0.5	1.0		0.5	1.0		۲
Short Circuit	ד. – אניר	K,R,P.Pkg.:		0.9		0	0.9		0.9			0.9			0.9		-	0.9		۷
Current	I I	T:Pkg:		0.2		0	0.2		0.2			0.2			0.2		-	0.2		۲
Ripple Rejection	TJ = 25°C, f	f = 120Hz, ΔVIN = 10V	54	60		54 6	60	54	4 60		54	60		54	8		5	8		æ
Output Noise Voltage	TJ = 25°C,	T _J = 25°C, f = 10Hz to 100 kHz		375		4	400		375			375			400			375		rms sm
Long Term Stability	1000 hrs at TJ	TJ = 125°C		80		-	15 150	0	8			80			15	150		8	_	Š
Thermal Shutdown	lo = 5mA			175		-	175		175	9		175			175			175		ပ့

THREE TERMINAL NEGATIVE REGULATORS NEG. 20 VOLTS

NOTES:

- 1. Minimum load current for full line regulation is 5mA. (SG120/220/320 only)
- 2. Maximum test current for T-Pkg. is 500mA.
- 3. Unless otherwise specified, VIN = -29V and IO = 500mA for K,R,P-Package (SG7900 Series). IO = 1A for K,R,P Pkg (120 Series), IO = 100mA for T-Pkg. CIN = $2\mu F$, COUT = $1\mu F$.
- All regulation tests are made at constant junction temperature with low duty-cycle testing.
 - 5. At TJ = -56°C, minimum (VIN VO) = 2.5V.
- 6. Short circuit protection is only assured to $V_{IN} = -35V$.
- 7. Line regulation @ lo = 5mA = 10mV (120:20) and 20mV (320:20).

PULSE WIDTH MODULATORS

Silicon General LINEAR INTEGRATED CIRCUITS

SG1524 / SG2524 / SG3524

Regulating Pulse Width Modulator

Description

This monolithic integrated circuit contains all the control circuitry for a regulating power supply inverter or switching regulator. Included in a 16-pin dual-in-line package is the voltage reference, error-amplifier, oscillator, pulse width modulator, pulse steering flip-flop, dual alternating output switches and current limiting and shut-down circuitry. This device can be used for switching regulators of either polarity, transformer coupled DC to DC converters, transformerless voltage doublers and polarity converters, as well as other power control applications. The SG1524 is specified for operation over the full military temperature range of $-55^{o}C$ to $+125^{o}C$, while the SG2524 and SG3524 are designed for commercial applications of 0°C to +70°C.

Features

- Complete PWM power control circuitry
- · Single ended or push-pull outputs
- Line and load regulation of 0.2%
- 1% maximum temperature variation
- Total supply current less than 10mA
- Operation beyond 100kHz

Absolute Maximum Ratings

Input Voltage	40V
Output Current (each output)	100mA
Reference Output Current	50mA
Oscillator Charging Current	5mA
Power Dissipation (package limitation)	1000mW
Derate above 25°C	8mW/°C

Operating Temperature Range
SG1524J
SG2524J
SG3524J
Storage Temperature Range

-55° C to +125° C -25°C to +85°C 0° C to +70° C -65° C to +150° C



CONNECTION DIAGRAM



CHIP LAYOUT



Electrical Characteristics (Unless otherwise stated, these specifications apply for $T_A = -55^{\circ}C$ to +125°C for the SG1524 and 0°C to +70°C for the SG2524 and SG3524, $V_{1N} = 20V$, and f = 20kHz)

		501	524	SG2524		SG352	A	
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Reference Section:								
Output Voltage:		4.8	5.0	5.2	4.6	5.0	5.4	v I
Line Regulation	V _{IN} = 8 to 40 Volts		10	20	-	10	30	mV
Load Regulation	1, = 0 to 20mA		20	50		20	50	mV
Ripple Rejection	f = 120 Hz, T _A = 25°C		66			66		dB
Short Circuit Current Limit	$V_{\text{REF}} = 0, T_{\text{A}} = 25^{\circ}\text{C}$	<u> </u>	100			100	<u> </u>	mA
Temperature Stability	Over Operating Temperature Range		0.3	1		0.3	1	8
Long Term Stability	$T_A \approx 25^{\circ}C$		20	_	_	20	<u> </u>	mV/khr
	1A - 25 C	_	20		_	20		III V/KIII
Oscillator Section:	0 001							
Maximum Frequency	$C_T = .001 \text{ mfd}, R_T = 2k\Omega$	-	300	-	-	300		kHz
Initial Accuracy	R _T and C _T constant	-	5	-		5	-	%
Voltage Stability	$V_{IN} = 8 \text{ to } 40 \text{ Volts}, T_A = 25^{\circ}\text{C}$	-	-	1	-	-	1	%
Temperature Stability	Over Operating Temperature Range	-	~	2	-	-	2	%
Output Amplitude	Pin 3, T _A = 25°C	-	3.5	-		3.5		V
Output Pulse Width	C _T = .01 mfd, T _A = 25°C	-	0.5	-		0.5	-	μS
Error Amplifier Section:								
Input Offset Voltage	V _{CM} = 2.5 Volts	-	0.5	5	-	2	10	mV
Input Bias Current	V _{CM} = 2.5 Volts	-	2	10	-	2	10	μA
Open Loop Voltage Gain		72	80	1	60	80	-	dB
Common Mode Voltage	$T_A = 25^{\circ}C$ $T_A = 25^{\circ}C$	1.8	-	3.4	1.8	-	3.4	V
Common Mode Rejection Ratio	T _A =25°C	-	70	-		70	-	dB
Small Signal Bandwidth	A _V = 0 _u B, T _A = 25°C	-	3	-	-	3	_	MHz
Output Voltage	T _A = 25°C	0.5	-	3.8	0.5	-	3.8	v
Comparator Section:								
Duty Cycle	% Each Output On	0	-	45	0	-	45	%.
Input Threshold	Zero Duty Cycle		1	-	-	1	_	v
Input Threshold	Max. Duty Cycle	-	3.5		-	3.5		v
Input Bias Current		-	1	-	-	1	_	μA
Current Limiting Section:	Pin 9 = 2V with Error Amplifier					-		
Sense Voltage	Set for Max Out, T _A = 25°C	190	200	210	180	200	220	mν
Sense Voltage T.C.		- 130	0.2	-		0.2	~	mV/°C
Common Mode Voltage		- 0.3		+ 0.3	- 0.3	-	+ 0.3	V
Output Section: (Each Output)								
Collector-Emitter Voltage		40		_	40			v
Collector Leakage Current	V _{CE} = 40V		0.1	- 50	-40	0.1	50	μA
Saturation Voltage	I _C = 50mA		1	2	-	1	2	μΑ V
Emitter Output Voltage	V _{IN} = 20V	17	18		17	18	-	- v
Rise Time	$R_{c} = 2K \text{ ohm}, T_{A} = 25^{\circ}C$		0.2		- 17	0.2	-	μS
Fall Time	$R_{c} = 2K \text{ ohm}, T_{A} = 25^{\circ}C$		0.2			0.2	-	μ3 μS
Total Standby Current:	V _{IN} = 40V							
(Excluding oscillator charging current, error and current limit dividers, and with outputs open)	v _{iN} = 40V	-	8	10	-	8	10	mA



Oscillator

The oscillator in the SG1524 uses an external resistor (R_{T}) to establish a constant charging current into an external capacitor (C_T). While this uses more current than a series connected RC, it provides a linear ramp voltage on the capacitor which is also used as a reference for the comparator. The charging current is equal to 3.6V \div R_T and should be kept within the range of approximately 30 μ A to 2 mA, i.e., $1.8k < R_T < 100k$. The range of values for C_T also has limits as the discharge time of C_T determines the pulse width of the oscillator output pulse. This pulse is used (among other things) as a blanking pulse to both outputs to insure that there is no possibility of having both outputs on simultaneously during transitions. This output dead time relationship is shown in Figure 1. A pulse width below approximately 0.5 microseconds may allow false triggering of one output by removing the blanking pulse prior to the flip-flop's reaching a stable state. If small values of C_T must be used, the pulse width may still be expanded by adding a shunt capacitance (\approx 100 pf) to ground at the oscillator output. (Note: Although the oscillator output is a convenient oscilloscope sync input, the cable and input capacitance may increase the blanking pulse width slightly.) Obviously, the upper limit to the pulse width is determined by the maximum duty cycle acceptable. Practical values of CT fall between .001 and 1.0 mfd.

The oscillator period is approximately $t = R_T C_T$ where t is in microseconds when $R_T =$ ohms and $C_T =$ microfarads.

The use of Figure 2 will allow selection of R_T and C_T for a wide range of operating frequencies. Note that for series regulator applications, the two outputs can be connected in parallel for an effective 0 - 90% duty cycle and the frequency of the oscillator is the frequency of the output. For push-pull applications, the outputs are separated and the flip-flop divides the frequency such that each output's duty cycle is 0 - 45% and the overall frequency is % that of the oscillator.

If it is desired to synchronize the SG1524 to an external clock, a pulse of \approx + 3 volts may be applied to the oscillator output terminal with $R_T C_T$ set slightly greater than the clock period. The same considerations of pulse width apply. The impedance to ground at this point is approximately 2k ohms.

If two or more SG1524's must be synchronized together, the easiest method is to interconnect all pin 3 terminals, tie all pin 7's together and to a single C_T , leave all pin 6's open except one which is connected to a single R_T .





Current Limiting

The current limiting circuitry of the SG1524 is shown in Figure 3.

By matching the base-emitter voltages of Q1 and Q2, and assuming negligible voltage drop across R_1 ,

Threshold =
$$V_{BE}$$
 (Q1) + $I_1R_2 - V_{BE}$ (Q2) = I_1R_2
 $\approx 200 \text{ mV}$

Although this curcuit provides a relatively small threshold with a negligible temperature coefficient, there are some limitations to its use, the most important of which is the ± 1 volt common mode range which requires sensing in the ground line. Another factor to consider is that the frequency compensation provided by R_1C_1 and $\Omega 1$ provides a roll-off pole at approximately 300 Hertz.

Since the gain of this circuit is relatively low, there is a

transition region as the current limit amplifier takes over pulse width control from the error amplifier. For testing purposes, threshold is defined as the input voltage to get 25% duty cycle with the error amplifier signaling maximum duty cycle.

If this current limit circuitry is unused, pins 4 and 5 should both be grounded.





In this conventional single-ended regulator circuit, the two outputs of the SG1524 are connected in parallel for effective 0 - 90% duty-cycle modulation. The use of an output inductor requires and R-C phase compensation network for loop stability.



Push-pull outputs are used in this transformer-coupled DC-DC regulating converter. Note that the oscillator must be set at twice the desired output frequency as the SG1524's internal flip-flop divides the frequency by 2 as it switches the P.W.M. signal from one output to the other. Current limiting is done here in the primary so that the pulse width will be reduced should transformer saturation occur.

SILICAN GENEPAL

SG1524B/SG2524B/SG3524B

REGULATING PULSE WIDTH MODULATOR

DESCRIPTION

The SG1524B is a pulse width modulator for switching power supplies which features improved performance over industry standards like the SG1524. A direct pin-for-pin replacement for the earlier device, it combines advanced processing techniques and circuit design to provide improved reference accuracy, and extended common mode range at the error amplifier and current limit inputs. A DC-coupled flip-flop eliminates triggering and glitch problems, and a PWM data latch prevents edge oscillations. The circuit incorporates true digital shutdown for high speed response. while an undervoltage lockout circuit prevents spurious outputs when the supply voltage is too low for stable operation. Full doublepulse suppression logic insures alternating output pulses when the Shutdown pin is used for pulse-by-pulse current limiting. The SG1524B is specified for operation over the full military ambient temperature range of -55°C to +125°C. The SG2524B is characterized for the industrial range of -25°C to +85°C, and the SG3524B is designed for the commercial range of 0°C to +70°C.

FEATURES

- 7 to 40 volt operation
- 5 volt reference trimmed to ±1%
- 100 Hz to 400 kHz oscillator range
- Excellent external sync capability
- Dual 100 mA output transistors
- Wide current limit common mode range
- DC-coupled toggle flip-flop
- PWM data latch
- Undervoitage lockout
- Full double-pulse suppression logic
- 60 volt output collectors



August 1983

SG1524B/SG2524B/SG3524B

-25°C to +85°C 0°C to +70°C

ABSOLUTE MAXIMUM RATINGS (Note	1)		
Input Voltage (+VIN)	+42V	Power Dissipation at $T_A = +25^{\circ}C$ (Note 2)	1000mW
Collector Voltage	+60V	Thermal Resistance: Junction to Ambient	100° C/W
Logic Inputs	-0.3V to +5.5V	Power Dissipation at $T_{C} = +25^{\circ}C$ (Note 3)	2000mW
Current Limit Sense Inputs	-0.3V to +VIN	Thermal Resistance: Junction to Case	60° C/W
Output Current (each transistor)	200mA	Operating Junction Temperature	+150°C
Reference Load Current	50mA	Storage Temperature Range	-65°C to +150°C
Oscillator Charging Current	5mA	Lead Temperature (Soldering, 10 seconds)	+300°C
Note 1. Values beyond which damage may occur. Note 2. Derate at 10 mW/°C for ambient temperatu Note 3. Derate at 16 mW/°C for case temperatures.			
	above +25°C.		
Note 2. Derate at 10 mW/°C for ambient temperatu Note 3. Derate at 16 mW/°C for case temperatures RECOMMENDED OPERATING CONDITION	above +25°C. FIONS (Note 4)	Oscillator Frequency Range	100Hz to 400kHz
Note 2. Derate at 10 mW/° C for ambient temperatu Note 3. Derate at 16 mW/° C for case temperatures RECOMMENDED OPERATING CONDIT Input Voltage (+VIN)	above +25°C.	Oscillator Frequency Range Oscillator Timing Resistor (R _T)	100Hz to 400kHz 2kΩ to 150kΩ
Note 2. Derate at 10 mW/° C for ambient temperatu Note 3. Derate at 16 mW/° C for case temperatures RECOMMENDED OPERATING CONDIT Input Voltage (+V _{IN}) Collector Voltage	above +25°C. FIONS (Note 4) +7V to +40V	Oscillator Frequency Range Oscillator Timing Resistor (RT) Oscillator Timing Capacitor (CT)	2kΩ to 150kΩ
Note 2. Derate at 10 mW/° C for ambient temperatu Note 3. Derate at 16 mW/° C for case temperatures RECOMMENDED OPERATING CONDIT Input Voltage (+VIN)	above +25°C. FIONS (Note 4) +7V to +40V 0V to +60V	Oscillator Timing Resistor (RT)	
Note 2. Derate at 10 mW/° C for ambient temperatu Note 3. Derate at 16 mW/° C for case temperatures RECOMMENDED OPERATING CONDIT Input Voltage (+V _{IN}) Collector Voltage Error Amp Common Mode Range	above +25°C. FIONS (Note 4) +7V to +40V 0V to +60V +2.3V to +5.2V	Oscillator Timing Resistor (R _T) Oscillator Timing Capacitor (C _T)	2kΩ to 150

Note 4. Range over which the device is functional and parameter limits are guaranteed.

ELECTRICAL CHARACTERISTICS (+VIN = 20 volts, and over operating temperature, unless otherwise specified)

0 to 20mA

25µA to 1.8mA

SG2524B

SG3524B

		SG1	524 B /2	524B	9	G3524	8	UNITS
PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	QNITS
REFERENCE SECTION (Note 5)								
Output Voltage	$T_J = +25^{\circ}C$	4.95	5.00	5.05	4.90	5.00	5.10	v
Line Regulation	$+V_{IN} = 7$ to 40 volts		3	20		3	30	mV
Load Regulation	$I_L = 0 \text{ to } 20 \text{ mA}$		5	30		5	50	mV
Temperature Stability (Note 9)	Over Operating Temperature Range		15	50		15	50	mV
Total Output Voltage Range	Over Line, Load and Temperature	4.90		5.10	4.80		5.20	v
Short Circuit Current	V _{REF} = 0 volts	25	50	100	25	50	100	mA
UNDERVOLTAGE LOCKOUT								
Threshold Voltage		4.3	4.5	4.7	4.3	4.5	4.7	v
OSCILLATOR SECTION (Note 6)								
Initial Accuracy	$T_{\rm J} = +25^{\circ}{\rm C}$	40	43	46	38	43	48	kHz
Voltage Stability	$+V_{IN} = 7$ to 40 volts		0.1	1		0.1	1	%
Temperature Stability (Note 9)	Over Operating Temperature Range		1	2		1	2	%
Minimum Frequency	$R_T = 300 k\Omega, C_T = 0.1 \mu F$		50	100		50	100	Hz
Maximum Frequency	$R_T = 2k\Omega$, $C_T = 470 pF$	400	600		400	600		kHz
Sawtooth Peak Voltage	+V _{IN} = 40 · volts		3.5	3.9		3.5	3.9	v
Sawtooth Valley Voltage	+V _{IN} = 7 volts	0.6	1		0.6	1		V
Clock Amplitude		3.0	4.0		3.0	4.0		v
Clock Pulse Width (Note 9)		0.2	0.5	1.2	0.2	0.5	1.2	µSec

85

Reference Load Current

Oscillator Charging Current

Note 5. I_L = 0 mA Note 6. F_{OSC} = 43 kHz (R_T = 2700 Ω , C_T = .01 μ F)

SG1524B/SG2524B/SG3524B

ELECTRICAL CHARACTERISTICS (Continued)

PARAMETERCONDITIONSERROR AMPLIFIER SECTION (Note 7)nput Offset Voltagenput Bias Currentnput Offset CurrentDC Open Loop Gain $R_L \ge 10$ MegohmsDutput Low LevelIsiNK = 100 μ A; V _{PIN 1} - V _{PIN 2} ≥ 150 mVDutput Low LevelIsOURCE = 100 μ A; V _{PIN 2} - V _{PIN 1} ≥ 150 mVDutput High LevelIsOURCE = 100 μ A; V _{PIN 2} - V _{PIN 1} ≥ 150 mVCommon Mode RejectionV _{CM} = +2.3 to 5.2 voltsSupply Voltage Rejection+V _{IN} = 7 to 40 voltsBain-Bandwidth Product (Note 9)TJ = +25° CP.W.M. COMPARATOR (Note 6)Minimum Duty CycleV _{COMP} = +0.5 voltsMaximum Duty CycleVCOMP = +3.9 voltsCURRENT LIMIT AMPLIFIER (Note 8)Sense Voltagenput Bias Current	MIN 60 3.8	TYP 0.5 1 78	MAX 5 5 1	MIN	TYP 2	MAX	UNITS
nput Offset Voltage $R_S \le 2k\Omega$ nput Bias Current nput Offset Current DC Open Loop Gain $R_L \ge 10$ Megohms Dutput Low Level ISINK = 100µA; V _{PIN 1} - V _{PIN 2} ≥ 150 mV Dutput High Level ISOURCE = 100µA; V _{PIN 2} - V _{PIN 1} ≥ 150 mV Common Mode Rejection $V_{CM} = +2.3$ to 5.2 volts Supply Voltage Rejection +V _{IN} = 7 to 40 volts Gain-Bandwidth Product (Note 9) T _J = +25° C P.W.M. COMPARATOR (Note 6) V _{COMP} = +0.5 volts Maximum Duty Cycle V _{COMP} = +3.9 volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current		1 78	5		2	L	
nput Bias Current 3 nput Offset Current $R_L \ge 10$ Megohms DC Open Loop Gain $R_L \ge 100\mu$ X; $V_{PIN 1} - V_{PIN 2} \ge 150 \text{ mV}$ Dutput Low Level $I_{SNK} = 100\mu$ X; $V_{PIN 1} - V_{PIN 2} \ge 150 \text{ mV}$ Dutput High Level $I_{SOURCE} = 100\mu$ X; $V_{PIN 2} - V_{PIN 1} \ge 150 \text{ mV}$ Common Mode Rejection $V_{CM} = +2.3 \text{ to } 5.2 \text{ volts}$ Supply Voltage Rejection $+V_{IN} = 7 \text{ to 40 volts}$ Gain-Bandwidth Product (Note 9) $T_J = +25^{\circ}$ C P.W.M. COMPARATOR (Note 6) $V_{COMP} = +0.5 \text{ volts}$ Maximum Duty Cycle $V_{COMP} = +3.9 \text{ volts}$ CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current		1 78	5		2		
nput Offset Current RL \geq 10 Megohms DC Open Loop Gain RL \geq 10 Megohms Dutput Low Level ISINK = 100µA; VPIN 1 - VPIN 2 \geq 150 mV Dutput High Level ISOURCE = 100µA; VPIN 2 - VPIN 1 \geq 150 mV Common Mode Rejection V _{CM} = +2.3 to 5.2 volts Supply Voltage Rejection +V _{IN} = 7 to 40 volts Gain-Bandwidth Product (Note 9) TJ = +25° C P.W.M. COMPARATOR (Note 6) V _{COMP} = +0.5 volts Maximum Duty Cycle V _{COMP} = +3.9 volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current		78				10	mV
DC Open Loop Gain $R_L \ge 10$ Megohms Dutput Low Level $I_{SINK} = 100\muA; V_{PIN 1} - V_{PIN 2} \ge 150 \text{ mV}$ Dutput High Level $I_{SOURCE} = 100\muA; V_{PIN 2} - V_{PIN 1} \ge 150 \text{ mV}$ Common Mode Rejection $V_{CM} = +2.3$ to 5.2 volts Supply Voltage Rejection $+V_{IN} = 7$ to 40 volts Bain-Bandwidth Product (Note 9) $T_J = +25^{\circ}$ C P.W.M. COMPARATOR (Note 6) $V_{COMP} = +0.5$ volts Maximum Duty Cycle $V_{COMP} = +3.9$ volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current		ł	1		1	10	μA
L L Dutput Low Level $I_{SINK} = 100\mu$ A; $V_{PIN 1} - V_{PIN 2} \ge 150 \text{ mV}$ Dutput High Level $I_{SOURCE} = 100\mu$ A; $V_{PIN 2} - V_{PIN 1} \ge 150 \text{ mV}$ Common Mode Rejection $V_{CM} = +2.3 \text{ to } 5.2 \text{ volts}$ Supply Voltage Rejection $+V_{IN} = 7 \text{ to } 40 \text{ volts}$ Gain-Bandwidth Product (Note 9) $T_J = +25^{\circ}$ C P.W.M. COMPARATOR (Note 6) $V_{COMP} = +0.5 \text{ volts}$ Maximum Duty Cycle $V_{COMP} = +3.9 \text{ volts}$ CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current		ł				1	μA
Dutput High Level $I_{SOURCE} = 100\mu$ A; $V_{PIN 2} - V_{PIN 1} \ge 150 \text{ mV}$ Common Mode Rejection $V_{CM} = +2.3 \text{ to } 5.2 \text{ volts}$ Supply Voltage Rejection $+V_{IN} = 7 \text{ to } 40 \text{ volts}$ Gain-Bandwidth Product (Note 9) $T_J = +25^{\circ}$ C P.W.M. COMPARATOR (Note 6) VCOMP = +0.5 volts Minimum Duty Cycle $V_{COMP} = +3.9 \text{ volts}$ CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current	3.8			60	78		dB
Common Mode Rejection $V_{CM} = +2.3$ to 5.2 volts Supply Voltage Rejection $+V_{IN} = 7$ to 40 volts Gain-Bandwidth Product (Note 9) $T_J = +25^{\circ}$ C P.W.M. COMPARATOR (Note 6) VCOMP = +0.5 volts Minimum Duty Cycle $V_{COMP} = +3.9$ volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current	3.8	0.2	0.5		0.2	0.5	v
Common Mode Rejection $V_{CM} = +2.3$ to 5.2 volts Supply Voltage Rejection $+V_{IN} = 7$ to 40 volts Gain-Bandwidth Product (Note 9) $T_J = +25^{\circ}$ C P.W.M. COMPARATOR (Note 6) VCOMP = +0.5 volts Minimum Duty Cycle $V_{COMP} = +3.9$ volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage Sense Voltage nput Bias Current		4.2		3.8	4.2		v
Gain-Bandwidth Product (Note 9) TJ = +25°C P.W.M. COMPARATOR (Note 6) Minimum Duty Cycle V _{COMP} = +0.5 volts Maximum Duty Cycle V _{COMP} = +3.9 volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage nput Bias Current	70	90		70	90		dB
P.W.M. COMPARATOR (Note 6) Vinimum Duty Cycle V _{COMP} = +0.5 volts Maximum Duty Cycle V _{COMP} = +3.9 volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage nput Bias Current	76	100		76	100		dB
Minimum Duty Cycle V _{COMP} = +0.5 volts Maximum Duty Cycle V _{COMP} = +3.9 volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage nput Bias Current	1	2		1	2		MHz
Maximum Duty Cycle VCOMP = +3.9 volts CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage nput Bias Current		•	•			L	
CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage nput Bias Current			0			0	%
CURRENT LIMIT AMPLIFIER (Note 8) Sense Voltage nput Bias Current	45	49		45	49		%
	180	200	220	170	200	230	mV
nput Bias Current	1.00	1	1				
		-3	-10	1	-3	-10	μA
SHUTDOWN INPUT							
HGH Input Voltage	2.0			2.0			v
HIGH Input Current V _{SHUTDOWN} = +5.0 volts		0.1	1		0.1	1	mA
OW Input Voltage			0.6			0.6	v
DUTPUT SECTION (Each transistor)		-					
Collector Leakage Current V _{CE} = 60 volts			50			50	μA
Collector Saturation Voltage		0.2	0.4		0.2	0.4	v
I _C = 100 mA		1.0	2.0		1.0	2.0	v
Emitter Output Voltage	17.5	19		17.5	19		v
$I_E = 100 \text{ mA}$	17	18		17	18		v
Emitter Voltage Rise Time (Note 9) $R_{E} = 2k\Omega, T_{A} = +25^{\circ}C$		0.2	0.5		0.2	0.5	µSec
Collector Voltage Fall Time (Note 9) $R_{C} = 2k\Omega, T_{A} = +25^{\circ}C$		0.1	0.2		0.1	0.2	µSec
POWER CONSUMPTION	•		-			•	
Standby Current +V _{IN} = 40 volts, V _{SHUTDOWN} = 2.0V	1	5	10		5	10	mA

Note 7. V_{CM} = +2.3V to +5.2V Note 8. V_{CM} = 0 to +17.5V Note 9. These parameters, although guaranteed over the recommended operating conditions, are not 100% tested in production.

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SILICAN GENEPAL LINEAR INTEGRATED CIRCUITS

SG1525A / SG2525A / SG3525A SG1527A / SG2527A / SG3527A

Regulating Pulse Width Modulators

DESCRIPTION

The SG1525A/1527A series of pulse width modulator integrated circuits are designed to offer improved performance and lowered external parts count when used to implement all types of switching power supplies. The on-chip +5.1 volt reference is trimmed to $\pm 1\%$ initial accuracy and the input common-mode range of the error amplifier includes the reference voltage, eliminating external potentiometers and divider resistors. A Sync input to the oscillator allows multiple units to be slaved together, or a single unit to be synchronized to an external system clock. A single resistor between the CT pin and the Discharge pin provides a wide range of deadtime adjustment. These devices also feature built-in soft-start circuitry with only a timing capacitor required externally. A Shutdown pin controls both the soft-start circuitry and the output stages, providing instantaneous turn-off with soft-start recycle for slow turn-on. These functions are also controlled by an undervoltage lockout which keeps the outputs off and the soft-start capacitor discharged for input voltages less than that required for normal operation. Another unique feature of these PWM circuits is a latch following the comparator. Once a PWM pulse has been terminated for any reason, the outputs will remain off for the duration of the period. The latch is reset with each clock pulse. The output stages are totem-pole designs capable of sourcing or sinking in excess of 200 mA. The SG1525A output stage features NOR logic, giving a LOW output for an OFF state. The SG1527A utilizes OR logic which results in a HIGH output level when OFF.

BLOCK DIAGRAM



FEATURES

- 8 to 35 volt operation
- 5.1 volt reference trimmed to ±1%
- 100 Hz to 500 kHz oscillator range
- Separate oscillator sync terminal
- Adjustable deadtime control
- Internal soft-start
- Input undervoltage lockout
- Latching P.W.M. to prevent multiple pulses
- Dual source/sink output drivers





non-"A" versions.

ABSOLUTE MAXIMUM RATINGS (Note 1)

Supply Voltage (+VIN)	+40V	Power Dissipation at $T_A = +25^{\circ}C$ (Note 2)	1000 mW
Collector Supply Voltage (VC)		Thermal Resistance: junction to ambient	100° C/W
Logic Inputs		Power Dissipation at $T_{C} = +25^{\circ}C$ (Note 3)	2000 mW
Analog Inputs		Thermal Resistance: junction to case	60° C/W
Output Current, Source or Sink		Operating Junction Temperature	+150° C
Reference Output Current		Storage Temperature Range	-65° C to 150° C
Oscillator Charging Current	5 mA	Lead Temperature (Soldering, 10 seconds)	+300° C
Note 1 Values beyond which damage may oc			

Note 2. Derate at 10 mW/°C for ambient temperatures above +50°C. Note 3. Derate at 16 mW/°C for case temperatures above +25°C.

RECOMMENDED OPERATING CONDITIONS (Note 4)

Input Voltage (+VIN)
Collector Supply Voltage (VC)
Sink/Source Load Current (steady state)
Sink/Source Load Current (peak)
Reference Load Current
Oscillator Frequency Range
Oscillator Timing Resistor

+8V to +35V
+4.5V to +35V
0 to 100 mA
0 to 400 mA
0 Coperating Ambient Temperature Range
0 to 400 mA
0 Coperating Ambient Temperature Range
0 to 20 mA
0 SG1525A, SG1527A
100 Hz to 400 kHz
2kΩ to 150kΩ

.001 μF to 0.1 μF 0 to 500Ω

-55° C to +125° C -25° C to +85° C 0° C to +70° C

Note 4. Range over which the device is functional and parameter limits are guaranteed.

ELECTRICAL CHARACTERISTICS (+VIN = 20V, and over operating temperature, unless otherwise specified)

1		SG1525A / 2525A SG1527A / 2527A			-			
PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
REFERENCE SECTION	- <u> </u>			· · ·				
Output Voltage	Tj = 25℃	5.05	5.10	5.15	5.00	5.10	5.20	v
Line Regulation	V _{IN} = 8 to 35V		10	20		10	20	m۷
Load Regulation	iL = 0 to 20 mA		20	50		20	50	mV
Temperature Stability ⁵	Over Operating Range		20	50		20	50	m۷
Total Output Variation ⁵	Line, Load, and Temp	5.00		5.20	4.95		5.25	v
Short Circuit Current	VREF = 0, Tj = 25°C		80	100		80	100	mA
Output Noise Voltage5	10 Hz \leq f \leq 10 kHz, T _j = 25°C		40	200		40	200	μVrms
Long Term Stability ⁵	T _j = 125°C		20	50		20	50	mV/kh
OSCILLATOR SECTION (Note 6)							
Initial Accuracy ^{5,6}	Tj = 25℃		±2	± 6		± 2	± 6	%
Voltage Stability ^{5,6}	VIN = 8 to 35V		± 0.3	± 1		± 1	± 2	%
Temperature Stability ⁵	Over Operating Range		± 3	± 6		± 3	± 6	%
Minimum Frequency	$R_{T} = 150 \text{ k} \Omega, C_{T} = 0.1 \mu \text{F}$			100			100	Hz
Maximum Frequency	$R_T = 2 k\Omega$, $C_T = 1 nF$	400			400			kHz
Current Mirror	I _{RT} = 2 mA	1.7	2.0	2.2	1.7	2.0	2.2	mA
Clock Amplitude ^{5,6}		3.0	3.5		3.0	3.5		v
Clock Width ^{5,6}	T _j = 25°C	0.3	0.5	1.0	0.3	0.5	1.0	µ sec
Sync Threshold		1.2	2.0	2.8	1.2	2.0	2.8	v
Sync Input Current	Sync Voltage = 3.5V		1.0	2.5		1.0	2.5	mA

Regulating Pulse Width Modulators

ELECTRICAL CHARACTERISTICS (Continued)

PARAMETER	CONDITIONS	SG1525A / 2525A SG1527A / 2527A				T		
		MIN	ТҮР	MAX	MIN	SG3527	MAX	
ERROR AMPLIFIER SECT	TION (V _{CM} = 5.1 Volts)		·•		-I	4		I
Input Offset Voltage			0.5	5	Γ	2	10	mv
Input Bias Current			1	10		1	10	μΑ
Input Offset Current			<u> </u>	1	<u>† </u>	1	1	μ Α
DC Open Loop Gain	$R_L \ge 10 Meg \Omega$	60	75	1	60	75	· · · ·	dB
Gain-Bandwidth Product ⁵	$A_V = 0 \text{ dB}, T_j = 25^{\circ}C$	1	2	1	1	2		MHz
Output Low Level			0.2	0.5		0.2	0.5	v
Output High Level		3.8	5.6		3.8	5.6	0.0	
Common Mode Rejection	V _{CM} = 1.5 to 5.2V	60	75	<u> </u>	60	75		dB
Supply Voltage Rejection	VIN = 8 to 35V	50	60	<u> </u>	50	60		dB
P.W.M. COMPARATOR				L				UB
Minimum Duty Cycle			<u></u>	0	Γ		0	%
Maximum Duty Cycle		45	49		45	49		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~
Input Threshold ⁶	Zero Duty Cycle	0.6	0.9		0.6	0.9		^~
Input Threshold ⁶	Max Duty Cycle		3.3	3.6		3.3	3.6	v
Input Bias Current ⁵			.05	1.0		.05	1.0	μ Α
SOFT-START SECTION					L	.05	1.0	<u>µ</u>
Soft Start Current	VSHUTDOWN = 0V	25	50	80	25	50	80	μA
Soft Start Voltage	VSHUTDOWN = 2V		0.4	0.6		0.4	0.6	V
Shutdown Input Current	VSHUTDOWN = 2.5V	_	0.4	1.0		0.4	1.0	mA
OUTPUT DRIVERS (Each (Output) (V _C = 20 Volts)			L		L(
Dutput Low Level	ISINK = 20 mA		0.2	0.4	r	0.2	0.4	v
	ISINK = 100 mA	· •	1.0	2.0		1.0	2.0	v
Output High Level	SOURCE = 20 mA	18	19		18	19		v
	SOURCE = 100 mA	17	18		17	18	ł	v
Undervoltage Lockout	VComp and VSS=high	6	7	8	6	7	8	<u>v</u>
Collector Leakage ⁷	V _C = 35V			200			200	μA
Rise Time ⁵	С∟ = 1 nF, Тј = 25°С		100	600		100	600	nsec
all Time ⁵	$C_L = 1 \text{ nF}, T_j = 25^{\circ}C$		50	300		50	300	nsec
Shutdown Delay ⁵	$V_{SD=3V, C_S} = 0, T_j = 25^{\circ}C$		0.2	0.5		0.2	0.5	μ sec
TOTAL STANDBY CURREN	and the second sec							
Supply Current	V _{IN} = 35V		14	20		14	20	mA

Note 5. These parameters, although guaranteed over the recommended operating conditions, are not 100% tested in production.

Note 6. Tested at fOSC = 40 kHz (RT = 3.6 k Ω , CT = .01 uF, RD = 0 Ω).

Note 7. Applies to SG1525A/2525A/3525A only, due to polarity of output pulses.

Regulating Pulse Width Modulators

APPLICATIONS

SHUTDOWN OPTIONS (See Block Diagram, Page 1)

1. Use an external transistor or open-collector comparator to pull down on the Comp Terminal (pin 9). This will set the PWM latch turning off both outputs. If the shutdown signal is momentary, pulse-by-pulse protection can be accomplished as the PWM latch will be reset with each clock pulse.

 The same results can be accomplished by pulling down on the Soft-Start terminal (pin 8) with the difference that on this pin, shutdown will not affect the amplifier compensation network but must discharge any Soft-Start capacitor.

3. Apply a positive-going signal to the Shutdown terminal (pin 10). This will provide most rapid shutdown of the outputs but will not immediately set the PWM latch if there is a Soft-Start capacitor. This capacitor will discharge but with a current of approximately twice the charging current.

4. The shutdown terminal (pin 10) can be used to set the PWM latch on a pulse-by-pulse basis if there is no external capacitance on pin 8. Slow turn-on may still be accomplished by applying an external capacitor, blocking diode, and charging resistor to the comp terminal (pin 9). (See SG1524 Application Note).

OSCILLATOR CHARGE TIME VS. RT AND CT







SG1525A OSCILLATOR SCHEMATIC



OSCILLATOR DISCHARGE TIME VS. RD AND CT



DISCHARGE TIME - MICROSECONDS





Regulating Pulse Width Modulators

OUTPUT APPLICATIONS (OUTPUT CIRCUITS)



Regulating Pulse Width Modulators



SILICON GENERAL

LINEAR INTEGRATED CIRCUITS

SG1526/SG2526/SG3526

REGULATING PULSE WIDTH MODULATOR

DESCRIPTION

The 1526 is a high performance monolithic pulse width modulator circuit designed for fixed-frequency switching regulators and other power control applications. Included in an 18-pin dual-in-line package are a temperature compensated voltage reference, sawtooth oscillator, error amplifier, pulse width modulator, pulse metering and steering logic, and two low impedance power drivers. Also included are protective features such as soft-start and undervoltage lockout, digital current limiting, double pulse inhibit, a data latch for single pulse metering, adjustable deadtime, and provision for symmetry correction inputs. For ease of interface, all digital control ports are TTL and B-series CMOS compatible. Active LOW logic design allows wired-OR connections for maximum flexibility. This versatile device can be used to implement single-ended or push-pull switching regulators of either polarity, both transformerless and transformer coupled. The SG1526 is characterized for operation over the full military junction temperature range of -55° C to +150° C. The SG2526 is characterized for operation from -25° C to +150°C, and the SG3526 is characterized for operation from 0°C to +125°C.

FEATURES

- 8 to 35 volt operation
- 5 volt reference trimmed to ±1%
- 1 Hz to 400 kHz oscillator range
- Dual 100 mA source/sink outputs
- Digital current limiting
- Double pulse suppression
- Programmable deadtime
- Undervoltage lockout
- Single pulse metering
- Programmable soft-start
- Wide current limit common mode range
- TTL/CMOS compatible logic ports
- Symmetry correction capability
- Guaranteed 6 unit synchronization



ABSOLUTE MAXIMUM RATINGS (Note 1)

Input Voltage (+VIN)	+40V	Power Dissipation at $T_A = +25^{\circ}C$ (Note 2)	1000 mW
Collector Supply Voltage (+ VC)	+40V	Thermal Resistance: junction to ambient	100° C/W
Logic Inputs	-0.3V to +5.5V	Power Dissipation at $T_C = +25^{\circ}C$ (Note 3)	3000 mW
Analog Inputs	-0.3V to +VIN	Thermal Resistance: junction to case	42° C/W
Source/Sink Load Current (each output)	200 mA	Operating Junction Temperature	+150° C
Reference Load Current	50 mA	Storage Temperature Range	-65° C to +150° C
Logic Sink Current	15 mA	Lead Temperature (soldering, 10 seconds)	+300° C

Note 1. Values beyond which damage may occur.

Note 2. Derate at 10 mW/°C for ambient temperaures above +50°C.

Note 3. Derate at 24 mW/°C for case temperatures above +25°C.

RECOMMENDED OPERATING CONDITIONS (Note 4)

Collector Supply Voltage +4.5V to +35V Availa Sink/Source Load Current (each output) 0 to 100 mA guara Reference Load Current 0 to 20 mA SG Oscillator Frequency Range 1 Hz to 400 kHz SG	ator Timing Capacitor 1nF to 20μF ible Deadtime Range at 40kHz 3% to 50% nteed. -55° C to +150° C 2526 -25° C to +150° C 3526 0° C to +125° C
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Note 4. Range over which the device is functional and parameter limits are

ELECTRICAL CHARACTERISTICS

(+VIN = 15V), and over operating junction temperature, unless otherwise specified)

	CONDITIONS	S	SG1526/2526			SG3526			
PARAMETER		MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS	
REFERENCE SECTION (N	ote 5)								
Output Voltage	Tj = +25°C	4.95	5.00	5.05	4.90	5.00	5.10	V	
Line Regulation	+VIN = 8 to 35V		10	20		10	30	mV	
Load Regulation	IL = 0 to 20 mA		10	30		10	50	mV	
Temperature Stability	Over Operating Tj		15	50		15	50	mV	
Total Output Voltage Range	Over Recommended Operating Conditions	4.90	5.00	5.10	4.85	5.00	5.15	v	
Short Circuit Current	VREF = 0V	25	50	100	25	50	100	mA	
UNDERVOLTAGE LOCKO	UT								
RESET Output Voltage	VREF = 3.8V		0.2	0.4		0.2	0.4	v	
RESET Output Voltage	VREF = 4.8V	2.4	4.8		2.4	4.8		v	
OSCILLATOR SECTION (Note 6)								
Initial Accuracy	Tj = +25°C		±3	±8		±3	±8	%	
Voltage Stability	+VIN = 8 to 35V		0.5	1		0.5	1	%	
Temperature Stability	Over Operating Tj		7	10		3	5	%	
Minimum Frequency	$RT = 150 \text{ k}\Omega, CT = 20 \mu\text{F}$			1			1	Hz	
Maximum Frequency	$RT = 2 k\Omega$, $CT = 1.0 nF$	400			400			kHz	
Sawtooth Peak Voltage	+VIN = 35V		3.0	3.5		3.0	3.5	v	
Sawtooth Valley Voltage	+ VIN = 8V	0.5	1.0		0.5	1.0	-	V	

Note 5. $I_L = 0$ mA.

Note 6. FOSC = 40 kHz (RT = 4.12 k $\Omega \pm 1$ %, CT = .01 μ F ± 1 %, RD = 0 Ω

ELECTRICAL CHARACTERISTICS (continued)

PARAMETER	CONDITIONS	5	G1526/25	26		Ţ		
CONDITIONS		MIN	ТҮР	MAX	MIN	ТҮР	MAX	דואט
ERROR AMPLIFIER SECTI	ON (Note 7)							.
Input Offset Voltage	RS ≤ 2 kΩ	1	2	5		2	10	m
Input Bias Current			-350	-1000		-350	-2000	nA
Input Offset Current		1	35	100		35	200	n/
DC Open Loop Gain	$R_L \ge 10 \text{ Meg } \Omega$	64	72	1	60	72	1	dE
High Output Voltage	Vpin1 -Vpin2≥150mV, I _{source} = 100µA	3.6	4.2		3.6	4.2	<u> </u>	v
Low Output Voltage	Vpin2 –Vpin1≥150mV, I _{sink} = 100µA	<u> </u>	0.2	0.4		0.2	0.4	v
Common Mode Rejection	$R_{S} \leq 2k\Omega$	70	94		70	94		dE
Supply Voltage Rejection	+VIN = 12 to 18V	66	80		66	80		dE
P.W.M. COMPARATOR (No	te 6)	L		I				I
Minimum Duty Cycle	Vcompensation = +0.4V			0		Τ	0	%
Maximum Duty Cycle	Vcompensation = +3.6V	45	49		45	49		%
DIGITAL PORTS (SYNC, SI	HUTDOWN, and RESET)		·	1	I.,		L	
HIGH Ouput Voltage	$i_{source} = 40 \mu A$	2.4	4.0		2.4	4.0		v
LOW Output Voltage	Isink = 3.6 mA		0.2	0.4		0.2	0.4	v
HIGH Input Current	VIH = +2.4V		-125	-200			-200	μΑ
LOW Input Current	VIL = +0.4V		-225	-360		-225	-360	μA
CURRENT LIMIT COMPAR	ATOR (Note 8)	I,	L	I		L		
Sense Voltage	$R_{S} \le 50 \Omega$	90	100	110	80	100	120	mv
Input Bias Current			-3	-10		-3	-10	μA
SOFT-START SECTION		L				1	L	,
Error Clamp Voltage	RESET = +0.4V		0.1	0.4		0.1	0.4	v
CS Charging Current	RESET = +2.4V	50	100	150	50	100	150	μA
OUTPUT DRIVERS (Each O	Putput) (Note 9)	L	L	I			L	
HIGH Output Voltage	Isource = 20 mA	12.5	13.5		12.5	13.5		v
High Output voltage	Isource = 100 mA	12	13		12	13		v
LOW Output Voltage	Isink = 20 mA		0.2	0.3	·	0.2	0.3	v
LOW Output Voltage	Isink = 100 mA		1.2	2.0		1.2	2.0	v
Collector Leakage	VC = 40V		50	150		50	150	μA
Rise Time	CL = 1000 pF		0.3	0.6		0.3	0.6	μSe
Fall Time	CL = 1000 pF		0.1	0.2		0.1	0.2	μSe
POWER CONSUMPTION (N						L	L	
Standby Current	SHUTDOWN = +0.4V		18	30		18	30	mA
Standby Current						1		

TYPICAL CHARACTERISTICS



FIGURE 7. OSCILLATOR PERIOD VS. RT AND CT

SG1526/SG2526/SG3526

Regulating Pulse Width Modulator

TYPICAL CHARACTERISTICS





ERROR AMPLIFIER OPEN LOOP GAIN vs FREQUENCY



FIGURE 8. UNDERVOLTAGE LOCKOUT CHARACTERISTIC



CURRENT LIMIT TRANSFER FUNCTION











SHUTDOWN INPUT TO DRIVER OUTPUT DELAY





COLLECTOR SUPPLY SATURATION VOLTAGE VI ISINK

STANDBY CURRENT VS SUPPLY VOLTAGE

ALL CHARACTERISTICS SHOWN ARE NOMINAL VALUES AT +25°C, UNLESS INDICATED OTHERWISE ON THE GRAPHS.

VOLTAGE REFERENCE

The reference regulator of the SG1526 is based on a temperature compensated zener diode. The circuitry is fully active at supply voltages above +8 volts, and provides up to 20 mA of load current to external circuitry at +5.0 volts. In systems where additional current is required, an external PNP transistor can be used to boost the available current. A rugged low frequency audio-type transistor should be used, and lead lengths between the PWM and transistor should be as short as possible to minimize the risk of oscillations. Even so, some types of transistors may require collector-base capacitance for stability. Up to 1 amp of load current can be obtained with excellent regulation if the device selected maintains high current gain.



FIGURE 17. EXTENDING REFERENCE OUTPUT CURRENT

UNDERVOLTAGE LOCKOUT

The undervoltage lockout circuit protects the SG1526 and the power devices it controls from inadequate supply voltage. If +V_{IN} is too low, the circuit disables the output drivers and holds the RESET pin LOW. This prevents spurious output pulses while the control circuitry is stabilizing, and holds the soft-start timing capacitor in a discharged state.

The circuit consists of a +1.2 volt bandgap reference and comparator circuit which is active when the reference voltage has risen to 3 V_{BE} or +1.8 volts at 25°C. When the reference voltage rises to approximately +4.4 volts, the circuit enables the output drivers and releases the RESET pin, allowing a normal soft-start. The comparator has 200 mV of hysteresis to minimize oscillation at the trip point. When +V_{IN} to the PWM is removed and the reference drops to +4.2 volts, the undervoltage circuit pulls RESET LOW again. The soft-start cycle.

The SG1526 can operate from a +5 volt supply by connecting the V_{REF} pin to the $+V_{IN}$ pin and maintaining the supply between +4.8 and +5.2 volts.



FIGURE 18. SIMPLIFIED UNDERVOLTAGE LOCKOUT

SOFT-START CIRCUIT

The soft-start circuit protects the power transistors and rectifier diodes from high current surges during power supply turn-on. When supply voltage is first applied to the SG1526, the undervoltage lockout circuit holds RESET LOW with Q3. Q1 is turned on, which holds the soft-start capacitor voltage at zero. The second collector of Q1 clamps the output of the error amplifier to ground, guaranteeing zero duty cycle at the driver outputs. When the supply voltage reaches normal operating range, RESET will go HIGH. Q1 turns off, allowing the internal 100 μ A current source to charge C_S. Q2 clamps the error amplifier output to 1 V_{BE} above the voltage on C_S. As the soft-start voltage ramps up to +5 volts, the duty cycle of the PWM linearly increases to whatever value the voltage regulation loop requires for an error null. Figure 10 gives the timing relationship between C_S and ramp time to 100% duty cycle.



DIGITAL CONTROL PORTS

The three digital control ports of the SG1526 are bi-directional. Each pin can drive TTL and 5 volt CMOS logic directly, up to a fan-out of 10 low-power Schottky gates. Each pin can also be directly driven by open-collector TTL, open-drain CMOS, and open-collector voltage comparators; fan-in is equivalent to 1 low-power Schottky gate. Each port is normally HIGH; the pin is pulled LOW to activate the particular function. Driving SYNC LOW initiates a discharge cycle in the oscillator. Pulling SHUTDOWN LOW immediately inhibits all PWM output pulses. Holding RESET LOW discharges the soft-start capacitor. The logic threshold is +1.1 volts at +25°C. Noise immunity can be gained at the expense of fan-out with an external 2K pullup resistor to +5 volts.



OSCILLATOR

The oscillator is programmed for frequency and dead time with three components: R_T, C_T, and R_D. Two waveforms are generated: a sawtooth waveform at pin 10 for pulse width modulation, and a logic clock at pin 12. The following procedure is recommended for choosing timing values:

- With R_D = 0 ohms (pin 11 shorted to ground) select values for R_T and C_T from Figure 7 to give the desired oscillator period. Remember that the frequency at each driver output is half the oscillator frequency, and the frequency at the +V_C terminal is the same as the oscillator frequency.
- 2. If more dead time is required, select a larger value of RD using Figure 6 as a guide. At 40 KHz dead time increases by 400 nSec/ohm.
- Increasing the dead time will cause the oscillator frequency to decrease slightly. Go back and decrease the value of R_T slightly to bring the frequency back to the nominal design value.

The SG1526 can be synchronized to an external logic clock by programming the oscillator to free-run at a frequency 10% slower than the sync frequency. A periodic LOW logic pulse approximately 0.5 μ Sec wide at the SYNC pin will then lock the oscillator to the external frequency.

Multiple devices can be synchronized together by programming one master unit for the desired frequency, and then sharing its sawtooth and clock waveforms with the slave units. All C_T terminals are connected to the C_T pin of the master, and all SYNC terminals are likewise connected to the SYNC pin of the master. Slave R_T terminals are left open or connected to V_{REF} . Slave R_D terminals may be either left open or grounded.





ERROR AMPLIFIER

The error amplifier is a transconductance design, with an output impedance of 2 megohms. Since all voltage gain takes place at the output pin, the open-loop gain/ frequency characteristics can be controlled with shunt reactance to ground. When compensated for unity-gain stability with 100 pF, the amplifier has an open-loop pole at 400 Hz.

The input connections to the error amplifier are determined by the polarity of the switching supply output voltage. For positive supplies, the common-mode voltage is ± 5.0 volts and the feedback connections in Figure 22A are used. With negative supplies, the common-mode voltage is ground and the feedback divider is connected between the negative output and the ± 5.0 volt reference voltage, as shown in Figure 22B.



OUTPUT DRIVERS

The totem-pole output drivers of the SG1526 are designed to source and sink 100 mA continuously and 200 mA peak. Loads can be driven either from the output pins 13 and 16, or from the $+V_C$ pin, as required. Curves for the saturation voltage at these outputs as a function of load current are found in Figures 14 and 15.

Since the bottom transistor of the totem-pole is allowed to saturate, there is a momentary conduction path from the + V_C terminal to ground during switching. To limit the resulting current spikes a small resistor in series with pin 14 is always recommended. The resistor value is determined by the driver supply voltage, and should be chosen for 200 mA peak currents, as shown in Figure 25.





FIGURE 23 PUSH-PULL CONFIGURATION

FIGURE 24 SINGLE-ENDED CONFIGURATION



FIGURE 25 DRIVING N-CHANNEL POWER MOSFETS

SG1526/SG2526/SG3526





SILICON GENEPAL

ADVANCED DATA SG1526A/SG2526A/SG3526A Performance Data described herein represent design goals.

Final device specifications are subject to change.

REGULATING PULSE WIDTH MODULATOR

DESCRIPTION

The SG1526A high performance pulse width modulator (PWM) circuit is a direct replacement for the SG1526 in all applications and features improved parametric performance in several key areas. Included are a temperature compensated voltage reference, sawtooth oscillator, error amplifier, pulse width modulator, pulse metering and steering logic, and two low impedance power drivers. Also included are protective features such as soft-start and under-voltage lockout, digital current limiting, double pulse inhibit, a data latch for single pulse metering, adjustable deadtime, and provision for symmetry correction inputs. For ease of interface, all digital control ports are TTL and B-series CMOS compatible. Active LOW logic design allows wired-OR connections for maximum flexibility. This versatile device can be used to implement single-ended or push-pull switching regulators of either polarity, both transformerless and transformer coupled. The SG1526A is characterized for operation over the full military junction temperature range of - 55 °C to + 150 °C. The SG2526A is characterized for operation from - 25 °C to + 150 °C, and the SG 3526A is characterized for operation from 0 °C to + 125 °C.

FEATURES

- Low drain and switching currents
- 7 to 35V operation
- High performance 5V ± 1% reference
- · Low tempco 1 Hz to 400 kHz oscillator
- Dual 100 mA source/sink outputs
- Digital current limiting
- Double pulse suppression
- Programmable deadtime
- Undervoltage lockout
- Single pulse metering
- Programmable soft-start
- Wide current limit common mode range
- TTL/CMOS compatible logic ports
- Symmetry correction capability
- Guaranteed 6 unit synchronization



ABSOLUTE MAXIMUM RATINGS (Note 1)

Input Voltage (+VIN)	+40V	Power Dissipation at $T_A = +25^{\circ}C$ (Note 2)	1000 mW
Collector Supply Voltage (+ VC)	+40V	Thermal Resistance: junction to ambient	100° C/W
Logic Inputs	-0.3V to +5.5V	Power Dissipation at $T_{C} = +25^{\circ}C$ (Note 3)	3000 mW
Analog Inputs	-0.3V to +VIN	Thermal Resistance: junction to case	42° C/W
Source/Sink Load Current (each output)	200 mA	Operating Junction Temperature	+150°C
Reference Load Current	50 mA	Storage Temperature Range	-65°C to +150°C
Logic Sink Current	15 mA	Lead Temperature (soldering, 10 seconds)	+300° C

Note 2. Derate at 10 mW/° C for ambient temperaures above $+50^{\circ}$ C. Note 3. Derate at 24 mW/° C for case temperatures above $+25^{\circ}$ C.

RECOMMENDED OPERATING CONDITIONS (Note 4)

Input Voltage Collector Supply Voltage Sink/Source Load Current (coch output)	+ 7V to + 35V +4.5V to +35V 0 to 100 mA	Oscillator Timing Capacitor Available Deadtime Range at 40kHz Operating Junction Temperature Range	1nF to 20µF 3% to 50%
Sink/Source Load Current (each output) Reference Load Current Oscillator Frequency Range	- 5 to 20 mA 1 Hz to 400 kHz	SG1526A SG2526A	−55°C to +150°C −25°C to +150°C
Oscillator Timing Resistor	$2 k\Omega$ to 150 kΩ	SG3526A	0°C to +125°C

Note 4. Range over which the device is functional and parameter limits are guaranteed.

ELECTRICAL CHARACTERISTICS

(+VIN = 15V, and over operating junction temperature, unless otherwise specified)

PARAMETER		SG	SG1526A/2526A			SG3526A			
	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS	
REFERENCE SECTION (N	lote 5)					•		-	
Output Voltage	$T_j = +25^{\circ}C$	4.95	5.00	5.05	4.90	5.00	5.10	v	
Line Regulation	+ VIN = 7 to 35V		2	10		2	15	mV	
Load Regulation	$I_{L} = -5 \text{ to } + 20 \text{ mA}$		5	10		5	20	mV	
Temperature Stability	Over Operating Tj		15	50		15	50	mV	
Total Output Voltage Range	Over Recommended Operating Conditions	4.90	5.00	5.10	4.85	5.00	5.15	v	
Short Circuit Current	VREF = 0V	25	50	100	25	50	100	mA	
UNDERVOLTAGE LOCKO	TUT								
RESET Output Voltage	VREF = 3.8V		0.2	0.4		0.2	0.4	v	
RESET Output Voltage	VREF = 4.8V	2.4	4.8		2.4	4.8		v	
OSCILLATOR SECTION (Note 6)								
Initial Accuracy	Tj = +25°C		±3	±8		±3	±8	%	
Voltage Stability	+ VIN = 7 to 35V		0.5	1		0.5	1	%	
Temperature Stability	Over Operating Tj		1	3		1	3	%	
Minimum Frequency	$RT = 150 \text{ k}\Omega, CT = 20 \mu\text{F}$			1			1	Hz	
Maximum Frequency	$RT = 2 k\Omega$, $CT = 1.0 nF$	400			400			kHz	
Sawtooth Peak Voltage	+VIN = 35V		3.0	3.5		3.0	3.5	v	
Sawtooth Valley Voltage	+ VIN = 7V	0.5	1.0		0.5	1.0		v	

Note 5. $I_L = 0 \text{ mA}$.

Note 6. FOSC = 40 kHz (RT = 4.12 k\Omega \pm 1%, CT = .01 μF \pm 1%, RD = 0\Omega

SG1526A/SG2526A/SG3526A

Regulating Pulse Width Modulator

ELECTRICAL CHARACTERISTICS (continued)

TYP 2 -350 35 72 4.2 0.2 94 80 49 4.0 0.2 -125	MAX 5 -1000 100 0.4 0 	MIN 60 3.6 70 66 45 2.4	TYP 2 -350 35 72 4.2 0.2 94 80 49	MAX 10 -2000 200 0.4 0	mV nA nA dB V V V dB dB
-350 35 72 4.2 0.2 94 80 49 49 4.0 0.2	-1000 100 0.4	3.6 70 66 45	-350 35 72 4.2 0.2 94 80	2000 200 0.4	nA nA dB V V dB dB
-350 35 72 4.2 0.2 94 80 49 49 4.0 0.2	-1000 100 0.4	3.6 70 66 45	-350 35 72 4.2 0.2 94 80	2000 200 0.4	nA nA dB V V dB dB
35 72 4.2 0.2 94 80 49 49 4.0 0.2	0	3.6 70 66 45	35 72 4.2 0.2 94 80	0.4	nA dB V V dB dB
72 4.2 0.2 94 80 49 49 4.0 0.2	0.4	3.6 70 66 45	72 4.2 0.2 94 80	0.4	dB V V dB dB
4.2 0.2 94 80 49 4.0 0.2	0	3.6 70 66 45	4.2 0.2 94 80		V V dB dB
0.2 94 80 49 4.0 0.2	0	70 66 45	0.2 94 80		V dB dB
94 80 49 4.0 0.2	0	66 45	94 80		dB dB
80 49 4.0 0.2		66 45	80	0	dB
49 4.0 0.2		45		0	
4.0 0.2		`	49	0	%
4.0 0.2		`	49	0	%
4.0 0.2	0.4	`	49		
0.2	0.4	2.4			%
0.2	0.4	2.4			
	0.4		4.0		v
-125			0.2	0.4	v
-	-200		-125	-200	μA
-225	-360		-225	-360	μA
	J		L	L I	
100	110	80	100	120	mV
-3	-10		-3	-10	μA
	1	L		L	
0.1	0.4		0.1	0.4	v
100	150	50	100	150	μA
	1		L		· · · · ·
13.5		12.5	13.5		v
13		12	13		v
0.2	0.3		0.2	0.3	v
1.2	2.0		1.2	2.0	v
50	150	· · · · ·	50	150	μA
0.3	0.6		0.3	0.6	μSec
0.1	0.2		0.1	0.2	μSec
			LJ		
14	20		14	20	mA
	50 0.3 0.1	50 150 0.3 0.6 0.1 0.2	50 150 0.3 0.6 0.1 0.2	50 150 50 0.3 0.6 0.3 0.1 0.2 0.1	50 150 50 150 0.3 0.6 0.3 0.6 0.1 0.2 0.1 0.2

SG1526A/SG2526A/SG3526A

Regulating Pulse Width Modulator





Silicon General

ADVANCED DATA SG1540/SG2540/SG3540

Performance data described herein represent design goals. Final device specifications are subject to change.

LINEAR INTEGRATED CIRCUITS

OFF-LINE START-UP CONTROLLER

DESCRIPTION

The SG1540 is an integrated circuit designed to efficiently provide start-up power from a high-voltage bus to a PWM control circuit in a switching power supply. When used on the primary side, it reduces start-up current to less than 1 mA and allows any standard PWM control circuit to be used as a primary-side controller. When used to power a controller on the secondary side, it effectively eliminates the need for a heavy 50/60 Hz line transformer with its associated low frequency magnetic fields.

The circuit consists of three sections: a micropower bandgap comparator/power switch referenced to +2.5 volts which isolates the start-up capacitor from its load; a high frequency square-wave oscillator with 200 mA totem-pole output for driving an isolation transformer; and a second bandgap comparator with latching crowbar to protect against overvoltage faults while starting or running.

The SG1540 is specified for operation over the full military ambient temperature range of -55 °C to +125 °C. The SG2540 is characterized for the industrial range of -25 °C to +85 °C, and the SG3540 is designed for the commercial range of 0 °C to +70 °C.

FEATURES

- Eliminates bulky 50/60 Hz transformer
- Minimizes high voltage bleeder current
- Usable with primary or secondary control PWM
- Programmable start voltage and hysteresis
- Programmable overvoltage latch


Silicon General

LINEAR INTEGRATED CIRCUITS

SG1731/SG2731/SG3731

DC MOTOR PULSE WIDTH MODULATOR

DESCRIPTION

The SG1731 is a pulse width modulator circuit designed specifically for DC motor control. It provides a bi-directional pulse train output in response to the magnitude and polarity of an analog error signal input. The device is useful as the control element in motor-driven servo systems for precision positioning and speed control, as well as in audio modulators and amplifiers using carrier frequencies to 350 kHz.

The circuit contains a triangle waveform oscillator, a wideband operational amplifier for error voltage generation, a summing/scaling network for level-shifting the triangle waveform, externally programmable PWM comparators and dual ± 100 mA, ± 22 volt totem pole drivers with commutation diodes for full bridge output. A SHUTDOWN terminal forces the drivers into a floating high-impedance state when driven LOW. Supply voltage to the control circuitry and to the output drivers may be from either dual positive and negative supplies, or single-ended.

FEATURES

- ± 3.5 to ± 15 volt control supply
- ± 2.5 to ± 22 volt driver supply
- 50Hz source/sink output drivers
- 5kHz to 350kHz oscillator range
- · High slew rate error amplifier
- Adjustable deadband operation
- Digital SHUTDOWN input

CHIP LAYOUT





SG1731/SG2731/SG3731

ABSOLUTE MAXIMUM RATINGS (Note 1) Power Dissipation at $T_A = +25^{\circ}C$ (Note 2) Supply Voltage (±Vs) ±18V 1000 mW ±Vs Thermal Resistance, junction to ambient 125°C/W Analog Inputs Power Dissipation at $T_{C} = +25^{\circ}C$ (Note 3) 3000 mW Output Driver Voltage $(\pm V_{\Omega})$ Thermal Resistance, junction to case 42°C/W ±35V SG1731/SG2731 Operating Junction Temperature ±25V +150°C SG3731 --65°C to +150°C 200 mA Storage Temperature Range Source/Sink Load Current (Continuous) Lead Temperature (Soldering, 10 seconds) +300°C Source/Sink Load Current (Peak, 1uSec) 400 mA Note 1. Values beyond which damage may occur. Note 2. Derate at 8 mW/°C for ambient temperatures above +25°C. Note 3. Derate at 24 mW/°C for case temperatures above +25°C. **RECOMMENDED OPERATING CONDITIONS** (Note 4) Supply Voltage Range ±3.5V to ±15V Oscillator Frequency Range 5 kHz to 350 kHz Error Amp Common Mode Range ±0.5V to ±12V Oscillator Voltage (Peak-to-Peak) 1V to 10V Output Driver Voltage Range Oscillator Timing Capacitor (CT) 200 pF to 0.5 µF SG1731/SG2731 ±2.5V to ±22V **Operating Junction Temperature Range** ±2.5V to ±22V SG3731 SG1731 -55°C to +125°C Source/Sink Load Current (Continuous) 100 mA SG2731 -25°C to +85°C 0°C to +70°C Source/Sink Load Current (Peak, 1µSec) 200 mA SG3731 Note 4. Range over which the device is functional and parameter limits are guaranteed. ELECTRICAL CHARACTERISTICS ($V_S = V_O = \pm 15V$, and over operating junction temperature, unless otherwise specified) SG1731/SG2731 SG3731 CONDITIONS UNITS PARAMETER MIN TYP MAX MIN TYP MAX OSCILLATOR SECTION

OSCILLATOR SECTION								
CT Charging Current	TJ = +25°C	450	500	550	400	500	600	μA
	Over Operating Temperature	400		600	350		650	μA
2V <u>∆+</u> Input Bias Current	$V_{CM} = -5V$ to $+5V$		-5			-5		μA
ERROR AMPLIFIER			1.2					
Input Offset Voltage			1	6		2	10	mν
Input Bias Current			0.2	1.0		0.4	2.0	μA
Input Offset Current			30	500		60	800	nA
Open Loop Voltage Gain	RL = 2K	80	106		75	106		dB
Output Voltage Swing	$R_L = 2K$	±10	±13		±10	±13		V
Short Circuit Output Current	VERROR = OV	10		35	10		35	mA
Slew Rate	Unity Gain Inverting		15			15		V/µSec
Unity Gain Bandwidth	10K Feedback Resistance		1			1		MHz
PWM COMPARATORS								
±VT Input Bias Current	$V_{CM} = -3V$ to $+3V$		1			1		μA
SHUTDOWN HIGH Voltage	Pin 15 Open			15			15	V
SHUTDOWN LOW Current	Pin 15 = - Vs		0.6	-1.0		-0.6	-1.0	mA
OUTPUT DRIVERS (Each Out	tput) (Note 5)							_
	ISOURCE = 20 mA		+21	1		+21		V
HIGH Output Voltage	ISOURCE = 100 mA	+19	+20		+19	+20		v
LOW Output Voltage	ISINK = 20 mA		-21			-21		v
LOW Output Voltage	ISINK = 100 mA		-20	-19		-20	-19	V
Rise Time	CL = 1000 pF		200			200		nSec
Fall Time	CL = 1000 pF		200			200		nSec
POWER CONSUMPTION (No	te 5)							
Vs Supply Current	FOSC = 50kHz		7			7		mA
Vo Supply Current	SHUTDOWN LOW		1			1		mA

Note 5. $\pm V_{O} = \pm 22$ volts.

APPLICATION NOTES

Supply Voltage

The SG1731 requires a supply voltage for the control circuitry (V_S) and for the power output drivers (V_O). Each supply may be either balanced positive and negative with respect to ground, or single-ended. The only restrictions are:

- 1. The voltage between +VS and -VS must be at least 7.0 volts, but no more than 30 volts.
- 2. The voltage between $+V_O$ and $-V_O$ must be at least 5.0 volts; but no more than 44 volts.
- +VO must be at least 5 volts more positive than -VS. This eliminates the combination of a singleended positive control supply with a single-ended negative driver supply.

Substrate Connection

The substrate connection (Pin 10) must always be connected to either -VS or -VO, whichever is more negative. The substrate must also be well bypassed to ground with a high quality capacitor.

Oscillator

The triangle oscillator consists of two voltage comparators, a set/reset flip-flop, a bi-directional 500 μ A current source, and an external timing capacitor C_T. A positive reference voltage (2V_A+) applied to Pin 2 determines the positive peak value of the triangle, and a negative reference voltage (2V_A-) at Pin 7 sets the negative peak value of the triangle waveform.

Since the value of the internal current source is fixed at a nominal $\pm 500 \,\mu$ A, the oscillator period is a function of the selected peak-to-peak voltage excursion and the value of C_T. The theoretical expression for the oscillator period is:

$$T_{OSC} = \frac{2CT \ dV}{5 \times 10^{-4}}$$
 (Eq. 1)

where C_T is the timing capacitor in Farads and dV is VOSC in volts peak-to-peak.



As a design aid, the solutions to Equation 1 over the recommended range of T_{OSC} and V_{OSC} are given in graphic form in Figure 1. The lower limit on T_{OSC} is 2.85 μ Sec, corresponding to a maximum frequency of 350 kHz.

The maximum value of VOSC, $(2V_{\Delta+}) - (2V_{\Delta-})$, is 10 volts peak-to-peak for linear waveforms.

Error Amplifier

The error amplifier of the SG1731 is a conventional internally-compensated operational amplifier with low output impedance. All of the usual feedback and frequency compensation techniques may be used to control the closed-loop gain characteristics. The control supply voltage \pm VS will determine the input common mode range and output voltage swing; both will extend to within 3 volts of the VS supply.

Pulse Width Modulation

Pulse width modulation occurs by comparing the triangle waveform to a fixed upper $(+V_T)$ and lower $(-V_T)$ threshold voltage. A crossing above the upper threshold causes Output A to switch to the HIGH state, and a crossing below the lower threshold causes Output B to switch to the HIGH state.

Threshold crossings are generated by shifting the triangle waveform up and down with the error voltage (Pin 5). A positive error voltage will result in a pulse width modulated output at Driver A (Pin 13). Similarly, a negative error voltage produces a pulse train at Driver B (Pin 12). Figure 2 illustrates this process for the case where $V_{\Delta+}$ is greater than $+V_T$.

It is important to note that the triangle shifting circuit also attenuates the waveform seen at C_T by a factor of 2. This results in a waveform at the PWM comparators with a positive peak of V_{Δ +} and a negative peak of V_{Δ -, and must be taken into account when selecting the values for +V_T and -V_T.}







Figure 3. In this simple battery-powered position servo, the control supply and driver supply are both singleended positive with respect to ground.





Figure 4. A high torque position servo is obtained by buffering the output drivers to obtain higher output current.



Figure 6. The two-quadrant transfer function of the SG1731 is ideal for pulse width modulated audio power amplifiers.

PROTECTION CIRCUITS

SILICON GENERAL LINEAR INTEGRATED CIRCUITS

SG1542 / SG2542 / SG3542

VOLTAGE SENSING CIRCUIT

DESCRIPTION

This monolithic integrated circuit provides the control functions necessary to protect sensitive electronic circuitry from over-voltage transients or the effects of voltage regulator failure. It is designed for use with an external SCR "crowbar" for immediate shutdown of the power supply, but additionally provides logic level outputs for regulator turn-off and/or operator or system out-of-tolerance indication.

This device contains an accurate, stable 2.6 volt reference which allows the sensing threshold to be set predictably without the need for potentiometers. Uncommitted availability of both polarity inputs to the sensing comparator allows a wide flexibility of use including the ability to sense voltages less than the reference voltage. An external capacitor can be used to program an accurate time delay between fault occurrence and crowbar triggering, but this delay may be bypassed by inputing at the Sense 2 terminal or by using the remote activation capability.

For additional circuit functions, see SG1543 data sheet.

FEATURES

- Operation from 4.5 to 40 volts
- Useful for either over- or under-voltage sensing
- Sensing threshold accurate to ±2%
- Built-in input hysteresis
- Zero to 35 volt sensing capability
- Programmable time delay
- SCR "Crowbar" drive of 200mA
- Remote activation capability
- 2.6V 1% reference available



SG1542 / SG2542 / SG3542

ABSOLUTE MAXIMUM RATINGS

ADSOLUTE MAAIMUM NATINGS			
Input Supply Voltage, V+ Collector Supply Voltage, V _C Sense Voltage (1)	40V 40V V+	Power Dissipation (Package Limitation) Derate above 25° C	1000mW 8.0 mW/° C
Sense Voltage (2)	6.5V	Operating Temperature Range SG1542	-55°C to +125°C
Remote Activation Input Voltage SCR Trigger Current	7.0V 300mA*	SG2542	-25° C to +85° C
Limit Indicators Output Voltage Limit Indicators Output Sink Current	40V 50mA	SG3542 Storage Temperature Range	0° C to +70° C -65° C to +150° C
*At higher input voltages, a dissipation	limiting resistor.		

*At higher input voltages, a dissipation limiting resistor, RG, is required. See graph.

ELECTRICAL CHARACTERISTICS

(Unless otherwise stated, these specifications apply for V+ = 5 to 35V and $T_J = -55^{\circ}$ C to +125° C for the SG1542, -25° C to +85° C for the SG2542, and 0° C to +70° C for the SG3542.)

		SG	SG1542/2542		_	SG354	2	
PARAMETER	CONDITIONS	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
Input Voltage Range	T _J = 25 ^o C to T _{max}	4.5	-	40	4.5		40	v
Input Voltage Range	T _{min} to T _{max}	4.7		40	4.7		40	V
Supply Current	V+ = 40V, Outputs open	-	5	7	-	5	10	mA
Reference Voltage	T _J = 25 ^o C	2.58	2.60	2.62	2.55	2.60	2.65	v
Reference Voltage	Over Temp. Range	2.55	-	2.65	2.50	-	2.70	V
Line Regulation	V+ = 5 to 40V	_	1	5		1	5	mV
Load Regulation	REF = 0 to 10mA	-	1	10	-	1	10	mV
Short Circuit Current	V _{REF} = 0	12	25	40	12	25	40	mA
Temperature Stability		-	.005	-	-	.005	_	%/°C
Sense 1 Offset Voltage	Sense 1 (+) rising	-10	0	+10	-20	0	+20	mV
Sense 1 Offset Voltage	Sense 1 (+) falling	-35	-25	-15	-50	-25	0	mV
Sense 1 Common Mode		0	-	(V+) -3	0	-	(V+) ~3	v
Sense 1 Bias Current		- 1	-0.3	-1.0	-	-0.3	-1.0	μA
Sense 2 Threshold		2.50	2.60	2.70	2.50	2.60	2.70	v
Sense 2 Bias Current			1.0	10	-	1.0	10	μA
Delay Current		200	250	300	200	250	300	μA
Remote Activation Current		-	120	180	-	120	180	μA
Remote Act. Threshold	· · · · ·	0.8	1.0	2.0	0.8	1.0	2.0	V
Peak Output Current	$V_{C} = 5V, R_{G} = 0, V_{O} = 0$	100	200	400	100	200	400	mA
Peak Output Voltage	I _O = 100mA	V _{IN} -2	V _{IN} -1.6	-	V _{IN} -2	V _{IN} -1.6	-	v
Output Off Voltage	$V + = V_C = 40V$	-	0	0.1		0	0.1	v
Limit Indicators V _{SAT}	ا _ل = -10mA	-	0.2	0.5		0.2	0.5	v
Limit Indicators Leakage	V _{IND} = 40V	-	.01	1.0	+	.01	1.0	μA
Propagation Delay	T _O Ind., T _J = 25 ^o C	-	500	· -	1	500	_	nS
Propagation Delay	T _O Trigger, T _J = 25 ^o C	_	500		-	500	. –	nS
Output Current Rise Time	$R_{L} = 50\Omega, T_{J} = 25^{O}C$	-	400	_	- 1	400	-	mΑ/μS



APPLICATIONS

SG1542 / SG2542 / SG3542



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See Applications Notes for additional information.

GILICON GENEPAL LINEAR INTEGRATED CIRCUITS

SG1543 / 2543 / 3543

Power Supply Output Supervisory Circuit

DESCRIPTION

This monolithic integrated circuit contains all the functions necessary to monitor and control the output of a sophisticated power supply system. Over-voltage (O.V.) sensing with provision to trigger an external SCR "crowbar" shutdown; an under-voltage (U.V.) circuit which can be used to monitor either the output or to sample the input line voltage; and a third op amp/comparator usable for current sensing (C.L.) are all included in this IC, together with an independent, accurate reference generator.

Both over and under-voltage sensing circuits can be externally programmed for minimum time duration of fault before triggering. All functions contain open collector outputs which can be used independently or wire-or'ed together, and although the SCR trigger is directly connected only to the over-voltage sensing circuit, it may be optionally activated by any of the other outputs, or from an external signal. The O.V. circuit also includes an optional latch and external reset capability.

The current sense circuit may be used with external compensation as a linear amplifier or as a high-gain comparator. Although nominally set for zero input offset, a fixed threshold may be added with an external resistor. Instead of current limiting, this circuit may also be used as an additional voltage monitor.

The reference generator circuit is internally trimmed to eliminate the need for external potentiometers and the entire circuit may be powered directly from either the output being monitored or from a separate bias voltage.

ABSOLUTE MAXIMUM RATINGS

Input Supply Voltage, V _{IN}	40V
Sense Inputs	VIN
SCR Trigger Current	400 mA*
Indicator Output Voltage	40V
Indicator Output Sink Current	50mA
Power Dissipation (Package Limitat Derate Above 25° C	ion) 1000mW 8.0mW/°C
Operating Temperature Range SG1543 SG2543 SG3543 SG3543	−55° C to +125° C −25° C to +85° C 0° C to +70° C
Storage Temperature Range	-65°C to+150°C
* At higher input voltages, a dissipation RG, is required.	on limiting resistor,

FEATURES

- Over-voltage, under-voltage, and current sensing circuits all included
- Reference voltage trimmed to 1% accuracy
- SCR "Crowbar" drive of 300 mA
- Programmable time delays
- Open-collector outputs and remote activation capability
- Total standby current less than 10mA

CHIP LAYOUT

CONNECTION DIAGRAM



BLOCK DIAGRAM



SG1543 / 2543 / 3543

ELECTRICAL CHARACTERISTICS (Unless otherwise stated, these specifications apply for $T_J = -55^{\circ}$ C to $+125^{\circ}$ C for the SG1543, -25° C to $+85^{\circ}$ C for the SG2543 and 0° C to $+70^{\circ}$ C for the SG3543; and for $V_{IN} = 10$ Volts.

			SG1543/2543			\$G3543			
PARAMETER	CONDIT	IONS	MIN	TYP	MAX	MIN	ТҮР	MAX	UNITS
Input Voltage Range	T _J = 25 ^o C	to T _{max}	4.5	-	40	4.5	-	40	v
Input Voltage Range	T _{min} to	T _{max}	4.7	-	40	4.7	-	40	v
Supply Current	T _J = 25 ^o C,		-	7	10	-	7	10	mA
REFERENCE SECTION (Pir	ns 15, 16)							<u></u>	
Output Voltage	Tj = 2	5 ⁰ C	2.48	2.50	2.52	2.45	2.50	2.55	v
Output Voltage	Over Tem	o. Range	2.45		2.55	2.40	-	2.60	V
Line Regulation	V _{IN} = 5	to 30V	-	1	5	-	1	5	mV
Load Regulation	IREF = 0 t	o 10 mA	-	1	10	-	1	10	mV
Short Circuit Current	VREF	= 0	12	25	40	12	25	40	mA
Temperature Stability	<u> </u>		-	50		_	50	-	ppm/ ⁰
SCR TRIGGER SECTION (F	ins 1, 2, 3)								
Peak Output Current	V _{IN} = 5V, R _G		100	200	400	100	200	400	mA
Peak Output Voltage	V _{IN} = 15V, I		12	13	-	12	13	-	V
Output Off Voltage	V _{IN} =		-	0	0.1	-	0	0.1	V
Remote Activate Current	Pin 2 =	Gnd	-	.4	.8	_	.4	.8	mA
Remote Activate Voltage	Pin 2 c	pen	-	2	6	-	2	6	V
Reset Current	Pin 3 = Gnd, I		-	.4	.8	-	.4	.8	mA
Reset Voltage	Pin 3 open, P	in 2 = Gnd		2	6		2	6	.v
Output Current Rise Time	R _L = 50Ω		-	400	-	-	400		mA/μ
Prop. Delay from Pin 2		5 ^o C V(Pin 2) = 0.4V		300	-	_	300	-	nS
Prop. Delay from Pin 6	C _D = 0 V(-	500	-		500	-	nS
COMPARATOR SECTIONS	(Pins 6, 7, 5, 8, 4,	9)							
Input Threshold (Input	T J = 2	5 ⁰ C	2.45	2.50	2.55	2.40	2.50	2.60	V
voltage rising on Pin 6 and falling on Pin 7)	Over Temp	, Range	2.40	-	2.60	2.35		2.65	V
Input Hysteresis	1		-	25	-		25	1	mV
Input Bias Current	Sense inp	ut = 0V	-	0.3	1.0		0.3	1.0	μA
Delay Saturation	1		-	0.2	0.5		0.2	0.5	v
Delay High Level			-	6	8		6	8	v
Delay Charging Current	V _D =	0V	200	250	300	200	250	300	μA
Indicate Saturation	I ₁ = -1			0.2	0.5	_	0.2	0.5	-v
Indicate Leakage	VIND =		-	.01	1.0		.01	1.0	μΑ
	V _(Pin 6) = 2.7V	C _D = 0	-	400	-	-	400	-	nS
Propagation Delay	V (Pin 7) = 2.3V T _J = 25 ⁰ C	$C_D = 1\mu f$	-	10	-	-	10	-	mS
CURRENT LIMIT SECTION	l (Pins 10, 11, 12,	13)							
Input Voltage Range			0	-	(V _{IN} -3V)	0	-	(V _{IN} -3V)	v
Input Bias Current	Pin 12 open,	V _{CM} = 0V		0.3	1.0	-	0.3	1.0	μΑ
Input Offset Voltage	Pin 12 open, V _{CM} = 0V			0	10	-	0	15	mV
Input Offset Voltage	10kΩ from Pi	n 12 to Gnd	80	100	120	70	100	130	mV
CMRR	0≤V _{CM} ≤12		60	70	-	60	70	-	dB
AVOL	Pin 12 open,		72	80	-	72	80	-	dB
Output Saturation	ار = -1		-	0.2	0.5		0.2	0.5	V
Output Leakage	VIND *			.01	1.0		.01	1.0	μΑ
Small Signal Bandwidth	$A_V = 0 dB$,	·		5	-	-	5	-	MHz
Propagation Delay	V _{overdrive} = 100	mV, Tj = 25 ⁰ C		200			200	<u> </u>	nS

SG1543 / 2543 / 3543





Silicon General

LINEAR INTEGRATED CIRCUITS

SG1544 / SG2544 / SG3544

LOW-VOLTAGE SUPERVISORY CIRCUIT

DESCRIPTION

This device was designed to provide all the operational features of the SG1543/ 2543/3543 devices but with the added advantage of uncommitted inputs to the voltage sensing comparators. This allows monitoring of voltage levels less than 2.5 volts by dividing down the internal reference supply.

In all other respects, the SG1544 series is identical to the SG1543 series. These monolithic devices contain all the functions necessary to monitor and control the output of a sophisticated power supply system. Overvoltage sensing with provision to trigger an external SCR "crowbar" shutdown; an undervoltage circuit which can be used to monitor either the output or sample the input line voltage; and a third op amp/comparator usable for current sensing are all included in this IC, together with an independent, accurate reference generator.

The voltage-sensing input comparators are identical and can be used with threshold levels from zero volts to (VIN -3V). Each has approximately 25 mv of hystersis which is offset so the switching differential threshold is zero on the non-inverting input for rising levels and zero on the inverting input for falling signals. All other operating characteristics are as described in the SG1543 data sheet and application note.

FEATURES

- Uncommitted comparator inputs for wide input flexibility
- Common-Mode range from zero to near supply voltage
- Reference voltage trimmed to 1% accuracy
- · All other features of SG1543 series









ELECTRICAL CHARACTERISTICS

Unless otherwise stated, these specifications apply for $T_J = -55^{\circ}C$ to $+125^{\circ}C$ for the SG1544, $-25^{\circ}C$ to $+85^{\circ}C$ for the SG2544 and 0°C to $+70^{\circ}C$ for the SG3544; and for $V_{IN} = 5$ to 35 Volts. Electrical tests are performed with $V_{IN} = 10$ Volts and $2k_{\Omega}$ pull-up resistors on all indicator outputs. All electrical ratings and specifications are tested with the inverting over-voltage input and the non-inverting under-voltage input externally connected to the 2.5 volt reference.

				SG1544/2544			SG3544			1
PARAMETER	CON	DITION	s	MIN	TYP	MAX	MIN	түр	MAX	UNITS
Input Voltage Range	Tj = 2	5°C to T	max	4.5	-	40	4.5	-	40	ν
Input Voltage Range	Tmir	to Trina	uk .	4.7	17	40	4.7	-	40	v
Supply Current	VIN = 401	/, Outpu	ts operi	-	7	10	-	7	10	mA
REFERENCE SECTION (Pins	17, 18)	÷.								
Output Voltage	T.J	= 25°C		2.48	2.50	2.52	2.45	2.50	2.55	v
Output Voltage	Over T	emp. Ra	inge	2.45	-	2.55	2.40	-	2.60	v
Line Regulation	Vin =	= 5 to 3	DV .	-	1	5	-	1	5	mV
Load Regulation	REF =	0 to 10	mA	-	1	10	-	1	10	mV
Short Circuit Current	VR	EF = 0		12	25	40	12	25	40	mA
Temperature Stability				-	50	-	-	50	-	ppm/°0
SCR TRIGGER SECTION (Pin	s 1, 2, 3)				L					
Peak Output Current	VIN = 5V, F	RG = 0,	V _O = 0	100	200	400	100	200	400	mA
Peak Output Voltage	VIN = 15	Ý, IO =	100mA	12	13	-	12	13	-	v
Output Off Voltage	VIN	v = 40V		-	0	0.1	-	0	0.1	v
Remote Activate Current	Pin	2 = Gn	đ	-	.4	.8	-	.4	.8	mA
Remote Activate Voltage	Pin	2 open		-	2	6	-	2	6	v
Reset Current	Pin 3 = Gr	nd, Pin 2	= Gnd	-	.4	.8	-	.4	.8	mA
Reset Voltage	Pin 3 oper	n, Pin 2	= Gnd		2	6	-	2	6	v
Output Current Rise Time	$R_L = 50 \Omega$			~	400	-	-	400	-	mA/μ
Prop. Delay from Pin 2	T」= 25℃	V(Pin	2) = 0.4V	-	300	-	-	300	-	nS
Prop. Delay from Pin 6	-1 1	<u> </u>	6) = 2.7V	-	500	-	-	500	-	nS
COMPARATOR SECTIONS (I	Pina 6, 7, 5, 4; 8,	9, 10,	11)		·					
Input Threshold (Input	ΤJ	T _{.1} = 25°C		2.45	2.50	2.55	2.40	2.50	2.60	v
voltage rising on Pin 6					<u>+</u>			├		
and falling on Pin 9)	Over T	emp. Ra	ange	2.40		2.60	2.35		2.65	V
Input Hysteresis	ļ				25	-	-	25	-	mV
Input Bias Current	Sense	input =	0V	-	0.3	1.0	-	0.3	1.0	μA
Delay Saturation					0.2	0.5		0.2	0.5	V
Delay High Level	ļ			-	6	8	-	6	8	V
Delay Charging Current		D = 0V		200	250	300	200	250	300	μA
Indicate Saturation		= -10m		-	0.2	0.5	-	0.2	0.5	V
Indicate Leakage		ID ≂ 40		-	.01	1.0	-	.01	1.0	μA
Propagation Delay	V(Pin 6) =		C _D = 0	-	400	-	-	400	- 1	nS
Topagalon Delay	V(Pin 9) = Tj = 25°C		C _D ≠ 1µf	-	10	-	-	10	-	mS
CURRENT LIMIT SECTION (P	ins 12, 13, 14, 15	5)								
Input Voltage Range				0	-	(V _{IN} -3V)	0	-	(V _{IN} -3V)	v
Input Bias Current	Pin 14 op	ben, VC	V0 = N	-	0.3	1.0	-	0.3	1.0	μA
Input Offset Voltage	Pin 14 op	oen, VC	V0 = N	-	0	10	-	0	10	m۷
Input Offset Voltage	10Ω from	Pin 14	to Gnd	80	100	120	80	100	120	mV
CMRR	0 < VCM <	12V, VII	v = 15V	60	70		60	70	-	dB
AVOL	Pin 14 op			72	80	-	72	80	-	dB
Output Saturation	· · · · · · · · · · · · · · · · · · ·	= - 10m		-	0.2	0.5	-	0.2	0.5	v
Output Leakage		ID = 40		-	.01	1.0	-	.01	1.0	μA
Small Signal Bandwidth	A _V = 00			-	5	-	-	5	-	MHz
Propagation Delay	Voverdrivé =			_	200	-	_	200	-	nS

See Applications Notes for additional information.

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

ADVANCED DATA SG1548/SG2548/SG3548

Performance data described herein represent design goals. Final device specifications are subject to change.

QUAD POWER FAULT MONITOR

DESCRIPTION

The SG1548 is an integrated circuit capable of monitoring up to four positive DC supply voltages simultaneously for overvoltage fault conditions. An on-chip inverting op amp also allows monitoring one negative DC voltage. The fault tolerance window is accurately programmable from $\pm 2\%$ to \pm 40% using a simple divider network on the \pm 2.5 volt reference. A single external capacitor sets the fault indication delay, eliminating false outputs due to switching noise, logic transition current spikes, and short-term AC line interruptions. An additional comparator referenced to ± 2.5 volts allows the AC line to be monitored for undervoltage conditions or for generation of a line clock. The comparator can also be used for programmable undervoltage lockout in a switching power supply. Uncomitted collector and emitter outputs permit both inverting and non-inverting operation. External availability of the precision ±2.5 volt reference and open-collector logic outputs permit expansion to monitor additional voltages using available open-collector guad comparators.

FEATURES

- · Monitors four DC voltages and the AC line
- Precision ± 2.5 volt $\pm 1\%$ low-drift reference
- Fault tolerance adjustable from $\pm 2\%$ to $\pm 40\%$
- Separate overvoltage, undervoltage and AC line outputs
- Fault delay programmable with a single capacitor
- · Comparator hysteresis to prevent oscillations
- On-chip inverting op amp for negative voltage
- Open-collector output logic for expandability
- Operation from +4.5 to +40 volt supplies
- · Standard 16 pin dual-in-line package



Silicon General

LINEAR INTEGRATED CIRCUITS

SG1549 / SG2549 / SG3549

CURRENT SENSE LATCH

DESCRIPTION

This monolithic integrated circuit is an analog latch device with digital reset. It was specifically designed to provide pulse-by-pulse current limiting for switch-mode power supply systems, but many other applications are also feasible. Its function is to provide a latching switch action upon sensing an input threshold voltage, with reset accomplished by an external clock signal. This device can be interfaced directly with many kinds of pulse width modulating control IC's, including the SG1524, SG1525A and SG1527A.

The input threshold for the latch circuit is 100mV, which can be referenced either to ground or to a wide-ranging positive voltage. There are high- and low-going output signals available, and both the supply voltage and clock signal can be taken directly from an associated PWM control chip.

With delays in the range of 200 nanoseconds, this latch circuit is ideal for fast-reaction sensing to provide overall current limiting, short circuit protection, or transformer saturation control.

FEATURES

- Current sensing with 100mV threshold
- Common-mode input at ground or to 40V
- Complementary outputs
- Automatic reset from PWM clock
- 180nS delay
- Interface direct to SG1524, SG1525A, SG1527A



SG1549 / SG2549 / SG3549

ABSOLUTE MAXIMUM RATINGS

Input Supply Voltage, V _S	25V	Operating Temperature Range	
HI CM Input Voltage	40V 40V	SG1549 Y	−55°C to +125°C −25°C to +85°C
LO Output "on" current	25mA	SG2549 Y or M SG3549 Y or M	0°C to +70°C
Power Dissipation Derate above 25°C	600mW 5.0 mW/°C	Storage Temperature Range	−65°C to +150°C

ELECTRICAL CHARACTERISTICS

(Unless otherwise stated, these specifications apply over the operating temperature range, with V_S = +5.0 volts, and with the circuit unlatched, or reset.)

		SG1549/2549		SG3549				
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	ТҮР	MAX	UNITS
CM Input	(Note 1)							
Threshold Voltage	Pin 1 & 2 shorted	90	100	110	80	100	120	mV
Input Impedance	V(Pin 3) = 50mV	400	500	600	400	500	600	Ω
HI CM Input	(Note 1)							
Threshold Voltage	VCM = 2V, Pin 3 open	90	100	110	80	100	120	mV
Threshold Voltage	VCM = 40V, Pin 3 open	90	100	110	80	100	120	mV
Input Current	V(Pin 1) = V(Pin 2) = 40V		200	300	-	200	300	μA
Clock Reset								
Min. Trigger Voltage			2.0	2.5	-	2.0	2.5	V
Input Current	V(Pin 7) = 4V		20	40	-	20	40	μΑ
HI Output								
Off Voltage			0	0.1		0	0.1	V
On Voltage	IL = 1mA	2.8	3.2	-	2.8	3.2		V
LO Output								
Off Leakage	V(Pin 5) = 40V	-	.01	1.0		.01	1.0	μA
On Voltage	IL = -10mA	—	.3	0.5	—	.3	0.5	V
Current Current	V(Pin 8) = 5V		2	3	-	2	5	mA
Supply Current	V(Pin 8) = 20V	-	10	15		10	15	mA

Note 1: Input threshold voltages and supply current are directly proportional to supply voltage, Vg.

TYPICAL SWITCHING CHARACTERISTICS VS = 5V, TA = 25° C

PARAMETER	SYMBOL	CONDITIONS	TYPICAL	UNITS
Reset Minimum Pulse Width	tw1	Amplitude = 3.0V	150	nSec
Delay from Reset to LO Output	tD (off)	$R_L = 470\Omega$ to V_S	300	nSec
LO Input Minimum Pulse Width	^t w2	Amplitude = 200mV	50	nSec
Delay from LO Input to LO Output	t _{D.} (on) LO CM	Amplitude = $200mV$ RL = 470Ω to VS	180	nSec
Delay from HI Input to LO Output	t _D (on) HI CM	Amplitude = 200mV V _{CM} = 5V	300	nSec
Delay from HI Output to LO Output		LO CM Input = 200mV	30	nSec

SG1549 / SG2549 / SG3549



SG1549 / SG2549 / SG3549

APPLICATIONS

HIGH LINE SENSING — The SG1549 will provide current sensing in the positive supply line in the typical SG1524 single-ended switching regulator application shown in Figure 1. The HI CM sense circuitry can be used with input voltages between 2 and 40 volts.

A value for R_{SC} is determined by dividing the 100mV input threshold by the peak current desired. High-frequency noise, or switching transients, can usually be eliminated by a small capacitor between pins 3 and 4.

Current control may be accomplished by either the HI OUTPUT pin connected to the SG1524's Shutdown pin, or the LO OUTPUT pin connected directly to the Compensation Terminal. In either case, activation of the current sense latch will tend to discharge the compensation capacitor, C_C, which may cause slow recovery from pulse limiting. If this feature is desired, the LO OUTPUT pin may be used to discharge a soft-start network instead of coupling directly to the SG1524. If it is not desired, the use of a small value of C_C, and perhaps a diode across R_C, will enhance recovery.

Another method of introducing the current shutdown signal is shown in Figure 2 where the SG1524 is used to activate a constant drive current to the high-current switch, in this case an SM600. The 2N2222 forms a constant current generator when driven from the SG1524's 5.0 volt reference through a 1K resistor. This transistor is then switched off by the LO OUTPUT transistor in the SG1549, achieving the fastest response to the output of the regulator.

LOW LINE SENSING — In many types of feed-forward or push-pull converters, current protection may be provided by sensing in an emitter resistor referenced to ground on the primary side of an output transformer. The fastreacting SG1549 can easily sense secondary overload as reflected back to the primary and, additionally, provide protection from unbalanced transformer saturation.

When using the LO CM inputs, the HI CM inputs should be shorted together. While the LO CM inputs may be connected directly across a sense resistor, R_{SC}, a small low-pass filter as shown in Figure 3 is often required to eliminate high frequency transients. It must be remembered that the 500 ohm input impedance at the LO CM terminals will cause the use of R1 to increase the effective threshold; however, this also offers the possibility of an easily adjustable threshold by incorporating a potentiometer at the input.

Coupling the output signal from the SG1549 to the control chip may be done in several ways including the use of either the Compensation or Shutdown pins on the SG1524 as described earlier.

Another convenient way to tie the output of the SG1549 into the PWM control in higher power applications is by using the SG1627 Dual Interface Driver and connecting the LO OUTPUT terminal of the SG1549 directly to the two Non-Inverting inputs of the SG1627 as shown in Figure 4.

And finally, keep in mind that the LO OUTPUT terminal of the SG1549 will easily drive most high-speed optical couplers should some type of isolation between current sense and shutdown control be required.







Figure 2 — Current control for a buck regulator with constant drive current.



Figure 3 — A push-pull converter with low-line emitter current sensing.



Figure 4 - Power Boost and current control with the SG1627.

Silicon General

ADVANCED DATA SG3509

LINEAR INTEGRATED CIRCUITS

Performance data described herein represent design goals. Final device specifications are subject to change.

AIR FAULT DETECTOR

DESCRIPTION

This monolithic integrated circuit provides the control functions necessary to protect equipment with forced air cooled system from loss of air flow. It is designed to provide a positive indication of the presence of air flow independent of air temperature. Outputs FAULT and FAULT are used to activate an alarm or shut-down equipment when air flow drops below a preset level for a programmed time period.

This device contains a regulated, stable 2.2 volt reference with - 2mV/°C temperature coefficient which provides a bias for the heater current source and the matching programmable current sources. Availability of both polarity inputs to the comparator #1 allows a wide flexibility of use. An external capacitor can be used to program an accurate time delay between occurence and fault indication.

FEATURES

- Operation from 4.5 to 40 volts
- 2.2 volt reference with respect to VIN
- Matching programmable current sources
- Programmable heater current source up to 100mA
- Zero to 35 volts sensing capability
- Programmable time delay
- Remote activation capability
- Latching/Non-latching capability
- · Fault and Fault output available
- Open-collector outputs with 50mA sink capability





ABSOLUTE MAXIMUM RATINGS (Note 1)	
Supply Voltage $(+V_{IN})$	+ 40V
Sink Load Current (continuous)	50mA
Power Dissipation at $T_{A} = +25^{\circ}C$ (Note 2)	600mW
Operating Junction Temperature	– 125°C
Storage Temperature Range	~ 55°C to 150°C
Lead Temperature (Soldering, 10 seconds)	+300°C
Note 1. Values beyond which damage may Note 2. Derate at 6.67mW/°C for ambient temperatures above + 35°C.	occur.

RECOMMENDED OPERATING CONDITIO	ONS (Note 3)
Input Voltage (+ V _{IN})	+ 4.5 to + 40V
Common-Mode Voltage Range Comp #1(V _{CM})	0 to V _{IN} - 1.5V
Collector Voltage FAULT/FAULT Outputs	0 to + 40V
Sink Load Current FAULT/FAULT Outputs	0 to 50mA
Programmable Current	
Sources Resistors (R _{EXT})	150KΩto 7.5KΩ
Reference Sink Current	
with $V_{IN} = 4.5V \text{ to } 6V$	0 to 1mA
with $V_{\rm IN} > 6V$	0 to 10mA
Buffer Out Sink Current	0 to 100mA
Note 3. Range over which the device is functi parameter limits are guaranteed.	onal and

ELECTRICAL CHARACTERISTICS

Unless Otherwise stated, these specifications apply for $T_A = 25^{\circ}C$

<u></u>		REQ			
NAME	SYMBOL	TEST CONDITION (3)	MIN	MAX	UNIT
Reference Section Output Voltage					
(Note 6)	V _{REF} 1	V _{IN} = 4.5V	2.09	2.31	<u>v</u>
Line Regulation	LINE REG	$V_{iN} = 4.5V \text{ to } 40V, I_{L} = 0$		10	mV
Load Regulation	LOAD REG	$I_{REF} = 0$ to 1mA, $V_{IN} = 4.5V$		10	mV
Short-Circuit Current	I _{OS}	V _{IN} = 12V	5	25	mA
Comparator 1, Input Offset Voltage	V _{OS}	$T_A = 25^\circ \text{ to } 70^\circ \text{C}$		± 10	mV
Input Bias Current	l I _B			-1	μA
Output Offset Current	I _{IO}	$I_{ N}(+) - I_{ N}(-)$		±100	nA
Input Common-Mode Voltage Range	V _{CM}		0	V _{IN} - 2	V
Voltage Gain	V _G	$R_L \ge 15K Ohms$	4		V/mV
Output Source Current	(SOURCE) IO	$V_{\text{PIN}}10 = 0$	34	52	μA
Comparator 2, + Input Bias Current	I _B +	$V_{\text{PIN}}12 = V_{\text{REF}}$		2	μA
- Input Reference Voltage	V _{REF} 2	$I_L = 0$	2.0	3.80	<u>v</u>
Input Resistance to Ground	R _{IN}		12.6	23.4	Kohms
Remote Activate Current	I _{BA}	$+V_{IN} = +12V$, Pin 14 = 0V		0.9	mA
Remote Activate Voltage	V _{BA}	+ V _{IN} = 12V, Pin 14 open	2	7	V
Reset Activate Current	BeA	$+V_{IN} = +12V, p 14 = 0V, V_{pin} 13 = 0V$		0.9	mA
Reset Activate Voltage	V _{BeA}	Pin 13 open, Pin 14 Gnd		1.5	V
Fault Low Output	VSAT	I _{SINK} = 50mA		2.0	V
Fault Low Output	VSAT	I _{SINK} = 16mA		0.5	V
Programmable Current Sources Output Current (Notes 4 & 5)	lout	$R_{EXT} = 20K = .1\%$	10	200	μA
Current Match	Иматсн	$R_{EXT} = 20K \pm .1\%$		±1	%
Buffer Output, Pin 2 Voltage	V _{PIN 2}	Input Current = 100mA 1.9		2.3	V

Notes: (3) $T_A = 25^{\circ}$ C unless otherwise specified. (4) Pin 6, 20K to V_{IN} measure Ic pin to 7 Gnd. (5) Pin 8 same 20K to V_{IN} measure Ic pin 9 to Gnd. (6) V_{REF} 1 is designed for a $-2mV^{\circ}$ C $\pm 1mV$ output voltage temperature coefficient.

SILICON GANAPAL

SG3523 | 3523A | 3423 | 3423A

Over-Voltage Sensing Circuit

DESCRIPTION

This monolithic integrated circuit provides the control functions necessary to protect sensitive electronic circuitry from over-voltage transients or the effects of voltage regulator failure. It is designed for use with an external SCR "crowbar" for immediate shutdown of the power supply, but additionally provides logic level outputs for regulator turn-off and/or operator or system out-of-tolerance indication.

This device contains an accurate, stable 2.6 volt reference which allows the sensing threshold to be set predictably without the need for potentiometers. An external capacitor can be used to program an accurate time delay between fault occurence and crowbar triggering, but this delay may be bypassed by inputing at the Sense 2 terminal or by using the remote activation capability.

For additional circuit functions, see SG1542 and SG1543 data sheets.

FEATURES

- Operation from 4.5 to 40 volts
- Highly accurate sensing threshold
- Built-in input hysteresis
- Programmable time delay
- SCR "Crowbar" drive of 200mA
- Remote activation capability



CHIP LAYOUT





SG3523 | 3523A | 3423 | 3423A

ABSOLUTE MAXIMUM RATINGS

Input Supply Voltage, V _{IN}	40V
Sense Voltage (1)	VIN
Sense Voltage (2)	6.5V
Remote Activation Input Voltage	7.0V
SCR Trigger Current	500mA
Indicator Output Voltage	40V
Indicator Output Sink Current	50mA

Power Dissipation (Package Lin	nitation)
Ceramic minidip (Y-pkg.)	800mW
Derate above 25° C	8.0mW/°C
Plastic minidip (M-pkg.)	400mW
Derate above 25° C	4.0 mW/° C
Operating Temperature Range	
SG3523/3523A	55° C to +125° C
SG3423/3423A	0° C to +70° C

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, these specifications apply for V_{IN} = 5 to 35V and T_J = -55°C to +125°C for the SG3523/3523A and 0°C to +70°C for the SG3423/3423A.)

			s	G3523	A	SG3423A			SG3423/SG3523			
PARAMETER	COND	ITIONS	MIN	түр	MAX	MIN	түр	MAX	MIN	ТҮР	MAX	UNITS
Supply Voltage Range	÷		4.5	-	40	4.5	-	40	4.5	· _	40	v
Supply Current			-	5	7	-	5	7	-	5	10	mA
Sense Threshold	T _J = 2!	5°C	2.55	2.60	2.65	2.50	2.60	2.70	2.45	2.60	2.75	V.
Sense Threshold	Over T	emp. Range	2.50	-	2.70	2.45	· · -	2.75	2.35	-	2.85	v
Input Hysteresis	Sense 1	only	-	25		-	25	-	-	25	-	mV
Input Bias Current	Sense 1		-	-0.3	-1.0	-	-0.3	-1.0	-	-	-	μΑ
	Sense 2	2	-	+5	+10		+5	+10	-	-	~-	μA
Current Source			200	250	300	200	250	300	100	250	300	μΑ
Remote Activation	V _{Pin 5}	= 2.0	-	5	40	_	5	40	-	5	40	μΑ
Input Current	VPin 5	≈ 0.8V	-	-120	-180	_	-120	-180	-	-120	-180	μΑ
Output Voltage	I ₀ = 10	00mA	V _{IN} -2.2	V _{IN} -1.8	-	V _{IN} -2.2	V _{IN} -1.8		V _{IN} -2.2	V _{IN} -1.8	-	v
Peak Output Current	V _{IN} =	5V, V _O = 0V.	100	200	400	100,	200	400	-	-	-	mA
Output Off Voltage	V _{IN} =	40V	-	0	0.1	-	0	0.1	-	-	-	v
Indicator Saturation	ا _ل = -1	.6mA	_	0.1	-	_	0.1	-	-	0.1	0.4	v
Voltage	۱ _L = -1	0mA	-	0.2	0.5	_	0.2	0.5	-	0.4	_	v
Indicator Leakage	V _{Pin 6}	= 40V	-	.01	1.0	-	.01	1.0		-	-	μΑ
Propagation Delay	T _{.1} = 25 ⁰ C	Sense 1	-	1.0	-	_	1.0	-	-	1.0	_	μS
to Output	1 J = 25 C	Sense 2	-	0.5	-	-	0.5			0.5	-	μS
Output Current Rise Time	T _J = 2	5 ⁰ C	-	400	-		400	-	-	400		mΑ/μS

Silicon General

LINEAR INTEGRATED CIRCUITS

ADVANCED DATA SG3551

Performance data described herein represent design goals. Final device specifications are subject to change.

TRIPLE CURRENT SENSE LATCH

DESCRIPTION

This monolithic integrated circuit is a triple current sense comparator with latch and digital reset. It was specifically designed for printer coil saturation control. Each comparator input has a fixed 360 mV threshold to allow direct current sensing across a sampling resistor. When coil current exceeds a preset level, the comparator changes state and latches the drive control off. A reset command unlatches the driver and initiates another current ramp to the solenoid.

An on-chip bandgap regulator allows this device to maintain threshold accuracy over a supply voltage range of +4.5 to +25 volts. The common-mode range of the differential current sense inputs is not limited by the latch supply voltage, and may be as high as +40 volts. The SG3551 is available in a 14 pin plastic dual-in-line package, and is rated for operation over an ambient temperature range of 0 to $+85^{\circ}$ C.

FEATURES

- Three Current Sense Latches
- ± 5% Accuracy on Current Sense Threshold
- + 4.5 to + 25 Volt Supply Voltage Range
- Common Mode Range up to 40 Volts
- On-chip Bandgap Reference
- 40 Volt, 25 mÅ Öpen-Collector Outputs



DIE SIZE : 73 X 93 MILS



ABSOLUTE MAXIMUM RATINGS

PARAMETER	RATING	UNIT
Input Supply	25	۷
IN +	40	۷
IN -	40	v
Output Off Voltage	40	۷
Output On Current	25	mA
Reset Input Voltage	7	۷
Power Dissipation	600	mW
Temperature Range Operating	0 to +85	°C
Storage	-65 to +150	٥C

ELECTRICAL CHARACTERISTICS

(Unless Otherwise stated, these specifications apply over the operating temperature range of 0-85°C with V_S = 5V $\pm~10\%$)

PARAMETER (+, - INPUTS)	CONDITIONS	MIN	MAX	UNITS
Threshold Voltage	$V_{OM} = 3.5 \text{ to } 40 \text{V}$	340	380	mV
Positive Input Current	$V_{S} = 4.5 \text{ to } 25V$ + $V_{N} = -V_{N} = 40V$ Reset = 0.4V		1.5	mA
Negative Input Current	$+V_{MC} = +40V\Delta V_{IN} = 360mV$ Reset = 2.4V		1.5	μA
RESET				
High-Level Reset Voltage Low-Level Reset Voltage High-Level Input Current Low-Level Input Current Reset Minimum Pulse Width	$V_S = 25V$, Reset = 2.4V $V_S = 25V$, Reset = 0.4V Amplitude = 3.0V	2	0.8 20 400 500	> > 4 4 S
OUTPUT VOLTAGE				
Off-State Leakage On-State Voltage (latched) Supply Current (unlatched)	$V_0 = 40V$ $I_0 \approx 10mA$, $+V_{IN} = -V_{IN}$ Reset = 2.4V $V_S = 25V$, Reset = 0.4V		1.0 0.5 10	µA V mA
PROPAGATION DELAYS				
From Reset to Output From Input to Output	$\begin{array}{l} R_L = 470\Omega \mbox{ to } V_S \mbox{(See figure 1)} \\ R_L = 470\Omega \mbox{ to } V_S \mbox{(See figure 2)} \end{array}$		1.5 1.5	μS μ



OPERATIONAL AMPLIFIERS

General Purpose, Compensated Op Amps General Purpose, Uncompensated Op Amps Quad Op Amps High Voltage Op Amps High Power Op Amp Micropower Op Amp

Silicon General LINEAR INTEGRATED CIRCUITS

SG101/201 SG101A/201A/301A

Uncompensated Operational Amplifiers

The SG101/201 are general purpose operational amplifiers. Features include excellent input bias/current and drift characteristics plus short circuit protection and pin compatibility with many industry-standard operational amplifiers.

- . Frequency compensated with a single capacitor - no resistor required
- Low current drain: 1.8mA at ±20V .
- **Continuous short circuit protection**
- Operation as a comparator with differential inputs as high as±30V
- No latch up when common mode range is exceeded

The SG101A/201A/301A offer improved performance over the SG101/ 201 operational amplifiers and also provide short circuit protection and pin compatibility with industry standard types.

- 3mV offset voltage over temperature
- ٠ 100nA input current over temperature
- . 20nA offset current over temperature
- **Guaranteed drift characteristics**
- Offsets guaranteed over full common mode range

PARAMETERS*	101	201	101A	201A	301A	UNITS
Supply Voltage	±5 to ±20	±5 to ±20	±5 to ±20		±5 to ±15	v
Operating Temperature Range	-55 to +125	0 to +70	-55 to +125	-25 to +85	0 to +70	°C
Package Types	T, Y, J, F	T,Y,J,F,N,M	T, Y, J, F	Т, Ү, Ј	F, N, M	_
Input Offset Voltage	5.0	7.5	2.0 (3	.0)	7.5 (10)	mV
Input Offset Current	200 (500)	500 (750)	10 (20	D)	50 (70)	nA
Input Bias Current	0.5 (1.5)	1.5 (2.0)	0.075	(0.1)	0.25 (0.30)	μA
Temp Coeff Input Offset Voltage	(3.0 typ)	(6.0 typ)	15		30	μV/ºC
Temp Coeff INput Offset Current	-	-	0.2		0.6	nA/ºC
Large Signal Voltage Gain ¹	50 (25)	20 (15)	50 (25)		(15)	V/mV
Common Mode Rejection	(70)	(65)	(80)		(80)	dB
Power Supply Rejection	(316)	(316)	(100)		(100)	μV/V
Input Common Mode Voltage Range ²	(±12)	(±12)	(+15,	5, -12) (+15, -12		V
Differential Input Voltage	±30	±30	±30	±30		v
Slew Rate A _v = 1,	0.2	0.2	0.2		0.2	
A _v = 10	3 (typ)	3 (typ)	3 (ty	p)	3 (typ)	V/µS
Unity Gain Bandwidth	0.5 (typ)	0.5 (typ)	0.5 (1	typ)	0.5 (typ)	MHz
Supply Current	3.0	3.0	3.0		3.0	mA
$V_{out} R_L = 2k\Omega$	±10	±10	±10		±10	v
RL = 10kΩ	±12	±12	±12		±12	v
Noise R _s = 1kΩ f = 10Hz to 1.0kHz	4	4	4		4	μV(rms
$R_s = 500k\Omega$ f = 10Hz to 10kHz	25	25	25		25	(typ)

*Parameters apply over supply voltage range and are min./max. limits either at TA = 25 $^{
m O}$ C (or over operating temperature range if enclosed in parentheses), unless otherwise indicated. $^{2}V_{s} = \pm 15V$

 $^{1}R_{L} = 2k\Omega$



SG 101/201 (See T-pack SG101A/201A/301A Chip

Feedforward Compensation

INCREASES SLEW RATE AND GAIN BANDWIDTH TYPICALLY BY A FACTOR OF 10







I NON-INVERTING

2 INVERTING

CONNECTION DIAGRAMS D NC NC 🗄 OFFSET 6 V_ NON-INVERTING INPUT OUTPUT TOP VIEW J or N INVERTING v+ 🗉 COMPENSATION OFFSET ADJUST/ NC NC NC



OUTPUT

NC III

OUTPUT 6

COMPENSATION A

V+ 17

Flatpack Flatpack

Minidip M or Y

5 V-

1 NC

NON-INVERTING INPUT

2 OFFSET ADJUST/COMP

INVERTING INPUT

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

SG107/207/307 SG741/741C

General-Purpose Compensated Operational Amplifiers

The SG107/207/307 offer excellent input bias currents and drift characteristics as well as short circuit protection and pin compatibility with the 741 class of amplifiers.

- 3mV max offset voltage over temperature
- 100 nA max input bias current over temperature
- 20nA max offset current over temperature
- Offsets guaranteed over full common mode range
- Guaranteed drift characteristics

SG741/741C are pin compatible with the most widely accepted operational amplifiers and provide excellent performance for a wide range of applications.

- Complete short circuit protection
- Offset voltage null capability
- High common mode voltage range
- High differential input voltage range

PARAMETERS*	107	207	307	741	741C	Units		
Supply Voltage	±5 to ±20		±5 to ±20	±15	±15	v		
Operating Temperature Range	-55 to +125	to +125 –25 to +85		-55 to +125 -25 to +85		-55 to +125	0 to +70	°C
Package Types	T, J, F, Y	T, J, F	, Y, M, N	T, J, F, Y	T,J,Y,F,M,N			
Input Offset Voltage	2.0 (3.	0)	7.5 (10)	5.0 (6.0)	6.0 (7.5)	mV		
Input Offset Current	10 (20)	50 (70)	200 (500)	200 (300)	nA		
Input Bias Current	0.075	(0.1)	0.25 (0.3)	0.5 (1.5)	0.5 (0.8)	μA		
Temp. Coeff. Input Offset Voltage	(15) ²		(30) ²	(3.0 typ)	(6.0 typ)	μ∨/⁰C		
Temp. Coeff. Input Offset Current	(0.2)	(0.2)		(0.5 typ)	(0.5 typ)	nA/ºC		
Large Signal Voltage Gain	50 (25)	25 (15)	50 (25)	20 (15)	V/mV		
Common Mode Rejection	(80)		(80)	(70)	70	dB		
Power Supply Rejection	(100)		(100)	(150)	150	$\mu V/V$		
Input Common Mode Range	+15,12		+15, -12	±12	±12	V		
Differential Input Voltage	±30		±30	±30	±30	V		
Unity Gain Bandwidth	0.5 (ty	p)	0.5 (typ)	0.8 (typ)	0.8 (typ)	MHz		
Slew Rate	0.2		0.2	0.3	0.3	V/µS		
Supply Current	3.0		3.0	2.8	2.8	mA		
Output Voltage Swing								
RL = 2kΩ	±10		±10	±10	±10	V		
R _L = 10kΩ	±12		±12	±12		V		
Noise (typ)	````							
R _s = 1kΩ f = 10Hz to 10kHz	4		4	3	3	μV (rms)		
R _s = 500kΩ f = 10Hz to 10kHz	25		25		25	25	25	(typ)

*Parameters apply over supply voltage range and are min./max. limits either at T_A = 25°C (or over operating temperature range if enclosed in parentheses), unless otherwise indicated.

 $V_{s} = \pm 15V$ $^{2}T_{A} = +25^{\circ}C \leq +$













SILICAN GENEPAL

Quad Operational Amplifier

The SG124 series integrated circuit contains four true-differential, independent operational amplifiers. Each amplifier has been designed to operate from either a single supply voltage or plus and minus voltages and features internal frequency compensation, high gain, and very low supply current requirements. An additional significant advantage of these amplifiers is that when using a single supply, the input and output can be operated down to ground potential. Thus, they can be powered by a standard +5V DC logic supply and still be compatible with all forms of logic inputs and outputs.

- · Four internally compensated op amps in a single package
- Inputs and outputs can go to ground with a single supply voltage
- input bias current is both low and constant with temperature
- · Wide supply voltage compatibility with low current drain
- Available in 14-pin plastic or cerdip package

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, V⁺ Differential Input Voltage Input Voltage Power Dissipation (Note 1) N Package (plastic) Derate above 25°C J Package (cerdip) Derate above 25°C Output Short-Circuit to Gnd (Note 2) V⁺≤15V_{DC} and T_A ≈ 25°C Operating Temperature Range SG124 SG224 SG324 Storage Temperature Range Lead Temperature (Soldering, 60 sec)

32VDC or ±16VDC

SG124/224/324

-0.3VDC to +32VDC

600mW 6.0mW/°C 1000mW 6.7mW/°C

Continuous

-55°C to +125°C -25°C to +85°C 0°C to +70°C -65°C to +150°C 300°C

CONNECTION DIAGRAM





CHIP BONDING DIAGRAM

Electrical Characteristics ($V^+ = +5V$ DC and $T_A = 25^{\circ}C$ unless otherwise noted)								
		SG12			SG	224/SG32	4	<u> </u>
Parameter	Conditions	Min.	Тур.	Max.	Min.	Typ.	Max.	Units
Input Offset Voltage	Rs = 0Ω		2	5		2	7	mVDC
Input Bias Current (Note 3)	$[I_{IN}(+) + I_{IN}(-)]/2$		45	300		45	500	nADC
Input Offset Current	1 _{IN} (+) - 1 _{IN} (-)		±3	±30		±5	±50	nADC
Input Common-Mode Voltage Range (Note 4)		0		V+-1.5	0	·	V+-1.5	VDC
Supply Current	RL = ∞ On All Op Amps		0.8	2		0.8	2	mADC
Large Signal Voltage Gain	$R_L \ge 2k\Omega$		100			100		V/mV
Output Voltage Swing	RL = 2 kΩ	0		V+-1.5	0		V ⁺ -1.5	VDC
Common Mode Rejection Ratio	DC		85			85		dB
Power Supply Rejection Ratio	DC		100			100		dB
Amplifier-to-Amplifier Coupling	f = 1 kHz to 20 kHz (Input Referred)		-120	·		-120		dB
Output Current Source	V _{IN} ⁺ = +1V _{DC} , V _{IN} = 0 V _{DC}	20	40		20	40		mADC
Output Current Sink	V _{IN} ⁻ = +1 V _{DC} , V _{IN} ⁺ = 0 V _{DC}	10	20		10	20		mADC

Note 1: For operating at high temperatures, the SG324 must be derated based on a +125°C maximum junction temperature and a thermal resistance of 175°C/W which applies for the device soldered in a printed circuit board, operating in a still air ampient. The SG224 and SG124 can be derated based on a +150°C maximum junction temperature.

Note 2: Short circuits from the output to V⁺ can cause excessive heating and eventual destruction. The maximum output current is approximately 40 mA independent of the magnitude of V⁺. At values of supply voltage in excess of +15VDC. con-

tinuous short-circuits can exceed the power dissipation ratings

and cause eventual destruction. Note 3: The direction of the input current is out of the IC due to the PNP input stage. This current is essentially constant, independent of the state of the output so no loading chance exists on the input lines.

Note 4: The input common-mode voltage of either input signal voltage should not be allowed to go negative by more than 0.3V. The upper end of the common-mode voltage range is V^{+} 1,5V, but either or both inputs can go to +30V_{DC} without damage.

APPLICATIONS INFORMATION

To reduce the power supply current drain, the amplifiers have a class A output stage for small signal levels which converts to class B in a large signal mode. This allows the amplifiers to both source and sink large output currents. Therefore both NPN and PNP external current boost transitors can be used to extend the power capability of the basic amplifiers. The output voltage needs to raise approximately 1 diode drop above ground to bias the on-chip vertical PNP transistor for output current sinking applications.

For AC applications, where the load is capacitively coupled to the out-

put of the amplifier, a resistor should be used, from the output of the amplifier to ground to increase the class A bias current and prevent crossover distortion. Where the load is directly coupled, as in DC applications, there is no crossover distortion.

Capacitive loads which are applied directly to the output of the amplifier reduce the loop stability margin. Values of 50 pF can be accommodated using the worst-case non-inverting unity gain connection. Large closed loop gains or resistive isolation should be used if larger load capacitance must be driven by the amplifier.







NTERFACE 136

SINGLE SUPPLY NON-INVERTING DC AMPLIFIER (OV INPUT + OV OUTPUT)

Silicon General

LINEAR INTEGRATED CIRCUITS

SG1173/SG3173 ADVANCE DATA

3.5 AMP POWER OP AMP

DESCRIPTION

The SG1173 is a monolithic operational amplifier with a high current output stage capable of sinking or sourcing up to 3.5 amps. It operates with supply voltages up to \pm 24V. Internal current limit, thermal shutdown, and on-chip compensation make the SG1173 easy to use both for new designs and retrofit applications. The input specifications of the amplifier are competitive with industry standard devices that offer much lower output currents.

FEATURES

- 3.5 Amps output current
- Current limit and thermal shutdown protection
- Internal compensation
- Available in TO-220 and TO-66 packages

APPLICATIONS

- Motor drivers
- Servo systems
- Power amplifers





NOTE: CASE & TAB INTERNALLY CONNECTED TO VEE



R-Package:TO-66	P-Package: TO-220
$\Theta_{JC} = 6 °C/W max$	$\Theta_{JC} = 5 \text{°C/W} \text{ max}$
$\Theta_{JA} = 50 °C/W max$	$\Theta_{JA} = 65 \text{°C/W} \text{ max}$
Order SG1173R	Order SG1173P
SG3173R	SG3173P



SG1173/SG3173

ABSOLUTE MAXIMUM RATINGS

Supply Voltage ± 25V	
Output Current Internally Limited	
Differential Input Voltage ± 50V	
Common Mode Voltage ± 25	
Operating Junction Temp 150 °C	

SYMBOL PARAMETER		PARAMETER		1173			3173		
	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNITS	
Vio	Input Offset Voltage	25°C		2.0	4.0		2.0	6.0	mV
		Tiow - Thigh			6.0			8.0	mV
l _{IB}	Input Bias Current	25°C		250	500		250	700	nA
		T _{low —} T _{high}			750		1000		nA
10	Input Offset Current	25 °C		50	150		50	200	nA
		T _{low —} T _{high}			250			300	nA
Vour	Output Voltage Swing	$R_L = 10\Omega$ 25°C	±18	±20		± 18	±20		Volts
		Tiow - Thigh	± 17.5			± 17.5			Voits
los	Output Short Circuit Current	25 °C	± 3.5			± 3.5			Amps
CMRR	Common Mode	$\Delta V_{CM} = \pm 12V 25 °C$	76	90		70	90		dB
	Rejection Ratio	T _{low —} T _{high}	70						dB
PSRR	Power Supply	$\Delta V_{\rm S} = 12V$ 25°C	80	90		76	90		dB
	Rejection Ratio	T _{low —} T _{high}	74						dB
Avol	Open Loop Voltage Gain	RL = 100 VOUT = 10V 25 °C	40K	100k		25K	100k		VN
		T _{low -} T _{high}	25K						VN
s	Supply Current	25°C			20			20	mA
		Tiow - Thigh			30				mA

ELECTRICAL CHARACTERISTICS Vs = ± 24V

Notes: $T_{low} = -55$ °C for SG1173R, 0 °C for SG1173P and SG3173 $T_{high} = 125$ °C for SG1173R, 70 °C for SG1173P and SG3173



Small Signal Transient Response 50mV/vertical division 1µsec/horizontal division



Large Signal Transient Response 5 V/vertical division 20μ sec/horizontal division

Δ

SG1173/SG3173



APPLICATIONS

Proper usage of the SG1173 requires the same design and layout considerations used with other op amps. Power supplies should be adequately bypassed and clamped with Zener diodes if transients are a problem. Leads to high impedance nodes should be kept as short as possible to minimize undesirable inputoutput coupling or RF pick-up. In addition to these, the high current capability of the SG1173 presents some new challenges that a designer must be aware of. Special care should be taken to avoid spurious feedback due to ground loops or voltage drops in high current paths. Kelvin connections should be used when applicable. When driving inductive loads, protection diodes must be used to clamp the output voltage to the power supplies. This protects the amplifier from high voltage transients caused by the stored energy in the inductor. Some loads may require external load compensation. Examples of this are shown in Figure 1 and 2. Safe operating area (SOA) is another area where extreme care must be used. Simultaneous conditions of high current and high voltage on the part may cause the junction temperature to exceed the maximum rating. In any application, the worst case power dissipations should be calculated and adequate heat sinking must be provided.



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SILICON GANAPAL LINEAR INTEGRATED CIRCUITS

SG1253/SG2253/SG3253

Low Power Operational Amplifiers — Triple

DESCRIPTION

SG1253/2253/3253 operational amplifiers are triple operational amplifiers which have been designed to offer exceptional performance under conditions of extremely low internal power consumption. Quiescent current is determined by a single external resistor which permits operation over a wide range of currents and voltages.

FEATURES

- Adjustable power consumption to less than 20 microwatts
- Supply voltages from ± 0.75 to ± 18 volts
- Less than 15 nA bias currents
- Complete short-circuit protection
- Internally compensated



ABSOLUTE MAXIMUM RATINGS

, **.**

Supply Voltage	±18V
Differential Input Voltage (Note 1)	±15V
Common Mode Input Voltage (Note 2)	±15V
Output Short Circuit Duration	Indefinite (Note 3)
Power Dissipation (Pkg. Limitation)	
J-Package	1000mW
Derate above 25°C	8.0mW/°C
Storage Temperature Range	
J-Package	- 65°C to + 150°C
M-Package	- 55°C to + 125°C

Note 1. This rating applies to maximum voltage differential between input terminals. The maximum input voltage on either input terminal is limited to supply voltage up to a limit of \pm 15V.

Note 2. This rating limited to \pm supply voltage to a maximum of \pm 15V.

Note 3. With the output shorted to ground or either supply. Rating applies to + 125°C case temperature or + 75°C ambient temperature.

ELECTRICAL CHARACTERISTICS

PARAMETERS/CONDITIONS		1253 '	2253	3253 '	UNITS
Operating Temperature Range		-55 to +125	0 to - 70	0 to · 70	°C
Supply Voltage			± 18		
Differential Input Voltage ³		±15			
Common Mode Range ³			: 15		·
Input Offset Voltage	Rs < 100KΩ Rs < 10KΩ	3(4)		- 6.0(7.5)	mV
Input Bias Current	$V_{S} = \pm 3V$ $V_{S} = \pm 15V$	18(20) 12(15)	18(20) 12(15)	40(50) 25(30)	nA
Input Offset Current		5(8)	5(8)	10(15)	nA
Input Resistance		3	3	3	M
Large Signal Voltage Gain	RL = 10K VS = ±3V $RL = 10K VS = ±15V$	40(25 400(50)	40(25) 100(50)	40(25) 75(50)	V/mV
Output Voltage Swing	$V_{S} = \pm 3V, R_{L} = 10K_{\Omega}$ $V_{S} = \pm 15V, R_{L} = 10K_{\Omega}$	±1.5(±1.0) ±11(±10)		v	
CMRR RS < 10K1		(70)	(70)	(70)	dB
PSRR RS~10K12	VS = 3V VS = ±15V	(200) (150)	(200) (150)	(200) (150)	µ۷/۷
Power Consumption	$VS = \pm 3V$ $VS = \pm 15V. RL = 0$	(240) (1200)	(240) (1200)	(240) (1200)	Wu
Average TC of Offset Voltage	Rs = 10K (±15V for 1250)	4(typ)	4(typ)	6(typ)	μ V /°
Average TC of Offset Current	Rs = 20K (±15V for 1250)	2(typ)	2(typ)	1(typ)	pA/°C
Equiv. Input Noise Voltage	f=10Hz (±15V for 1250)	35(typ)	35(typ)	35(typ)	nV/√ł
Equiv. Input Noise Current	f=10Hz (±15V for 1250)	0.5(typ)	0.5(typ)	0.5(typ)	pA/√ł
Slew Rate	RL ≈ 10K, CL ≈ 100pF	0.2(typ)	0.2(typ)	0.2(typ)	V/µS
Small Signal Unity Gain-Bandwidth	$R_{f} = 0$ Vin = 20mV, RL = 20KΩ		-	-	kHz

SG1253/SG2253/SG3253

SETTING QUIESCENT CURRENT

RESISTOR BIASING						
QUIESCENT CURRENT						
A µ01	30 µ A	100 µ A				

	10 µ A	30 µ A	100 µ A	A µ 300	
±1.5	1.5M Ω	470K Ω	150K Ω		
: 3	3.3M Ω	1,1MΩ	330K M	100K Ω	
16	7.5MΩ	2.7MΩ	750K n	220K S	
± 9	13M រា	4M Ω	1.3MΩ	350K 🛙	
±12	18MΩ	5.6MΩ	1.5MΩ	510K រា	
115 t	22M Ω	7.5MΩ	2.2M Ω	620K n	

	CURRENT SOURCE BIASING						
10	A µ10	30µA	100 ₄ A	300 µ A			
Iset	1.3µA	4 µ A	15µA	50 µ A			



٧s



V/mV

Parameters for the SG1253 are min/max limits either at $T_A = 25^{\circ}C$ (or over operating temperature range if enclosed in parentheses), for supply voltage of +3V to +15V and for a quiescent current of 30 A established by an R_{Set} of 1.1.
Silicon General

LINEAR INTEGRATED CIRCUITS

SG1536/1436/1436C

General-Purpose Compensated Operational Amplifiers

SG1536/1436/1436C are intended specifically for use in high voltage applications where high common mode input ranges, high output voltage swings and low input currents are required. These devices are internally compensated and are pin compatible with industry-standard operational amplifiers.

- Usable with up to ±40V supplies
- Provides up to ±30V output voltage swing
- Common mode voltages to ±24V
- Input current 35nA max over temperature

PARAMETERS*	1536 ¹	1436 ¹	1436C ¹	UNITS
Supply Voltage	±40	±34	±30	V
Operating Temperature Range	-55 to +125	0 to +75	0 to +75	°C
Package Types		-		
Input Offset Voltage	5.0 (7.0)	10	12	mV
Input Offset Current	3.0 (7.0)	10 (14)	25	nA
Input Bias Current	20 (35)	40 (55)	90	nA
Large Signal Voltage Gain	100 (50)	70 (50)	50	V/mV
Common Mode Rejection	80	70	50	dB
Power Supply Rejection	100	200	50	μV/V
Input Common Mode Range ²	±24	±22	±18	V
Differential Input Voltage (V)	±(V	V		
Unity Gain Bandwidth	1.0 (typ)	1.0 (typ)	1.0 (typ)	MHz
Slew Rate ⁴	2.0 (typ)	2.0 (typ)	2.0 (typ)	V/µS
Supply Current	4.0	5.0	5.0	mA
Output Voltage Swing $R_L = 2k\Omega$	±22 ¹	±20 ¹	±20 ¹	V
$R_L = 10k\Omega$	±30 ⁵	-	_	V
Noise (typ) $A_V = 100, R_s = 10k\Omega, f = 1.0 \text{ KHz},$ BW = 1.0 Hz	50	50	50	nV/(Hz)½ (typ)

*Parameters apply over supply voltage range and are min./max. limits either at T_A = 25⁰C (or over operating temperature range if enclosed in parentheses), unless otherwise indicated.

³Inputs are shunted with back-to-back diodes for over voltage protection

¹V_s = ±28V ⁴R_L = 5 κΩ $^{2}V_{s} = \pm 15V$ 3 inpu $^{5}R_{L} = 5.0k\Omega, V_{s} = \pm 36V.$



SG1536/1436/1436C Chip (See T-peckage diagram

Balancing Circuit (Optional)



CONNECTION DIAGRAMS





INTERFACE CIRCUITS

Sense Amplifiers Core Drivers Dual Peripheral Drivers

SILICON GANAPAL LINEAR INTEGRATED CIRCUITS

ADVANCE DATA

SG55236/SG75236

Performance data described herein represent design goals. Final device specifications are subject to change.

Dual Sense Amplifier/Data Registers

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, VCC+		4.75	- 5	5.25	v
Supply voltage, VCC-		-4.75	-5	-5.25	V
Reference voltage, Vref		±1.5	±2.1	±4.5	V
High-level output voltage, VOH	Detector and buffer			Vcc	V
	Register			-400	MA
	Register			16	
Low-level output current, IOL	Buffer			25	mA
· · · · · · · · · · · · · · · · · · ·	Detector	F		3.2	
Width of reset pulse, tw(R)		115			TH6

Supply voltages (see Note	1)																				
V _{CC+}												:				٠		٠	•	•	7 V
Voc																		٠	•	•	/ V
Reference voltage, Vref				Ì	÷																±5 V
Differential input voltage,	ż,	n																			±5 V
Voltage from any input to) on	oun	d														•		•	•	5.20 V
Continuous total dissipation (see Note 3)-	on	at (or I	bel	0%	/) 7	70°	'C	fre	6-8	ir	ten	np	era	tu	re.	·	·	·	4	50 mW
Operating free-air tempera	atu	re ri	Ing	•:	s	G	55	23	6		•	•	•	•	•	·	-1	56`	ç	to	125°C
					S	G	75	23	6		•	•		•	•	•	•	. 1	0-0	cυ	5 70°C
Storage Temperature rang																•	-	65	°C	to	150°C
Leed temperature 1/16 in	ch	fror	n c	.89	e fe	pr (60	30	cor	nda								•		•	300°C

NOTE: 1. Voltage values, except differential input voltage, are with respect to the network ground terminal.

electrical characteristics over recommended operating free-air temperature range, $V_{ref}=\pm 2.1V$ (unless otherwise noted)

	PARA	METER		TE	ST CONDITIONS		MIN	TYPT	MAX	UNIT
						SG55236	5	7	9	
				VCC+ = 5 V.	Vcc = -5 V,					
				TA = 25°C		SG75236	4	7	10	
	Differential-	inout th	reshold							۳V
۷T	voltage (see	•		V _{CC+} = 5 V ± 5%,		\$G55236	4.5	7	9.5	
				VCC5 V ± 5%						
				Vcc+=5V,	Vcc_ = -6 V	SG75236	4	7	10	
				VCC+ - 5 V,		L				
VICF	Common-m firing voltag	•	ut	f = 0.1 MHz to 20 M	Hz			±1.5		V
168	Differential		les current	Vcc+=5 V.	VCC =5 V.	VID = 0		20		- 10
10			ffset current	Vcc+ = 5 V,	V _{CC} _ = -5 V,	VID * 0		0.5		<u> </u>
VIH	High-level in	nput vol	tage				2			۱v
•1H	(strobe and									+-
VIL	Low-level in		•						0.8	•
	(strobe and	logic in	puts)	V _{CC+} = 4.75 V,	Vcc_ = -4.75	/ VIII = 2 V.				+
	High-level		Register	VIL = 0.8 V.	IOH = -400 #A					Ι.
۷он	output volt			Vcc+ = 4.75 V,	Vcc4.75	/, VIH = 2 V,	2.4			ľ
	004001	~	Detector	VIL = 0.8 V						-
	High-level			Vcc+ = 4.75 V,	Vcc4.75	V, VIH = 2 V,			250	س ا
юн	output curr	ent	Buffer	VIL = 0.8 V,	VOH = 4.75 V					
			Register	VCC = 4.75 V.	Vcc4.75	V, V _{IH} = 2 V,	l		0.4	۱v
			ringester	V _{IL} = 0.8 V,	IOL = 16 mA		_			┿
VOL	Low-level		Buffer	VCC = 4.75 V.	Vcc_ = -4.75	v. viH = 2 v.			0.5	1
-02	output volt	age		VIL = 0.8 V.	IOL = 25 mA	V VIII = 2 V				
			Detector	V _{CC} = 4.75 V, V _{IL} = 0.8 V	•uu= 4				0.4	Ľ
	Input curr	ent at m	aximum	V _{CC+} = 5.25 V,	Vcc_ = -5.25	v, v _{iH} = 5.25 v			1	_
4	input volta	_		*****						+-
		Date in							40	
	High-level		N select	4					-750	1
чн	input		r input 2RI	V _{CC+} = 5.25 V,	V _{CC-} = -5.25 V	, ∨ _{iH} = 2.4 ∨			80	1 "
	current	buffer								
	· ·	Data I	bed				[160	+-
		Strobe	, reset, or						-3.2	
	Low-level	buffer		1					-3	-
ίι.	input	_	er input 2RI	VCC+ = 5.25 V,	VCC	, V _{IL} = 0.4 V			-1.6	
	current	Chann Data I	el select	4			<u> </u>		-6.4	1
		Data i		4					2	1_
105	Short-circu output cur	lit	Register	V _{CC+} = 5.25 V,	V _{CC} _ = -5.25	v, v _o =0	-20		60	-
Iref	Reference		I	V _{CC+} = 5.25 V,	Vcc- = -5.25	V, V _{ref} = -2.1 V,			0.5	٦,
				T _A = 25°C	V _{CC} _ = -5.25	V TA = 25°C	+		55	+ 7
100+ 100-				V _{CC+} = 5.25 V, V _{CC+} = 5.25 V,	V _{CC} _ = - 5 26	V TA # 25°C	+		18	_

HIGH-SPEED SENSE AMPLIFIERS WITH BUILT-IN DATA REGISTER AND BUFFER FOR APPLICATION IN COINCIDENT-CURRENT CORE MEMORIES

24 121

> 2 3

22 21 28

- ± 2-mV Threshold Sensitivity with Threshold Voltage Independent of Temperature and Supply-Voltage Variations
- Adjustable Differential-Input Threshold Voltage
- **Reference Amplifier Inherently Stable** with No External Frequency Compensation Required
- **Built-In Data Register with Provisions** . for External Data Inputs
- Built-In Data Buffer Drives 450-pF . Load in 15 ns
- Low Power Consumption .
- Internal Reference Voltage Attenuator Makes Reference Amplifier Less Sensitive to Noise .
- Two Independent Channels with TTL Compatible Logic Inputs and Outputs .

			FUN	CTI	ON	TA	BLI	E	
		_	OUTPUTS						
A	C	8	W/RIT	L	D	R	G	Y	_ Z_
н	H	Ħ	1	x	x	X	н	H	Ľ
H	н	H	L	x	X	X	L	н	H
Ŧ	н	I	+	L	х	н	н	н	L
4	н	H	+	L	х	н	L	н	н
н	ŧ	н	+	L	х	н	н	н	L
н	ŧ.	H	+	L	х	н	L	[н	빝
н	н	÷	+	L	х	н	н	н	
н	н	÷	t	L	X	н	L	н	H
L	х	х	н	н	н	X	X	L	н
L	х	х	н	н	L	х	н	н	L
L	х	X	н	н	L	х	L	н	н
L	х	X	н	L	х	L	х	L	н
L	X	X	н	L	х	t	x	L.	н
X	L	X	H	H	н	х	X	L	x
х	L	x	н	н	L	х	н	н	L
x	L	x	н	н	L	х	Ε,	н	н
х	Ł	X	н	L	х	L	х	L	н
x	L	X	н	L	х	t	X	L	н
х	х	٢	±.	н	н	х	х	L	X
х	х	L	н	н	L	х	H	н	L
х	x	L	н	н	L	х	L	н	н
x	х	١.	н	L	x	L	X	L	н
х	х	L)	н	L	х	t	х	L	-н]







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[22]

11

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	18	OUTPUT			
1A	1C	1W-2W			
н	н	x	x	н	L
x	х	н	н	H	L
ŧ.	н	È.	х	н	+
ŧ.	н	х	٤	H	+
L	x	Ŧ	н	H	1 1
х	L	÷	н	н	t
		y Oti Ibina			н

H = high level (steady state), L = low level (steady state) X = irrelevant (any input, including transitions) \pm transition from high level to low level, 1 = transition from low level to high level The W/RI column shows the output from the detector resulting from the inputs A, C, and S. In positive logic, W = ACS. For dual operation with 2W connected to 2RI, this column represents an intermediate node and can be ignored.

For independent operation of register 2, this column is an input and the A, C, and S columns should be ignored.

For dual-channel operation with 2W connected to 1W/1RI, this column is the result of W = $\overline{S(1A+1C+2A+2C)}$ as shown in the table above.

definition of logic levels

INPUT	н	L
At	VID > VT max	VID < VT min
LOGIC	VI > VIH min	VI < VIL max

[‡]A is a differential voltage (V_{1D}) between A1 and A2. For these circuits, V_{1D} is consider positive regardless of which terminal is positive with respect to the other.





SILICON GARAPAL

Memory Drivers

PERFORMANCE

- 600-mA Output Capability
- Fast Switching Times
- Output Short-Circuit Protection
- Dual Sink and Dual Source Outputs
- Minimum Time Skew between Address and Output Current Rise
- 24-Volt Output Capability

- EASE OF DESIGN
 Source Base Drive Externally Adjustable
- TTL or DTL Compatibility
- Input Clamping Diodes
- Transformer Coupling Eliminated
- Reliability Increased
- Drive-Line Lengths Reduced
- Use of External Components Minimized

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

		SG55325	SG75325	UNIT
Supply voltage VCC1 (see Note 1)		7	7	V
Supply voltage VCC2 (see Note 1)		25	25	V
Input voltage (any address or strobe input)		5.5	5.5	V
Continuous total dissipation at (or below) 100°C case temperat	ure	1	1	W
Operating free-air temperature range		-55 to 125	0 to 70	°C
Storage temperature range		65 to 150	-65 to 150	°C
Lead temperature 1/16 inch from case for 60 seconds	J package	300	300	°C
Lead temperature 1/16 inch from case for 10 seconds	N package	260	260	°C

NOTE: 1. Voltage values are with respect to network ground terminal.

electrical characteristics over rated operating free-air temperature range (unless otherwise noted)

					S	3553	25	S	UNIT		
	PARAMETER		TEST CONDI	TIONS	MIN	TYPT	MAX	MIN	TYPT	MAX	UNI
VIH	High-level input voltag				2			2			v
VIL	Low-level input voltag						0.8			• 0.8	V
Vi	Input clamp voltage		V _{CC1} = 4.5 V,	V _{CC2} = 24 V. T _A = 25°C		-1.3	-1.7		-1.3	-1.7	v
	Source-collectors term	inal	Vcc1 = 4.5 V,	Full range			500			200	μA
(off)	off-state current		VCC2 = 24 V	TA = 25°C		3	150		3	200] "^
VOH	High-level sink output	voltage	VCC1 = 4.5 V,	VCC2 = 24 V,	19	23	_	19	23		v
			VCC1 = 4.5 V, VCC2 = 15 V,	Full range			0.9			0.9	
		Source outputs	RL = 24 Ω, I(source) ≈ ~600 mA,	T _A = 25°C		0.43	0.7		0.43	0.75	
V _(sat)	V _(sat) Saturation voltage		$V_{CC1} = 4.5 V.$ $V_{CC2} = 15 V.$ $B_1 = 24 \Omega.$	Fuli range			0.9			0.9] `
		Sink outputs	HL = 24 52, I _(sink) ≈ 600 mA,	T _A = 25°C		0.43	0.7		0.43	0.75	
	Input current at maxi	address inputs	VCC1 = 5.5 V,	V _{CC2} = 24 V,			۴	[1	mé
۹.	mum input voltage	strobe inputs	VI = 5.5 V				2			2	1 ""
	High-level input	address inputs	VCC1 = 5.5 V.	VCC2 = 24 V,		3			3	40	μA
ін	current	strobe inputs	Vi = 2.4 V			6	80		6		L
	Low-level input	address inputs	VCC1 = 5.5 V,	VCC2 = 24 V,		-1	-1.6		-1		mA
ήL	current	strobe inputs	V1 = 0.4 V			-2	-3.2		-2		
1	Supply current, all	from VCC1	VCC1 = 5.5 V,	VCC2 = 24 V,		14	22		14	22	1
ICC(off)	sources and sinks off	from VCC2	T _A = 25°C			7.5	20		7.5	20	
ICC1	Supply current from V either sink on	VCC1.	V _{CC1} = 5.5 V, I(sink) = 50 mA,	V _{CC2} = 24 V, T _A = 25°C		55	70		55	70	
ICC2	Supply current from t either source on	V _{CC2} ,	VCC1 = 5.5 V, I(source) = -50 mA,			32	50		32	50	m#

SG55325/SG75325

switching characteristics, VCC1 = 5 V, TA = 25°C

PARAMETER	TO (OUTPUT)	TEST FIGURE	TEST CONDITIONS	MIN TY	MAX	UNII
tPLH	0	9	V _{CC2} = 15 V, R _L = 24 Ω,	25	50	0.5
1PHL	Source collectors	9	C _L = 25 pF	25	50	
^t TLH	<u>.</u>	10	$V_{CC2} = 20 V$, $R_L = 1 k\Omega$,	55		ns
THL	Source outputs		CL = 25 pF	7		1
TPLH	Ciali autouta	9	V _{CC2} = 15 V, R _L = 24 Ω,	20	45	ns
TPHL	Sink outputs	3	С _L ≃ 25 рF	20	45	1
^t TLH	Cieli euteute	9	V _{CC2} = 15 V, R _L = 24 Ω,	7	15	ns
^t THL	Sink outputs	9	CL = 25 pF	9	20] ""
ts	Sink outputs	9	V _{CC2} = 15 V, R _L = 24 Ω, C _L = 25 pF	15	30	ns

 $\Psi_{tPLH} = propagation delay time, low-to-high-level output$ tPHL = propagation delay time, high-to-low-level output

ADD	RESS	INPL	JTS	STROBE I	NPUTS	OUTPUTS					
SOU	RCE	SINK		SOURCE	SINK	SOU	RCE.	SINK			
A	8	С	D	S1	S2	w	x	Y	z		
L	н	×	х	L	н	ON	OFF	OFF	OFF		
н	L	x	х	l L) н (OFF	ON	OFF	OFF		
х	x	L	н	н	L L	OFF	OFF	ON	OFF		
х	x	н	L	н	L	OFF	OFF	OFF	ON		
х	x	x	х	н	н	OFF	OFF	OFF	OFF		
н	н	н	н	×	×	OFF	OFF	OFF	OFF		

H = high level, L = low level, X = irrelevant

NOTE: Not more than one output is to be on at any one time.



J. OR N DUAL-IN-LINE OR F FLAT PACKAGE (TOP VIEW)







SILICAN GANAPAL LINEAR INTEGRATED CIRCUITS

Memory Drivers

SG55326/SG75326 SG55327/SG75327

FEATURES

- Quad Positive or Sink Memory Drivers
- 600 mA Output Current Sink Capability
- 24V Output Capability
- Clamp Voltage Variable to 24V SG55327, SG75327 PERFORMANCE
- Quad Memory Switches
- 600 mA Output Current Capability
- VCC2 Drive Voltage Variable to 24V
- Output Capable of Swinging Between VCC2 and Ground

- High-Repetition-Rate Driver Compatible with High-Speed Magnetic Memories
- Inputs Compatible with TTL Decoders
- Minimum Time Skew between Strobe and Output-Current Rise
- Pulse-Transformer Coupling Eliminated
- Drive-Line Lengths Reduced

ABSOLUTE MAXIMUM RATINGS

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

	SG55326	SG75326	SG55327	SG75327	UNIT
Supply voltage, VCC or VCC1 (see Note 1)	7	7	7	7	v
Supply voltage, V _{CC2}			25	25	V
Input voltage, any address or strobe	5.5	5.5	5.5	5.5	V
Output collector voltage	25	25	25	25	V
Output clamp voltage	25	25			V
Output collector current	750	750	750	750	mA
Continuous total dissipation at (or below) 100°C case temperature (see Note 2)	1	1	1	1	w
Operating free-air temperature range	-55 to 125	0 to 70	55 to 125	0 to 70	°C
Storage temperature range	-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C
Lead temperature 1/16 inch from case for 60 seconds: J, Y or M package	300	300	300	300	°C
Lead temperature 1/16 inch from case for 10 seconds: N package	260	260	260	260	°c

recommended operating conditions

	SG55326				SG7532	6	SG5532		27 SG753		G75327		UNIT
	MIN	NOM	MAX	MIN	NOM	MAX	MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Supply voltage, VCC or VCC1	4.5	5	5.5	4.5	5	5.5	4.5	5	5.5	4.5	5	5.5	v
Supply voltage, VCC2							4.5		24	4.5		24	V
Output collector voltage		-	24		_	24			24			24	v
Output-clamp voltage, V(clamp)	4.5		24	4.5		24					-		v
Output collector current			600			600			600			600	mA
Operating free-air temperature, TA	-55		125	0		70	-55		125	0		70	°C

NOTE: 1. Voltage values are with respect to network ground terminal(s).

	PARAMETE	ė	TEST CO	NOITIONS		SG5532	6	SG75326			
			TEST CO	I CONDITIONS		TYP‡	MAX	MIN	TYP‡	MAX	UNI
VIH	High-level input	voltage			2			2			l v
VIL	Low-level input	voltage			1		0.8			0.8	t v
V <u>I</u>	Input clamp volt	age	V _{CC} = 4.5 V, T _A = 25°C	l₁ = −10 mA,		-1	-1.7		-1	1.7	v
VOH	High-level output	t voltage	V _{CC} = 4.5 V,	I _O = 0	19	23		19	23		V
V _(sat)	Saturation voltag		V _{CC} = 4.5 V, I _(sink) = 600 mA [§] ,	Full range			0.9			0.9	
- (sat/		6	See Note 3	T _A = 25°C		0.43	0.7		0.43	0.75	l v
VF(clamp)	Output-clamp-die forward voltage	ode	V _{(clamp}) ≈ 0, T _A = 25°C	(clamp) = ~10 mA,			1.5			1.5	v
^I (clamp)	Output-clamp cu one output on	rrent,	l _(sink) = 50 mA,	T _A = 25°C		5	7		5	7	mA
4	Input current at	Address					1			1	
·1	maximum input voltage	Strobe	V ₁ = 5.5 V				4			4	mA
чн	High-level	Address					40			40	
-111	input current	Strobe	Vi = 2.4 V				160			160	μA
11	Low-level	Address				-1	-1.6		-1	-1.6	
·it.	input current	Strobe	- V ₁ = 0.4 ∨	f			-6.4		-4	-6.4	mΑ
CC(off)	Supply current, a	Il outputs off	All inputs at 5 V,	T _A = 25°C		18	25		18	25	mA
CC(on)	Supply current, o	ne output on	$I_{(sink)} = 50 \text{ mA},$	T _A = 25°C		58	75		58	75	mA

SG55326, SG75326 electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

SG55326, SG75326 switching characteristics, $V_{CC} = 5V$, $T_A = 25^{\circ}C$

PARAMETER	TO (OUTPUT)	TEST CONDITIONS 8	MIN	TYP	MAY	UNIT
^t PLH	W V V 3			30	50	
^t PHL	W, X, Y, or Z		├───	25		ns
<u>t</u> т.н	W, X, Y, or Z	$V_S = V(clamp) \approx 15 V, R_L = 24 \Omega, C_L \approx 25 pF,$	<u> </u>		15	
^t THL	W, X, T, OF Z	See Figure 5	ŀ	10	20	ns
ts	W, X, Y, or Z			24	35	
VOH	W, X, Y, or Z	$V_S = V_{(clamp)} = 24 V, R_L = 47 \Omega, C_L = 25 pF,$				ns
		I(sink) ≈ 500 mA, See Figure 5	VS−25			mV

SG55327, SG75327 electrical c	haracteristics over recommended operating free-air temperature
range (unless otherwise noted)	

	PARAMETEI	3	TEST CON	DITIONS	L 9	G5532	7		SG7532	7	
		-		Diffond	MIN	TYP	MAX	MIN	TYP [‡]	MAX	
VIH	High-level input	voltage			2			2			v
VIL	Low-level input	voltage			t		0.8	<u> </u>		0.8	t v
vı	Input clamp volt	age	$V_{CC} = 4.5 V,$ I _j = -10 mA T _A = 25°C			-1	-1.7		~1	-1.7	v
l(off)	Collectors termi	nal	V _{CC1} = 4.5 V,	Full range	t		500			200	
10111	off-state current		V _(col) = 24 V	T _A = 25°C			150			200	μA
V _(sat) Saturation voltage		V _{CC1} = 4.5 V, V _O = 0,	Full range			0.9	1		0.9	\vdash	
* (sat)	() Saturation voltage		I (source) = -600 mA [§] , See Notes 3 and 4	T _A = 25°C		0.43	0.7		0.43	0.75	ľ
	Input current at maximum	Address		• • • • • • • • • • • • • • • • • • •			1	1		1	
1	input voltage	Strobe	V _I = 5.5 V				4	1		4	mA
	High-level	Address			1		40	<u> </u>	· · ·	40	<u> </u>
1H	input current	Strobe	V ₁ = 2.4 V				160			160	μ Α
	Low-level	Address		·····		-1	-1.6		-1	1.6	<u> </u>
IL.	input current	Strobe	VI= 0.4 V			-4	-6.4		-4	-6.4	i mA
	Supply current,	From VCC1				7	10	1	7	10	
CC(off)	all outputs off	From VCC2		T _A = 25°C	<u> </u>	13	20		13	20	mA
	Supply current,	From VCC1	V(col) = 6 V,	I (source) = -50 mA,	-	8	12		8	12	
CC(on)	one output on	From VCC2		See Note 3		36	55	t	36	55	(m/

SG55327, SG75327 switching characteristics, V_{CC1} = 5V, T_{A} = 25°C

PARAMETER 1	TO (OUTPUT)	TEST CONDITIONS §	MIN	TYP	MAX	UNIT
ΨLH	Collectors	$V_{S} = V_{CC2} = 15 V$, $R_{L} = 24 \Omega$, $C_{L} \approx 25 pF$,		35	55	
TPHL	W, Z or X, Y	See Figure 5 and Note 4		30	55	ns
ЧТLH	W, X, Y, or Z	$V_{(col)} = V_{CC2} = 20 V, R_{L} = 100 \Omega, C_{L} = 25 \mu F,$		30		<u> </u>
THL	M, A, T, O Z	See Figure 6 and Note 4		10		ns
∨он	Collectors W, Z or X, Y	$V_{S} = V_{CC2} = 24 V$, $R_{L} = 47 \Omega$, $C_{L} = 25 pF$, $I_{(sink)} \approx 500 \text{ mA}$, See Figure 5 and Note 4	V _S -25			mV

SG55326/SG75326 SG55327/SG75327



SG55326/SG75326 SG55327/SG75327



ilicon General LINEAR INTEGRATED CIRCUITS

SG55450B/75450B SG55460/75460

Dual Peripheral Drivers

The SG55450B and SG55460 Series are general purpose dual peripheral drivers whose output stage includes a completely uncommitted, high-voltage, high current NPN transistor. Inputs to the standard TTL gates are diode clamped and fully DTL/TTL compatible. The output transistors of the SG55450B and SG75450B are capable of sinking 300 mA and will withstand 30 volts when off. The SG55460 and SG75460 devices have the same current rating but with higher voltage capability of 40 volts and only slight reduction in switching speeds.

The SG55450B and SG55460 are characterized for operation over the full military temperature range of -55°C to +125°C while the SG75450B and SG75460 are designed for 0°C to +70°C operation.

- Current capacity of 300 mA per driver
- High output voltage capability
- High-speed switching characteristics
- · Both military and commercial temperature ranges

ELECTRICAL CHARACTERISTICS

(over operating temperature range and with $V_{CC} = 5V \pm 5\%$, unless otherwise specified)

Parameter	Test Conditions	Min.	Typ.	Max.	Units
High-level input voltage, VIH	V _{OL} < 0.4V, I _{OL} = 16mA	2			v
Low-level input voltage, VIL	V _{OH} > 2.4V, I _{OH} =4mA			0.8	V
High-level output voltage, VOH	VIL = 0.8V, IOH =4mA	2.4	3.3		V
Low-level output voltage, VOL	VIH = 2.0V, IOL = 16 mA		.25	0.4	V
Input clamp voltage, Vi	ij = −12mA		- 1.2	- 1.5	V
High-level input current, IIH	V1 = 2.4V			40	μA
High-level strobe current, ISH	VI = 2.4V			80	μA
Low-level input current, IL	VI = 0.4V			- 1.6	mA
Low-level strobe current, ISL	VI = 0.4V			- 3.2	mA
Input current at max. V, II	VI = 5.5V			1.0	mA
Strobe current at max, V, Is	V _S = 5.5V			2.0	mA
Output short circuit current, IOS		-18	-35	-65	mA
Supply current, high out, ICCH	V ₁ = 0		2	4	mA
Supply current, low out, ICCL	VI = 5V		6	11	mA

Parameter	Test Conditions	55450B	75450B	55460	75460	Units
Collector-base breakdown BVCBO	$I_{C} = 100 \mu A, I_{E} = 0$	35	35	40	40	V min.
Collector-emitter breakdown BVCER	IC = 100μA, RBE = 500Ω	30	30	40	40	V min.
Emitter-base breakdown BVEBO	IE = 100µA, IC = 0	5	5	5	5	V min.
Base-emitter voltage VBE	IB = 10mA, IC = 100 mA	1.2	1.0	1.2	1.0	V max.
	IB = 30mA, IC = 300 mA	1.4	1.2	1.4	1.2	V max.
Collector-emitter saturation VCE (SAT)	1B = 10mA, 1c = 100mA	.5	.4	.5	.4	V max.
	I _B = 30mA, I _C = 300mA	.8	.7	.8	.7	V max.
Current transfer ratio hre	VCE = 3V, 1C = 100mA, TA = 25°C	25	25	25	25	min.
	VCE = 3V, IC = 300mA, TA = 25°C	30	30	30	30	min.
	$V_{CE} = 3V$, $I_{C} = 100mA$, $T_{A} = min$.	10	20	10	20	min.
	$V_{CE} = 3V$, $I_C = 300 \text{ mA}$, $T_A = min$.	15	25	15	25	min.

		55450E	, 75450B	55460,	75460	
Parameter	Test Conditions	Typ.	Mex.	Typ.	Max.	Unit
TTL GATES						
Propagation delay time						
Low-to-high-level output, tpLH	С _L ≈ 15 рF	12	22	22		nS
Propagation delay time						
High-to-low-level output, tpHL	R ₁ = 400Ω	8	15	8		nS
OUTPUT TRANSISTORS						
Delay time, td	1c = 200mA	8	15	10		nS
Rise time, t _r	¹ b(1) = 20mA	12	20	16		nS
	¹ b(2) =40mA					
Storage time, t _s	VBE(OH) = -1V	7	15	23		nS
Fall time, tf	CL = 15 pF,	6	15	14		nS
	RL = 50Ω					
GATES & TRANSISTORS COMBINED)					
Propagation delay time						
Low-to-high-level out, tpLH	IC = 200mA	20	30	45	65	nS
High-to-low-level out, tpHL	CL = 15 pF	20	30	35	50	nS
Transition time		· · · · · ·				
Low-to-high-level out, tTLH	$R_{L} = 50\Omega$	7	12	10	20	nS
High-to-low-level out, tTHL		9	15	10	20	nS

ABSOLUTE MAXIMUM RATINGS (Note 1)	SG55450B SG75450B	SG55460 SG75460
Supply Voltage, VCC	7V	7V
Input Voltage	5.5V	5.5V
V _{CC} to Substrate Voltage	35V	40V
Collector to Substrate Voltage	35V	4 0∨
Collector to Base Voltage	35V	40V
Collector to Emitter Voltage (Note 2)	30V	40V
Emitter to Base Voltage	5V	5V
Collector Current (Note 3)	300mA	300mA
Power Dissipation		
N Package (plastic)	600mW	600mW
Derate above 25°C	6.0mW/ ^o C	6.0mW/ ^o C
J Package (cerdip)	1000mW	1000mW
Derate above 25°C	6.7mW/ ⁰ C	6.7mW/ ^o C
Operating, Free Air Temperature Range		
SG55450B, SG55460	-55 ⁰ C t	o +125°C
SG75450B, SG75460	0°C to	+70°C
Storage Temperature Range	-65°C t	o +150°C

NOTES:

- 1. Voltage values shown are with respect to ground terminal unless otherwise specified.
- ce less than 500 Ω . 2. With base-to-emitter resist
- Both sides of circuit may conduct rated current simultaneously provided power dissipation rating is not exceeded.



Note: The substrate (pin 8) must always be at the most negative voltage for proper device operation.



CHIP BONDING DIAGRAM

SILICON GENERAL

DISK DRIVE INTERFACE

ADVANCED DATA SG82727

DESCRIPTION:

The SG82727 is a monolithic integrated circuit designed to interface the standard disk drive bus to the actuator stepping motor, read/write circuitry and a microprocessor. A full featured 5¼ inch disk drive can be implemented with only three devices: the SG82727, an integrated read/write circuit and a microprocessor.

The SG82727 is designed for direct interface to the 8048 or 8049 microcontroller. The device can also be addressed by 8051, 6500/1, 6805 and similar microcontrollers with some external circuitry.

No external components are required between the host cable and the SG82727 (a single resistor packet may be required to pull up inputs in one drive per system). Internally clamped stepping motor outputs can sink and source 275 mA and the door latch solenoid driver can source 250 mA. The SG82727 supports direct interface to optical sensors. All other inputs are TTL compatible.

FEATURES:

- Direct drive of stepping motor (bipolar, 275 mA)
- Direct drive of door lock solenoid (250 mA)
- Direct Drive of LED activate indicator
- Direct interface to host disk drive bus
- Power saving feature for door lock
- 300 Hz output for spindle motor control
- Direct interface to microprocessor
- Two internal one-shots to shape index pulse
- TTL compatible logic input and outputs
- Packaged in a 40 pin DIP

CONNECTION DIAGRAM (Top View) 12 V (SWITCHED) STEP 4 40 1 39 STEP 3 STEP 2 2 3 38 STEP 1] GND SOLENOID DRIVE 4 37 **MTR CLOCK** 12 V 5 ALE 36 6 35] P23 V_{cc} I SPARE OUT [7 34 7 P22 LED OUT [8 33 **P21** 5/12 SELECT 9 32 P20 WGATE SPARE IN [10 31 INTR 11 30 RD DATA READ DATA WRITE ENABLE 29 12 28 TRACKO MOTOR ON [13 READY Т1 14 27 WRPROT STEP 15 26 DIR INDEX 16 25 DS 17 24 PROG TRACKO SENSOR 18 23 WRITE SENSOR INSERT SENSOR 19 22 INDEX SENSOR TRC (DELAY) RC (DELAY) 20 21

FUNCTION

- 12 Volt Input, Switched Power to the stepping motor drivers. May be switched to 5 volts through an external transistor to save power. The output signal to select 5 or 12 volts is supplied at pin 9 (5/12 select).
- 2 Step Output 2 Pins 2, 3, 39 and 40 are 275 mA push-pull drivers which can directly control the actuator arm stepping motor. These outputs have internal clamping diodes.
- 3 Step Output 1 See pin 2.
- 4 Door Solenoid Driver Output The output can source 250 mA. It is intended to drive a door lock solenoid.
- 5 12 Volt Input Power for the door lock solenoid driver.
- 5 Volt Input (V_{CC}) Power to the SG82727 logic circuits.
- 7 Spare Output This TTL compatible output is user definable. It is gated with DS' (Drive Select) and controlled by the microprocessor.
- 8 Activated LED Output Driver Directly drives the activated LED.
- 9 5/12 Select Output This output can be used to control a power save feature. It should be connected, through a resistor, to the base of the external transistor which supplies power to pin 1.
- 10 Spare Input This TTL compatible input is user definable. The signal is inverted when read by the microprocessor.
- 11 INTR' Output TTL compatible interrupt signal to the microprocessor. An INTR' is generated for each STEP' input. The signal may be masked by the microprocessor.
- 12 WRITE ENABLE' Input Write enable input from the host system.
- 13 MOTOR ON' Input Motor on input from the host system.
- 14 T1 Output This TTL compatible output is toggled every other STEP' input.
- 15 STEP' Input Step input from the host system.

- 16 DIR' Input Direction input from the host system.
- 17 DS' Input Drive select input from the host system.
- 18 Track 0 Sensor Input Direct interface for optical sensor. This input has a minimum of 200 mV input hysterisis and 22K input resistance.
- 19 Insert Sensor Input Direct interface for optical sensor. This input has a minimum of 200 mV input hysteristis and 22K input resistance.
- 20 RC Control An external resistor and capacitor adjust the time out of an internal one-shot to control the index to data delay.
- 21 RC Control An external resistor and capacitor adjust the time out of an internal one-shot to control the width of the index pulse.
- 22 Index Sensor Input Direct interface for optical sensor. This input has a minimum of 200 mV input hysterisis and 22K input resistance.
- 23 Write Protect Sensor Input Direct interface for optical sensor. This input has a minimum of 200 mV input hysterisis and 22K input resistance.
- 24 PROG Input The negative transition of this TTL compatible input strobes commands to the SG82727 from the microprocessor; data are passed between the microprocessor and the SG82727 on the positive transition. This signal is directly compatible with the PROG output of an 8048 or 8049.
- 25 INDEX' This TTL compatible output provides the index pulse to the read/write circuit. It is gated with DS' (drive select).
- 26 WRPROT' Output Write protect output to the host system. Gated by DS' (drive select).
- 27 READY' Output Ready output to the host system. Gated by DS' (drive select).
- 28 TRACK0' Output Track 0 output to the host system. Gated by DS' (drive select).
- 29 READ DATA' Output Read data output to the host system. Gated by DS' (drive select).

SG82727

30 RD DATA Input — A TTL compatible input from the read/write circuit. This signal is the data from the disk. The SG82727 gates the data with DS' (drive select) and makes it available to the host system on pin 29.

31 WGATE' Output — This is a TTL compatible output to the read/write circuit. It is gated by WRITE ENABLE' (pin 12), DS' (drive select) and the input from the write protect sensor. It can be enabled by the microprocessor.

32 P20 — P20, P21, P22 and P23 form a 4 bit TTL compatible interface to the microprocessor. They are directly compatible with the lower 4 bits of port 2 of an 8048 or 8049.

- 33 P21 See pin 32.
- 34 P22 See pin 32.

- 35 P23 --- See pin 32.
- 36 ALE Clock Input A TTL compatible input used in conjunction with MTR clock output to generate a 300 Hz signal to control the speed of the spindle motor. The ALE clock of an 8048 or 8049 running at a 4.608 MHz clock rate may be input to this pin. The SG82727 will function without this input if spindle motor timing is generated from some other source.
- 37 MTR Clock Output TTL compatible output. See pin 36.
- 38 Ground Drive and device common.
- 39 Step Output 3 See pin 2.
- 40 Step Output 4 See pin 2.

	8048		FUNCTION	BITS		
COMMAND	PORT	DIRECTION	0	1	2	3
1	5	Read	Track Sensor	Write Prot. Sensor	Index Sensor F/F	Spare In.
2	6	Read	DIR	MOTOR ON	WENABLE	DS
3	7	Read	Insert Sensor			_
4	4	Write	S	TEPPING MOTO	R BIT PATTERN	
5	5.	Write	Preset INT	Clock INT	Act LED	12/5 Select
6	6	Write	Reset Index Sensor F/F	READY	TRACK 0	Enable WGATE
7	7	Write	5/12 Enable	Door Lock Solenoid	Spare Output	_

NOTE: 8048 instructions MOVD P,A and MOVD A,P select the SG82727. ORLD and ANLD instructions are ignored. P defines the 8048 port. A is the accumulator. Other microprocessors should send the appropriate command to the SG82727 as the PROG input is strobed.

SG82727

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNITS
Output High Voltage (WGATE', MTR Clock, INTR', T1	Voh	$I_{OH} = -400 \mu A$	3.5			Volts
Output Low Voltage	VOL	IOL = 4 mA		T	.4	Volts
High Level Output Current (INDEX', WR PROT', READY' TRACKO', READ DATA', SPARE ACLED, 5/12 Select)	ЮН	V _{OH} = 5V			250	μA
Low Level Output Current	IOL IOL		48			mA
Low Level Output Voltage	VOL	$I_{OL} = 48 \text{ mA}$.4	Volts
Output High Voltage (P20 — P23)	VOH	IOH = 400 μA	2.4		1	Volts
Output Low Voltage	VOL	$I_{OL} = 1.6 \text{ mA}$.45	Volts
Positive Going Threshold (DIR', STEP', DS', WENABLE', MOTOR ON', SPARE)	VT+		1.2	1.6	1.9	Volts
Negative Going Threshold	VT-		0.5	0.8	1.0	Volts
Input High Current	l'IN	VI = 2.7V			20	μA
Input Low Current	ΗL	$V_{I} = .4V$			-400	μA
Input High Voltage (ALE, PROG)	VIH		2			Volts
Input Low Voltage	VIL				0.8	Volts
High Level Input Current	ЧН	$V_{I} = 2.7V$			20	μA
Low Level Input Current	۱ _{۱۲}	V _I =.4V			-400	μA
Input High Voltage	VIH		2			Volts
Input Low Voltage	VIL				0.8	Volts
Input High Current	Чн				-500	μA
Input Low Current	11				400	μA
Comparator Positive Threshold (TRACKO SENSOR, WRITE PROT SENSOR, INDEX SENSOR, INSERT SENSOR)	VT+		1.6		2.2	Volts
Comparator Negative Threshold	VT-		1.1		1.7	Volts
Hystersis (V _T + V _T)	VHYS		200		600	mV
Input Resistance	RIN		17.6		26.4	KΩ
Input Current	¹ IN	$V_{IN} = 1.5V$	L	4		_μΑ
Output Low Voltage (Step 1 — Step 4)	VSATSINK	I = 275 mA			0.7	
Output High Voltage	VSATSOURCE				V ₁₂ V1.8	
Positive Clamp Voltage	V _D +	l = 275 mA			V _{12V} +1.2	
Negative Clamp Voltage	VD-	Ī = 275 mA	-1.2			Volts
Output High Voltage 5 Volt Mode (Solenoid Driver)	VSAT5V	I = 100 mA			V5V-2.6	
Output High Voltage	VSAT12V	I = 250 mA			V _{12V} -3.6	
Negative Clamp 12V Mode	VD-	I = 250 mA	-1.2			Volts

Min.

Min.

Max.

AC CHARACTERISTICS

tpp PROG' Pulse Width	2.03 µS	Min.
tCP Port Control Setup to PROG'	355 nS	Min.
tpc Port Control Hold to PROG'	669 nS	Min.
tDP Output Data Setup	1.15 µS	Min.

 tpp
 Output Data Hold
 276 nS

 tpF
 Input Data Hold from PROG'
 326 nS

 tpR
 PROG' to P2 Input Valid
 1.84 μS



SG82727 Timing Diagram

APPLICATIONS

8048 or 8049 Interface

The SG82727 may be directly connected with an 8048 or 8049 microprocessor. The P21 to P24 pins should be connected to bits 1 through 4 of port 2. The PROG' pin on the SG82727 should be connected to the same pin on the 8048 or 8049. At a clock rate above 4.608 MHz the SG82727 must be controlled from a standard I/O port with an appropriate software driver.

8051 Interface

The SG82727 can be controlled from any I/O port on the 8051. The following software driver subroutine assumes that the lower 4 bits of port 2 are connected to P21 through P24 and that bit 4 of port 2 is connected to the PROG' input of the SG82727. To call this driver the A register must contain the command and the R0 register the data for a write command. After execution the A register will have the data on both a read and a write.

DRIVER	URL	A, IUH	
	MOV	P2,A	;OUTPUT COMMAND
1	CLR	P2,4	SET PROG' LOW
	JB	ACC.2,WRITE	;IF BIT 2=1
			;WRITE,ELSE READ
READ	ORL	P2,0FH	SET P2 FOR INPUT
4	MOV	A,P2	;READ DATA
1	SETB	P2,4	;SET PROG' HIGH
1		RET	
WRITE	MOV	A,R0	PLACE DATA IN ACC
	ANL	A,0FH	;KEEP PROG'LOW
1	MOV	P2,A	WRITE DATA
1	SETB	P2,4	;SET PROG' HIGH
1	RET		

6500/1 Interface

The SG82727 can be controlled from any I/O port on the 6500/1. The following software driver subroutine assumes that the lower 4 bits of any port are connected to P21 through P24 and that bit 7 of that port is connected to the PROG' input of the SG82727. To call this driver the A register must contain the command and the X register the data for a write command. After execution the A register will have the data on both a read and a write.

DRIVER ORA #\$80

511121	STA	PORT	WRITE COMMAND TO
	AND	#\$0F	STROBE PROG' AND
	STA	PORT	,
	CMP	#\$04	;IF BIT 4 READ, ELSE ;WRITE
WRITE	BMI TXA	READ	;GO READ ;GET DATA IN A
	STA	PORT	WRITE DATA TO
OUT	ORA STA		SET PROG' HIGH
	AND RTS	#\$0F	CLEAN UP DATA
READ	LDA	#\$0F	;SET BITS 0-3 FOR ;INPUT
	STA LDA BPL		;GET DATA ;NOTE: BIT 7 IS A 0



POWER DRIVERS

High Current Output Drivers Switch Drivers Half Bridge Drivers Dual H Bridge Power Drivers Quad Darlington Drivers Motor Control Circuits Quad Drivers

Silicon General

ADVANCED DATA SG293D

LINEAR INTEGRATED CIRCUITS

Performance data described herein represent design goals. Final device specifications are subject to change.

QUAD BI-POLAR DRIVER

DESCRIPTION

The SG293D is a four channel high current high voltage bi-polar driver. It is designed to provide a dual H bridge interface between most standard logic families and fractional horsepower motor coils. The circuit has built in thermal protection and clamp diodes for inductive load suppression.

FEATURES

- 2 Full H bridges with clamp diodes
- · Current source and sink to 1.5 amps peak
- 40 Volts operation
- Thermal protection
- Chip enable
- 16 Pin dip package



SG293D





ABSOLUTE MAXIMUM RATINGS

ELECTRICAL CHARACTERISTICS (each channel)

 $V_{\rm S} = 24$ Volts, $V_{\rm SS} = 5$ Volts

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
V _{SS} Supply Current	I _{SS}				15	mA
V _S Supply Current	Is	$I_0 = 0$. 6	mA
"0" Input Current	I _{IN} (0)	Inputs = Gnd			100	μA
"1" Input Current	l _{IN} (1)	Inputs = 5.0V			10	μA
"0" Input Voltage	V ₁ (0)				0.8	Volt
"1" Input Voltage	V ₁ (1)		2.0			Volt
V _{CE} (Sat) Source	V _{OUT} (H)	I _{SOURCE} = 1.0 Amp			1.8	Volt
V _{CE} (Sat) Sink	V _{OUT} (L)	I _{SINK} = 1.0 Amp			1.8	Volt
Diode Forward Voltage	V _F	I _F = 1.0 Amp			1.8	Volt

SILICON GANAPAL LINEAR INTEGRATED CIRCUITS

ADVANCED DATA SG298D

Performance data described herein represent design goals. Final device specifications are subject to change.

QUAD BI-POLAR DRIVER

DESCRIPTION

The SG298D is a four channel high current high voltage bi-polar driver. It is designed to provide a dual H bridge interface between most standard logic families and fractional horsepower motor coils. The circuit has built in thermal protection and clamp diodes for inductive load suppression.

FEATURES

- 2 Full H bridges with clamp diodes
- · Current source and sink to 2.5 amps peak
- 46 Volts operation
- Thermal protection
- · Chip enable
- 15 sip package



SYMBOL	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Vs	Supply Voltage	Operative co	Operative condition			46	v
V _{SS}	Logic Supply Voltage			4.5		7	V
ls	Quiescent Supply Current	V _{inh} = H	V ₁ = L		3	5	
-		I _L = 0	$V_i = H$		15	20	mA
		V _{inh} = L				1	
Iss	Quiescent Current from VSS	V _{inh} = H	$V_I = L$		5	8	
	-	I _L = 0	$V_I = H$		1.5	2	mA
	V _{inh} = L			1	1.5		
VIL	Input Low Voltage			- 0.3		1.5	v
VIH	Input High Voltage			2.3		V _{SS}	v
ηL	Low Voltage Input Current	V _I = L				- 10	μA
<u>,</u> н	High Voltage Input Current	V ₁ = H			30	100	
V _{inh} L	Inhibit Low Voltage			- 0.3		1.5	v
V _{inh} H	Inhibit High Voltage			2.3		7	v
I _{inh} L	Low Voltage Inhibit Current	V _{inh} = L				- 10	μΑ
I _{inh} H	High Voltage Inhibit Current	$V_{inh} H = \leq V_{SS}06V$			30	100	
V _{CE sat (H)}	Source Saturation Voltage	ا _ل = 1A			1.2	1.6	v
		I _L = 2A			1.8	2.6	v v
V _{CE sat (L)}	Sink Saturation Voltage	I _L = 1A			1.2	1.6	
		I _L = 2A			1.7	2.4	V
V _{CE sat}	Total Drop	I _L = 1A				3.2	
		I _L = 2A		1		4.8	v
VSENS	Sensing Voltage			-1		2	v
T ₁ (V _I)	Source Current Turn Off Delay	0.5 V _I to 0.9) IL		1.7		μS
T ₂ (V _I)	Source Current Fall Time	0.9 I _L to 0.1	۱		0.2		μS
T ₃ (V _I)	Source Current Turn On Delay	0.5 V ₁ to 0.1	 ار		2.5		μS

PACKAGE



Silicon General

LINEAR INTEGRATED CIRCUITS

SG1627 / SG2627 / SG3627

DUAL HIGH-CURRENT OUTPUT DRIVER

DESCRIPTION

The SG1627 series devices are monolithic, high-speed driver integrated circuits designed to interface digital control logic with high current loads. Each device contains two independent drivers which will either source or sink up to 500 mA of current. The sink transistor is designed as a saturating switch while the source transistor can be used either as a switch or as a constant current generator with external resistor programming.

Each half of this device contains both inverting and non-inverting inputs which have two volt thresholds for high noise immunity. Either input can be used alone to switch the output, or one input can be strobed with the other. These units have been designed to directly interface with the SG1524 Regulating Pulse Width Modulator Circuit.

These devices are supplied in ceramic 16-pin D.I.L. packages. The SG1627 is specified for operation over a -55°C to +125°C temperature range while the SG2627 and SG3627 are intended for industrial applications of 0°C to +100°C.

FEATURES

- Two independent driver circuits
- Outputs will source or sink currents to 500 mA
- 100 nSec response time
- Full compatibility with SG1524 PWM circuit
- · Constant current drive capability
- Two volt threshold for high noise immunity
- Source and sink can be separated for complementary outputs



CHIP LAYOUT



CONNECTION DIAGRAM (TO-116 OUTLINE) (TOP VIEW)



SG1627/SG2627/SG3627

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, VCC SG1627, 2627	30V
3627	20V
Output Collector Voltage SG1627, 2627	30V
SG362	7 20V
Source or Sink Current, DC	500 mA
Peak Current (<2% duty cycle)	1A
Input Voltage	5.5V
Input Current	10 mA
Avg. Total Power Dissipation (Note 1)	1000 mW
Derate Above 50° C	10 mW/° C

 Operating Junction Temperature Range

 SG1627
 -55° C to +125° C

 SG2627 & 3627
 0° C to +100° C

Storage Temperature Range

−65° to +150°C

Note 1: Total power dissipation is the sum of the control logic power plus the power of each source and sink output transistor, factored duty cycle.

ELECTRICAL CHARACTERISTICS

Unless otherwise stated, these specifications apply for $T_J=-55^\circ\,C$ for the SG1627 and 0°C to $+100^\circ\,C$ for the SG2627 and 3627. VCC = 5V.

PARAMETER	CONDITIONS	MIN	түр	MAX	UNITS
High-Level Input Voltage		2.8	-	5.5	Volts
Low-Level Input Voltage		0	-	1.4	Volts
Input Threshold		-	2.0	_	Volts
Low-Level Input Current	V ₁ = 0	_	-1.0	-2.0	mA
Source Off, Leakage Current	Collector $V = V_{max}$	-	0.3	1.0	mA
Source On, Collector Sat.	I _{source} = 50 mA	-	1.1	1.7	Volts
(Source Emitter Grounded,	I _{source} = 300 mA	-	1.2	1.9	Volts
R _{SC} = 0)	I _{source} = 500 mA	-	1.3		Volts
Source On, Emitter Voltage	I _{source} = -50 mA	(V _{cc} -3V)	-	-	Volts
Sink Off, Leakage Current	Collector $V = V_{max}$	-	1.0	100	μΑ
	l _{sink} ≈ 50 mA	-	0.2	0.4	Volts
Sink On, Collector Sat.	I_{sink} = 300 mA, V _{CC} = 20V		0.5	0.7	Volts
	I _{sink} = 500 mA, I _{boost} = 25 mA		0.5		Volts
Current Limit Sense Voltage	$R_{SC} = 10\Omega, T_{A} = 25^{\circ}C$	600	700	900	mV
Sense Voltage Temp. Coef.	R _{SC} = 10Ω	_	1.8	-	mV/ºC
Supply Current	V _{CC} = 5V		15	22	mA
(Both sink transistors on)	V _{CC} = 20V		50	73	mA
	V _{CC} = 30V (ex. 3627)		80	115	mA
Output Response, Turn On	Fig. 4, RL = 24Ω, TA = 25°C		50	-	nS
Output Response, Turn Off	Fig. 4, R _L = 24Ω, T _A = 25°C	-	100		nS
Thermal Resistance θ_{JA}		-	80	110	°C/W
Thermal Resistance θ_{JC}			45	60	oC/M

TOTEM POLE OUTPUT SWITCH CIRCUIT







SOURCE TRANSISTOR SATURATION



100 Source and Sink Collector Currents are not included ₹ ⁸⁰ TJ = 25°C Current 60 Sink Viddo 8 40 One Sint 20 Both Sink Transistors Of 25 10 15 20 30 VCC Supply Voltage - V

V_{CC} SUPPLY CURRENT vs. VOLTAGE

SINK TRANSISTOR SATURATION



DYNAMIC RESPONSE (See Figure 4 for Test Circuit, $R_L = 24\Omega$)





SG1627 / SG2627 / SG3627



Figure 1. Basic 300 mA switched drive circuit. If the external output transistor is to be on when the driving transistor is on, use the inverting input with the non-inverting input left open. For opposite phasing, use the non-inverting input with the inverting input grounded.



Figure 3. Additional source current or power handling capability may be added with the use of an external PNP transistor. For optimum performance, a low storage-time unit should be selected. If current limiting is not required, an NPN emitter follower could also be used for source boost.



Figure 5. Source and sink transistors can be used separately for an efficient transformer driver. Here the source provides constant current drive with magnetic reset accomplished by a flux champ utilizing the sink transistor. With the source current sense terminal connected to ground, there will be a residual collector current of approximately 300µA. If this is objectionable, insert a diode between current sense and ground.



Figure 2. Use of higher input voltage provides greater drive for higher sink-transistor peak current while R2 provides constant source current. R1 heips minimize power in the SG1627. Although the sink emitter may be connected to a different ground point from pin 5, any voltage differences between them will directly affect the input threshold level.



Figure 4. Source and sink transistors can be used separately for complementary outputs. At low supply voltages the sink current is limited to approximately 100mA, but if current limiting is not required sink drive boost may be added with R1. The current in R1 should be .05 times the sink load current to insure saturation.



Figure 6. Simultaneous conduction of the output switching transistors can be positively prevented by using diodes to cross-couple a gating signal into the non-inverting inputs. For maximum power handling capability, the source transistor is driven into saturation with the current limiting provided by R1.

See Applications Notes for additional information.

Data subject to change without notice.

SILICON GENERAL LINEAR INTEGRATED CIRCUITS

SG1629/SG3629

HIGH-CURRENT FLOATING SWITCH DRIVER

DESCRIPTION

The SG1629 and SG3629 are monolithic integrated circuits designed to generate the positive and negative base drive currents (lb1 and lb2) required for high-speed, high power switching transistors. These units are intended to interface between the secondary of a drive transformer and the base of an NPN switching device. Positive drive current can be made constant with an external programming resistor, or can be clamped with a diode to keep the switching device out of saturation. Negative turn-off current is derived from a negative voltage generated in an external capacitor. All operating power is supplied by the transformer secondary and these devices can be floated at high levels with respect to ground for off-line, bridge converters.

For medium power applications, these units are available in 10-pin, TO-100 package; while high power capability is offered in a 9-pin, TO-66 case. In either package, the SG1629 is specified for operation over an ambient temperature range of -55°C to +125°C while the SG3629 is intended for industrial applications of 0 to 70°C.

FEATURES

- Self-generating positive and negative currents
- Constant source current (I_{b1}) to one amp
- Two amp peak sink current (Ib2) to negative voltage
- Floating operation
- Baker clamp input for non-saturated switching
- Provisions for source and sink gating
- 100 nanosecond response





ABSOLUTE MAXIMUM RATINGS

Input Voltage + or - Inputs	20V
Collector to Emitter Voltage, Source	
or Sink	20V
Source Current	2.0 A
Sink Current	3.0 A
Sink Rectifier Current (peak)	2.0 A
Average Total Power Dissipation (No	ote 1)
R-Package (TO-66)	3000 mW
Derate above 50 ^o C	24 mW/ºC
T-Package (TO-100)	680 mW
Derate above 50 ⁰ C	5.4 mW/°C

Operating Junction Temperat	ure Range
SG1629	-55°C to +150°C
SG3629	0°C to +125°C
Storage Temperature Range	-65°C to +175°C

Note 1: Total power dissipation must include the power in both source and sink transistors times the duty cycle for each.

ELECTRICAL CHARACTERISTICS

Unless otherwise stated, these specifications apply for $T_J = -55^{\circ}C$ to +150°C for the SG1629 and 0°C to 125°C for the SG3629.

PARAMETER	CONDITIONS			ТҮР	МАХ	UNITS
Collector to Emitter Voltage Source or Sink	V _{BE} =	0	20	30	1	Volts
Collector to Emitter Leakage Source or Sink	V _{BE} = 0, V _{CE}	<u>=</u> = 15V	-	5	100	μA
Input Leakage V+ to V-	Input Voltage	= +15V		1	100	μA
Input Leakage V- to V+	Input Voltage	= -15V	-	2	4	mA
Standby Current from Sink Emitter Voltage	Sink Emitter = -5V $1k\Omega$ from -V _{IN} to Sink Drive Source Emitter Connected to Sink Collector +V _{IN} = -V _{IN} = 0V			5	10	mA
Clamp Current	+V _{IN} = 15V V clamp = 0V			15	20	mA
	I source = 100 mA (T-Package)			1.7	-	Volts
Source Saturation Voltage	l source = 500 mA	-	1.8	-	Volts	
	I source = 1A	Т _Ј = 25 ⁰ С		2.0	3	Volts
Sink Saturation Voltage	I sink = 100 mA (T-Package)			1.2	_	Volts
Force beta = 100	I sink = 500 mA (R-Package)			1.3		Volts
	$I sink = 1A$ $T_J = 25^{\circ}C$			1.5	2	Volts
Sink Current Gain	1 sink = 2A, V	CE = 3V	300	500		
Current Limit Sense Voltage	R _{SC} = 0.7Ω	Г _Ј = 25 ⁰ С	0.55	0.65	0.80	Volts
Sink Rectifier Forward Voltage	I _F = 1A T _J	= 25 ^o C		1.0	2.0	Volts
Sink Gate Output Saturation	Sink Drive = 10 mA Sink Gate Input Current = 1 mA			0.2	0.4	Volts
Source Response	I source = 1A		~	100	-	nS
Sink Response	I sink = 1A		-	100	_	nS
		θJA	-	40	_	°C/W
Thermal Resistance	R-Package	θJC		5	-,	°C/W
Thermal Resistance	T-Package	θJA		150	-	°C/W
L		θJA		25	-	°C/W

SG1629/SG3629



SG1629/SG3629



Silicon General

SG1635A/3635A SG1635/SG3635

LINEAR INTEGRATED CIRCUITS

TWO-AMP, HALF-BRIDGE DRIVER

DESCRIPTION

The SG1635 and SG3635 are monolithic integrated circuits designed to interface low-level, logic signals with high-current, inductive or capacitive loads. These devices are particularly adept at high speed pulse width modulation for motor drives or Class D audio amplifiers, and when used in pairs, they can provide full bridge drive for bi-directional control.

With TTL compatible inputs, these devices will either source or sink up to 5 amps of peak current with interlock protection to insure that source and sink cannot be on simultaneously. Additional protection is provided by thermal shutdown of the source output if the chip temperature rises above 160 °C. High speed internal commutating diodes are also included.

FEATURES

- · Source or sink five amps peak
- 100 nanosecond response
- Half-bridge with internal diodes
- TTL input compatibility
- Either dual or tri-state output
- Direct PWM motor drive from microprocesser
- Built-in thermal protection

TRUTH TABLE

Enable	Pulse	Output
1	1	Off (High with no load)
0	1	High
1	0	Low
0	0	High

(1= open or high)

LOGIC DIAGRAM





CHIP LAYOUT

ABSOLUTE MAXIMUM RATINGS

Input supply voltage,		Operating junction	Av
SG1635/3635, VS	35V	temperature range	
SG1635A/3635A, VS	40V	SG1635/1635A -55 °C to + 150 °C	
Peak output current	5A	SG3635/3635A - 0 °C to + 125 °C	
Continuous output current	2A	Storage temperature	
Peak diode current	5A	range -65 °C to + 150 °C	
		•	

Average total power dissipation without heat sink (Note 1) P-Package (TO-220) 2W Derate above 50 °C 20mW/°C R-Package (TO-66) 3W Derate above 50 °C 30mW/°C NOTE 1: Total power dissipation must include power in both source and sink plus diodes, with factors for duty cycle.

ELECTRICAL CHARACTERISTICS

Unless otherwise stated, VS = 24V VE = 2V, VP = 2V, and $T_J = -55^{\circ}$ C to +125°C for the SG1635 and 0°C to 70°C for the SG3635. Input limits apply to either Enable or Pulse inputs.

PARAMETER	TEST	TEST CONDITION		TYP.	MAX.	UNITS
Input Voltage	I _{IN} = O		1.0	1.8	2.5	V
Input High Current	$V_{IN} = 4.5V$		-	3	200	μA
Input Low Current	VIN = OV			- 1	- 3.2	mA
Input Threshold			0.8	1.2	2.0	V
Output High Leakage	$V_0 = 24V$		-	1.0	500	μA
Output Low Leakage	$V_0 = 0V$		-	20	40	mA
Source Saturation	V _E = 0.8V, I ₀ =	– 100mA	-	1.4	2	v
V _S -V _{OH}	$V_{\rm E} = 0.8V, I_0 = -$	- 2A	- 1	2.0	3	v
Sink Saturation	VP = 0.8V, I ₀ =	100mA		0.8	2	v
VOL	Vp = 0.3V, I0 =	2A	- 1	2.0	3	V
Source Diode Forward Voltage	$I_D = 2A$	$I_D = 2A$			3	V
Sink Diode Forward Voltage	í _D = 2A		-	1.8	3	V
	SG1635A/3635A	V _S = 40V	<u> </u>	10	25	mA
		V _{OH} , V _E = OV	-	10	25	mA
		V _{OL} , V _P = OV		27	70	mA
Supply Current	SG SG1635/3635	$V_{\rm S} = 35V$		10	25	mA
		V _{OH} , V _E = OV		10	25	mA
		$V_{OL}, V_P = V$	- 1	27	65	mA
	P-pkg 0	JA		60	70	°C/W
Thermal Resistance	θ	JC		3.0	5.0	°C/W
	B-pkg 0	JA	-	40	50	°C/W
	θ	JC	—	4.0	6.0	°C/W

SWITCHING CHARACTERISTICS See test circuit, TJ = 25°C.

PARAMETER		TEST CONDITION				MAX.	UNITS
	Turn on	Delay Time	^t PDHL	-	50	_	nSec
Pulse Switching		Transition Time	t PTHL		200	_	nSec
Characteristics	Turn off	Delay Time	t PDLH	_	100	_	nSec
		Transition Time	tPTLH	-	100	_	nSec
Enable Switching Characteristics	Turn on	Delay Time	t EDLH	_	200	_	nSec
		Transition Time	tetlh		100	_	nSec
	Turn off	Delay Time	tEDHL	_	100	-	nSec
		Transition Time	tETHL	-	100	_	nSec

SG1635A/SG3635A SG1635/SG3635





SG1635A/SG3635A SG1635/SG3635





Silicon General

LINEAR INTEGRATED CIRCUITS

SERIES 2000

HIGH VOLTAGE, HIGH CURRENT DRIVER ARRAYS

DESCRIPTION

These high voltage, medium current driver arrays are comprised of seven silicon NPN Darlington pairs on a common monolithic substrate. All units feature open collector outputs and integral suppression diodes for inductive loads. Peak inrush currents to 600 mA are allowable, making these devices ideal for driving tungsten filament lamps.

Five different input configurations provide optimized designs for interfacing with TTL, DTL, PMOS or CMOS drive signals.

In all cases, the individual Darlington pair collector current rating is 500 mA. However, outputs may be paralleled for higher load current capability. All devices are supplied in a 16-pin dual in-line ceramic package.

FEATURES

- Collector currents to 600 mA
- Low saturation voltage
- High speed switching
- Closely matched parameters
- Plastic and hermetic packages



SERIES 2000

SG2001 through SG2005 Electrical Characteristics (Parameters are specified at $T_A = +25^{\circ}$ C unless otherwise noted)

		APPLICABLE		L	IMITS	MITS	
CHARACTERISTIC	SYMBOL	DEVICES	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Output Leakage Current	CEX	ALL	$V_{CE} = 50V, T_{A} = 25^{\circ}C$	-	—	50	μA
			$V_{CE} = 50V, T_{A} = 70^{\circ}C$	-	-	100	μA
		SG2002	$V_{CE} = 50V, T_{A} = 70^{\circ}C, V_{IN} = 6.0V$	-	—	500	μA
		SG2004	$V_{CE} = 50V, T_{A} = 70^{\circ}C, V_{IN} = 1.0V$	-	—	500	μA
Collector-Emitter	V _{CE(SAT)}	ALL	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 250 \mu\text{A}$	-	0.9	1.1	v
Saturation Voltage			$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 350 \mu\text{A}$		1.1	1.3	V
			$I_{\rm C} = 350 \text{ mA}, I_{\rm B} = 500 \mu\text{A}$		1.3	1.6	v
Input Current	IN(ON)	SG2002	$V_{IN} = 17V$		0.82	1.25	mA
		SG2003	$V_{IN} = 3.85V$	-	0.93	1.35	mA
		SG2004	$V_{IN} = 5.0V$	-	0.35	0.5	mA
			$V_{IN} = 12V$	-	1.0	1.45	mA
		SG2005	V _{IN} = 3.0V	—	1.5	2.4	mA
$I_{IN(OFF)}$ ALL $I_{C} = 500 \mu A, T_{A} = 70^{\circ} C$ 50	65	_	μA				
Input Voltage	V _{IN(ON)}	SG2002	$V_{CE} = 2.0V, I_{C} = 300 \text{ mA}$	-	—	13	V
	(- · ·)	SG2003	$V_{CE} = 2.0V, I_{C} = 200 \text{ mA}$	—	—	2.4	V
			$V_{CE} = 2.0V, I_{C} = 250 \text{ mA}$		-	2.7	V
			$V_{CE} = 2.0V, I_{C} = 300 \text{ mA}$		—	3.0	V
		SG2004	$V_{CE} = 2.0V, I_{C} = 125 \text{ mA}$	-	-	5.0	v
			$V_{CE} = 2.0V, I_{C} = 200 \text{ mA}$	-	-	6.0	V
			$V_{CE} = 2.0V, I_{C} = 275 \text{ mA}$	-	—	7.0	v
			$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	-	—	8.0	v
		SG2005	$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	-	-	2.4	V
D-C Forward Current Transfer Ratio	h _{FE}	SG2001	$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	1000	-	-	
Input Capacitance	C _{IN}	ALL		-	15	25	pF
Turn-On-Delay	^t PLH	ALL	0.5 E _{IN} to 0.5 E _{OUT}		0.25	1.0	µSec.
Turn-Off Delay	^t PHL	ALL	0.5 EIN to 0.5 EOUT	-	0.25	1.0	µSec.
Clamp Diode	^I B	ALL	$V_{R} = 50V, T_{A} = 25^{\circ}C$	—	—	50	μA
Leakage Current			$V_{R} = 50V, T_{A} = 70^{\circ}C$	-	—	100	μA
Clamp Diode Forward Voltage	V _F	ALL	I _F = 350 mA	_	1.7	2.0	y

SG2011 through SG2015 Electrical Characteristics (Parameters are specified at ${\sf T}_{\sf A}=+25^{\circ}{\rm C}$ unless otherwise noted)

		APPLICABLE		LIMITS			
CHARACTERISTIC	SYMBOL	DEVICES	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Output Leakage Current	ICEX	ALL	$V_{CE} = 50V, T_{A} = 25^{\circ}C$	-	-	50	μA
			$V_{CE} = 50V, T_{A} = 70^{\circ}C$	-	-	100	μA
		SG2012	$V_{CE} = 50V, T_A = 70^{\circ}C, V_{IN} = 6.0V$	-	-	500	μA
		SG2014	$V_{CE} = 50V, T_A = 70^{\circ}C, V_{IN} = 1.0V$	-	-	500	μA
Collector-Emitter VC	V _{CE(SAT)}	ALL	$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 350 \mu\text{A}$		1.1	1.3	V
Saturation Voltage			$I_{\rm C} = 350 \text{ mA}, I_{\rm B} = 500 \mu\text{A}$	-	1.3	1.6	V
			$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 600 \mu\text{A}$	_	1.7	500 1.3 1.6 1.9 2 1.25 3 1.35 5 0.5	v
Input Current	IN(ON)	SG2012	$V_{ N} = 17V$		0.82	1.25	mA
		SG2013	V _{IN} = 3.85V	_	0.93	1.35	mA
		SG2014	$V_{IN} = 5.0V$	-	0.35	0.5	mA
			$V_{IN} = 12V$	-	1.0	1.45	mA
		SG2015	$V_{ N} = 3.0V$		1.5	2.4	mA
	IN(OFF)	ALL	$I_{\rm C} = 500 \ \mu \text{A}, \ T_{\rm A} = 70^{\circ} \text{C}$	50	65	-	μA
SERIES 2000

Input Voltage	V _{IN(ON)}	SG2012	$V_{CE} = 2.0V, I_{C} = 500 \text{ mA}$		-	17	v
		SG2013	$V_{CE} = 2.0V, I_{C} = 250 \text{ mA}$			2.7	V
	-		$V_{CE} = 2.0V, I_{C} = 300 \text{ mA}$	-	1	3.0	v
			$V_{CE} = 2.0V, I_{C} = 500 \text{ mA}$	-	-	3.5	v
		SG2014	$V_{CE} = 2.0V, I_{C} = 275 \text{ mA}$	—	1	7.0	V
			$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	-	—	8.0	v
			$V_{CE} = 2.0V, I_{C} = 500 \text{ mA}$	·—-	—	9.5	V
		SG2015	$V_{CE} = 2.0V, I_{C} = 500 \text{ mA}$	-	—	2.6	v
D-C Forward Current	h _{FE}	SG2011	$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	1000		_	
Transfer Ratio			$V_{CR} = 2.0V, I_C = 500 \text{ mA}$	900			
Input Capacitance	C _{IN}	ALL		—	15	25	pF
Turn-On Delay		ALL	0.5 E _{IN} to 0.5 E _{OUT}		0.25	1.0	µSec.
Turn-Off Delay	tPHL	ALL	0.5 E _{IN} to 0.5 E _{OUT}		0.25	1.0	µSec.
Clamp Diode	1 _B	ALL	$V_{R} = 50V, T_{A} = 25^{\circ}C$		—	50	μA
Leakage Current			$V_{R} = 50V, T_{A} = 70^{\circ}C$	-		100	μA
Clamp Diode	V _F	ALL	I _F = 350 mA		1.7	2.0	v
Forward Voltage	•		$I_{\rm F} = 500 {\rm mA}$	-	2.1	2.5	v

SG2021 through SG2025 Electrical Characteristics (Parameters are specified at $T_A = +25^{\circ}C$ unless otherwise noted)

		APPLICABLE			LIMITS		
CHARACTERISTIC	SYMBOL	DEVICES	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Output Leakage Current	^I CEX	ALL	$V_{CE} = 95V, T_{A} = 25^{\circ}C$	-	-	50	μA
			$V_{CE} = 95V, T_{A} = 70^{\circ}C$	-	-	100	μA
		SG2022	$V_{CE} = 95V, T_{A} = 70^{\circ}C, V_{IN} = 6.0V$	-	—	500	μA
		SG2024	$V_{CE} = 95V, T_A = 70^{\circ}C, V_{IN} = 1.0V$	-	-	500	μA
Collector-Émitter	V _{CE(SAT)}	ALL	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 250 \mu\text{A}$	-	0.9	1.1	v
Saturation Voltage			$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 350 \mu\text{A}$		1.1	1.3	V
			$I_{\rm C} = 350 \text{ mA}, I_{\rm B} = 500 \mu\text{A}$		1.3	1.6	v
Input Current	IN(ON)	SG2022	V _{IN} = 17V	-	·0.82	1.25	mA
		SG2023	V _{IN} = 3.85V	-	0.93	1.35	mA
		SG2024	V _{IN} = 5.0V	—	0.35	0.5	mA
			$V_{IN} = 12V$	_	1.0	1.45	mA
		SG2025	$V_{1N} = 3.0V$	-	1.5	2.4	mA
	IN(OFF)	ALL	$I_{\rm C} = 500 \ \mu {\rm A}, \ T_{\rm A} = 70^{\circ} {\rm C}$	50	65	-	μA
Input Voltage	VIN(ON)	SG2022	$V_{CE} = 2.0V, I_{C} = 300 \text{ mA}$	-	—	13	v
		SG2023	$V_{CE} = 2.0V, I_{C} = 200 \text{ mA}$	—	-	2.4	V
			$V_{CE} = 2.0V, I_{C} = 250 \text{ mA}$	-	-	2.7	v
			$V_{CE} = 2.0V, I_{C} = 300 \text{ mA}$	-		3.0	V
		SG2024	$V_{CE} = 2.0V, I_{C} = 125 \text{ mA}$		-	5.0	v
			$V_{CE} = 2.0V, I_{C} = 200 \text{ mA}$	-	-	6.0	v
			$V_{CE} = 2.0V, I_{C} = 275 \text{ mA}$		-	7.0	v
			$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	-	—	8.0	v
		SG2025	$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	-	—	2.4	v
D-C Forward Current Transfer Ratio	h _{FE}	SG2021	$V_{CE} = 2.0V, I_{C} = 350 \text{ mA}$	1000	-	-	
Input Capacitance	CIN	ALL		-	15	25	pF
Turn-On Delay	t _{PLH}	ALL	0.5 E _{IN} to 0.5 E _{OUT}	-	0.25	1.0	µSec.
Turn-Off Delay	^t PHL	ALL	0.5 E _{IN} to 0.5 E _{OUT}	-	0.25	1.0	µSec.
Clamp Diode	¹ 8	ALL.	$V_{R} = 95V, T_{A} = 25^{\circ}C$		-	50	μA
Leakage Current		_	$V_{R} = 95V, T_{A} = 70^{\circ}C$		-	100	μΑ
Clamp Diode Forward Voltage	V _F	ALL	I _F = 350 mA	_	1.7	2.0	v

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DEVICE	VCE MAX	IC MAX	LOGIC INPUTS	DEVICE	VCE MAX	IC MAX	LOGIC INPUTS
SG2001	50V	500mA	General Purpose	SG2014	50V	600mA	6-15V CMOS, PMOS
	······································		PMOS, CMOS	SG2015	50V	600mA	High Output TTL
SG2002	50V	500mA	14-25V PMOS	SG2021	95V	500mA	General Purpose
SG2003	50V	500mA	5V TTL, CMOS	001021			PMOS, CMOS
SG2004	50V	500mA	6-15V CMOS, PMOS	SG2022	95V	500mA	14-25V PMOS
SG2005	50V	500mA	High Output TTL	SG2023	95V	500mA	5V TTL, CMOS
SG2011	50V	600mA	General Purpose	SG2024	95V	500mA	6-15V CMOS, PMOS
			PMOS, CMOS	SG2025	95V	500mA	High Output TTL
SG2012	50V	600mA	14-25V PMOS				
SG2013	50V	600mA	5V TTL. CMOS				

Silicon General

LINEAR INTEGRATED CIRCUITS

SG2064 THRU SG2077

QUAD 1.5 AMP DARLINGTON SWITCHES

DESCRIPTION

These high-voltage, high-current Darlington arrays are monolithic bipolar devices especially designed for interfacing low-level control logic and peripheral loads such as relays, solenoids, DC and stepping motors; multiplexed LED and incandescent displays; and heaters. The logic inputs are designed to be compatible with TTL, DTL, LSTTL, CMOS and NMOS logic families. Several of the arrays include integral clamp diodes for driving inductive loads, and breakdown voltage ratings to 80 volts are available.

All devices are supplied in a modified 16-lead plastic dual-in-line package. A copper alloy lead frame with webbing between the central pins provides low thermal resistance to ambient air, and allows a 2.8 watt total power dissipation rating within a standard footprint.

These devices are direct replacements for ULN-2064B thru ULN-2077B devices.

FEATURES

- · Four power drivers per package
- 1.5 amp collector currents
- 80 and 50 volt BVCEX ratings
- Integral clamp diodes for inductive loads
- · Compatibility with all popular logic families
- Low internal parasitics



SG2064 THRU SG2077

ABSOLUTE MAXIMUM RATINGS (Note 1)

Logic Input Voltage	See Selection Guide	Power Dissipation at $T_A = +25^{\circ}C$ (Note 2)	2.77W
Logic Input Current	25mA	Thermal Resistance: junction to ambient	45° C/W
Supply Voltage		Operating Junction Temperature	+150° C
SG2068, 2069 SG2070, 2071	10V 20V	Operating Ambient Temperature Range 0°	°C to +70°C
Output Voltage	See Selection Guide	°	C to +125° C
Output Current	1.75A	Lead Temperature (Soldering, 10 seconds)	+300° C

Note 1. Values beyond which damage may occur. Note 2. Derate at 22.2 mW/°C for ambient temperatures above +25°C.

SELECTION GUIDE

DEVICE	VCEX MAX	VCE (SUS) MAX	VIN MAX	LOGIC INPUTS
SG2064W	50V	35V	15V	TTL, DTL, Schottky TTL,
SG2065W	80V	50V	15V	5V CMOS and NMOS
SG2066W	50V	35V	30V	6 to 15V CMOS
SG2067W	80V	50V	30V	and PMOS
SG2068W	50V	35V	15V	TTL, DTL, Schottky TTL,
SG2069W	80V	50V	15V	5V CMOS and NMOS
SG2070W	50V	35V	30V	6 to 15V CMOS
SG2071W	80V	50V	30V	and PMOS
SG2074W	50V	35V	30V	
SG2075W	80V	50V	60V	General Purpose
SG2076W	50V	35V	30V	6 to 15V CMOS
SG2077W	80V	50V	60V	and PMOS

SG2064 THRU SG2067 ELECTRICAL CHARACTERISTICS

(Parameter limits are specified at $T_A = +25^{\circ}$ C unless otherwise noted.)

PARAMETER	DEVICES	CONDITIONS	MIN	MAX	UNITS
Output Leakage Current	SG2064/66	$V_{CE} = 50V$		100	μA
		V _{CE} ≈ 50V, T _A = 70°C		500	μA
	SG2065/67	V _{CE} = 80V		100	μA
		V _{CE} = 80V, T _A = 70°C		500	μA
Output Sustaining Voltage	SG2064/66	I _C ≈ 100 mA, V _{IN} = 0.4V	35		V
	SG2065/67	I _C = 100 mA, V _{IN} = 0.4V	50		V
Collector-Emitter	All	$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 625 μ A		1.1	V
Saturation Voltage		$I_{C} = 750 \text{ mA}, I_{B} = 935 \mu\text{A}$		1.2	V
		I _C = 1.0 A, I _B = 1.25 mA		1.3	V
	SG2064/66	I _C = 1.25 A, I _B = 2.0 mA		1.4	V
	SG2065/67	I _C = 1.5 A, I _B = 2.25 mA		1.5	V
Input Current	SG2064/65	$V_{IN} = 2.4V$	1.4	4.3	mA
		$V_{IN} = 3.75V$	3.3	9.6	mA
	SG2066/67	V _{IN} = 5.0V	0.6	1.8	mA
		V _{IN} = 12V	1.7	5.2	mA
Input Voltage	SG2064/65	V _{CE} = 2.0V, I _C = 1.0 A		2.0	V
		V _{CE} = 2.0V, I _C = 1.5 A		2.5	V
	SG2066/67	V _{CE} = 2.0V, I _C = 1.0 A		6.5	V
		V _{CE} = 2.0V, I _C = 1.5 A		10	V
Turn-On Delay	All	0.5 E _{in} to 0.5 E _{out}		1.0	μS
Turn-Off Delay	All	0.5 E _{in} to 0.5 E _{out}		1.5	μS
Clamp Diode	SG2064/66	V _R = 50V		50	μA
Leakage Current		V _R = 50V, T _A = 70°C		100	μA
	SG2065/67	$V_{R} = 80V$		50	μA
		$V_{R} = 80V, T_{A} = 70^{\circ}C$		100	μA
Clamp Diode	All	I _F = 1.0 A		1.75	V
Forward Voltage	}	$I_{\rm F} = 1.5 {\rm A}$		2.0	V

SG2064 THRU SG2077

SG2068 THRU SG2071 ELECTRICAL CHARACTERISTICS

(Parameter limits are specified at $T_A = +25^{\circ}C$ unless otherwise noted.)

PARAMETER	DEVICES	CONDITIONS	MIN	MAX	UNITS
Output Leakage Current	SG2068/70	V _{CE} = 50V	T	100	μA
Output Leakage Garrent		$V_{CE} = 50V, T_A = 70^{\circ}C$		500	μA
	SG2069/71	$V_{CE} = 80V$		100	μA
	JG2000//	$V_{CE} = 80V, T_A = 70^{\circ}C$		500	μA
Output Sustaining Voltage	SG2068/70	$I_{\rm C} = 100 {\rm mA}, V_{\rm IN} = 0.4 {\rm V}$	35		V
Output outlanding to the	SG2069/71	$I_{\rm C}$ = 100 mA, $V_{\rm IN}$ = 0.4V	50		V
Collector-Emitter	SG2068/69	$I_{\rm C} = 500 {\rm mA}, V_{\rm IN} = 2.75 V$		1.1	V
Saturation Voltage		I _C = 750 mA, V _{IN} = 2.75V		1.2	V
	}	$I_{\rm C} = 1.0 \text{A}, V_{\rm IN} = 2.75 \text{V}$		1.3	V
		$I_{C} = 1.25 \text{ A}, V_{IN} = 2.75 \text{V}$		1.4	V
	SG2069	$I_{\rm C} = 1.5 \text{A}, V_{\rm IN} = 2.75 \text{V}$		1.5	V
	SG2070/71	$I_{\rm C} = 500 {\rm mA}, V_{\rm IN} = 5.0 {\rm V}$		1.1	V
		$I_{C} = 750 \text{ mA}, V_{1N} = 5.0 \text{ V}$		1.2	V
	1	IC = 1.0 A, VIN = 5.0V		1.3	V
	1	$I_{\rm C} = 1.25 \text{A}, V_{\rm IN} = 5.0 \text{V}$		1.4	V
	SG2071	I _C = 1.5 A, V _{IN} = 5.0V		1.5	V
Input Current	SG2068/69	V _{IN}		550	μΑ
		$V_{IN} = 3.75V$		1000	μΑ
	SG2070/71	$V_{1N} = 5.0V$		400	μA
		$V_{\rm IN} = 12V$		1250	μA
Input Voltage	SG2068/69	$V_{CF} = 2.0V, I_{C} = 1.5A$		2.75	V
• ,,=	SG2070/71	$V_{CE} = 2.0V, I_{C} = 1.5A$		5.0	V
Supply Current	SG2068/69	$I_{C} = 500 \text{ mA}, V_{IN} = 2.4 \text{ V}$		6.0	mA
	SG2070/71	I _C = 500 mA, V _{IN} = 5.0V		4.5	mA
Turn-On Delay	All	0.5 E _{in} to 0.5 E _{out}		1.0	μS
Turn-Off Delay	All	0.5 E _{in} to 0.5 E _{out}		1.5	μS
Clamp Diode	SG2068/70	$V_{\rm B} = 50V$		50	μA
Leakage Current	1 .	V _B = 50V, T _A = 70°C		100	μΑ
	SG2069/71	V _R = 80V		50	μΑ
		V _R = 80V, T _A = 70°C		100	μΑ
Clamp Diode	All	I _F = 1.0 A		1.75	V
Forward Voltage		$l_{\rm F} = 1.5 {\rm A}$		2.0	V

SG2074 THRU SG2077 ELECTRICAL CHARACTERISTICS (Parameter limits are specified at $T_A = +25^{\circ}C$ unless otherwise noted.)

PARAMETER	DEVICES	CONDITIONS	MIN	MAX	UNITS
Output Leakage Current	SG2074/76	V _{CE} = 50V		100	μA
		V _{CE} = 50V, T _A = 70°C		500	μA
	SG2075/77	$V_{CE} = 80V$		100	μA
		V _{CE} = 80V, T _A = 70°C	-	500	μA
Output Sustaining Voltage	SG2074/76	IC = 100 mA, VIN = 0.4V	35		V
	SG2075/77	I _C = 100 mA, V _{IN} = 0.4V	50		V
Collector-Emitter	All	$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 625 μ A		1.1	V
Saturation Voltage		I _C = 750 mA, I _B = 935 μA		1.2	V
		$I_{\rm C}$ = 1.0 A, $I_{\rm B}$ = 1.25 mA		1.3	V
	SG2074/76	$I_{\rm C} = 1.25 \text{A}, I_{\rm B} = 2.0 \text{mA}$		1.4	V
	SG2075/77	$I_{\rm C} \approx 1.5 \text{A}, I_{\rm B} = 2.25 \text{mA}$		1.5	V
Input Current	SG2074/75	V _{IN} = 2.4V	2.0	4.3	mA
		$V_{1N} = 3.75V$	4.5	9.6	mA
	SG2076/77	V _{IN} = 5.0V	0.9	1.8	mA
		$V_{IN} = 12V$	2.75	5.2	mA
Input Voltage	SG2074/75	$V_{CE} = 2.0V, I_{C} = 1.0A$		2.0	V
		$V_{CE} = 2.0V, I_{C} = 1.5A$		2.5	V
	SG2076/77	$V_{CE} = 2.0V, I_{C} = 1.0 \text{ A}$		6.5	V
		$V_{CE} = 2.0V, I_{C} = 1.5 A$		10	V
Turn-On Delay	All	0.5 E _{in} to 0.5 E _{out}		1.0	μS
Turn-Off Delay	All	0.5 E _{in} to 0.5 E _{out}		1.5	μS

SG2064 THRU SG2077

CHARACTERISTIC CURVES















SILICON GANAPAL LINEAR INTEGRATED CIRCUITS

ADVANCED DATA SG3636

Performance data described herein represent design goals. Final device specifications are subject to change.

1.5 AMP DUAL HALF BRIDGE DRIVER

DESCRIPTION

The SG3636 is a monolithic integrated circuit designed especially for driving loads connected in an H bridge configuration. Inputs to this device are TTL compatible and the outputs are capable of sourcing and sinking up to 1.5 Amps of current. Suppression diodes are included on chip for use with inductive loads.

FEATURES

- · Low voltage operation 8 to 25 volts
- Source or sink up to 1.5 Amps
- TTL compatible inputs
- Built-in clamp diodes for inductive loads
- Built in thermal protection

ABSOLUTE MAXIMUM RATINGS

 $V_S = 30 \text{ volts}$ $I_{OUT} = 2.0 \text{A}$ Diode current 2.0A V_{IN} = 7 volts

ELECTRICAL CHARACTERISTICS Unless otherwise stated, $V_s = 25$ Volts

PARAMETER	SYMBOI	TEST CONDITIONS	TYP	UNITS
Input High Current	l _{in} (1)	$V_{in} = 2.4V$	200	μA
Input Low Current	l _{in} (0)	$V_{in} = 0V$	2.4	mA
Low Level Input Voltage	V _{in} (0)		0.8	Volts
High Level Input Voltage	V _{in} (1)	-	2.0	Volts
Source Saturation	V _{ce} (sat)	I _{source} = 1 amp	2.0	Volts
Sink Saturation	V _{ce} (sat)	I _{sink} = 1 amp	2.0	Volts
Supply Current	ا _S	$V_{\rm S} = 25 v$	50	mA
Diode Forward Voltage	V _F	I _F = 1.0A	1.2	Volt

TRUTH TABLE EACH HALF BRIDGE

Enable	Pulse	Output
1	1	Off (High with no load)
0	1	High
1	0	Low
0	0	High

(1= open or high)



ilicon General LINEAR INTEGRATED CIRCUITS

ADVANCED DATA SG3637

Performance data described herein represent design goals. Final device specifications are subject to change.

UNIVERSAL QUAD 2 AMP DRIVER

DESCRIPTION

The SG3637 is a four channel high current, high voltage integrated circuit designed to provide the interface between stepper motors and micro-processor or logic motor control circuitry. The SG3637 will accept most standard logic signal inputs and provide motor drive current to both positive and negative supply rails.

FEATURES

- Output currents to 2.0 amps
- 40 volt outputs to positive or negative rails
- Compatibility with all popular logic families
- · Built-in clamp diodes for inductive loads
- Chip enable for microprocessor control

ABSOLUTE MAXIMUM RATINGS

 $V_{SS} = 20$ volts $I_{OUT} = 2.5 \text{ amps}$

 $V_{OUT} = 45$ volts $V_{IN} = 25 \text{ volts}$

ELECTRICAL CHARACTERISTICS @ 25°C Unless otherwise stated, V_{SS} = 15V, pins 4, 5, 12 and 13 are ground

PARAMETER	SYMBO	TEST CONDITION	MIN	TYP	MAX	UNITS
"O" Level Supply Current	I _{SS} (O)				40	mA
"I" Level Supply Current	I _{SS} (1)	All inputs = 5.0V			20	mA
"O" Input Current Except Enable	I _{IN} (O)	All inputs ground			200	μA
"O" Input Current Enable Input	I _{INE} (O)	Enable input ground			400	μΑ
"I" Input Current All Inputs	I _{IN} (1)	Driven input = 15V			50	μA
Output Leakage Current	I _{cex}	V _{out} = 60V, V _{in} = 2.0V, other inputs ground			500	μA
Output Sustaining Voltage	V _{ce} (sus)	l _{out} = 100mA, inputs = 5.0V	35			Volts
Output ON Voltage	V _{ce} (sat)	l _{out} = 2.0 Amp, inputs ground			2.2	Volts
Diode Leakage	I _R	$V_{R} = 60V$			50	μA
Diode Forward Voltage	VF	IF = 2.0 Amp			2.5	Volts



SILICON GENERAL

ADVANCED DATA SG3638/SG3638A SG3639/SG3639A

Performance data described herein represent design goals. Final device specifications are subject to change.

4 AMP SOLENOID AND MOTOR DRIVER

DESCRIPTION

The SG3638 and SG3639 are high voltage integrated circuits designed to be used as "H" bridge drivers, dual solenoid drivers and more. These devices allow current control of loads by means of external series sense resistors and a threshold control input. The SG3638 and SG3639 feature built-in thermal protection. They are designed for use with a split power supply for the motor or solenoid.

FEATURES

- Chopped Mode Current Control
- Output Current to 4 Amps
- 60 Volt Output Drivers (A Suffix)
- TTL Compatible INPUT and MODE pins
- Combined Threshold and Logic Input
- Built-in Thermal Protection
- Built-in Clamp Diodes for Inductive Loads
- Split Voltage Power Supply Operation
- Packaged in a 12 Lead Power SIP



ADVANCED DATA SG3638/SG3638A SG3639/SG3639A

ABSOLUTE MAXIMUM RATINGS

Supply Voltage VEE to VCC	±20 (±25)	Continuous Output Current ± 1A
Input Voltage Range	0.0V to 7.0V	Package Power Dissipation (average) 4.5 watts (without heatsink $T_{A} = 25 ^{\circ}\text{C}$)
Peak Output Current	±5A	Operating Temperature Range -20°C to +85° C
Output Current 33% D.C.	± 4.4A	Storage Temperature Range -55 °C to + 150 °C

ELECTRICAL CHARACTERISTICS ($V_S = 40V$, $T_A = -20^{\circ}C$ to $+85^{\circ}C$)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Supply Voltage	V _{CC} , V _{EE}	operating	± 15	-	±20 (±25)	volts
Package Power Dissipation		$V_{\rm S} = \pm 20 (\pm 25)$	+	10		Watts
Supply Current		$V_{\rm S} = \pm 20 (\pm 25)$	-	12	20	mA
Signal Input Threshold	V sig			1.4		volts
Mode Input Threshold	V _{mode}			1.4		volts
Internal Chopping Threshold	V _{THE chop}		-	4.0		volts
Threshold Input Disable Voltage	V _{THE enable}		<u> </u>	0.45	- 1	volts
Signal Input Current (low)	I sig L	$V_{\overline{sig}} = .4V$	- 1.6	1		mA
Signal Input Current (high)	I sig H	$V_{\overline{sig}} = 2.4V$			100	μΑ
Mode Input Current (low)	I _{mode L}	$V_{mode} = .4V$	- 1.6			mA
Mode Input Current (high)	I _{mode H}	$V_{mode} = 2.4V$	- 1	- 1	100	μA
Threshold Input Current (low)	ITHEL	V _{THE} < V _{THE enable}	+	-6.0	_	μΑ
Threshold Input Current (high)	ITHEH	V _{THE} > V _{THE enable}	- 1	- 2.0	_	μΑ
Internal Hysteresis Current	I _{HYS}		-	1 i peak	_	<u> </u>
External Hysteresis Current	I _{HYS ext}		140	200	260	μA
Output SAT Voltage sink	V _{SAT sink}	$I_{at} = 4.4A$	- 1	2.0	2.5	volts
Output SAT Voltage source	V _{SAT source}	$I_{out} = -4.4A$	-	2.5	3.0	volts
Output SAT Voltage sink	V _{SAT sink}	$I_{out} = 1.0A$	-	1.0	1.2	volts
Output SAT Voltage source	V _{SAT source}			1.5	1.8	volts
Output Leakage sink	IOL sink	$V_{CE} = 40V(60)$	1	1	1.0	mA
Output Leakage source	OL source	V _{CE} = 40V (50)	-		1.0	mA
Output Current		30% on	-	+4.0	+ 4.4	A
Transconductance Tolerance	(note 1)	$V_{THE} = 2.0 \text{ to } 3.6 \text{V}$ $V_{THE} = 1.0 \text{ to } 2.0 \text{V}$ $V_{THE} = 0.6 \text{ to } 1.0 \text{V}$		5% 10% 25%	-	+ 5% +10% +25%
Clamp Diode Voltage sink	V _{C sink}	I = 4.4A	-	2.0	2.5	volts
Clamp Diode Voltage source	V _{C source}	I = 4.4A	-	3.0	3.5	voits
GAIN Iout / VTHE (RS)				.1		
NOTE (1) Assumes R _S is exactly kn addition to the intended sense resis	101.		ces exter	nal to the	e I.C. pa	ckage in
SWITCHING CHARACTERISTICS						
PARAMETER	SYMBOL	CONDITION	MIN	ΤΥΡ	MAX	UNIT
Source Turn On Delay	t _D on	1.4V V sig to 10% V source		300		ns
Source Rise Time	t _R on	V _{source} 10% to 90%		100		ns
Source Fall Time	t _F on	V _{source} 90% to 10%		500		ns
Sink Turn Off Delay	t _D off	1.4V V sig to 10% V _{sink}		500		ns
Sink Rise Time	t _R off	V _{sink} 10% to 90%		400		ns
Sense Loop Turn On Delay	t _{DS} on	V _{TH sense 1} to 50% V _{source}		TBD*		
Sense Loop Turn Off Delay	t _{DS} off	V _{TH sense 2} to 50% V _{sink}		TBD*		

*To Be Determined

FUNCTIONAL DESCRIPTION

SG3638 (non-chop drive)

The state of the INPUT pin directly controls the state of the sink transistor. When INPUT (V_{sig}) is is high the sink transistor is turned off. When INPUT is low sink transistor acts as a saturation switch.

The source transistor acts as a saturation switch. The source transistor is directly controlled by a high to the INPUT pin. When INPUT is low the source is controlled by the result of a comparison of the voltage across an external resistor and the THRESHOLD IN-PUT.

With a high on the INPUT, both the output sink and source transistors are turned off which force SENSE to be pulled to ground through an external resistor. This produces a high on the output of the internal comparator and forces the output of the latch to a low state. As INPUT is switched low, both the sink and source transistors are turned on. This causes both the current in a coil, located between the SINK and SOURCE outputs, as well as the voltage across the sense resistor to rise. When the voltage across the sense resistor reaches one tenth the THRESHOLD IN-PUT voltage the comparator trips and sets the latch thus turning the source transistor off. The latch is reset when the INPUT returns to a high state.

SG3639 (chop drive)

The initial conditions are the same as in the SG3638 except the latch is disabled and acts as a simple inverter. Both SINK and SOURCE turn on as INPUT goes low. When the voltage across the external sense resistor reaches one tenth the THRESHOLD INPUT voltage the comparator switches turning SOURCE off and causing the voltage across the sense resistor to decay. The tripping of the comparator also turns on a current source (I_{HYS}, typically 200 μ A) which is tied to the THRESHOLD INPUT and lowers the threshold by an amount determined by the external impedance at the THRESHOLD INPUT (R_{HYS}). This impedance sets up the externally adjustable hysteresis. When the current decays to the new lower threshold level the comparator trips again turning the SOURCE on and resetting the threshold to its original value.

Chop Mode Default Hysteresis

In the Chop Mode, if the THRESHOLD INPUT signal becomes larger than 4 volts (approx.) the output current will no longer increase. At this point the chop hysteresis will switch to an internally controlled value of approximately 10%. This allows the threshold to be left floating and provides a default to the maximum operating current with a 10% hysteresis.



ADVANCED DATA SG3638/SG3638A SG3639/SG3639A



APPLICATIONS

The SG3638 or 3639 can be used to drive a solenoid as seen in Figure 4. The coil is connected between the collector of the source and the collector of the sink transistors. The internal clamp diodes make this application possible without external diodes.

When driving a motor, both halves of the device are used in a cross coupled configuration as seen in Figure 5. In this configuration external diodes must be used to isolate an internal paracitic diodes. Without these external diodes the device will be damaged. These diodes must be of the high speed type with voltage ratings above 70 volts and capable of handling 4 Amps. Both inputs should not be turned on at the same time.

The SG3639 requires a resistor (R_{HYS}) in series with the THRESHOLD INPUT and the external circuit which controls the THRESHOLD INPUT to set the amount of hysteresis.

CIRCUIT CONSIDERATIONS

PC Board Layout — The output current is controlled by both the voltage at the SENSE pin and the sense resistor. Because of the large currents and low resistances, it is critical to have an extremely good PC board layout to reduce paracitic wiring resistances which could add to the sense resistor and reduce the output current.

Thermal — Because of the large power dissipation usually associated with this device, a heat sink is recommended. Air flow around the package may also reduce package temperature. The device has built in thermal shutdown capabilities which will turn the output off when the substrate reaches a temperature of 140 to 160 degrees C.

ADVANCED DATA SG3638/SG3638A SG3639/SG3639A



SILICON GENERAL LINEAR INTEGRATED CIRCUITS

ADVANCED DATA SG3640/SG3641

Performance data described herein represent design goals. Final device specifications are subject to change.

4 AMP SOLENOID AND MOTOR DRIVER

DESCRIPTION

The SG3640 and SG3641 are high voltage integrated circuits designed to be used as ½ "H" bridge drivers, solenoid drivers and more. Both devices allow current control of loads by means of internal series sense resistors and a current level control input. Both feature builtin thermal protection.

The built-in sense resistors, the current input and the 5 lead TO-220 package offer substantial advantages over the SG3638 and SG3639 in many applications.

The SG3640 provides continuous chop mode control, while the SG3641 provides a single pulse which drives the source output to the controlled current.

FEATURES

- Chopped Mode Current Control
- Output Current to 4 Amps
- 40 Volt Output Drivers
- Source Current 500 Times Input Current
- Combined Threshold and Logic Input
- Built-in Thermal Protection
- Built-in Clamp Diodes for Inductive Loads
- Available in a 5 lead Power TO-220 Package



ADVANCED DATA SG3640/SG3641

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	40V
Input Voltage Range	- 1.0V to 7.0V
Peak Output Current	±5A
Output Current 33% D.C.	± 4.4A
Continuous Output Current	±1A
Operating Temperature Range	-20°C to +85° C
Storage Temperature Range	-55°C to +150°C

ELECTRICAL CHARACTERISTICS

PARAMETER	CONDITIONS	MIN	ΤΥΡ	MAX	UNIT
Temperature Range, Operating	т _А	- 20	—	85	°C
Package Power Dissipation	$V_{\rm S} = 40V$		10	_	Watts
Supply Voltage, VS	Operating	15		40	Volts
Supply Current, Idle	$V_{\rm S} = 40$	_	12	20	mA
Input Voltage Range	All	- 0.1	_	6	Volts
Input Current	$V_{iN} = 2.5V$		- 2.0	10.0	μA
Input Hysteresis Current	$V_{IN} = 2.5V$	140	200	260	μA
Current Regulation	$V_{IN} = 2 \text{ to } 4V$	-		5	%
Output Current	30% ON		± 4.0	± 4.4	A
Output Sat Voltage, Sink	+ 4.4A		2.0	2.5	Volts
Output Sat Voltage, Source	- 4.4A	_	2.5	3.0	Volts
Output Sat Voltage, Sink	+ 1.0A	-	1.0	1.2	Volts
Output Sat Voltage, Source	- 1.0A	-	1.5	1.8	Volts
Output Leakage	$V_{CE} = 40V$		_	±1	mA
Clamp Diode, VF	4.4A		2.0	2.5	Volts

SWITCHING CHARACTERISTICS ($V_S = -20^{\circ}C \text{ to } +85^{\circ}C$)

PARAMETER SYMBOL CO		CONDITION	MIN	TYP	MAX	UNIT
Source Turn On Delay	t _D on	1.4V V sig to 10% V source	T .	300		ns
Source Rise Time	t _R on	V _{source} 10% to 90%		100		ns
Source Fall Time	t _F on	V _{source} 90% to 10%		500		ns
Sink Turn Off Delay	t _D off	1.4V V sig to 10% Vsink		500		ns
Sink Raise Time	t _R off	V _{sink} 10% to 90%		400		ns
Sense Loop Turn On Delay	t _{DS} on	V _{TH sense 1} to 50% V _{source}		TBD*		
Sense Loop Turn Off Delay	t _{DS} off	V _{TH sense 2} to 50% V _{sink}		TBD*		

*To Be Determined

ADVANCED DATA SG3640/SG3641

FUNCTIONAL DESCRIPTION

The following discussion assumes an inductive load between the SOURCE and SINK outputs. Current into the INPUT pin directly controls the state of the SINK output. When the INPUT is above 1.4 volts the SINK output will be held low. When the INPUT is below 0.8 volts the SINK output will be off.

SG3640

The SOURCE output is controlled by the INPUT current and the state of an internal comparator. One input to the comparator is the voltage across the internal sense resistor and the other is a voltage produced by the INPUT current. Initially, when the INPUT goes above the threhold both the SOURCE and SINK transistors are turned on. When current through the sense resistor reaches 500 times the INPUT current the SOURCE will be turned off. Threshold hysteresis of 10% is built into the comparator. When the voltage across the sense resistor falls to the new threshold the SOURCE transistor will again be turned on and the comparator threshold will be raised to its initial state.

SG3641

The SG3641 works in the same manner as the SG3640 except that when the comparator turns the SOURCE transistor off it also sets a flip/flop to inhibit the SOURCE from being turned on until the flip/flop is reset by INPUT going low.



ADVANCED DATA SG3640/SG3641



APPLICATIONS

The SG3640 or SG3641 can be used to drive a solenoid as illustrated in Figure 1. R IN and V IM-PACT should be chosen to provide input current to the SG 3640 or SG3641 (8 mA will provide 4 Amps of peak SOURCE current). Changing V IMPACT will control the peak current. No external diodes are required.

Two SG3640 or SG3641 devices can be used to drive a motor as illustrated in Figure 2. When used in this

way external diodes are required to protect the devices against parasitic diodes which may form in the devices when the source is turned off. These external diodes must be the high speed type with voltage ratings above 70 volts and capable of handling 4Amps. Care should be taken to insure that both INPUTS are not on at the same time. 10 to 20 ms off dead time may be required from the time one INPUT is turned off and the alternate INPUT is turned on.





Performance data described herein represent design goals. Final device specifications are subject to change.

4 AMP SOLENOID AND MOTOR DRIVER

DESCRIPTION

The SG3643 is a high voltage integrated circuit designed to be used as a "H" bridge driver, dual solenoid driver and more. This device allows current control of loads by means of external series sense resistors and a threshold control input. The SG3643 and SG3643A feature built-in thermal protection.

FEATURES

- Chopped Mode Current Control
- Output Current to 4 Amps
- 60 Volt Output Drivers (A suffix)
- TTL compatable INPUT and MODE pins
- · Combined Threshold and Logic Input
- Built-in Thermal Protection
- Built-in Clamp Diodes for Inductive Loads
- Single Voltage Power Supply Operation
- · Packaged in a 12 lead power SIP



ABSOLUTE MAXIMUM RATINGS

Supply Voltage SG3643	45V	Continuous Output Current	± 1A
SG3643A	60V	Package Power Dissipation (average)	4.5 watts
Input Voltage Range	0V to 7V	(without heatsink $T_{\Delta} = 25^{\circ}C$)	
Peak Output Current	±5A	Operating Temperature Range	-20°C to +85° C
Output Current 33% D.C.	± 4.4A	Storage Temperature Range	-55°C to +150°C

ELECTRICAL CHARACTERISTICS ($V_S = 40V$, $T_A = -20^{\circ}C$ to $+85^{\circ}C$)

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Supply Voltage	Vs	operating	15		40(60)	volts
Package Power Dissipation		$V_{\rm S} = 40$		10		Watts
Supply Current		$V_{\rm S} = 40$		12	20	mA
Signal Input Threshold	V _{sig}		_	1.4	_	volts
Mode Input Threshold	V _{mode}			1.4		volts
Internal Chopping Threshold	V _{THE chop}			4.0		volts
Threshold Input Disable Voltage	V _{THE enable}		—	0.45	_	volts
Signal Input Current (Iow)	I sig L	$V_{\overline{sig}} = .4V$	- 1.6	—		mA
Signal Input Current (high)		$V_{\overline{sig}} = 2.4V$	_	_	100	μA
Mode Input Current (low)	I _{mode L}	$V_{mode} = .4V$	- 1.6	—		mA
Mode Input Current (high)	I _{mode} H	$V_{mode} = 2.4V$	_	—	100	μA
Threshold Input Current (low)	ITHEL	V _{THE} < V _{THE enable}	—	- 6.0	—	μA
Threshold Input Current (high)	ITHE H	V _{THE} < V _{THE enable}	_	- 2.0	—	μA
Internal Hysteresis Current	I _{HYS}		-	.11 peak		
External Hysteresis Current	I _{HYS ext}		140	200	260	μĂ
Output SAT Voltage sink	V _{SAT sink}	$I_{at} = 4.4A$		2.0	2.5	volts
Output SAT Voltage source	V _{SAT source}	$I_{out} = -4.4A$	-	2.5	3.0	volts
Output SAT Voltage sink	V _{SAT sink}	$I_{out} = 1.0A$		1.0	1.2	volts
Output SAT Voltage source	V _{SAT source}	$I_{out} = -1.0A$		1.5	1.8	volts
Output Leakage sink	I _{OL sink}	$V_{CE} = 40V(60)$			1.0	mA
Output Leakage source	I _{OL source}	$V_{CE} = 40V$			1.0	mA
Output Current		30% on		+ 4.0	+ 4.4	A
Transconductance Tolerance	(note 1)	$V_{THE} = 2.0 \text{ to } 3.6 \text{V}$ $V_{THE} = 1.0 \text{ to } 2.0 \text{V}$ $V_{THE} = 0.6 \text{ to } 1.0 \text{V}$		-5% -10% -25%	=	+ 5% + 10% + 25%
Clamp Diode Voltage sink	V _{C sink}	I = 4.4A	_	2.0	2.5	volts
Clamp Diode Voltage source	V _{C source}	I = 4.4A	—	3.0	3.5	volts
GAIN Iout / VTHE (RS)				.1	T	

NOTE (1) Assumes R_S is exactly known. R_S includes parasitic wiring resistances external to the I.C. package in addition to the intended sense resistor.

SWITCHING	CHARACTERIST	ICS (Ve =	20°C to	+85°C)
OTTI OTTING				

PARAMETER	SYMBOL	CONDITION	MIN	TYP	MAX	UNIT
Source Turn On Delay	t _D on	1.4V V sig to 10% V source		300		ns
Source Rise Time	t _R on	V _{source} 10% to 90%		100		ns
Source Fall Time	t _F on	V _{source} 90% to 10%		500		ns
Sink Turn Off Delay	t _D off	1.4V V sig to 10% Vsink		500		ns
Sink Rise Time	t _R off	V _{sink} 10% to 90%		400		ns
Sense Loop Turn On Delay	t _{DS} on	V _{TH sense 1} to 50% V _{source}		TBD*	1	
Sense Loop Turn Off Delay	t _{DS} off	V _{TH sense 2} to 50% V _{sink}		TBD*		

*To Be Determined

FUNCTIONAL DESCRIPTION

Non-Chop Mode (MODE Pin tied low):

The state of the INPUT pin directly controls the state of the sink transistor. When INPUT $(V_{_})$ is sig

high the sink transistor is turned off. When INPUT is low the sink transistor acts as a saturation switch.

The source transistor is directly controlled by a high to the INPUT pin. When INPUT is low the source is controlled by the result of a comparison of the voltage across an external sense resistor and the THRESHOLD INPUT.

With a high on the INPUT, both the output sink and source transistors are turned off which force SENSE to be pulled to ground through an external resistor. This produces a high on the output of the internal comparator and forces the output of the latch to a low state. As INPUT is switched low, both the sink and source transistors are turned on. This causes both the current in a coil, located between the SINK and SOURCE outputs, as wells as the voltage across the sense resistor to rise. When the voltage across the sense resistor reaches one tenth the THRESHOLD IN-PUT voltage the comparator trips and sets the latch thus turning the source transistor off. The latch is reset when the INPUT returns to a high state.

Chop Mode (MODE pin tied high):

The initial conditions are the same as in the non-choo mode except the latch is disabled and acts as a simple inverter. Both SINK and SOURCE turn on as INPUT goes low. When the voltage across the external sense resistor reaches one tenth the THRESHOLD INPUT voltage the comparator switches turning SOURCE off and causing the voltage across the sense resistor to decay. The tripping of the comparator also turns on a current source (IHYS, typically 200 µA) which is tied to the THRESHOLD INPUT and lowers the threshold by an amount determined by the external impedance at the THRESHOLD INPUT (RHYS). This impedance sets up the externally adjustable hysteresis. When the current decays to the new lower threshold level the comparator trips again turning the SOURCE on and resetting the threshold to its oroiginal value.

Chop Mode Default Hysteresis:

In the Chop Mode, if the THRESHOLD INPUT signal becomes larger than 4 volts (approx.) the output current will no longer increase. At this point the chop hysteresis will switch to an internally controlled value of approximately 10%. This allows the threshold to be left floating and provides a default to the maximum operating current with a 10% hysteresis.

THERMAL AND POWER CHARACTERISTICS CASE TEMP. (°C) 130 120 110 100 80 = 25.8 °C/WAT1 70 WATTS 60 40 30 2 POWER IN (WATTS) **Figure 2 SIP Package Dissipation** (No Air Flow or Heat Sink) Thermal Shutdown



 $\Theta_{JC} = 2^{\circ} C/W (typical)$

6

Thermal Resistance



APPLICATIONS

The SG3643 can be used to drive a solenoid as seen in Figure 4. the coil is connected between the collector of the source and the collector of the sink transistors. the internal clamp diodes make this application possible without external diodes.

When driving a motor, both halves of the SG3643 are used in a cross coupled configuration as seen in Figure 5. In this configuration external diodes must be used to isolate an internal paracitic diode. Without these external diodes the device will be damaged. These diodes must be of the high speed type with voltage ratings above 70 volts and capable of handling 4 Amps. Both inputs should not be turned on at the same time.

When in the Chop Mode a resistor (R_{HYS}) in series with the THRESHOLD INPUT and the external circuit which controls the THREHOLD INPUT will set the amount of hysteresis (see the design example).

CIRCUIT CONSIDERATIONS

PC Board Layout — The output current is controlled by both the voltage at the SENSE pin and the sense resistor. Because of the large currents and low resistances, it is critical to have an extremely good PC board layout to reduce paracitic wiring resistances which could add to the sense resistor and reduce the output current. Thermal — Because of the large power dissipation usually associated with this device, a heat sink is recommended. Air flow around the package may also reduce package temperature. the device has built in thermal shutdown capabilities which will turn the output off when the substrate reaches a temperature of 140 to 160 degrees C.

6





SILICON GENERAL LINEAR INTEGRATED CIRCUITS

DUAL HAMMER DRIVER

DESCRIPTION

The SG3700 is a monolithic integrated circuit that will provide up to 1 Amp of current to each output. An external sense resistor and an external reference control voltage is required for programming the output current to the desired value. On chip TTL compatible logic is provided for timing of the output current pulse duration.

FEATURES:

- Output Currents to 1 Amp
- Output Voltage to 35 Volts
- Built in Clamp Diodes
- Thermal Protection
- Logic Control of Pulse Duration



SG3700

SG3700

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ABSOLUTE MAXIMUM RATINGS
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V _{CC = 7} Volts	^V S = 40 Volts
$V_{in} = 5.5$ Volts	^I OUT = 1 Amp

ELECTRICAL CHARACTERISTICS Vcc = 5V T = 25°C

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
"O" Input Current	I _{in} (0)	Logic inputs Vin = gnd		200		μA
"l" Input Current	I _{in} (1)	Logic inputs Vin = gnd		10		μA
"O" Input Voltage	V _{in} (0)				0.8	Volts
"}" Input Voltage	V _{in} (1)		2.0			Volts
Control Voltage Input Current	I _{c1}	V _{cl = 1.0 to} 1.8 Volts			10	μA
Output Leakage	^I off	V _s = 35 Volts			500	μA
^V fault Sense Output	V _{prot} .	I _{prot. =} 1.5 mA			1.5	Volts
Clamp Diode Forward Voltage	۷ _F	^I F = 1.0 Amp			3.0	Volts
Clamp Diode Leakage Current	IR	V _R = 35 Volts			100	µА



POWER OUTPUT STAGES

SILICON GENERAL

01 02

COMMON

DRIVE

SWITCHING REGULATOR POWER OUTPUT STAGES

Power Output Stages for 5 Amp Positive and Negative Switching Regulators **FEATURES** Equivalent to the Unitrode PIC 600, 601, 602, 610, 611, 612 Designed and characterized for switching regulator applications Cost saving design reduces size, improves efficiency, reduces noise and RFI (See note 4) High operating efficiency, Typical 2A circuit performance -• Rise and Fall time < 75ns Efficiency > 85% No reverse recovery spike generated by commutating diode. (See note 4 and Fig. 2) . Electrically isolated, 4-Pin, TO-66 hermetic case DESCRIPTION The SM600 series Power Output Stages are designed and characterized to be driven with standard integrated circuit voltage regulators. They are completely characterized over their entire operating range of -55°C to +125°C. The devices are enclosed in a special 4-pin TO-66 package, hermetically sealed for high reliability. The hybrid circuit construction utilizes thick film resistors on a beryllia substrate for maximum thermal conductivity and resultant low thermal impedance. All of the active elements in the hybrid are fully passivated. **MECHANICAL SPECIFICATIONS** SCHEMATIC SM600, 601, 602, 610, 611, 612 SM600 SM601 SM602 POS. POS. OUTPUT C \cap DRIVE (3) INPUT (4) 210 .350 MAX .620 MAX Ċз .590 DRIVE COMMON SM610 COMMON (2) 6 152 SM611 .360 MIN OUTPUT (1) NEG. NEG. 4 SM612 1 OUTPUT INPUT \cap O 4-Pin TO-66 NOTES: 1. Case is electrically isolated.

 Loads may be soldered to within 1/16" of base provided temperaturetime exposure is less than 260°C for 10 seconds.

ABSOLUTE MAXIMUM	RATINGS			SN	1600	SM601	I SM	602	SM610	SM611	SM612
input Voltage, V ₄₋₂				6	ov	80V	10	ov	- 60V	- 80V	- 100V
Output Voltage, V1-2				6	ov	80V	10	0/V	~ 60V	- 80V	- 100V
Drive Input Reverse Voltage, V	V ₃₋₄			(5V	5V	5	v	- 5V	- 5V	- 5V
Output Current, I1				ŧ	5A	5A	5	A	- 5A	- 5A	- 5A
Drive Current, 13				(0.2A	- 0.2A	- 0	.2A	0.2A	0.2A	0.2A
Thermal Resistance Junction to Case, 9 _{J-C} Power Switch									4.0%		
Commutating Diode					·	<u> </u>			4.0%		
Case to Ambient, 9C-A						·	·		60.0%		
Operating Temperature R	ange, T _C							- 55	°C to +12		
Maximum Junction Tempe										150°	
Storage Temperature Ran								- 65		<u> </u>	
ELECTRICAL SPECIFICA	TIONS (a	+ 25	°C unk								
			1600, 60		÷ .	610, 611	610		1		
Test	Symbol	Min	Тур	Max	Min	Тур	Max	Units	Condi	tions	
Current Delay Time	^t di	1	20	40	-	20	40	ns	Vin=25	5V(-25V)	
Current Rise Time	t _{ri}	-	50	75	-	50	75	ns	V _{out} =	5V(-5V)	
Voltage Rise Time	t _{rv}	1	30	50	-	30	50	ns	lout=	2A(-2A)	
Voltage Storage Time	t _{sv}	-	175	500	-	150	700	ns	l3=-2	20mA(20mA)
Voltage Fall Time	tfv	-	50	75	-	50	75	ns	See Fi	gure 2.	
Current Fall Time	tfi	-	70	150	-	70	150	ns	See no	otes 1, 2, 4	
Efficiency (Notes 2 & 4))	η	-	85	-	-	85	-	%			
On-State Voltage (Note 3)	V _{4-1(on)}	-	1.0	1.5	-	-1.0	-1.5	v	14=2/	A(-2A),I3=	02A(.02A
On-State Voltage (Note 3)	V _{4-1(on)}	-	2.5	3.5	-	-2.5	-3.5	v	14=5A	(-5A),I3=	02A(.02A
Diode Forward Voltage (Note 3)	V _{2-1(on)}	-	.8	1.0		8	-1.0	v	<u> </u>	(-2A)	`
	V _{2-1(on)}	-	1.0	1.5	-	-1.0	-1.5	v	l2=5A		
Diode Forward Voltage (Note 3)					-	-0.1	-10	µA		ited input vi	oltage
	I4-1	-	0.1	10							
Off-State Current	<u> </u>	-	0 .1 .10	10 1.0		10	1.0	mA		ted input vo	
Diode Forward Voltage (Note 3) Off-State Current Off-State Current Diode Reverse Current	l4-1					10 -1.0	1.0 10	mA µA	V4 = Ra		olt.,T _A = 10

600 Series Power Output Stages

Notes:

1. In switching an inductive load, the current will lead the voltage on turn-on and lag the voltage on turn-off (see Figure 2). Therefore, Voltage Delay Time (t_{DV}) 🔤 t_{di} + t_f and

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3. Pulse test: Duration = 300ms, Duty Cycle ≤ 2%.

4. As can be seen from the switching waveforms shown in Figure 2, no reverse or forward recovery spike is generated by the commutating diode during switching! This reduces self-generated noise, so no current spike is fed through the switching regulator. It also improves efficiency and reliability, since the power only carries current during turn-on.



SILICON GENERAL

SWITCHING REGULATOR POWER OUTPUT STAGES

Power Output Stages for 15 Amp Positive and Negative Switching Regulators **FEATURES** . Equivalent to PIC 625, 626, 627, 635, 636, 637 Designed and characterized for switching regulator applications Cost saving design reduces size, improves efficiency, reduces noise and RFI (See note 4) High operating frequency (to > 100kHz) results in smaller inductorcapacitor filter and improved power supply response time High operating efficiency: Typical 7A circuit performance — Rise and Fall time < 300ns Efficiency > 85% Electrically isolated, 4-pin, TO-66 hermetic case DESCRIPTION The SM600 series Power Output stages are designed and characterized to be driven with standard integrated circuit voltage regulators. They are completely characterized over their entire operating range of -55°C to +125°C. The devices are enclosed in a special 4-pin TO-66 package, hermetically sealed for high reliability. The hybrid circuit construction utilizes thick film resistors on a beryllia substrate for maximum thermal conductivity and resultant low thermal impedance. All of the active elements in the hybrid are fully passivated. **MECHANICAL SPECIFICATIONS** SM625, 626, 627, 635, 636, 637 SCHEMATIC SM625 SM626 SM627 POS POS INPUT OUTPUT 0 $\overline{}$ DRIVE (3) PUT (4) .620 MAX. .590 570 DRIVE COMMON COMMON (2) 152 SM635 .360 MIN OUTPUT (1) SM636 SM637 NEG. NEG. INPUT \cap n OUTPUT 4-Pin TO-66 NOTES: 1. Case is electrically isolated. 2. Loads may be soldered to within 1/16" of base provided temeperature-Óз Ó 2 time exposure is less than 260°C for DRIVE COMMON 10 seconds

600 Series Power Output Stages

ABSOLUTE MAXIMUM RATINGS	SM625	SM626	SM627	SM635	SM636	SM637
nput Voltage, V ₄₋₂	60V	80V	100V	- 60V	- 80V	- 100V
Dutput Voltage, V ₁₋₂	60V	80V	100/V	- 60V	- 80V	- 100V
Drive Input Reverse Voltage, V ₃₋₄	5V	5V	5V	- 5V	- 5V	– 5V
Dutput Current, I ₁	15A	15A	15A	- 15A	- 15A	- 15A
Drive Current, I3	- 0.4A	- 0.4A	- 0.4A	0.4A	0.4A	0.4A
Thermal Resistance Junction to Case, ဓյ _{-C} Power Switch				4.0°C/	w	
Commutating Diode				4.0°C/	w	
Case to Ambient, 0C-A				60.0°C	w	
Operating Temperature Range, TC			-58	5°C to +125	°C	
Maximum Junction Temperature, Tj				+ 150	°C	
Storage Temperature Range			-65	5°C to +150	°C	

ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

	SM625/625/627					SM635/6	336/637		
Test	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Units	Conditions
Current Delay Time	tdi	[-]	35	60	-	35	60	ns	V _{in} =25V(-25V)
Current Rise Time	t _{ri}	-	65	150	-	65	175	ns	V _{out} =5V(-5V)
Voltage Rise Time	trv	-	40	60	-	40	60	ns	l _{out} =7A(7A)
Voltage Storage Time	tsv	-	500	1000	-	500	1000	ns	I3=-30mA(30mA)
Voltage Fall Time	tfv	-	70	175	-	100	300	ns	See Figure 2
Current Fall Time	t _{fi}	-	175	300	-	175	300	ns	See notes 1, 2, 4
Efficiency (Notes 2 and 4)	η	-	85	-		85	-	%	
On-State Voltage (Note 3)	V _{4-1(on)}	-	1.0	1.5	-	-1.0	-1.5	v	I4=7A(-7A), I3=03A(.03A)
On-State Voltage (Note 3)	V4-1(on)	-	2.5	3.5		-2.5	-3.5	v	I4=15A(-15A), I3=03A(.03A)
Diode Fwd, Voltage (Note 3)	V _{2-1(on)}	-	.85	1.25	-	85	-1.25	V	l ₂ =7A(-7A)
Diode Fwd. Voltage (Note 3)	V _{2-1(on)}	$\boxed{-}'$.95	1.75		95	-1.75	v	l2=15A(-15A)
Off-State Current	l4-1	-	0.1	10	_	-0.1	- 10	μA	V ₄ =Rated input voltage
Off-State Current	I4-1	-	.10	1.0	-	10	1.0	mA	V ₄ =Rated input voltage, T _{A=100} %
Diode Reverse Current	I1-2	-	1.0	10	-	-1.0		μA	V1=Rated output voltage
Diode Reverse Current	I1-2	[-]	.500	1.0	-	.500	1.0	mA	V1=Rated output voltage, TA=100°

Notes: 1. In switching an inductive load, the current will lead the voltage on turn-on and lag the voltage on turn-off (see Figure 2). Therefore, Voltage Delay Time (t_{DV}) $\approx t_{di} + t_{\gamma}$ and Current Storage Time (tei) = tev + tev.

2. The efficiency is a measure of internal power losses and is equal to Output Power divided by Input Power. The switching speed circuit of Figure 1, in which the efficiency is measured, is representative of typical operating conditions for the SM800 series switching regulators.

3. Pulse Test: Duration = 300ms, Duty Cycle ≤ 2%.

4. As can be seen from the switching waveforms shown in Figure 2, no reverse or forward recovery spike is generated by the commutating diode during switching! This reduces selfgenerated noise, since no current spike is fed through the switching regulator. It also improved efficiency and reliability, since the power switch only carries current during turn-on.



Silicon General

FUNCTION MODULE PRODUCTS

SWITCHING REGULATOR POWER OUTPUT STAGES



600 Series Power Output Stages

ABSOLUTE MAXIMUM RATINGS	SM645	SM646	SM647	SM655	SM656	SM657
Input Voltage, V ₄₋₂	60V	80V	100V	- 60V	- 80V	100V
Output Voltage, V ₁₋₂	60V	80V	100/V	- 60V	- 80V	- 100V
Drive Input Reverse Voltage, V ₃₋₄	5V	5V	5V	- 5V	- 5V	- 5V
Continuous Output Current, I ₁	15A	15A	15A	- 15A	- 15A - 20.A	- 15A
Peak Output Current	20A	20A	20A	- 20A		- 20.A
Drive Current, I3	- 0.4A	- 0.4A	- 0.4A	0.4A	0.4A	0.4A
Thermal Resistance Junction to Case, θ _{J-C} Power Switch					2°C/W	
Commutating Diode					2°C/W	
Case to Ambient, ^O C-A				3	0.0°C/W	
Operating Temperature Range, TC				-55°C to	+ 125°C	
Maximum Junction Temperature, Tj					+150°C	
Storage Temperature Range				-65°C to	+ 150%C	

ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

	SM645/646/647				S	M655/65	6/657		
Test	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Units	Conditions
Current Delay Time	tdi	-	35	60	-	35	60	ns	V _{in} =25V(-25V)
Current Rise Time	t _{ri}	-	65	150	-	65	175	ns	V _{out} =5V(-5V)
Voltage Rise Time	t _{rv}	-	40	60	-	40	60	ns	l _{out} =7A(-7A)
Voltage Storage Time	t _{sv}	-	500	1000	-	500	1000	ns	I3=-30mA(30mA)
Voltage Fall Time	tfv	-	70	175	-	100	300	ns	See Figure 2
Current Fall Time	tfi	-	175	300	-	175	300	ns	See notes 1, 2, 4
Efficiency (Notes 2 and 4)	η	-	85	-	-	85	-	%	
On-State Voltage (Note 3)	V4-1(on)	-	1.0	1.5	-	-1.0	-1.5	v	I ₄ =7A(-7A), I ₃ =03A(.03A)
On-State Voltage (Note 3)	V _{4-1(on)}	-	2.5	3.5	-	-2.5	-3.5	V	I ₄ =15A(-15A), I ₃ =03A(.03A)
Diode Fwd, Voltage (Note 3)	V _{2-1(on)}		.85	1.25	-	85	-1.25	v	l2=7A(-7A)
Diode Fwd. Voltage (Note 3)	V _{2-1(on)}		.95	1.75	-	95	- 1.75	V	l ₂ =15A(-15A)
Off-State Current	l4-1	-	0.1	10	-	-0.1	- 10	μA	V ₄ =Rated input voltage
Off-State Current	l4-1	-	.10	1.0	-	10	1.0	mA	V4=Rated input voltage, TA=100
Diode Reverse Current	11-2	-	1.0	10	-	-1.0	10	μA	V1=Rated output voltage
Diode Reverse Current	I1-2	-	.500	1.0	-	.500	1.0	mΑ	V1=Rated output voltage, TA=100

Notes: 1. In switching an inductive load, the current will lead the voltage on turn-on and lag the voltage on turn-off (see Figure 2). Therefore, Voltage Delay Time (t_{DV})≅t_{di} + t_{ri} and Current Storage Time (t_{si}) ≅t_{sy} + t_{fy}. 2. The efficiency is a measure of internal power kases and is equal to Output Power divided by Input Power. The switching speed circuit of Figure 1, in which the efficiency is

measured, is representative of typical operating conditions for the SM600 series switching regulators.

3. Pulse Test: Duration = 300ms, Duty Cycle ≤ 2%.

4. As can be seen from the switching waveforms shown in Figure 2, no reverse or forward recovery spike is generated by the commutating diode during switching! This reduces self-generated noise, since no current spike is fed through the switching regulator. It also improved efficiency and reliability, since the power switch nonly carries current during turn-on.





Figure 1. SM645, 646, 647 Switching Speed Circuit

Figure 2. SM645, 646, 647 Switching Waveforms

Note: SM655, 656, 657 Circuit and waveforms are identical but of opposite polarity ($V_{in} = -25V$, $V_{out} = -5V$, $I_{DRIVE} = +30$ mA).

SILICON GENERAL INC.

11651 Monarch Street, Garden Grove, California 92641 • 714/892-5531 • TWX: 910-596-1804

SPECIFICATION HRT 600-1

HYBRID SWITCHING REGULATORS HIGH RELIABILITY TYPES (4 LEAD TO-66)

SM600A,B/SM601A,B/SM602A,B SM610A,B/SM611A,B/SM612A,B SM625A,B/SM626A,B/SM627A,B SM635A,B/SM636A,B/SM637A,B

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- 1.0 Scope
- 2.0 Applicable Documents
- 3.0 Requirements
- 4.0 Quality Assurance Provisions

High Rel Construction with T ₁ Testing	High Rel Construction with T ₂ Testing
SM600B	SM600A
SM601B	SM601A
SM602B	SM602A
SM610B	SM610A
SM611B	SM611A
SM612B	SM612A
SM625B	SM625A
SM626B	SM626A
SM627B	SM627A
SM635B	SM635A
SM636B	SM636A
SM637B	SM637A
	Construction with T ₁ Testing SM600B SM601B SM602B SM610B SM610B SM611B SM612B SM625B SM626B SM626B SM627B SM635B SM635B SM636B

1.0 SCOPE

This specification defines the detail requirements for High Reliability Hybrid Switching Regulators. (Reference MIL-STD-750). Extensive 100% testing for parameter stability has been included in the Quality Assurance Provisions.

1.1a ABSOLUTE MAXIMUM RATINGS

	SM600	SM601	SM602	SM610	SM611	SM612
Input Voltage, V₄₂	60V	80V	100V	- 60V	- 60V	- 100V
Output Voltage, V ₁₋₂	60V	80V	100V	- 60V	– 80V	– 100V
Drive-Input Reverse Voltage, V ₃₋₄	5V	5V	5V	– 5V	- 5V	– 5V
Output Current, I ₁	5A	5A	5A	– 5A	– 5A	- 5A
Drive Current, I ₃	– 0.2A	– 0.2A	– 0.2A	0.2A	0.2A	0.2A
Thermal Resistance						
Junction to Case, $\theta_{\rm J-C}$						
Power Switch			4.0°	C/W		
Commutating Diode			4.0°	C/W ————		
Case to Ambient, θ_{C-A}				0° ————		
Operating Temperature Range, T _C			—— – 55 °C to	+125°C		
Maximum Junction Temperature, T _i				0°C ———		
Storage Temperature Range			—— – 65°C to	+150°C		

1.1b ABSOLUTE MAXIMUM RATINGS

	SM625	SM626	SM627	SM610	SM611	SM612					
Input Voltage, V4-2	60V	80V	100V	- 60V	- 60V	– 100V					
Output Voltage, V ₁₋₂	60V	80V	100V	– 60V	– 80V	– 100V					
Drive-Input Reverse Voltage, V ₃₋₄	5V	5V	5V	– 5V	– 5V	– 5V					
Output Current, I	15A	15A	15A	- 15A	– 15A	– 15A					
Drive Current, I	- 0.4A	– 0.4A	– 0.4A	0.4A	0.4A	0.4A					
Thermal Resistance Junction to Case, θ _{LC}											
Power Switch	4.0°C/W										
Commutating Diode		4.0°C/W									
Case to Ambient, $\theta_{C,\Delta}$											
Operating Temperature Range, T _C	55°C to + 125°C										
Maximum Junction Temperature, Ti											
Storage Temperature Range			—— — 65°Cto	o + 150 ℃ —-							

1.1c ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

			SM6	00, 601 AN	0, 601 AND 602 SM610, 611 AND 612					
	Test	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Units	Conditions
		t _{di}		20	40	-	20	40	ns	$V_{in} = 25V (-25V)$
2	Current Delay Time (I ₃ – I ₄) Current Rise Time (I ₄)	t _{ri}	-	50	75	-	50	75	ns	$V_{out} = 5V (-5V)$
3	Voltage Rise Time (V_{A-1})	t _{rv}		30	50		30	50	ns	lout = 2A (-2A)
4	Voltage Storage Time $(V_4 - 1)$ Voltage Storage Time $(V_4 - 1 - I_3)$	t _{sv}	~	700		~	700	-	ns	I ₃ = -20 mA (20 mA)
5	Voltage Fall Time $(V_4 - 1 - 13)$	t _{fv}		50	75	-	50	75	ns	5
6	Current Fall Time (I_A)	t _{fi}		70	150	- 1	70	150	ns	
7	Efficiency (Note 1)	η		85		-	85	-	8	
8	On-State Voltage (Note 2)	V ₄₋₁ (on)	-	1.0	1.5	- 1	- 1.0	- 1.5	l v	I ₄ = 2A (-2A), I ₃ = -0.02A (0.02A)
9	On-State Voltage (Note 2)	V _{4~1} (on)	-	2.5	3.5	-	- 2.5	- 3.5	l v	14 = 5A (-5A), 13 = -0.02A (0.02A)
10	Diode Forward Voltage (Note 2)	V _{2-1 (on)}		0.8	1.0	-	- 0.8	-1.0	l v	$I_2 = 2A(-2A)$
11	Diode Forward Voltage (Note 2)	V ₂₋₁ (on)	-	1.0	1.5	-	- 1.0	- 1.5	v	12 = 5A (-5A)
12	Off-State Current	¹ 4-1		0.1	10.0		- 0.1	- 10.0	μA	$V_A = Rated input voltage$
13	Off-State Current	¹ 4-1		0.01	1.0		- 0.1	- 1.0	mA	$V_A = Rated input voltage, T_A = 100^{\circ}C$
14	Diode Reverse Current	11-2		1.0	10.0	-	-1.0	- 10.0	μA	V1 = Rated output voltage
15	Diode Reverse Current	¹ 1-2	_	0.5	1.0	-	0.5	- 1.0	mA	$V_1 = Rated output voltage, T_{\Delta} = 100^{\circ}C$

			SM6	25, 626 AM	ID 627	SM635, 636 AND 637				
	Test	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Units	Conditions
1	Current Delay Time (I3 - I4)	t _{di}	-	35	60	-	35	60	ns	V _{in} = 25V (-25V)
2	Current Rise Time (IA)	t _{ri}		65	150		65	175	ns	$V_{out} = 5V (-5V)$
3	Voltage Rise Time (V_{4-1})	try		40	60	-	40	60	ns	1 _{out} = 7A (-7A)
• 4	Voltage Storage Time (V4 - 1 - 13)		-	900	-		900	-	ns	I ₃ = -30 mA (30 mA)
5	Voltage Fall Time (V ₄₋₁)	t _{fv}		70	175	-	100	300	ns	ů
6	Current Fall Time (IA)	t _{fi}	-	175	300		175	300	ns	
7	Efficiency (Note 1)	η.	-	85	-	-	85		%	
8	On-State Voltage (Note 2)	V ₄₋₁ (on)	~	1.0	1.5	-	- 1.0	-1.5	l v	I ₄ = 7A (-7A), I ₃ = -0.03A (0.03A)
9	On-State Voltage (Note 2)	V ₄₋₁ (on)		2.5	3.5	-	- 2.5	-3.5	l v	IA = 15A (-15A), I3 = -0.03A (0.03A)
10	Diode Forward Voltage (Note 2)	V ₂₋₁ (on)	~~	0.85	1.25		- 0.85	- 1.25	l v	1 ₂ = 7A (-7A)
11	Diode Forward Voltage (Note 2)	V ₂₋₁ (on)		0.95	1.75		- 0.95	- 1.75	l v	$I_2 = 15A (-15A)$
12	Off-State Current	¹ 4-1	-	0.1	10.0	-	-0.1	- 10.0	μA	$V_A = Rated input voltage$
13	Off-State Current	4-1	_	0.01	1.0	_	- 0.1	- 1.0	mA	$V_A = Rated input voltage, T_A = 100^{\circ}C$
14	Diode Reverse Current	1-2		1.0	10.0	-	- 1.0	- 10.0	μA	V1 = Rated output voltage
15	Diode Reverse Current	¹ 1-2	-	0.5	1.0	-	-0.5	-1.0	mA	$V_1 = Rated output voltage, T_A = 100^{\circ}C$

Notes:

The efficiency is a measure of internal power losses and is equal to Output Power divided by Input Power. The switching speed circuit of Figure 1, in which the efficiency is measured, is representative of typical operating conditions for the SM600 series switching regulators.
Pulse test: Duration = 300 µs, Duty Cycle ≤ 2%, 25 °C.





SM600, 601, 602 Switching Waveforms

Note: SM610, 611, 612 Test Circuit and waveforms are identical but of opposite polarity (V_{in} = -25V, V_{out} = -5V, I_{DRIVE} = +20mA).

Figure 1a



SM625, 626, 627 Switching Speed Circuit

SM625, 626, 627 Switching Waveforms

Note: SM635, 636, 637 Circuit and waveforms are identical but of opposite polarity (V in = -25V, V out = -5V, I DRIVE = +30mA.

Figure 1b

SCHEMATIC





MECHANICAL SPECIFICATION



Figure 2. Physical Dimensions and Biasing Diagrams
2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of invitations for bids, form a part of this specification to the extent specified herein.

MIL-S-19500 – General Specification for Semiconductor Devices

3.0 Requirements

3.1 Design and Construction

The Hybrid devices supplied under this specification shall have a design and construction such that they will meet all of the requirements specified herein. The dimensions and physical characteristics shall be as specified in Figure 2.

3.2 Performance Characteristics

The performance characteristics of the Hybrid device supplied under this specification shall be as specified in Group A inspection defined in Table I.

3.3 Quality Assurance

The Quality Assurance Provisions shall be as defined in paragraph 4.0.

3.4 Test Methods

Test methods shall be as specified herein.

3.5 Marking

The markings on the devices supplied shall be permanent and legible and shall include the Manufacturer's name or trademark, a Manufacturing Date Code in accordance with MIL-S-19500 and the specific device type number.

3.6 Preparation for Delivery

The Hybrid devices supplied under this specification shall be preapred for delivery in accordance with level C of MIL-S-19491 unless otherwise directed in the specific contract or purchase order.

3.7 Ordering Data

Procurement document should specify the following:

- a. Specific item type number
- b. Number and date of this specification
- c. Quality Assurance Test level required
- d. Any special packaging if required

4.0 QUALITY ASSURANCE PROVISIONS

4.1 General Provisions

4.1.1 Inspection Responsibility – The supplier is responsible for the performance of all inspection requirements and acceptability of results as specified herein for the Test Level identified in the contract or purchase order. 4.1.2 Controlled Manufacturer – The devices supplied under this specification shall be manufactured under controlled conditions using formally defined quality assurance methods and systems.

4.1.3 Manufacturing Traceability — Each device supplied under this specification shall be traceable to a specific process group, to permit tracing of its full manufacturing history. Process group records shall indicate the exact date that each manufacturing operation was performed and identify materials and process procedures which were used. The manufacturer shall keep these records on file for at least five years.

4.1.4 Definitions

4.1.4.1 Inspection Lot – An "inspection lot" is a collection of devices from which a sample is withdrawn and inspected to determine compliance with the acceptability criterion. It shall consist of one or more "inspection sublots" of the device types defined in this specification. The maximum inspection lot size shall be 5000 units.

4.1.4.2 Inspection Sublot – An "inspection sublot" shall consist of a collection of devices of a single type which have been manufactured under the same conditions and with the same materials.

4.1.4.3 Shipment Lot - A "shipment lot" shall consist of devices taken from an accepted inspection lot for the purpose of shipment on a specific contract or order.

4.1.4.4 Group A Inspection – Group A inspection shall consist of the examinations and tests specified in Table I, and shall be performed on a sublot basis.

4.1.4.5 Controlled Inventory – The controlled inventory shall consist of lots which have successfully passed the acceptance inspection and are being held in storage prior to actual shipment. A controlled inventory shall have adequate safeguards to insure that no defective or untested devices can be included in it. It shall be accessible only to those individuals who are formally identified as authorized personnel.

4.2 Acceptance Inspection

The acceptance inspection requirements shall be as defined by the applicable test level. The procedures of MIL-S-19500 shall apply to Group A inspection. Inspection lots which have been inspected and accepted shall be kept in a controlled inventory. Shipment lots shall be formed using devices taken from accepted inspection lots.

4.2.1 Test Level T2 Requirements – Test level T2 shall consist of the following requirements.

4.2.1.1 The supplier shall perform the Parameter Stability Testing defined in paragraph 4.3 on each device to be supplied. Prior to starting the Blocking Stability test defined in paragraph 4.3.6, each device shall be serialized for individual identity. Variables test data for the controlled electrical parameters shall be recorded before and after stressing. The same procedure shall apply for the Power Stress stability test defined in paragraph 4.3.8. 4.2.1.2 The supplier shall perform the Group A inspections in accordance with the defined LTPD requirements on each inspection sublot. Electrical parameter testing as specified shall be performed by variables with test data recorded.

4.2.1.3 With each shipment lot, the supplier shall provide a Certificate of Compliance to test level T2 of this specification.

4.2.2 Test Level T1 Requirements – Test level T1 shall consist of the following requirements.

4.2.2.1 The supplier shall perform the Parameter Stability Testing defined in paragraph 4.3 on each device to be supplied. Electrical parameter testing as specified shall be performed by attributes.

4.2.2.2 The supplier shall perform the Group A inspections in accordance with the defined LTPD requirements on each inspection sublot. Electrical parameter testing as specified shall be performed by attributes with test data recorded.

4.2.2.3 With each shipment lot, the supplier shall provide a Certification of Compliance to test level T1 of this specification.

4.3 Parameter Stability Tests

Each Hybrid device is to be supplied under this specification and shall receive the following tests in addition to other standard testing performed by the manufacturer.

4.3.1 Hermetic Seal Test – Fine Leak – Each Hybrid device shall be tested for a case leakage rate of 1×10^{-8} cc/sec or smaller using a helium mass spectrometer or equivalent method. Devices with a case leakage rate greater than specified shall be removed from the lot.

4.3.2 Hermetic Seal Test – Gross Leak – Each Hybrid device shall be tested for gross leaks using fluorocarbon gross leak test or equivalent method. Devices with any indication of case leakage shall be removed from the lot.

4.3.3 Temperature Storage – Each Hybrid device shall be subjected, in a non-operating state, to a temperature of 150° C for a minimum period of 48 hours.

4.3.4 Temperature Cycling – Each Hybrid device shall be temperature cycled from -55° C to 150° C for a minimum of 10 cycles. Each cycle shall consist of at least 15 minutes at each temperature extreme with a maximum transition time of 5 minutes between each temperature extreme.

4.3.4 Reverse Bias Clamp Inductive Test -

 V_{CEO} = Rated Input Voltage I_C = 5A, f = 25 kHz, E_{out} = 5V T_C = 25^oC, see Figure 4 4.3.6 High Temperature Reverse Bias -- Each Hybrid device will be high temperature reversed biased in the circuit shown in Figure 3. The conditions of this test are as follows:

Circuit and voltages as shown in Figure 3.



Figure 3. High Temperature Reverse Bias Circuit

4.3.7 The following measurements will be made before and after the high temperature reverse bias test. The unit measurements shall be recorded or the devices will be celled in order to compare and guarantee the delta (Δ) requirements depending on the test level to which the lot is being prepared.

			Maximum Readings		
C	Device	Test	Initial	Delta	
	Туре	1.1.C	and Final	Change	Symbol
	600-602	8	1.5∨	±0.3∨	V4-1 (on)
SM	625-627	8	1.5V	±0.3∨	V4-1 (on)
SM	610-612	8	-1.5V	±0.3∨	V4-1 (on)
SM	635-637	8	1.5V	±0.3∨	V4-1 (on)
	600-602	10	1.0V	±0.25∨	V2-1 (on)
SM	625-627	10	1.25V	±0.30V	V2-1 (on)
SM	510-612	10	-1.0V	±0.25V	V2-1 (on)
SM	635-637	10	-1.25V	±0.30∨	V2-1 (on)
	500-602	12	10µA	±1.0 ¹ μΑ	14-1
SM6	625-627	12	10µA	±1.0 ¹ µA	14-1
SM6	510-612	12	~ 10µA	±1.0 ¹ µA	14-1
SM	535-637	12	-10µA	±1.0 ¹ μΑ	14-1
SM	600-602	14	10µA	±2.0 ¹ μΑ	11-2
SM	625-627	14	10µA	$\pm 2.0^{1} \mu A$	11-2
SM	610-612	14	– 10µA	±2.0 ¹ μΑ	11-2
SM	635-637	14	-10µA	±2.0 ¹ μΑ	11-2

4.38 Power Stress – Each Hybrid device shall be burnedin using the circuit shown in Figure 4. The conditions are as follows:

Time = 40 hours minimum

Circuit and conditions as shown in Figure 4.

4.3.9 The readings before and after burn-in shall be as specified in paragraph 4.3.7 above.

 1 or ±100% whichever is greater

.

TABLE I. GROUP A INSPECTION

Examination or Test	Symbol	Electrical Spec Test Number	Sample Size (LTPD)	Max. Acc. No. of Failures
Subgroup 1				
Visual and Mechanical			22 (10)	0
Subgroup 2 25 ⁰ Tests				
On-State Voltage On-State Voltage	V4-1 on V4-1 on	8		
Diode Forward Voltage	V2-1 on	10	45	0
Diode Forward Voltage	V2-1 on	11	(5)	0
Off State Current	14-1	12		
Diode Reverse Current	11-2	14		
Subgroup 3 100 ⁰ C Tests				
Off State Current	14-1	13	45	0
Off State Current	11-2	15	(5)	
Subgroup 4 25 ⁰ C Tests				
Current Delay Time	tdi	1		
Current Rise Time	tri	2		
Voltage Rise Time	trv	3	45	0
Voltage Fall Time	tfv	5	(5)	
Current Fall Time	rfi	6		



Figure 4. POWER BURN-IN CIRCUIT

SILICON GENERAL INC.

11651 Monarch Street, Garden Grove, California 92641 • 714/892-5531 • TWX: 910-596-1804

SPECIFICATION HRT 600-2

HYBRID SWITCHING REGULATORS HIGH RELIABILITY TYPES (3 LEAD TO-3)

SM645 SM646 SM647 SM655 SM656 SM657

CONTENTS

- 1.0 Scope
- 2.0 Applicable Documents
- 3.0 Requirements
- 4.0 Quality Assurance Provisions

	High Rel	High Rel
	Construction	Construction
Standard Type	with T_1 Testing	with T_2 Testing
SM645	SM645B	SM645A
SM646	SM646B	SM646A
SM647	SM647B	SM647A
SM655	SM655B	SM655A
SM656	SM656B	SM656A
SM657	SM657B	SM657A

1.0 SCOPE

This specification defines the detail requirements for High Reliability Hybrid Switching Regulators. (Reference MIL-STD-750). Very extensive 100% testing for parameter stability has been included in the Quality Assurance Provisions.

1.1a ABSOLUTE MAXIMUM RATINGS

	SM645	SM646	SM647	SM655	SM656	SM657
Input Voltage, V _{4 - 2}	60V	80∨	100V	-60V	-80V	-100V
Output Voltage, V ₁₋₂	60V	80V	100V	-60V	-80V	-100V
Drive-Input Reverse Voltage, V ₃₋₄	5V	5V	5V	-5V	-5V	-5V
Output Current, I ₁	15A	15A	15A	~15A	-15A	-15A
Peak Output Current	20A	20A	20A	~ -20A	-20A	-20A
Drive Current, I ₃	-0.4A	~0.4A	-0.4A	0.4A	0.4A	0.4A
Thermal Resistance						
Junction to Case, θ_{1-C}						
Power Switch			2° C/	W		
Commutating Diode			2 ^o C/	W		
Case to Ambient, θ_{C-A}				C/W		
Operating Temperature Range, T			55 ⁰ C to	+ 125 ⁰ C		
Maximum Junction Temperature, T				° c		
Storage Temperature Range			65 ⁰ C to	+150 ⁰ C		

			SM6	45, 646 A	ND 647	SM6	5, 656 AN	D 657		
	Test	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Units	Conditions
1	Current Delay Time (I ₃ – I ₄)	^t di	-	35	60	-	35	60	ns	v _{in} = 25V (~25V)
2	Current Rise Time (14)	t _{ri}	-	65	150		65	175	ns	V _{out} = 5V (-5V)
3	Voltage Rise Time (V _{4 – 1})	۲ _{rv}	-	40	60	-	40	60	ns	l _{out} = 7A (-7A)
4	Voltage Storage Time (V _{4 - 1} - I ₃)	t _{sv}		900	-	-	900	-	ns	l ₃ = -30 mA (30 mA)
5	Voltage Fall Time (V _{4 - 1})	^t fv	~	70	175	-	100	300	ns	
6	Current Fall Time (۱д)	t _{fi}	~	175	300	-	175	300	ns	
7	Efficiency (Note 1)	η		85	-	-	85	-	%	
8	On-State Voltage (Note 2)	V _{4-1 (on)}	~	1.0	1.5	-	-1.0	-1.5	v	I ₄ = 7A (-7A), I ₃ = -0.03A (0.03A)
9	On-State Voltage (Note 2)	V _{4-1 (on)}	-	2.5	3.5	-	-2.5	-3.5	·v	t ₄ = 15A (-15A), I ₃ = -0.03A (0.03A)
10	Diode Forward Voltage (Note 2)	V _{2-1 (on)}	-	0.85	1.25	-	-0.85	- 1.25	v	1 ₂ = 7A (-7A)
11	Diode Forward Voltage (Note 2)	V _{2-1 (on)}	-	0.95	1.75	-	-0.95	-1.75	v	1 ₂ = 15A (-15A)
12	Off-State Current	^I 4-1		0.1	10.0	-	-0.1	-10.0	μA	V ₄ = Rated input voltage
13	Off-State Current	¹ 4-1	-	10.0	1000.0	-	-10.1	-1000.0	μA	V ₄ = Rated input voltage, T _A = 100 ⁰ C
14	Diode Reverse Current	I1-2		1.0	10.0	-	-1.0	-10.0	μA	V ₁ = Rated output voltage
15	Diode Reverse Current	I ₁₋₂	-	500.0	1000.0	-	-500.0	-1000.0	μA	V ₁ = Rated output voltage, T _A = 100 ^o C

Notes:

1. The efficiency is a measure of internal power losses and is equal to Output Power divided by Input Power. The switching speed circuit of Figure 1, in which the efficiency is measured, is representative of typical operating conditions for the SM600 series switching regulators.

Pulse test: Duration = 300µs, Duty Cycle ≤2%, 25 °C.

POWER DISSIPATION CONSIDERATIONS

The total power losses in the switching regulator is the sum of the switching losses, and the power switch and diode D.C. losses. Once total power dissipation has been determined, the Power Dissipation curve, or thermal resistance data may be used to determine the allowable case or ambient temperature for any operating condition.





Note: SM655, SM656, SM657 Circuit and waveforms are identical but of opposite polarity ($V_{in} = -25V_1 V_{out} =$

-5V1 IDRIVE = +30mA).

Figure 1.

2.0 APPLICABLE DOCUMENTS

The following documents of the issue in effect on the date of invitations for bids, form a part of this specification to the extent specified herein.

MIL-S-19500 – General Specification for Semiconductor Devices

MIL-S-19491 — Preparation for Delivery of Semiconductor Devices

3.0 Requirements

3.1 Design and Construction

The Hybrid devices supplied under this specification shall have a design and construction such that they will meet all of the requirements specified herein. The dimensions and physical characteristics shall be as specified in Figure 2.

3.2 Performance Characteristics

The performance characteristics of the Hybrid device supplied under this specification shall be as specified in Group A inspection defined in Table I.

3.3 Quality Assurance

The Quality Assurance Provisions shall be as defined in paragraph 4.0.

3.4 Test Methods

Test methods shall be as specified herein.

3.5 Marking

The markings on the devices supplied shall be permanent and legible and shall include the Manufacturer's name or trademark, a Manufacturing Date Code in accordance with MIL-S-19500 and the specific device type number.

3.6 Preparation for Delivery

The Hybrid devices supplied under this specification shall be prepared for delivery in accordance with level C of MIL-S-19491 unless otherwise directed in the specific contract or purchase order.

3.7 Ordering Data

Procurement document should specify the following:

- a. Specific item type number
- b. Number and date of this specification
- c. Quality Assurance Test level required
- d. Any special packaging if required



Figure 2. Physical Dimensions and Biasing Diagrams

4.0 QUALITY ASSURANCE PROVISIONS

4.1 General Provisions

4.1.1 Inspection Responsibility – The supplier is responsible for the performance of all inspection requirements and acceptability of results as specified herein for the Test Level identified in the contract or purchase order.

4.1.2 Controlled Manufacturer – The devices supplied under this specification shall be manufactured under controlled conditions using formally defined quality assurance methods and systems.

4.1.3 Manufacturing Traceability – Each device supplied under this specification shall be traceable to a specific process group, to permit tracing of its full manufacturing history. Process group records shall indicate the exact date that each manufacturing operation was performed and identify materials and process procedures which were used. The manufacturer shall keep these records on file for at least five years.

4.1.4 Definitions

4.1.4.1 Inspection Lot – An "inspection lot" is a collection of devices from which a sample is withdrawn and inspected to determine compliance with the acceptability criterion. It shall consist of one or more "inspection sublots" of the device types defined in this specification. The maximum inspection lot size shall be 5000 units.

4.1.4.2 Inspection Sublot – An "inspection sublot" shall consist of a collection of devices of a single type which have been manufactured under the same conditions and with the same materials.

4.1.4.3 Shipment Lot - A "shipment lot" shall consist of devices taken from an accepted inspection lot for the purpose of shipment on a specific contract or order.

4.1.4.4 Group A Inspection – Group A inspection shall consist of the examinations and tests specified in Table I, and shall be performed on a sublot basis.

4.1.4.5 Controlled Inventory – The controlled inventory shall consist of lots which have successfully passed the acceptance inspection and are being held in storage prior to actual shipment. A controlled inventory shall have adequate safeguards to insure that no defective or untested devices can be included in it. It shall be accessible only to those individuals who are formally identified as authorized personnel.

4.2 Acceptance Inspection

The acceptance inspection requirements shall be as defined by the applicable test level. The procedures of MIL-S-19500 shall apply to Group A inspection. Inspection lots which have been inspected and accepted shall be kept in a controlled inventory. Shipment lots shall be formed using devices taken from accepted inspection lots.

4.2.1 Test Level T2 Requirements - Test level T2 shall consist of the following requirements.

4.2.1.1 The supplier shall perform the Parameter Stability Testing defined in paragraph 4.3 on each device to be supplied. Prior to starting the Blocking Stability test defined in paragraph 4.3.6, each device shall be serialized for individual identity. Variables test data for the controlled electrical parameters shall be recorded before and after stressing. The same procedure shall apply for the Power Stress stability test defined in paragraph 4.3.8.

4.2.1.2 The supplier shall perform the Group A inspections in accordance with the defined LTPD requirements on each inspection sublot. Electrical parameter testing as specified shall be performed by variables with test data recorded.

4.2.1.3 With each shipment lot, the supplier shall provide a Certificate of Compliance to test level T2 of this specification.

4.2.2 Test Level T1 Requirements – Test level T1 shall consist of the following requirements.

4.2.2.1 The supplier shall perform the Parameter Stability Testing defined in paragraph 4.3 on each device to be supplied. Electrical parameter testing as specified shall be performed by attributes.

4.2.2.2 The supplier shall perform the Group A inspections in accordance with the defined LTPD requirements on each inspection sublot. Electrical parameter testing as specified shall be performed by attributes with test data recorded.

4.2.2.3 The supplier shall provide a Certificate of Compliance to test level T1 of this specification with each shipment lot.

4.3 Parameter Stability Tests

Each Hybrid device is to be supplied under this specification and shall receive the following tests in addition to other standard testing performed by the manufacturer.

4.3.1 Hermetic Seal Test – Fine Leak – Each Hybrid device shall be tested for a case leakage rate of 1×10^{-8} cc/sec or smaller using a helium mass spectrometer or equivalent method. Devices with a case leakage rate greater than specified shall be removed from the lot.

4.3.2 Hermetic Seal Test – Gross Leak – Each Hybrid device shall be tested for gross leaks using fluorocarbon gross leak test or equivalent method. Devices with any indication of case leakage shall be removed from the lot.

4.3.3 Temperature Storage – Each Hybrid device shall be subjected, in a non-operating state, to a temperature of 150° C for a minimum period of 48 hours.

4.3.4 Temperature Cycling – Each Hybrid device shall be temperature cycled from -55° C to 150° C for a minimum of 10 cycles. Each cycle shall consist of at least 15 minutes at each temperature extreme with a maximum transition time of 5 minutes between each temperature extreme.

4.3.5 Reverse Bias Clamp Inductive Test -

4.3.6 High Temperature Reverse Bias – Each Hybrid device will be high temperature reversed biased in the circuit shown in Figure 3. The conditions of this test are as follows:

TA = +125⁰C

Time = 16 hours $\frac{+8}{-0}$ hours

Circuit and voltages as shown in Figure 3 for appropriate device.





Figure 3. High Temperature Reverse Bias Circuit

4.3.7 The following measurements will be made before and after the high temperature reverse bias test. The unit measurements shall be recorded or the devices will be celled in order to compare and guarantee the delta (Δ) requirements depending on the test level the lot is being prepared to.

Type Number	Test 1.1.6	Maximum Readings Initial & Final	Delta Change	Symbol
SM645/646/647	8	-1.5V	± 0.3∨	V4-1 (on)
SM655/656/657	8	-1.5V	± 0.3∨	V4-1 (on)
SM645/646/647	10	1.25∨	±0.3∨	V2-1 (on)
SM655/656/657	10	~1.25∨	±0.3∨	V2-1 (on)
SM645/646/647	12	10μΑ ¹	± 1.0μA ¹	14-1
SM655/656/657	12	-10μΑ	± 1.0μA ¹	14-1
SM645/646/647	14	10μΑ	± 2.0μA ¹	1-2
SM655/656/657	14	-10μΑ	± 2.0μA ¹	1-2

¹ or ± 100% whichever is greater.

4.3.8 Power Stress — Each Hybrid device shall be burnedin using the circuit shown in Figure 4. The conditions are as follows:

$$T_{C} = 140^{\circ}C$$

Time = 40 hours minimum

Circuit and conditions as shown in Figure 4.

4.3.9 The readings before and after burn-in shall be as specified in paragraph 4.3.7 above.





TABLE I. GROUP A INSPECTION

-7

Examination or Test	Symbol	Electrical Spec Test Number	Sample Size (LTPD)	Max. Acc. No. o Failures
Subgroup 1				
Visual and Mechanical	_		22 (10)	0
Subgroup 2 25 ⁰ C Tests				
On-State Voltage On-State Voltage Diode Forward Voltage Diode Forward Voltage Off-State Current Diode Reverse Current	V4-1 on V4-1 on V2-1 on V2-1 on I4-1 I1-2	8 9 10 11 12 14	45 (5)	0
Subgroup 3 T _A = +100 ⁰ C Tests				
Off-State Current Off-State Current	14-1 11-2	13 15	45 (5)	0
Subgroup 4 25 ⁰ C Tests				
Current Delay Time Current Rise Time Voltage Rise Time	tdi t _{ri} trv	1 2 3	45	0
Voltage Fall Time Current Fall Time	t _{fv}	5 6	(5)	

TRANSISTOR ARRAYS

SILICON GANEPAL LINEAR INTEGRATED CIRCUITS

SG3183/3183A

FEATURES

High voltage capability

Low saturation voltage

Collector current to 100 mA

Closely matched parameters

High Current NPN Transistor Arrays

This series of arrays consists of five closely-matched, high current NPN transistors. Although sharing a common monolithic substrate, the transistors are connected such that all terminals are independent, including the substrate bias connector. With current capability to 100 mA per transistor, these arrays are ideally suited for all types of driving applications including relays, lamps, and thyristors. The SG3183A are higher voltage versions of the SG3083.

ABSOLUTE MAXIMUM RATINGS

Power Dissipations: Any one transistor Total package Above 25°C derate linearly Ambient Temperature Range: Operating (N-Package) Operating (J-Package) Storage (both packages) Maximum Collector Current Maximum Base Current

500 mW 750 mW 6.67 mW/°C

--40 to +85°C --55 to +125°C --65 to +150°C 100 mA 20 mA





NOTE: The collector of each transistor is isolated from the substrate by an integral diode which must be reverse biased by connecting the substrate to a voltage more negative than any collector. To preven undesigned coupling between transistors, the substrate connection should be connected to an AC or DC ground.

ELECTRICAL CHARACTERISTICS AT TA = 25°C

PARAMETER SYMBOL CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector-Substrate Breakdown Voltage, BV _{CSO} , I _C = 100 µA				
SG3183	40	70	~	v
SG3183A	50	70		v
Collector-Base Breakdown Voltage, BV _{CBO} , I _C = 100 µA				
SG3183	40	70	-	v
SG3183A	50	70	~	v
Collector-Emitter Breakdown Voltage, BV _{CEO} , I _C = 1 mA				
SG3183	30	40	-	v
SG3183A	40	50	-	v
Emitter-Base Breakdown Voltage, BV _{ERO} , I _E = 100 µA	,			
All types	5	6.9	~	v
Collector Cutoff Current, ICEO, VCE = 10V		-	10	μA
Collector Cutoff Current, ICBO, VCR = 10V	-	-	1	μA
DC Forward Current Transfer Ratio, hFE				
All types V _{CE} = 3V, I _C = 10 mA	50	100	-	
V _{CE} ' = 5V, I _C = 50 mA	40	75		
Collector-Emitter Saturation Voltage, VCE (SAT)				
SG3183 /SG3183A I _C = 50 mA, 1 _B = 5 mA	-	1.7	3.0	v
Base to Emitter Voltage, V _{BE} , V _{CE} = 3V, I _C = 10 mA	0.65	0.75	0.85	v
For Q ₁ and Q ₂ Matched Pair				
Input Offset Voltage V _{1O} V _{CE} = 3V, I _C = 1 mA	-	1.2	5	mV
Input Offset Current II IOI VCE = 3V, IC = 1 mA	-	0.7	2.5	μA

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

Transistor Arrays

These transistor arrays offer VBE typically matched to ± 0.5 mV, less than 10% variation in hfe, operation from dc to 300 MHz, high current gain from 10 μ A to 10 mA and high voltage capability.

SG3821 (CA3046, 3045) Matched Transistor Array — five general purpose monolithic NPN transistors internally connected to form two independent differential amplifiers, each with its associated current source transistor.

ABSOLUTE MAXIMUM RATINGS

Collector-base Voltage 4	OV (CA	Series 20V) Series 20V) Series 15V)	Emitter-base Voltage Collector-Current Operating Temperature Range	5V 50mA 0—125 ^o C(CA Series	0 - 70ºC)
PARAMETERS*		CONDITIONS	3821,	3046/3086	UNITS
Collector-Substrate Breakdown		$I_{C} = 10\mu A$, $I_{B} = 0$	40	20	V
Collector-Base Breakdown		$I_{\rm C} = 10\mu A$, $I_{\rm F} = 0$	40	20	V
Collector-Emitter Breakdown		$I_{\rm C} = 100\mu A$, $I_{\rm B} = 0$	25	15	V
Emitter-Base Breakdown		$I_{\rm E} = 10\mu A$, $I_{\rm C} = 0$	5	5	V
Collector-Substrate Leakage		V _{CS} = 20V, I _B = 0	80	80	nA
Collector-Base Leakage		V _{CB} = 20V, I _E = 0	40	40	nA
Collector-Emitter Leakage		V _{CE} = 20V, I _B = 0	500	500	nA
Forward Current-Transfer Ratio		V _{CE} = 5V, I _C = 10µA	80 (typ)	80 (typ)	
Forward Current-Transfer Ratio		V _{CE} = 5V, I _C = 1mA	50/400	50/400	
Forward Current-Transfer Ratio		V _{CE} = 5V, I _C = 10mA	80 (typ)	80 (typ)	-
Collector-Emitter Saturation		I _C = 10mA, I _B = 1mA	0.5 (typ)	0.5 (typ)	V
Gain-Bandwidth Product		V _{CE} = 5V, I _C = 3mA	500 (typ)	500 (typ)	MHz
Collector-Substrate Capacitance		V _{CS} = 5V, I _C = 0	2.0 (typ)	2.0 (typ)	pF
Collector-Base Capacitance		V _{CB} = 5V, I _C = 0	0.4 (typ)	0.4 (typ)	рF
Noise Figure		f = 1kc, V _{CE} = 5V, I _C = 100	μ A, R _S = 1k Ω 4 (typ)	4 (typ)	dB
Input Offset Voltage for any two transisto	rs	V _{CE} = 5V, I _C = 1mA	5	5	mV
Input Offset Current for any two transisto	rs	V _{CE} = 5V, I _C = 1mA	4	2	μA

*Parameters apply for $T_A = 25^{\circ}C$ and are min/max limits unless otherwise specified.

Note: Substrate pin (///) must be connected to the most negative DC potential -- which should also be a good AC ground -- for proper isolation between transistors.

 (\mathbf{i}) 3821/3046/3045/



OTHER CIRCUITS

Wideband Amplifiers/Multipliers Multipliers Modulators Line Receivers Voltage Comparators Precision Voltage Reference

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

SG111/211/311

Voltage Comparators

The SG111/211/311 are medium speed, high input impedance devices which are especially well suited for use in level detection and low level voltage sensing applications. Operation may be obtained from supply voltages ranging from $\pm 15V$ down to a single $\pm 5V$ source.

The output, an open collector NPN capable of switching 50V and 50mA, can drive RTL, DTL, TTL, MOS logic, relays or lamps. Both input and output can be isolated from ground and the output can drive loads referred to a positive supply, ground or a negative supply. These devices also offer offset balance, strobe capability and pin configuration of the SG710 Comparator.

211 311 UNITS 111 PARAMETERS* -55 to +125 -25 to +85 0 to +70 oC Operating Temperature Range т, ј Т, J Package Types ±15 v Supply Voltage 7.5 (10.0)² m∖ Input Offset Voltage Rg < 50k 3 (4.0)2 $10(20)^2$ $50(70)^2$ nΑ Input Offset Current 250 (300) nΑ 100 (150) Input Bias Current V/mV 200 (typ) 200 (typ) Voltage Gain 200 (typ) nS Response Time 200 (typ) v Saturation Voltage Isink = 50 mA 1.5 1.5 V⁺ = 4.5V v 0.4 0.4 I_{sink} = 8 mA V--- = 0V 10 (500) 50 nΑ Output Leakage Current v ±30 ±30 Differential Input Voltage max 36 v 36 Total Supply Voltage, V84 max v Input Voltage Range ±14 (typ) ±14 (typ) 7.5 mΑ 6.0 **Positive Supply Current Negative Supply Current** 5.0 5.0 mΑ 50³ 40³ v Output Voltage, V74

*Parameters apply over supply voltage range and are min./max. limits either at $T_A = 25^{\circ}C$ (or over operating temperature range if enclosed in parentheses), unless otherwise indicated.

 1 The response time specified is for a 100mV input step with 5mV overdrive.

 2 The offset voltages and offset currents given are the maximum values required to drive the output down to 1V or up to 14V with 1mA load.

³Output voltage levels can be changed for compatibility with DTL and T2L logic levels.



Differential input voltage range of ±30V

- 150nA maximum bias current
- Consumes 135mW at ±15V

SILICON GANAPAL LINEAR INTEGRATED CIRCUITS

SG1401/2401/3401

Video Amplifiers

The SG 1401/2401/3401 video amplifiers are useful over a frequency range from DC to 200MHz. Internal emitter followers are used to achieve high input and low output impedances, allowing simple capacitor coupling. Biasing and gain-setting resistors are internally diffused, eliminating external resistor networks. The gain may be externally varied through the use of AGC diodes which are included in the circuit.

- 20dB voltage gain at 100MHz
- 5nsec rise and fall times
- Fixed or variable gain
- Single power supply voltage
- Minimum external components
- Symmetrical limiting

PARAMETERS/CONDITIONS*	1401	2401	3401	UNITS
Operating Temperature Range	-55 to +125	0 to +70	0 to +70	°C
Package Types	T, J	Т, Ј	, N	-
Supply Voltage	6/20		6/20	v
Power Consumption, no AGC voltage	110		120	mW
DC Output Voltage	8.7 (ty	(p)	8.7 (typ)	v
Peak-to-Peak Output, Pin 3 (4) to AC gnd	4 (typ)	3 (typ)	v
Voltage Gain, Pin 3 (4) ² open	2.2/3.3	2	2.2/3.2	dB
Voltage Gain, Pin 3 $(4)^2$ coupled to Pin 8 $(11)^2$	9/11		9/11	dB
Voltage Gain, Pin 3 $(4)^2$ coupled to Pin 9 $(12)^2$	18/21		18/21	dB
Voltage Gain, Pin 3 (4) ² to AC gnd	26/31		24/31	dB
Unity Gain Frequency, Pin 3 $(4)^2$ to AC gnd	200 (t	yp)	200 (typ)	MHz
Input Resistance, 20 dB gain	2.5 (ty	p)	2.5 (typ)	kΩ
Output Resistance, 20 dB gain	25 (ty	o)	50 (typ)	Ω
Input Capacitance, 20 dB gain	5 (typ)		5 (typ)	pF
Maximum Power Gain, 20 dB gain, $R_L = 50\Omega$	30 (typ	o)	30 (typ)	dB
Temperature Stability, 20 dB gain	±1 ¹		±2 ¹	dB
AGC Range	20 (mi	n)	22 (typ)	dB
Noise Figure, 20 dB gain, R _S = 1k	8 (min)	6 (typ)	dB

*Parameters apply only for $T_A = 25^{\circ}C$, $V_S = +12V$, and f = 1 MHz, and are

min/max limits unless otherwise specified.

¹Over operating temperature range. ²Numbers in parentheses refer to dual-in-line package.







AGC

232

GND 🗹



See Applications Notes for additional information.

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Silicon General LINEAR INTEGRATED CIRCUITS

Wideband Amplifier/Multiplier

SG1402/2402/3402 are monolithic four quadrant multipliers offering excellent frequency response and provision for use as a variable gain amplifier with both non-inverting and inverting outputs available. In addition to linear amplification, the device is also ideal for balanced modulation, pulse or gated amplification, and coincidence detection.

SG1402/2402/3402

- Single power supply voltage
- Self-contained biasing .
- 25dB voltage gain
- Differential or single ended inputs and outputs
- Large bandwidth
- Low power dissipation

PARAMETERS, CONDITIONS*	1402	2402	3402	UNITS
Supply Voltage	+1	8	+18	V
Load Current	15		15	mA
Operating Temperature Range	-55 to +125	0 to +70	0 to +70	°C
Package Types	J, T	J, ⁻	Т, N	_
Maximum Voltage Gain, single ended	23		20	dB
Variable Gain Range, with ext. balance	55		40	dB
Frequency Response, f – 3 dB	40	(min)	50 (typ)	MHz
Input Impedance, Pin 5 or 7 (7 or 10) ¹	1.	2 (typ)	1.2 (typ)	ΚΩ
Input Impedance, Pin 2 or 9 (3 or 12) ¹	1.	8 (typ)	1.8	ΚΩ
Output Impedance, Pin 3 or 8 (4 or 11)	1 10	0 (typ)	100 (typ)	Ω
Output Voltage Swing RL = 100K	3		3	Vpp
R _L = 1K	1.	3	1.3	
Quiescent DC Levels Pins 5, 6 and 7 (7, 8 & 10) ¹	3.	6 (typ)	3.6 (typ)	v
Pins 2 and 9 (3 & 12) ¹	1.	8 (typ)	1.8 (typ)	V
Pins 3 and 8 (4 & 11) ¹	6.	5/7.5	7.0 (typ)	V
Output Offset Voltage Minimum Gain	10		300	mV
Maximum Gain	200		500	
DC Output Shift, with max gain change	10	00	200	mV
Differential Control Voltage, for max gain change	20	00 (typ)	200 (typ)	mV
Maximum Gain Variation, over temperature	2		3	dB
Equivalent Input Noise (BW = 10MHz, R _S = 50Ω)	2!	5 (typ)	25	μVrms
Power Consumption	8	5	85	mW



*Parameters are for $T_A = 25^{\circ}C$, V⁺ = 10V, f = 100KHz and are min./max. limits unless otherwise specified.

¹Numbers in parentheses refer to dual-in-line package.

OUTPUT



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SG1402/2402/3402 Chip (See T-nackage diagram for pad functions)



CONNECTION DIAGRAMS



See Applications Notes for additional information.

7 INPUT

6 NC

5 BIAS

OUTPUT

3 CONTROL

2 NC

1 V+

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

Line Receivers

The SG1489A monolithic quad line receiver is designed to interface data terminal equipment with data communications equipment in conformance with the specifications of EIA Standard No. RS-232C.

- Input Resistance 3.0k to 7.0kΩ
- Input Signal Range ±30 Volts
- Input Threshold Hysteresis Built In
- Response Control
 - a) Logic Threshold Shifting
 - b) Input Noise Filtering

	PARAMETERS*	SG1489A	UNITS
Power Supply Voltage (n	nax, T _A = 25°C)	10	V
Input Signal Range (max	±30	v	
Output Load Current (T	4 = 25°C)	20	mA
Package Types	· · · · · · · · · · · · · · · · · · ·	J	
Power Dissipation (Packa	age Limitation, Ceramic Dual In-Line Package)	1000	mW
Derate above $T_A = +25$	5°C	6.7	mW/ºC
Operating Temperature F	Range	0 to +75	°C
Storage Temperature Ran	nge	-65 to +175	°C
Positive Input Current	(V _{in} = +25 Vdc)	3.6/8.3	
	(V _{in} = +3.0 Vdc)	0.43	mA
Negative Input Current	(V _{in} =25 Vdc)	-3.6/8.3	
	(V _{in} = -3.0 Vdc)	-0.43	mA
Input Turn-On Threshold (T _A = +25°C, V _{OL} ≤ 0	Voltage		
		1.75/2.25	v
Input Turn-Off Threshold $(T_A = +25^{\circ}C, V_{OH} \ge 2)$	Voltage		
	$2.5 \vee, 1 = -0.5 \text{ mA}$	0.75/1.25	v
Output Voltage High	$(V_{in} = 0.75V, I_{L} = -0.5mA)$	2.6/5.0	
	(Input Open Circuit, Iլ = –0.5 mA)	2.6/5.0	v
Output Voltage Low	(V _{in} = 3.0V, IL = 10mA)	0.45	v
Power Supply Current	(V _{in} = +5.0Vdc)	26	mA
Power Consumption	(V _{in} = +5.0Vdc)	130	mW
WITCHING CHARACTI	ERISTICS (T _A = +25°C)		
Propagation Delay Time	$(R_{L}=3.9\mathrm{k}\Omega)$	85	nS
Rise Time	(R _L = 3.9kΩ)	175	nS
Propagation Delay Time	(R _L = 390 Ω)	50	nS
Fall Time	(R _L = 390 Ω)	20	nS
			-

*Parameters are min./max. limits with response control pin open, V^+ = +5.0 Vdc ±1%, T_A = 0 to +75°C unless otherwise noted.







SG1489A

SILICON GENEPAL LINEAR INTEGRATED CIRCUITS

SG1503/SG2503/SG3503

PRECISION 2.5 VOLT REFERENCE

DESCRIPTION

This monolithic integrated circuit is a fully self-contained precision voltage reference generator, internally trimmed for ±1% accuracy. Requiring less than 2 mA in quiescent current, this device can deliver in excess of 10 mA with total load and line induced tolerances of less than 0.5%. In addition to voltage accuracy, internal trimming achieves a temperature coefficient of output voltage of typically 10 ppm/°C. As a result, these references are excellent choices for application to critical instrumentation and D to A converter systems. The SG1503 is specified for operation over the full military temperature range of -55°C to +125°C, while the SG2503 and SG3503 are

FEATURES

- Output voltage trimmed to ±1%
- Input voltage range of 4.5 to 40V
- Temperature coefficient of 10 ppm/°C
- Quiescent current typically 1.5 mA
- Output current in excess of 10 mA
- Interchangeable with MC1503 and AD580

ABSOLUTE MAXIMUM RATINGS

Input Voltage Power Dissipation Derate Over 25°C 4.5 – 40V 600 mW 4.8 mW/^oC Operating Temperature Range SG1503 SG2503/3503 Storage Temperature Range

TOP VIEWS

-55°C to +125°C 0°C to +70°C -65°C to +150°C

CONNECTION DIAGRAMS



CHIP LAYOUT

M or Y PACKAGE MINIDIP



T-PACKAGE TO-39



ELECTRICAL CHARACTERISTICS

(Input Voltage = 15V, IL = 0 mA, TA = Operating Temperature Range unless otherwise stated.)

		SG	1503/2	503	SG3503				
PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	MIN	TYP	MAX	UNITS	
Output Voltage	T _A = 25°C	2.485	2.50	2.515	2.475	2.50	2.525	Volts	
Input Voltage Range	T _A = 25°C	4.5	_	40	4.5	-	40	Volts	
Input Voltage Range	Over Operating Temperature	4.7	_	40	4.7		40	Volts	
Line Regulation	V _{IN} = 5 to 15V		1	3		1	3	mV	
Line Regulation	V _{IN} = 15 to 40V	-	3	5	-	3	10	mV	
Load Regulation	ΔIL = 10 mA	_	3	5	-	3	10	mV	
Load Regulation	$\Delta I_{L} = 10 \text{ mA}, \text{V}_{IN} = 30 \text{V}$	-	4	8	-	4	15	mV	
Temperature Regulation	~55° to +125°C	_	15	20		_	-	mV	
Temperature Regulation	0°C to +70°C		2.5	5	-	5	10	mV	
Quiescent Current	VIN = 40V	_	1.5	2.0	_	1.5	2.0	mA	
Short Circuit Current	$T_A = 25^{\circ}C$	15	20	30	15	20	30	mA	
Ripple Rejection	f = 120 Hz, T _A = 25°C	_	76	-	-	76		dB	
Output Noise	B.W. = 10 kHz, T _A = 25°C	-	100	-	-	100	_	μV _{rms}	
Stability			250	-	-	250		μV/ _{kHr}	

OUTPUT VOLTAGE vs. TEMPERATURE



RIPPLE REJECTION



9

SG1595/1495

Multipliers

The SG1595/1495 four quadrant analog multipliers are designed for applications where the output voltage required is a linear product of two input voltages. Both types provide excellent linearity and operation over a wide supply range and input voltage range. Applications include use as multipliers, dividers, squarers, phase detectors, frequency doublers and as balanced modulators.

- Excellent linearity •
- Adjustable scale factor
- Excellent temperature stability
- Wide bandwidth
- High input voltage range
- Wide supply voltage operation

Multiply with Op Amp Level Shift



*Parameters apply over operating temperature range and are min/max limits unless otherwise specified.

f = 20 Hz

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²Voltage applied between pins 2-1, 14-1, 1-9, 1-12, 1-4, 1-8, 12-7, 9-7, 8-7, 4-7.



	RESISTOR*	R1	R ₅	R ₆	R ₇	R ₈				RB			
	TOLERANCE	5%	1%	1%	1%	1%	1%	1%	5%	20%	0.5%	5%	5%
1	V ⁺ = +32 V, V ^{-−} = −15 V −10 V ≤V _X ≤+10 V −10 V ≤V _Y ≤+10 V	9.1	121	100	11	121	15	13.7	12	5.0	11	15	15
2	$V^+ = +15 V, V^- = -15 V$ -5 V <v<sub>x < +5 V -5 V <v<sub>y < +5 V</v<sub></v<sub>	3.0	300	100	100	300		13.7	12	5.0	3.4	8.2	8.2
3	V ⁺ = +15 V, V [−] = −15 V −10 V ≤V _x ≤+10 V −10 V ≤V _y ≤+10 V	1.2	121	100	11	910	13.7	13.7	12	5.0	1.5	15	15



SG1595/1495 Chip (See D-package diagram for pad functions)



CONNECTION DIAGRAM

Silicon General LINEAR INTEGRATED CIRCUITS

Modulators

The SG1596/1496 are monolithic double-balanced modulator/demodulator devices designed for use where the output voltage is a product of an input voltage (signal) and a switching function (carrier). Typical applications include modulation and demodulation of AM, SSB, DSB, FSK, FM and phase encoded signals. Additional uses include frequency doubling, linear mixing and chopping.

SG1596/1496

- Excellent carrier suppression .
- Fully balanced inputs and output
- Low offsets and drift
- High common mode rejection
- Adjustable gain and signal handling
- Useful to 100MHz

PARAMETERS/CONDITIONS*	1596	1496	UNITS			
Operating Temperature Range	-55 to +125	0 to +70	oC			
Applied Voltage ¹	30	30	v			
Differential Input Signal, (V7 - V8)	±5.0	±5.0	v			
Differential Input Signal, (V4 - V1)	±(5 + 1	5 R _e)	v			
Input Signal, (V ₂ - V ₁ , V ₃ - V ₄)	5.0	5.0	v			
Package Types	J, T	J, T, N				
Carrier Feedthrough			· · · · · ·			
$v_c = 60 \text{ mV}(\text{rms})$ sine wave, $f_c = 1.0 \text{kHz}$, offset adjusted (typ)	40	40	μVrms			
v _c = 60 mV(rms) sine wave, f _c = 10MHz, offset adjusted (typ)	140	140				
v _c = 300 mV _{pp} square wave, f _c = 1.0kHz, offset adjusted (max)	0.2	0.4				
$v_c = 300 \text{ mV}_{pp}$ square wave, $f_c = 1.0 \text{ kHz}$, offset not adjusted (max)	100	200				
Carrier Suppression						
f _s = 10kHz, 300 mV(rms), f _c = 500kHz, 60 mV(rms) sine wave offset adjusted (min)	50	40				
f _s = 10kHz, 300 mV(rms), f _c = 10MHz, 60 mV(rms) sine wave offset adjusted (typ)	50	50	dB			
Transadmittance Bandwidth						
R_L = 50 Ω , Carrier Input Port, v_c = 60 mV(rms) sine wave, f_s = 1.0kHz, 300 mV(rms) sine wave	300 (typ)	300 (typ)				
Signal Input Port, v _s = 300 mV(rms) sine wave ²	80 (typ)	80 (typ)	MHz			
Voltage Gain, Signal Channel v _s = 100 mV(rms), f = 1.0kHz ²	2.5	2.5	V/V			
Input Resistance, Signal Port f = 5,0MHz ²	200 (typ)	200 (typ)	kΩ			
Input Capacitance, Signal Port f = 5.0MHz ²	2.0 (typ)	2.0 (typ)	pF			
Single Ended Output Resistance f = 10MHz	40 (typ)	40 (typ)	kΩ			
Single Ended Output Capacitance, f = 10MHz	5.0 (typ)	5.0 (typ)	pF			
Input Bias Current (I1 + I4)/2 or (I7 + I8)/2	25	30	μΑ			
Input Offset Current $(I_1 - I_4)$ or $(I_7 - I_8)$	5.0	7.0	μΑ			
Average TC of Input Offset Current	2.0 (typ)	2.0 (typ)	nA/ºC			
Output Offset Current (I ₆ - Ig)	50	80	μΑ			
Average TC of Output Offset Current	90 (typ)	90 (typ)	nA/ºC			
Signal Port Common Mode Input Voltage Range f _s = 1,0kHz	5.0 (typ)	5.0 (typ)	V _{p-p}			
Signal Port Common Mode Rejection Ratio ²	-85 (typ)	-85 (typ)	dB			
Common Mode Quiescent Output Voltage	8.0 (typ)	8.0 (typ)	 			
Differential Output Swing Capability	8.0 (typ)	8.0 (typ)	-			
Positive Supply Current (16 + 19)	3.0	4.0	V _{p-p}			
Negative Supply Current (110)	4.0	5.0	μA mA			
Power Dissipation	33 (typ)	33 (typ)	mA mW			
	00 (typ)	55 (typ/	11100			

*Parameters are for $T_A = 25^{\circ}C$ and are min/max limits unless otherwise specified.

¹Voltage applied between pins 6-7, 8-1, 9-7, 9-8, 7-4, 7-1, 8-4, 6-8, 2-5 and 3-5.

 $^{2}v_{7} - v_{8} = 0.5 \, \text{Vdc}$

TYPICAL MODULATOR CIRCUIT









SG1596/1496 Chip (See for ped functions)

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APPLICATION NOTES

SG1401 Video Amplifier SG1402 Videoband Amplifier/Multiplier SG1501A Dual Polarity Tracking Regulator SG1524 Regulating Pulse Width Modulator - Simplifying Converter Design - Deadband Control - Improving Dynamic Response SG1524B Regulating Pulse Width Modulator - Converting 1524 Designs - Versatile Control For Switching **Power Supplies** SG1524/1525A/1526/1527A, 1627/1629 Power Supply Circuits SG1542, 1543, 1544, 3523 Power Supply Supervisory Circuits SG1549 Current Sense Latch SG1627/1629 Dual High Current Output Driver SG1635 Motor Drive IC SG1731 High Efficiency Motor Drive Systems SG1731 Feedback Controllers

Applications Notes - The SG1401 Video Amplifier

The SG 1401-SG 3401 has been designed to provide maximum versatility as a general-purpose, single-ended amplifier. With its broad frequency capability, this circuit will be useful in a wide range of applications provided that the usual considerations for high-frequency circuit designs are observed. The following information is presented toward aiding in the optimization of the many possible configurations of this device.

FIXED GAIN

In the circuit configuration shown in Figure 1, the overall voltage gain is approximated by resistors R1 and the parallel combination of R2 and R3, as

Av
$$\approx 1 + \frac{R_1}{R}$$
, where R = $\frac{R_2R_3}{R_2 + R_3}$









VARIABLE GAIN

Since the dynamic impedance of a forward-biased diode is inversely proportional to the current through it, a convenient gain control can be achieved by using a pair of diodes as a variable impedance. In the circuit of Figure 4, R3 has been replaced by two diodes whose impedances act in parallel due to the decoupling of CD. If the diodes are driven from a voltage source, a logarithmic relationship between gain and control signal is achieved (see Figure 5); while if a current source is used, the relationship is linear as shown in Figure 6.

There are two limitations on this form of gain control. First, the diodes' capacitance limits their effectiveness to frequencies below 20 MHz and, secondly, the signal voltage across the diodes should be held to less than 50 millivolts RMS to minimize self-modulation of amplifier gain. Additionally, the AGC current should be limited to 3 mA maximum to keep the diodes out of saturation.

With no external connections, the voltage gain is determined solely by R1 and R2 and is $1\frac{1}{2}$ or 3 dB. Decreasing the effective value of R2 by capacitively coupling a lower resistor in parallel, raises the gain. Four fixed gain settings are provided internal to the circuit; however, any other setting within the maximum gain of the amplifier is possible with external resistors as shown in Figure 2.

The value of the coupling capacitor, CF is determined by the low frequency response desired, as its capacitive reactance will add to the value of the resistance it couples. Therefore, the lower cutoff frequency will be

$$f_c \approx \frac{1}{2\pi R_3 C_F}$$

Utilizing the internal 90 or 460 ohm resistors for higher gain settings provides the added advantage of maximum temperature stability since the close tracking of adjacent diffused resistors keeps their ratio constant. Typical temperature variation of this circuit is shown below:

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Figure 4.

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Figure 7. Frequency Response.





With the capability of operation at 100 MHz, the SG1401-SG3401 also has some susceptibility to external stray reactances; however, with reasonable care, complete stability may be assured. Some general precautions which should be considered include the following:

- (1) Power supply decoupling close to the circuit terminals (a 0.1 mfd capacitor is usually adequate).
- (2) Maintain separation of input and output lines.
- (3) Minimize load capacitance or insert a series resistor (up to 50 ohms) in the output.
- (4) Purposely limit the high frequency response with a stabilizing capacitor CS between pins 3 and 4.

Since the gain of this circuit is reduced by increasing the amount of feedback, the potential for instability is greatest when the gain is at its minimum value. This characteristic and the stabilizing effects of a 4.7 picofarad capacitor between pins 4 and 3 are illustrated in the frequency response curves presented in Figure 7. The relationship between the value of CS and the upper cutoff frequency of a 20 dB gain setting is shown in Figure 8 below.



Figure 8. Upper Cutoff Frequency vs. CS Value.







Figure 6. Gain vs. AGC Diode Current.

Application Notes-SG1402- Wideband Amplifier/Multiplier

INTRODUCTION

Rapid advances in the state-of-the-art of processing monolithic linear integrated circuits have made the use of tightly matched components a practical reality. This in turn has opened the doors to a new class of circuit characterized by its utility, versatility, and ease of application. It is now possible to include on a monolithic chip, many of the components which, because of relatively poor tolerances, were formerly required to be external to the circuit. The SG1402, shown schematically in Figure 1, illustrates this capability both by its inclusion of all necessary biasing networks and by the nature of the circuit itself which requires extremely well matched component parameters for successful operation.



Figure 1. SG1402 Schematic Diagram.

HOW IT WORKS

The heart of the SG 1402 is a four quadrant multiplier consisting of two cross-coupled differential amplifiers which are jointly controlled by a third differential amplifier. This part of the circuit is shown in simplified form as Figure 2. The constant current, I₀, is divided by Q6 and Q10 and divided again by each of the upper diff amps such that, for balanced operation, transistors Q5, Q7, Q9, and Q12 each have $\frac{1}{2}$ Iowing through them. An examination of the way in which the above diff amps are cross-coupled will show that while the collector load resistors receive a portion of their current from each diff amp, the signals will arrive out of phase with respect to each other. This is because the input voltage, v_c, is amplified common emitter — with 180° phase shift — through Q9 and summed at resistor R7 with the signal which has gone common collector-common base — with 0° phase shift — through Q5. Therefore, with the circuit perfectly balanced, the two signals completely cancel out and the output has zero signal. This can be shown mathematically as follows:



Figure 2. Simplified Schematic of the Multiplier Section of the SG 1402.

The collector current in one side of a simple differential amplifier (Q5 and Q7, for example) is:

$$i_{c1} = \frac{I_{E1}}{1 + exp\left(\frac{q}{kT}v_{c}\right)}$$

where: IF1 = sum of currents in each collector

$$\frac{kT}{q} = 26 \text{ millivolts at } 25^{\circ}\text{C}$$

$$v_{c} = \text{differential input voltage}$$

This equation can be differentiated to obtain the transconductance which, for small values of v_c , is:

$$gm = \frac{di_{c1}}{dv_c} = \frac{ql_{E1}}{4kT}$$

In a similar manner, the transconductance through Q9 is:

$$gm = \frac{di_{c2}}{dv_c} = \frac{qI_{E2}}{4kT}$$

and the total voltage gain, Av is:

$$Av = R_{L} \frac{di_{c1}}{dv_{c}} + \frac{di_{c2}}{dv_{c}}$$
$$= \frac{R_{L}q}{4kT} (I_{E2} - I_{E1})$$

Since $I_{E1} + I_{E2} = I_0$, it can be seen that when $v_m = 0$, $I_{E1} = I_{E2} = \frac{1}{2}$ I_0 and Av = 0. With I_{E1} and I_{E2} being collector currents of another differential amplifier, the total small-signal gain equation may be written:

$$Av = \frac{v_0}{v_c} = \frac{R_L l_0 q}{4 kT} \left[\frac{1}{1 + exp\left(\frac{q}{kT} v_m\right)} - \frac{1}{1 + exp\left(\frac{q}{-kT} v_m\right)} \right]$$

The circuit gain of the SG1402 is less than that predicted by the above equation due to the local feedback offered by the 20 ohm emitter resistors. The actual relationship between Av and v_m is shown in Figure 3 while Figure 4 graphs the full four-quadrant transfer function between the input voltage, v_c, the control voltage, v_m, and the output voltage. Note that the 20 ohm emitter resistors provide linearity for ±60 millivolts of input voltage while the modulating voltage is only linear for approximately half that value. It should be recognized from Figure 4 that output limiting occurs at a constant input voltage regardless of the modulating voltage. In other words, reducing the gain reduces the maximum peak-to-peak output swing.





BIASING CIRCUITRY

Key to the utility of the SG1402 is the inclusion of all the biasing and level shifting circuitry normally required as external components. This is provided by matched current sources and low impedance voltage sources.

Resistors R1, R2, R3 and R4 are directly across the supply voltage and establish a current:

$$I_b = \frac{V_S - V_{BEQ1}}{R1 + R2 + R3 + R4} = 1 \text{ mA at 10 volts}$$

Transistors Q14 and Q16 have the same geometries and emitter resistors as Q1 and therefore, with the same base voltage, they each are also conducting one milliamp and provide the loads for the output emitter followers, Q13 and Q15. This saves chip area as a transistor requires less space than a resistor which would establish the same current.

Transistor Q8 has four times the emitter area and $\frac{1}{2}$ the emitter resistor as Q1 and thus defines a current level I₀ of 4 milliamps.

The bias voltage levels required at different points in the circuit are all defined by the same resistors which set the current levels but there is no mutual interaction due to the insertion of Q2 and Q3 which act as low-impedance isolators.

Transistors $\Omega 4$ and $\Omega 11$ serve only as common-base stages to isolate the load resistor from the collector capacitance of the parallel diff-amp transistors. Thus, frequency response is improved with only slight increase in circuit complexity.

The chip layout of the SG 1402 was done to optimize the component matching regardless of mask registration and process variations. From the photomicrograph shown in Figure 5, it can be seen how the symmetrical nature of the circuit was exploited to obtain matched parameters. The chip has an area of 48 by 39 mils.



Figure 5. Photomicrograph of SG1402 Chip.

VARIABLE GAIN AMPLIFICATION

The circuit of Figure 6 shows the simplest application of the SG1402 as a single-ended, variable-gain amplifier. The signals at the two outputs are always equal in magnitude and opposite in phase. As the gain control potentiometer is moved from one end to the other, each output will start with a maximum signal, reduce to a minimum when the pot is centered, and increase to maximum again in the opposite phase as the wiper gets to the other end of the potentiometer.



Figure 6. Single-Ended Variable-Gain Amplifier Configuration with Manual Gain Control to Provide Maximum Output of Either Phase.

For applications where a phase change is not desired, the incorporation of a diode as shown in Figure 7 will allow a DC control voltage to vary the input-output transfer function from a gain of +25 dB to an attenuation of -25 dB. This relationship is plotted in the graph of Figure 8.

Since this change in transfer function is accomplished with no net change in either operating currents or bias levels, it is transient-free and extremely fast-reacting. Thus, the circuit of Figure 7 may also be used as a gated amplifier with the control requirements compatible with 0 to 5 volt logic levels. The waveform in Figure 9 shows a 1 MHz signal controlled with a 10 microsecond pulse.



Figure 7. Addition of Diode Provides Gain Control Without Phase Change. Balance May be Eliminated if Maximum Attenuation is not Required.

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Figure 8. Gain Variation as a Function of Control Voltage with Diode Coupled Input.



Figure 9. Gate Amplifier or Pulse Modulator Response. Input is 10 mVrms, 1 MHz and Control Voltage is 0 to 5 Volt Square Wave with f = 50 kHz.

MODULATION

The multiplying function of the SG1402 can be used to provide both balanced and amplitude modulation utilizing the basic circuit shown in Figure 10. With the potentiometer adjusted for optimum balance, the carrier signal is canceled out producing a doublesideband waveform at the output. Depending upon the amplitude of the carrier signal, higher frequency harmonics can also be generated; however, if only the lower sideband is used, filtering of the upper sideband will also eliminate all the harmonics. It should be noted that this balanced modulation is achieved without the need for the usual transformers and only capacitive coupling is required. Typical waveforms are shown in Figure 11.



Figure 10. Balanced Modulator.



Figure 11. Balanced Modulator Output Waveform. (0.1V/cm, 50 μ s/cm, f_c = 1 MHz, f_m = 10 KHz).

If the potentiometer is adjusted so that the circuit is unbalanced, then the carrier is included in the output signal and amplitude modulation as shown in Figure 12 results. The optimum adjustment can most readily be made while observing the output waveform on an oscilloscope. Care should be taken that neither signal overdrive the circuit.



Figure 12. Amplitude Modulator Output Waveform. (0.2V/cm, $50 \ \mu s/div$, f_c = 1 MHz, f_m = 10 KHz).

By using a signal to modulate itself with the circuit shown in Figure 13, the input is squared and since

$$\cos^2 \omega t = \frac{1}{2} [1 + \cos 2 \omega t]$$

the output frequency is twice that of the input. Typical waveforms for this frequency doubler application are shown in Figure 14.



Figure 13. Frequency Doubler.



Figure 14. Frequency Doubler Input and Output Waveform. (50mV/cm, 0.2 μ s/div, f₁ = 1 MHz, f₂ = 2 MHz).

DEMODULATORS

The same features which make the SG1402 an excellent modulator provide superior performance when the circuit is used as a single or double sideband demodulator. The circuit of Figure 15 illustrates the simplicity of this application. The balance pot is not necessary since the inserted carrier is eliminated by the low-pass filter at the output.



Figure 15. Balanced Demodulator.

The same general approach may be used for amplitude modulation and a block diagram of a simple AM detector is shown in Figure 16. Thus, the SG1402 can be used in receivers which combine SSB and AM to provide complete signal transformation in either mode of operation.



Figure 16. AM Detector Block Diagram.

CONCLUSIONS

With the introduction of the SG1402, Silicon General has provided a powerful tool to the communications engineer and all others working with information processing. Because of its versatility and capability, this device opens the way to a much greater utilization of carrier transmission schemes for data handling in applications ranging from outer space to home kitchens.

Application Notes-SG1501A-Dual-Polarity Tracking Regulators

CIRCUIT OPERATION

The first IC to combine a positive and negative voltage regulator on a single chip was the SG1501, and this device has since been supplemented with three new tracking regulator designs – the SG1502, the SG1501A, and the SG1568.

All four of these tracking regulators operate in a similar manner which is best visualized through the block diagram shown in Figure 1. This circuit is fundamentally a tracking regulator. That is, the negative voltage is regulated and the positive output tracks the negative. (Note: In the SG 1568, the circuit is reversed in that the negative side tracks the regulated positive output; however, the principle is the same.) Negative regulation is accomplished by providing a constant-voltage reference for the negative error amplifier, but the reference input to the positive error amplifier is grounded. This amplifier forces its other input, which is the center-tap between equal resistors, to also be at zero volts, thus requiring the positive output.



Figure 1. Block Diagram

With this technique, a single adjustment of the negative voltage divider — which changes the negative output level — will also provide exactly the same change to the positive output voltage. This tracking will hold all the way from approximately one volt above the reference voltage to a maximum value of about two volts less than the input supply voltage.

DESIGNER'S CHOICE

With four IC's to choose from some discussion of the significant features of each type is in order. Three of the devices, the SG1501A, the SG1501 and the SG1568 are factory set at \pm 15V regulators while the fourth, the SG1502, is user-adjusted to provide outputs from \pm 8V to \pm 28V.



The SG1501 and SG1501A are interchangeable and both can be used by themselves to provide load currents to the maximum defined by package dissipation, or can be combined with external pass transistors for currents in excess of two amps. Both devices feature constant current limiting with the value set by an external resistor. The SG1568 is similar in all respects to the SG1501 except that it is frequency compensated in a slightly different way.

The SG1502 uses the same basic circuit as the SG1501 but has two important differences. First, the voltage setting resistors are external to the device providing greater flexibility in adjusting the output voltage levels to other than $\pm 15V$. Secondly, the current limit circuitry has been changed to allow its use in a foldback mode. Foldback current limiting provides for a short circuit current value less than the maximum load current and is a significant feature when the major power dissipation is in external pass transistors rather than the IC.

Self-contained thermal shutdown is the primary improvement offered by the SG1501A although increases in both the maximum input voltage and load current have also been made. With thermal shutdown, temperature sensing circuitry on the chip is designed to turn off the output current when the junction temperature exceeds a safe limit – typically 1700C. The significance of this feature is that the designer now need not design around short-circuit power dissipation limits – the device will take care of itself. Since short-circuit power is typically more than twice as much as maximum operating power, this means a two-times, or better, improvement in load current is possible. It should be noted that even with thermal limiting circuitry, the maximum current must be controlled to allow time for this protection to react.

APPLICATIONS

The simplest way to use the SG1501 and SG1501A is in the basic circuit shown in Figure 2. In this form, the device will handle 50 to 100 mA, depending on the heat sinking (more about this later) and will provide $\pm 15V$ outputs with typically less than two millivolts of sensitivity to either line or load variations. Because of this excellent line regulation, there is no need for symmetrical input supply voltage levels. The only requirement is that each level be greater than its associated output and that the total voltage between positive and negative supplies be less than 60V (70V for the SG1501A). The minimum input voltage is defined by the regulator dropout characteristics shown in Figure 3.



Figure 3. Regulator Dropout Voltage



Figure 4. Artificial ground for use with an ungrounded or single level voltage.

When operating from a single voltage source, an ungrounded supply is required. An artificial ground can be provided as shown in Figure 4. In this circuit, the external transistors will conduct as necessary to accommodate unbalanced load requirements and while the outputs will float between the two input levels, they will be held constant with respect to this artificial ground.

CURRENT LIMITING

Current sensing is provided by transistors Q12 and Q13 (see schematic, Figure 5) which are normally held off by an external base-to-emitter resistor, Rsc. When the load current passing through this resistor develops enough voltage, the transistor turns on and diverts drive current away from the series pass transistors. The sense voltage is equal to approximately 0.6V at Tj = 25° C, but it is temperature dependent decreasing to 0.4V at 125°C as shown in Figure 6. Note that it is junction temperature that determines the sense level, and thus increasing the power dissipation within the circuit can lower the value at which limiting will occur. The value of the limiting resistor, Rsc, should be selected by:

$$Rsc = \frac{Sense Voltage at Maximum Tj}{Allowable Short Circuit Current}$$

where, for maximum regulation, the allowable short circuit current should be at least 20% more than the maximum expected load current.

Under some conditions, a low-level oscillation may be present on the negative side when the device goes into current limiting. Should this be a problem, it may be eliminated by by-passing Rsc with a capacitor whose



Figure 5. SG1501A Schematic Diagram

value is such that the time constant, Rsc C, is equal to 10×10^{-6} second. This capacitor, as well as the output capacitors, C3 and C4, must be low ESR types such as solid tantalum.



Figure 6. Current Limiting Characteristics

POWER CONSIDERATIONS

Although these dual regulators are designed to handle large load currents and high input voltages, the product of the two can easily exceed the maximum total device dissipation allowed by the package. The functional limitation which should be considered for each application is that for maximum reliability the junction temperature of the chip should not exceed 170° C. This is usually derated to give a maximum design operating Tj of 150° C.

To evaluate the maximum junction temperature possible in a given application, the following three parameters must be known:

- 1. The power dissipation within the chip
- 2. The thermal resistance from junction to ambient (or heat sink)
- 3. The ambient (or heat sink) temperature

The power dissipation within the chip is equal to the sum of the input voltage times the standby current plus the input-output voltage differential times the load current, for each side of the regulator. For example, the total power dissipation for $\pm 20V$ inputs, $\pm 15V$ outputs, and 50 mA load currents is:

Pd = 20 (2) + 20 (3) + 5 (50) + 5 (50) = 100 mW standby + 500 mW load current = 600 mW

The thermal resistance is the resistance to heat flow from the junction to the ultimate heat sink. For parts mounted in the open, still air, the thermal resistance (∂jA) is equal to $185^{\circ}C$ /watt for the T0-100 metal can and $125^{\circ}C$ /watt for the T0-116 ceramic DIP. Blowing air across the package, or the use of some form of heat radiator can significantly reduce these numbers. For example, the use of IERC's model TXBF-032-025B top hat radiator on the T0-100 package, reduces ∂jA to $130^{\circ}C$ /watt, while their model LIC-214A-2B radiator for the T0-116 will give an ∂jA of $50^{\circ}C$ /watt for that package. Finally, a perfect heat sink reduces ∂jA to ∂jC which is $50^{\circ}C$ /watt for the T0-100 and $20^{\circ}C$ /watt for the T0-116. With the above information, the maximum power handling capability of the package can be determined as follows:

1. Calculate the maximum allowable junction temperature rise:

$$\Delta T_j = 150^{\circ}C - T_A (max)$$

2. Calculate the power availability:

3. From this number, subtract the maximum standby dissipation:

$$Psb = (V + max) (Isb+) + (V - max) (Isb-)$$

4. The remainder can be used to determine the maximum load current as a function of input-output voltage differential.

The curves of Figure 7 show these relationships for each package under the assumptions of 25°C ambient, and symmetrical input and output voltages and load currents.



EXTERNAL POWER TRANSISTORS

Additional current handling capability may be provided through the use of external power transistors in the configuration shown in Figure 8. In this circuit, the 75 ohm base-to-emitter resistors provide a path for the regulator standby current and should not be increased in value. An additional consideration is the use of solid tantalum output capacitors as most common electrolytic types have too high an equivalent series resistance, particularly at high frequencies.

The power transistors are not critical and can be selected on the basis of current and voltage capability, and on mechanical requirements for practical heat sinking. Note that only one transistor need be used if only one side has excessive load current. Although low-frequency devices will minimize the risk of oscillation, unique transistor characteristics may require a small capacitor (0.1 mfd) from base to ground or a larger value (5 mfd) from base to emitter for complete stability.



Figure 8. High Current Configuration, One Amp Output

FOLDBACK CURRENT LIMITING

With constant-current limiting as shown in Figure 8, the power dissipation in the pass transistors under short circuit conditions can be substantial. Here, the thermal limiting feature of the SG1501A can't do much good since it senses the IC temperature rather than the external transistors. To eliminate the problem of having to heat sink a short circuit power two to three times normal operating levels, the use of the SG1502 in the circuit of Figure 9 should be considered. The dividers of R5' and R6 pre-bias the current limiting such that when the output is shorted, the maximum current is substantially reduced from its normal operating level. The values for R5 and R6 are most easily determined from an itterative solution of the equations below with the trade-off being that a greater amount of foldback requires a larger voltage drop across Rsc:





VOLTAGE ADJUSTMENTS

With both output voltage levels internally set for 15V, ($\pm 200 \text{ mV}$ for the SG1501/2501 and $\pm 500 \text{ mV}$ for the SG3501) these devices require no additional resistors for many applications. It is possible, however, to externally vary the output voltages from ± 10 to $\pm 23V$ by using external resistors to shunt one or both of the internal resistors which set the negative output level. The positive output will, of course, track the negative value.



Figure 10. External parallel resistor required for voltages other than $\pm 15V$.

The simplest way of changing the output levels is to use a single resistor

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in parallel with R17 (see Figure 5) for voltages less than 15V and in parallel with R16 for voltages above 15V. The graph of Figure 10 shows the approximate value to use in either case.

This method of adjusting output levels has one disadvantage, however. Diffused resistors have a positive temperature coefficient and while they can be made to track each other extremely well, with one of them shunted this tracking becomes degraded. A method offering greater temperature stability is the use of a pair of resistors with values' low enough to swamp out the internal divider. By shunting R16 with 1.2k, and R17 with a resistor selected by:

$$R17'' = \frac{1.2 (V_0 - 6.2)}{6.2} k\Omega$$

where Vo is the desired output voltage, a four-fold improvement in temperature performance is achieved at the expense of the additional divider current. Figure 11 shows that temperature variation which may be expected both with a single shunt resistor and with a divider drawing approximately five milliamps of current. Note that these temperature shifts are caused by changes in chip temperature which could result from variations of either ambient temperature or internal power dissipation.



Figure 11. Temperature Coefficient of Output Voltage

In the 14 pin dual-in-line package, a connection is provided to the junction of R21 and R22. An external resistor divider can be used here in the same manner to either balance the two outputs so that they are exactly equal in magnitude or to unbalance them for non-symmetrical output levels.

Although all of these dual regulator types have provisions for adjustment of the output voltage levels, with its user-supplied voltage setting resistors, the SG1502 is the best choice for applications very far from \pm 15V. The divider resistors (see Figure 9) are selected as follows:

Negative Vo =
$$\frac{6.2 (R1 + R2)}{R1}$$

Positive Vo = $\frac{R3}{R4}$ (Negative Vo)

One common application for positive and negative voltages is as a power source for the widely used 710 and 711 IC voltage comparators. Since these devices are designed for +12 and -6V operation, it takes a circuit as shown in Figure 12 to get around the \pm 8V minimum output

limitation of these regulators. Here, the nominal $\pm 15V$ output of the SG1501 has been reduced to $\pm 12V$ by the 2.0k and 1.8k voltage divider. Six volts are then subtracted from the negative output by the IN4735 zener diode. Because the diode is outside the feedback loop, some minor variations in the -6V output may be observed due to its temperature coefficient or dynamic impedance. These variations have negligible effect on the comparators, however, as the negative voltage is used only to bias high impedance current sources.



Figure 12. Using the SG1501 to provide +12 and -6V outputs.

Zener diodes can also be put to use in applications requiring high input voltages. In the circuit of Figure 13, the small signal zener diodes reduce the voltage applied to the IC while allowing the easily heat-sinked power transistors to absorb the added power dissipation caused by a large inputoutput differential.



Figure 13. Zener diodes used to prevent high input voltages from appearing across the device.

CONCLUSIONS

With two complete regulators in a single IC, these new regulators offer an improved approach to power distribution. Their high degree of performance and freedom from large numbers of external components make "on-card", or distributed regulation a practical reality. By regulating at the point of use, the system designer has eliminated many knotty problems such as lead inductance, decoupling, line drop through connectors, etc. In addition, since each circuit card or module can now regulate its own voltage, complete interchangeability is more nearly assured and the problems of equipment maintenance are greatly eased.
Application Notes-SG1524

SIMPLIFYING CONVERTER DESIGN WITH A NEW INTEGRATED REGULATING PULSE WIDTH MODULATOR

R. A. Mammano Edited by Stan Dendinger Manager, Advanced Product Development SILICON GENERAL, INC.

Abstract

A new monolithic integrated circuit is described which contains all the control circuitry for a regulating power supply converter or switching regulator. Included in this 16-pin dual-in-line package is the voltage reference, error amplifier, oscillator, pulse width modulator, pulse steering flip-flop, dual alternating output switches, and current limiting and shutdown circuitry. This device can be used for switching regulators of either polarity, transformer coupled DC to DC converters, transformer-less voltage doublers and polarity converters, as well as other power control applications.

INTRODUCTION

Implementing a switching power supply has just become significantly easier with the introduction of the SG 1524 series of Regulating Pulse Width Modulator integrated circuits. Long recognized as offering greatly improved efficiencies, the development of switching supplies has been hampered by the complexity of the low-level circuitry required to provide the proper signals for adequate control of the switching transistors. As a result, these supplies have tended to be more costly, larger in size, and with poorer reliability than could be justified by their improved efficiency. Even when threats of higher energy costs and potential brown-outs have made switching supplies mandatory, their complexity has made the engineering design task a most formidable undertaking.

With the introduction of the SG 1524, a major portion of the complex low-level control circuitry has been integrated into a single LSI linear integrated circuit. This monolithic chip, packaged in a 16-pin dual-in-line outline, implements the entire block diagram shown in Figure 1.

It is the integration of all these different functions into a single IC that qualifies the SG 1524 as one of the best examples to date of large scale integration as applied to analog circuits. The remainder of this paper will describe each of the individual blocks in the following diagram in considerable detail and then offer a few basic application suggestions.



FIGURE 1 - SG1524 BLOCK DIAGRAM

VOLTAGE REFERENCE

The reference circuit of the SG 1524 is shown in Figure 2. This is a complete linear regulator designed to provide a constant 5 volt output with input voltage variations of 8 to 40 volts. It is internally compensated and short circuit protected. It is used both to generate a reference voltage and as the regulated source for all the internal timing and controlling circuitry. This regular may be bypassed for operation from a fixed 5 volt source by connecting pins 15 and 16 together to the input voltage. In this configuration, the maximum input voltage is 6 volts. While discussing input power, it should be mentioned that the entire SG 1524 IC draws less than 10 mA of current, regardless of input voltage.



FIGURE 2 - SG1524 REFERENCE CIRCUIT

This reference regulator may be used as a 5 volt source for other circuitry. It will provide up to 20 mA of output current itself and can easily be expanded to higher currents with an external PNP transistor as shown in Figure 3.



FIGURE 3 - SG1524 EXPANDED CURRENT SOURCE

OSCILLATOR

The oscillator in the SG 1524 uses an external resistor (R_7) to establish a constant charging current into an external capacitor (C_7). This constant-current charging gives a linear ramp voltage which provides an overall linear relationship between error voltage and output pulse width. The SG 1524 oscillator circuits is shown in Figure 4.





A second output from the oscillator is a narrow clock pulse which occurs each time C_r is discharged. This output pulse is used for several functions as outlined below:

- (1) As a blanking pulse to both outputs to insure that there is no possibility of having both outputs on simultaneously during transitions. The width of this blanking pulse can be controlled to some extent by the value selected for C_n.
- (2) As a trigger for an internal flip-flop which directs the PWM signal to alternate between the two outputs. Note that for single-ended applications, the two outputs can be connected in parallel and the frequency of the output is the frequency of the oscillator. For push-pull applications, the outputs are separated and the action of the flip-flop provides and output frequency ½ that of the oscillator.
- (3) As a convenient place to synchronize an oscilloscope for system de-bugging and maintenance.
- (4) As a bi-directional port for external timing synchronization. The output pulse from this oscillator — which is stable to within 2% over variations in both input voltage and temperature — can be used as a master clock for other circuitry, including other SG 1524's. It thus follows that a positive pulse applied to this terminal can synchronize the SG 1524 to an external clock signal.

The waveforms of the two outputs from the oscillator are shown in Figure 5.



FIGURE 5 - SG1524 OSCILLATOR WAVEFORMS

ERROR AMPLIFIER

The error amplifier circuit, shown in Figure 6, is a simple differential input, transconductance amplifier. Both inputs and the output are available for maximum versatility.





The gain of this amplifier is

nominally 10,000 (80dB) but can be easily reduced by either feedback or by shunting the output to ground with an external resistor. The overall frequency response of this amplifier which, by the way, is not internally compensated but yet is stable with unity gain feedback, is plotted with various values of external load resistance in Figure 7.



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Phase shifting to compensate for an output filter pole may readily be accomplished with an external series R-C combination at the output terminal of the amplifier.

Since the error amplifier is powered by the 5-volt reference voltage, the acceptable common-mode input voltage range is restricted to 1.8 to 3.4 volts. This means the reference must be divided down to be compatible with the amplifier input, but yet provides the advantage of being able to be used to regulate negative output voltages. required input dividers are shown in Figure 8.



FIGURE 8 - ERROR AMPLIFIER CONNECTIONS

Since this amplifier is a transconductance design, the output is a very high impedance (approximately 5 MΩ) and can source or sink only 100 microamps. This makes the output terminal (Pin 9) a very convenient place to insert any programming signal which is to override the error amplifier. Internal shutdown and current limit circuits are connected here, but any other circuit which can sink 100 μ A can pull pull this point to ground, thereby shutting off both outputs.

For example, the soft start circuit of Figure 9 can be used to hold Pin 9 to ground — and thus both outputs off — when power is first applied. As the capacitor charges, the output pulse slowly increases from zero to the point where the feedback loop takes control. The diode then isolates this turn-on circuit from whatever frequency stabilizing network might also be connected to Pin 9.





CURRENT LIMITING

The current limiting circuit, while shown in the block diagram as an op amp, is really only a single transistor amplifier as shown in Figure 10. It is frequency compensated and has a second transistor to provide temperature compensation and a reduction of input threshold to 200 mV. When this threshold is exceeded, the amplify-



FIGURE 10 - SG1524 CURRENT LIMITING

ing transistor turns on and, by pulling the output of the error amplifier toward ground, linearly decreases the output pulse width. One consideration in using this circuit is that the sense terminals have a ± 0.3 volt common mode range which requires sensing in the ground line. However, since differential inputs are available, foldback current limiting can be implemented as shown in Figure 11.



FIGURE 11 - FOLDBACK CURRENT LIMITING

While on the subject of protection circuitry, although overvoltage protection is not built into the SG 1524, it is relatively easy to add by using the internal shutdown circuit in conjunction with a few external components as shown in Figure 12.



FIGURE 12 - SG1524 OVER VOLTAGE PROTECTION

This circuit will provide a low level sensing and latching function and while it won't protect against a shorted output transistor, it will remove the drive signals with no power dissipation.

OUTPUT STAGES

The outputs of the SG 1524 are two identical NPN transistors with both collectors and emitters uncommitted. These circuits are as shown in Figure 13 and include an antisaturation network for fast response and current limiting set for a maximum output current of approximately 100 mA.



FIGURE 13 - SG1524 OUTPUT STAGE

The availability of both collectors and emitters allows maximum versatility to enable driving either NPN or PNP external transistors; however, it must be remembered that this is only a switch which closes and opens. Power transistor turn-off drive must be developed externally. Some suggestions for output drive circuits are shown in Figure 14.



FIGURE 14 – DRIVING EXTERNAL TRANSISTORS

APPLICATIONS

In considering applications for the SG 1524, it appears that there are three general classifications of switching power supply systems. Included in the first are the transformerless voltage multiplier circuits shown in Figure 15. These circuits are primarily used for low level applications but can step up, step down, or change the polarity of an input voltage. The switches shown can be either the output stages of the SG 1524 or external transistors. Note that one extra diode is required to protect the emitter-base junction of switch SA during the times when both switches are open.





For higher current applications, the single-ended inductor circuits of Figure 16 represent another classification. Here the two outputs of the SG 1524 are connected in parallel, but note that this does not give twice the current as the switches are alternating internally. This does not affect external performance, however, and the SG1524 can be used to provide 0-90% duty cycle modulation in any of the configurations shown.



The third general classification of power supply systems are transformer coupled, two types of which are shwon in Figure 17.

The push-pull circuit represents the conventional DC to DC converter with each switch being controlled for 0 - 45% duty cycle modulation. The second transformer circuit is a single-ended flyback converter, useful at light loads without a separate output inductor.

To illustrate the use of the SG 1524 in each of the above general classifications, the following simple, but practical, circuits are presented:



FIGURE 17 - TRANSFORMER COUPLED CIRCUITS

Figure 18 shows the use of the SG 1524 as a low current polarity converter providing a regulated – 5 volt output at currents up to 20 mA from a single positive input voltage. The external components required include the divider resistors to interface the reference and output voltages with the error amplifier, a resistor/capacitor to set the operating frequency, and the output diodes and capacitors. The combination of the built-in current limiting of the SG1524 output stages and the capacitor coupling of the output signal provide full protection against short circuits and the current limit amplifier is unused. Since this circuit has no inductor, the output capacitor is more than enough to stabilize the regulating loop and no additional compensation is required.



FIGURE 18 - LOW CURRENT POLARITY CONVERTER

Another low-level circuit is the flyback converter shown in Figure 19.

The circuit is designed to develop a regulated ± 15 volt supply from a single +5 volt source. Note that the reference terminal is tied to the input, disabling the internal regulator. The error amplifier resistors are also tied to the input line so the output regulation can be no better than the input; however, an external reference could just as easily have been used.



FIGURE 19 - +5 TO ±15 VOLT, FLYBACK CONVERTER

In this application, the two output stages are connected in parallel and used as emitter followers to drive a single external transistor. Since the currents in the secondary of a flyback transformer are out of phase with the primary current, current limiting is very difficult to achieve. In this circuit, protection was provided through the use of a soft-start circuit. If either output is shorted, the transformer will saturate, providing more current through the drive transistor. This current is sensed and used to turn on the 2N2222 which resets the soft-start circuit and turns off the drive signal. If the short remains, the regulator will repetitively try to start up and reset with a time constant set by the soft-start circuit. Removing the short will then allow the regulating loop to re-establish control.

For higher current applications, the single-ended conventional switching regulator of Figure 20 is shown.



FIGURE 20 – 1 AMP, SINGLE-ENDED SWITCHING REGULATOR

In this case, an external PNP darlington is used to provide a 1-amp current switch. The SG1524 has the two outputs in parallel, connected as a grounded emitter amplifier. The current sense resistor is inserted in the ground line and the voltage across it used for constant current limiting. Note that in addition to the divider resistors and frequency setting R_rC_r , a phase compensation resistor and capacitor is used to stabilize the loop now that an inductor has been added.

A fourth application would have to be a push-pull, DC to DC regulating converter as shown in Figure 21.



FIGURE 21 - 5V, 25W, DC TO DC CONVERTER

Here the outputs of the SG 1524 are connected as separate emitter followers driving external transistors. Current limiting in this application is done in the primary for several reasons: First, it's easier to live within the \pm 0.3 volt common mode limits of the current limit amplifier; second, since this is a step-down application; the current — and therefore the power in the sense resistor — is lower; and third, if the output drive were to become non-symmetrical causing the transformer to approach saturation, the resultant current spikes will shorten the pulse width on a pulse-by-pulse basis, providing a first order correction. Note that the oscillator is set to run at 40kHz to obtain a 20 kHz signal at the transformer.

This application as shown does not provide input-output isolation and, of course, that feature is difficult to achieve within a single IC. There are a couple of ways the SG 1524 can be used with isolated power supply systems, however. The first is shown in Figure 22 where the SG 1524 is direct coupled on the secondary side of the output transformer. The outputs from the IC are transformer-coupled back to the primary side to drive the switching transistrors. Of course, a separate start-up power source is needed for the SG 1524 but that shouldn't present much of a problem remembering that the IC draws less than 10 mA of supply current.



FIGURE 22 - INPUT/OUTPUT ISOLATION

A different method of providing isolation is shown in Figure 23 where the IC is direct coupled on the primary side. Here a separate reference and error amplifier (most easily implemented with a SG 1532 regulator IC) is connected on the secondary and then optically coupled back to the primary side.



FIGURE 23 - INPUT/OUTPUT ISOLATION

As should be evident from the above, the SG 1524 was designed as the first of what will undoubtedly become a larger family of regulator ICs specifically designed for switching power supplies. As such, versatility was the primary design goal of this device and hopefully this goal has been achieved to the degree that will allow the SG 1524 to find application to a wide range of power control systems.

Application Notes-SG1524

DEADBAND CONTROL WITH THE SG1524 REGULATING PULSE WIDTH MODULATOR CIRCUIT

The SG1524 Regulating P.W.M. integrated circuit provides two outputs which alternate in turning on for pushpull inverter applications. The internal oscillator sends a momentary blanking pulse to both outputs at the end of each period to provide a deadband so that there cannot be a condition when both outputs are on at the same time. The amount of deadband is determined by the width of the blanking pulse appearing on pin 3 and can be controlled by four techniques:

1. For 0.2 to 1.0 microseconds, the deadband is controlled by the timing capacitor, C_T , on pin 7. The relationship between C_T and deadband is shown in Figure 3 on the SG1524 data sheet. Of course, since C_T also helps determine the operating frequency, the range of control is somewhat limited.

2. For 0.5 to 3.0 microseconds, the blanking pulse may be extended by adding a small capacitor from pin 3 to ground. The value of the capacitor must be less than 1000 pf or triggering will become unreliable.

3. For longer and more well-controlled blanking pulses, a simple one-shot latch similar to the circuit shown below should be used:



TRANSISTORS – Small-signal general purpose types. For 5 μ sec width, C_B = 200 pf, R_B = 10k

When this circuit is triggered by the oscillator output

pulse, it will latch for a period determined by $C_B R_B$ providing a well-defined deadband.

Another use for this circuit is as a buffer when several other circuits are to be synchronized to one master oscillator. This one-shot latch will provide an adequate signal to insure that all the slave circuits are completely reset before allowing the next timing period to begin.

Note that with this circuit, the blanking pulse holds off the oscillator so its width must be subtracted from the overall period when selecting R_T and C_T .

4. Another way of providing greater deadband is just to limit the maximum pulse width. This can be done by using a clamp to limit the output voltage from the error amplifier. A simple way of achieving this clamp is with the circuit below:



This circuit will limit the error amplifier's voltage range since its current source output will only supply 100μ A. Additionally, this circuit will not affect the operating frequency.

Application Notes-SG1524

IMPROVING SWITCHING REGULATOR DYNAMIC RESPONSE

R. A. Mammano Edited by Stan Dendinger Manager, Advanced Product Development Silicon General, Inc.

ABSTRACT

Recent introductions of LSI integrated circuits for P.W.M. control have offered considerable simplification to the job of optimizing the design of switching regulators. In addition to greatly reducing the necessary circuitry, the linear transfer function of these devices eases the task of stabilizing the feedback loop and offers several possibilities for improved response. Experimental methods for evaluating the response characteristics of the P.W.M. switching and output stages can be used to confirm simplifying assumptions of linear operation. With this data, several approaches to equalization networks can be compared for performance optimization.

The past few years have seen a major revolution take place in the field of power supply design. Whether forced upon us by the need for energy conservation or finally made practical thru recent advances in semiconductor technology, switching regulators are now the name of the game in voltage control. Novices soon learn, however, that the implementation of a welldesigned switching supply involves a little more skill than that required for a linear regulator.

Although the theory of switching regulation has long been known, there is much practical technology – or art – in designing efficient and reliable systems. This is still true even though recently introduced semiconductor devices have made the job at least a little easier. It is the purpose of this discussion to cover a few of the practical aspects of implementing and stabilizing switching regulators using these newer devices.

INTEGRATED P.W.M. CONTROL CIRCUITS

Recognizing a rapidly growing market, many component suppliers have introduced new devices designed specifically for switching regulator applications. These include faster power transistors with improved S.O.A., low E.S.R. electrolytic capacitors, hybrid power devices which include a matched commutating diode, and monolithic IC control devices such as the SG124(1) which contain all of the P.W.M. control circuitry in a single 16-pin, dual-in-line package.



Figure 1. SG1524 Block Diagram

From the block diagram shown in Figure 1, it can be seen that the SG1524 contains the elements necessary to implement either single-ended switching regulators or DC to DC converters of several different configurations. This device includes a voltage reference, error amplifier, constant frequency oscillator, pulse width modulator, pulse steering logic, dual alternating output switches, and current limiting and shutdown circuitry. Since many of the different types of applications for this IC have been discussed earlier⁽¹⁾ it should suffice to review only two of the more common usages as shown in Figures 2 and 3.

The single-sided regulator of Figure 2 is unique because of its simplicity. This circuit combines an SG1524 with an SM625 hybrid to build a 5 volt, 5 amp regulator with all the semi-

conductor devices contained in only two packages. This circuit has an efficiency of over 70% with an input voltage range of 20 to 30 volts, 0.1% line and load regulation, and some added benefits of constant frequency operation and short circuit protection.



Figure 2. SG1524 Single-Ended Switching Regulator

Figure 3 shows the same 5-volt, 5 amp output requirement met this time with a DC to DC converter. The use of high speed transistors and Shottky rectifiers keep the efficiency more than 80% – significant for a low-voltage output – while maintaining all the other benefits included in the single-ended circuit.



Figure 3. SG1524 Regulating DC-DC Converter

It should be recognized that the above circuits represent very basic applications of an IC control chip. Most practical power supply systems would probably incorporate many other features which may be accomplished by interfacing these IC's with a small amount of external circuitry to add characteristics such as: soft-start, oscillator synchronization, dead-band controls, additional current and/or voltage step-up stages, input-output isolation, remote overvoltage or overload shutdown, and response modifying circuitry. It is this latter subject we wish to explore more fully below.

SWITCHING REGULATOR CONTROL

The basic switching regulator control loop which applies to the most common forms of implementation is illustrated in Figure 4. In analyzing this control loop stability, the obvious immediate problem is the transfer function of the P.W.M. and output stage. A detailed and accurate analysis of the nonlinear characteristics of this stage is an extremely difficult and complex task if one is to account for all the parameters which could possibly be a factor. (2, 3, 4) On the other hand, if this stage could be assumed to have a linear transfer function, analysis becomes a relatively simple application of basic feedback theory.



Figure 4. Basic Regulating Control Loop

A significance of the SG1524 is that it uses a design approach which makes a linear assumption accurate enough for most applications. The fact that this device features constant frequency operation, a linear-slope ramp for P.W.M., and fastresponse logic and output circuitry all contribute to minimizing the errors associated with a linear assumption. Of course, there are factors external to the IC which could destroy this assumption. Such things as excessive delay in the switching transistors, parasitic ringing or oscillation in the power stages, or nonlinear operation of the magnetics could all cause a resultant nonlinear performance. A first exercise for the designer, then, is to confirm linear operation of the P.W.M. and output stages of his regulator by evaluating his early breadboard models.

OUTPUT STAGE ANALYSIS

The pulse width modulation is accomplished in the SG1524 by comparing the output of the error amplifier with a linear ramp, or saw-tooth signal from the oscillator. Because the comparator has both high gain and high input impedance, and the error amplifier has a high output impedance, this node (pin-9) becomes a very convenient place for inserting a test signal. A voltage source applied as shown in Figure 5 will completely override the error amplifier and essentially open the loop without actually breaking any connections. In addition, the test signal is easily managed because the voltage gain from this point to the output is relatively low. (A voltage level on pin 9 of from 1 to 4 volts will change the pulse width from zero to maximum which will yield zero to maximum output voltage.)



Figure 5. Measuring Output Stage Transfer Function

In experimentally attempting to confirm satisfactory operation of the output stages, the designer hopes to prove that a linear equivalent circuit model is valid for reasonable analysis. One such model as proposed by Middlebrook⁽⁵⁾ is shown in Figure 6. This model describes the overall AC and DC transfer function and input and output impedances in terms of the duty cycle and modulation constant. This model assumes that the effects of operating frequency, switching delays, and parasitic elements are well above the frequencies of interest as defined by the output LC filter.



Figure 6. Linear Equivalent Circuit

Values for the inductor and capacitor are normally calculated on the basis of output ripple current and voltage as follows:

For constant frequency operation,

$$L = \frac{V_{O}(V_{IN} - V_{O})}{V_{IN}f(\Delta I_{L})}$$

and

$$C = \frac{V_0(V_{IN} - V_0)}{8Lf^2 V_{IN}(\Delta V_0)}$$

where:

VIN = peak input voltage to the inductor

V_O = output voltage across the capacitor

f = switching frequency

 ΔI_L = peak-to-peak current variation in the inductor ΔV_0 = peak-to-peak ripple voltage across the capacitor.

Note that the actual ripple voltage at the output of the filter will be ΔV_{O} , plus ΔI_{L} times the capacitor E.S.R.

Regardless of the requirements for minimizing the output ripple, an additional requirement on the filter is that its cutoff frequency be well below the switching frequency if our original goal of simple linear analysis is to be met. Specifically, the switching operation introduces a second order lag at one-half the switching frequency and for the output filter to dominate, its cutoff should be at least an order of magnitude below that number, or

$$\frac{1}{2\pi\sqrt{LC}} \leqslant \frac{f}{20}$$

To verify the performance of the resultant hardware, a Bode plot of the output stage response can be most meaningful. Ideally, a plot as shown in Figure 7 should show a flat response to the filter cutoff and then a linear 12 dB/octave rolloff with a



Figure 7. Linear Output Stage Response

180° phase shift. By making these plots with varying input voltage and load current, factors affecting stability such as leakage inductance, capacitor E.S.R., and either saturation or discontinuous operation of the magnetics may be evaluated over the operating conditions of interest. Figure 8 shows typical plots with less than ideal component parameters. With the characteristics of the output stage defined, attention can be turned to the error amplifier to develop an equalizing network which will allow satisfactory closing of the loop.

ERROR AMPLIFIER COMPENSATION

The error amplifier contained within the SG1524 is a transconductance amplifier in that it has a high-impedance, current source output. The gain is a function of the output loading and

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can be reduced from a nominal 80 dB by shunt resistance as shown in Figure 9. Note also in Figure 9 that the uncompen-



Figure 8. Measured Output Stage Response



Figure 9. Open-Loop Error Amplifier Response

sated amplifier has a single pole at 300 Hz and 90° of phase shift. The unity gain cross-over frequency is 3 MHz and the large scale slew rate is 0.5 volt per microsecond.

This type of amplifier can be compensated in two ways: The compensation network can go from the output to ground or it can be connected from output back to the inverting input.⁽⁶⁾ In the first case, the voltage gain is:

$$A_{v} = gmZ_{c} = \frac{8I_{c}Z_{c}}{2kT} \approx 0.002Z_{c}$$

where Z_c is the complex compensation network impedance. If a feedback approach is used, the gain is:

$$A_v = \frac{Z_c}{Z_s}$$

where Z_s is the source impedance driving the input. In cases where relatively low impedances are desired in a feedback network, it may be necessary to buffer the high output impedance of the error amplifier. Figure 10c shows the use of an external emitter follower to provide a low driving impedance for the feedback network.



Figure 10. Error Amplifier Compensation Networks

To stabilize the overall regulator feedback loop of Figure 4, it should be apparent that the uncompensated loop contains at least two poles in the output filter and one more in the error amplifier, a situation which typically results in significant gain remaining when the total loop phase equals 360°. One of the simplest compensation schemes is to convert the error amplifier to an integrator by adding a single dominate pole at a frequency so low that the loop gain falls below unity well before the cutoff frequency of the output filter. While this approach yields a stable closed loop gain as shown in Figure 11, the response to



Figure 11. Closed Loop Frequency Response

disturbances is very slow. For example, the waveforms of Figure 12 show the response to a 20%, or one amp, step change in load to the circuit of Figure 3 when compensated with a 0.2 mfd capacitor around the error amplifier.

If instead of slowing down the error amplifier, a zero, or lead network is added to cancel one of the output filter poles, we can keep the total loop phase less than 360° to well beyond the output filter cutoff.



STIMULUS: ONE AMP STEP CHANGE IN IO UPPER TRACE: ERROR AMP OUTPUT, 500 mV/DIV LOWER TRACE: REGULATOR OUTPUT, 200 mV/DIV TIME BASE: 5 MILLISECONDS/DIV

Figure 12. Integrator Compensation Step Response

Figure 13 shows a circuit for accomplishing this by moving the amplifier pole lower in frequency and adding a zero at the output filter cutoff frequency. Figure 14 shows the effects of this network on the Bode plot of the error amplifier, and Figure 15 indicates the improvement in recovery from the same one-amp load change. Note how the output of the error amplifier overshoots to give a boost to the output.



Figure 13. Series RC Phase Compensation



Figure 14. Phase Compensated Bode Plot

Even faster response can be achieved by providing additional lead networks. For example, another zero may be added by bypassing the sense feedback resistor. As can be seen in Figure 16, this greatly improves loop response but offers the hazard of coupling ripple noise directly into the error amplifier.



 $R_C = 30 K\Omega$, $C_C = .022 mfd$

STIMULUS: UPPER TRACE:	ONE AMP STEP CHANGE IN IO ERROR AMP OUTPUT, 500 mV/DIV
LOWER TRACE:	REGULATOR OUTPUT, 100 mV/DIV
TIME BASE:	5 MILLISECONDS/DIV







UPPER TRACE: ERROR AMP OUTPUT, 50 mV/DIV LOWER TRACE: REGULATOR OUTPUT, 50 mV/DIV TIME BASE: 2 MILLISECONDS/DIV



TWO LOOP CONTROL

From the examples presented above, it should be apparent that the integration method of error amplifier compensation provides good stability by making the dominate pole so low in frequency that variations in all other circuit parameters become inconsequential. This technique also provides high accuracy at DC where high gain can be used and is the type of feedback one would want to take directly from the output of a regulator since a user might add additional external capacitance, thereby changing the output filter characteristics. Another reason for using single-pole compensation is to accommodate the use of a two-stage output filter which can add phase shifts well beyond 180°.

The problem of poor response can then be accommodated by adding a differentiated signal taken from somewhere else in the loop. If the time constants and gain factors are properly selected, the differentiated signal can compensate for the error in the integrated signal taken from the regulated output.

While it may be possible to combine these two signals with passive signal conditioning at the input to the error amplifier, a more straightforward approach is with two separate op amps.⁽⁷⁾ shown in Figure 17. Here the error amplifier in the SG1524 has

SUMMARY

Although integrated circuit controllers for switching supplies have removed much of the circuit complexity from this type of regulator, the dynamic analysis of the control loop must still be optimized for each application. This optimization is made easier, however, if a linear approximation of the switching stages can be shown to be valid. The SG1524 controller offers benefits in this regard as it does provide a linear transfer function through its pulse width modulation scheme. Therefore, experimental techniques can be used to simply confirm proper operation of the power switches and output filter.

With a linear output stage, conventional feedback analysis can be used to define the best equalizing network achieving a compromise between stability and fast response. In some cases it may even be desirable to provide separate signal paths for these two parameters but thus, too, can be adapted to the SG1524 controller with a minimum of external circuitry.

Obviously, no recipes for optimum performance have been provided herein. Only a few directions which, it is hoped, will point the way toward the development of specific solutions for specific applications.

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SILICON GENEPAL Inc.

CONVERTING 1524 SWITCHING POWER SUPPLY DESIGNS TO THE SG1524B

Stan Dendinger Manager — Advanced Product Development SILICON GENERAL, INC. 11651 Monarch Street Garden Grove, California 92641

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1. INTRODUCTION

Many power control engineers have designed successful switching power supplies around the SG1524 Pulse Width Modulator integrated circuit. This application note explains the differences between this earlier device and the more sophisticated SG1524B. While the functional pinouts are identical for the two devices, there are some distinct operational differences which the user should be aware of when designing new supplies or when updating an existing design. In many cases design changes are minimal (such as adjustment of frequency compensation) or not required at all. At the same time the improvements in control architecture and circuit design of the SG1524B allow the designer to obtain levels of performance in new power supply designs not possible with the older device.



2. GENERAL COMPARISON

Figures 1 and 2 show respectively the block diagrams of the SG1524 and the SG1524B. Both devices were designed for voltage-mode control, but both can be used to implement current-mode control as well with the addition of an external dual op amp. For further details see the Silicon General Application Note "Current Mode Control with the SG1524B."

The main functional difference between the two circuits is in the action of the shutdown pin. In the SG1524, a voltage at Pin 10 greater than ± 0.7 volts will turn on an internal tran-

sistor which pulls the error amplifier output to ground. In the 1524B, a voltage greater than +1.2 volts at Pin 10 activates a logic gate which inhibits the pulse output of the PWM comparator. The error amplifier output voltage is not affected directly.

Other improvements include the addition of an undervoltage lockout function and fault suppression logic. These provide protection against inadequate supply voltage to the control IC and insure constant-frequency alternating output pulses to the power devices.

INDIVIDUAL SECTION DIFFERENCES

3.1 VOLTAGE REFERENCE

The voltage reference is a low-drift bandgap design which provides a precision +5.0 volt reference for the control loop. Initial accuracy is $\pm 1\%$ for the SG1524B/2524B, and $\pm 2\%$ for the SG3524B. This is a factor of four improvement over the original reference. Line regulation is typically better by a factor of 3:3mV instead of 10mV. Load regulation is better by a factor of 4:5mV rather than 20mV. The temperature coefficient is also lower and more uniform from device to device. All these features translate directly into tighter tolerances on the switcher output voltage.



At 25 °C the differential drop across the regulator is only 1.2 volts, as opposed to 2.7 volts for the 1524. Figure 3 shows the relationship between VIN and VREF for both devices. As a result the SG1524B is fully functional with a 6.2 volt supply. Under worse case conditions of ILOAD = 20 mA and TA = -55 °C, all devices are guaranteed to function at VIN = 7 volts.

3.2 UNDERVOLTAGE LOCKOUT

This circuit has two sections: a controlled current source which forces the error amp low and the output transistors off, and a bandgap comparator which overrides the lockout source. The current source is fully active when VIN is + 1.2 volts. Since the error amp and output driver cannot function until VIN is approximately 3 volts, it is impossible for spurious output pulses to ocur when the supply voltage is too low for normal operation.

The bandgap comparator monitors the reference voltage. It enables the SG1524B when the reference rises to +4.3 volts. This arrangement allows operation from a +5 volt $\pm 5\%$ supply by connecting VIN and VREF together.



UNDERVOLTAGE LOCKOUT TEST CIRCUIT

The action of the undervoltage lockout can be observed with the test circuit of Figure 4. A 100K pull-up resistor is connected from Compensation to VIN. VIN is swept from 0 to +6.5 volts with a 5Hz triangle waveform from a function generator. An oscilloscope in XY Mode displaying VIN horizontally and Compensation vertically will generate the display shown in Figure 5.



As V_{IN} slowly sweeps from 0 to 1 volt, the lockout current source becomes active and pulls the error amp to ground, guaranteeing 0% duty cycle from the controller. From 1 volt to approximately 5.5 volts the controller is inhibited while the internal circuitry stabilizes. At 5.5 volts the bandgap comparator overrides the lockout current, releasing the output of the error amp. The reverse portion of the voltage sweep is identical, except that approximately 200 mV of hysteresis can be observed at the comparator trip point.

3.3 OSCILLATOR

The oscillator of the SG1524B is programmed for frequency with an external Rt and Ct in the same manner as the SG1524. Both initial accuracy and temperature coefficient have been improved with the "B" version.

There are two methods to synchronize multiple units together.

- A. Program a master unit with Rt and Ct for the desired frequency. Connect the Ct terminal (Pin 7) of the master to the Ct terminal of the slave. Connect the OSC terminal (Pin 3) of the master to the OSC terminal of the slave. Leave the slave Rt terminal (Pin 6) open or tied to the reference. This is the recommended approach if the PWM controllers are close together (on the same printed circuit board and within six inches of each other.)
- B. Program a master unit for the desired frequency. Select Rt and Ct for the slave units such that they free-run at a frequency 10% slower than the master. Connect all the Oscillator terminals together. This method is recommended if the PWM controllers are not close together, since it avoids routing a high impedance line (Ct) around a noisy environment.



OSCILLATOR SYNC TO AN EXTERNAL CLOCK

To synchronize one or more devices to an external clock frequency, one of the connections shown in Figure 6 should be used. The device(s) to be synchronized should free-run 10% slower than the clock. Pulse width of the external clock should be at least 200nsec, but not longer than the desired deadtime.



FREQUENCY COMPENSATION OF THE ERROR AMPLIFIER

3.4 ERROR AMPLIFIER

The error amplifier of the SG1524B is, like its predecessor, a transconductance design with an output impedance of approximately 4 megaohms. This allows use of exteral clamp circuitry to obtain soft-start and duty cycle limit, as on the original 1524. Since all the voltage gain takes place at the output pin, open-loop gain/ frequency characteristics are easily controlled by shunt reactance from Pin 9 to ground (Figure 7). Also, this type of amplifier has a very predictable 1/T variation of open-loop gain with absolute temperature as shown in Figure 8.

The input common mode range is +2.3 to +5.2 volts, so that existing designs at +2.5 volts will function with no modifications. For new designs the +5 volt reference may be applied directly to the non-inverting input, eliminating the necessity for two divider resistors.



Since the lower common mode limit is +2.3 volts for the 1524B and +1.8 volts for the 1524, neither amplifier should ever be used in the non-inverting unity-gain configuration shown in Figure 9. The error voltage must swing down to +0.5 volts to guarantee 0% duty cycle from the pulse width modulator, and this violates the common mode range specification.

In general, any frequency compensation for the voltage control loop which works with the SG1524 can also be used with the SG1524B with no modification.



3.5 CURRENT LIMIT AMPLIFIER

The current limit amplifier of the SG1524B is one of the most significant areas of change from an applications viewpoint. Like the original circuit, there is a fixed 200mV threshold designed into Pins 4 and 5 to permit direct sensing across a current sampling resistor. Differences in the "B" circuit affect the input bias current, allowable common mode range, and stability in current-limit.

3.5.1 INPUT BIAS CURRENT

In the SG1524, there is a constant 130 µA flowing out of Pin 4, while the current out of Pin 5 is variable from 0 to $100 \mu A$ depending on the differential input voltage. Because of this characteristic the current limit sense terminals must be driven from source impedances less than 20 ohms to avoid modulating the current limit threshold. The "B" device features bias currents which are identical at each pin, are independent of current sense voltage, and are a factor of 10 lower. This allows predictable foldback current limiting without wasteful lowresistance divider networks.





SENSING PRIMARY CURRENT WITH AN EMITTER RESISTOR

3.5.2 COMMON MODE RANGE

The guaranteed common mode range of the current sense inputs is 0 volts to VIN - 2.5 volts. Current sensing in a supply ground line is possible, but the configuration of Fig. 10 should be used to avoid damaging the IC. The 100 ohm resistor is required because of delays through the controller and storage time in any bipolar power device. The SG1524B will reduce the pulsewidth as Pin 5 is driven 200 mV below ground, but in practice it is overdriven due to the aforementioned delays. If Pin 5 is driven below -0.3v at Ta = +125 °C the substrate diode will conduct. The 100 ohm resistor will limit the peak substrate current to a safe value without shifting the C.L. threshold.

Current sensing may also be accomplished with a common emitter or source resistor to ground as shown in Figure 11; or it may be placed in the supply output line, as indicated in Figure 12. At - 55 °C the value of VIN must be at least 2.5 volts greater than the switcher output voltage.



CURRENT SENSING IN THE OUTPUT LINE

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3.5.3 FREQUENCY COMPENSATION

The original SG1524 current limit amplifer had a typical open loop gain of 44dB, and was internally compensated to produce a single-pole rolloff above 300 Hz. The SG1524B exhibits 75dB of gain and has no internal compensation. The circuit may be used as a moderate speed comparator, or it may be used as an analog gain block to override the error amplifer.

Because of the higher gain and bandwidth, designers may find that the control loop will oscillate when the supply goes into current limiting. The cure is to add frequency compensation externally to the current limit circuit or to rework the existing voltage loop compensation. See the Silicon General Application Note "A New, Versatile P.W.M. Control Circuit for Switching Power Supplies."

3.6 SHUTDOWN

The shutdown circuit of the "B" is illustrated in Figure 13. It has the following differences compared to the 1524:

- A. Logic threshold is + 1.2 volts instead of + 0.7 volts for compatibility with TTL logic and improved noise immunity.
- B. Input current is very low (usually under 100 nA) even at +5 volts input. The pin may be driven directly from TTL logic (all families) or TTL-output comparators.
- C. Response time is very fast, between 35 and 100 nanoseconds depending on output transistor loading.

The shutdown pin should never be left floating. If not used, the pin should be grounded. If the shutdown function is used, the pin should be driven from a low impedance source to prevent noise pickup. The internal logic is very fast, and will respond readily to spurious pickup from the normally noisy environment of a switcher.





FIGURE 14. DRIVING POWER BI-POLAR TRANSISTORS WITH THE SG1524B

3.7 OUTPUT TRANSISTORS

The output devices have been redesigned to provide 100 mA continuous and typically 200 mA peak, with BV_{CEX} ratings of 60 volts. Saturation voltage is guaranteed both at 10 and 100 mA to ease the interface with external power devices.

3.7.1 BIPOLAR DRIVE

For driving bipolar power devices the circuit in Figure 14 is recommended. The output transistor is used as a phase-splitter to generate the necessary base drive. Figure 15 illustrates forward and reverse base current, and collector current of a PMD 20K 120 volt, 14 amp Darlington using this driver configuration.





FIGURE 16. DRIVING POWER MOSFETS WITH THE SG1524B

3.7.2 POWER MOSFET DRIVE

Highly capacitive loads such as presented by the gates of power MOSFETs can be readily driven with the circuit in Figure 16. At turn-on, 200mA of charging current is conducted by D1. During turn-off D1 becomes back-biased by the pulldown resistor. Q1 turns on and provides 500mA of discharge current. Figure 17 shows the turn-off gate voltage and drain current of an IRF130 100 volt, 14 amp power MOSFET driven directly with this circuit.

4. CONCLUSION

A designer who is familiar with the SG1524 will find it relatively easy to adapt his designs to use the SG1524B. The immediate benefits are higher levels of power supply performance, worthwhile reductions in total component count, a greater degree of protection for the power devices, and lower overall costs.



A NEW, VERSATILE P.W.M. CONTROL CIRCUIT FOR SWITCHING POWER SUPPLIES

Stan Dendinger

Manager — Advanced Product Development SILICON GENERAL, INC. Garden Grove, California 92641

ABSTRACT

A new control circuit for pulse-width-modulated switchmode power supplies is described. This device offers improved electrical and functional performance over earlier designs, while retaining the familiar pin-out of the industry-standard SG1524. Innovative circuit design techniques and optimized control architecture result in improved reference accuracy, protection against inadequate supply voltage, elimination of harmful output switching transients, improved current limiting, and higher voltage and current capabilities from the output transistors. A 50 kHz power supply utilizing the new controller is described, and performance characteristics are analyzed.

1. INTRODUCTION

Since the introduction in 1976 of the first monolithic control chip for switchmode power supplies, and its subsequent wide acceptance as the basic building block for high-efficiency regulator designs, the semiconductor industry has found itself in a bit of quandry when attempting to define an improved device. On the one hand, the initial device, being rather simple and straightforward, had a number of deficiencies when its capabilities were compared with the total requirements of most switchers. As a result, new, more complex controllers were introduced with improved reference accuracy. protection against inadequate or fluctuating supply voltage, improved current limit circuitry, fault suppression logic, and a host of other features.

On the other hand, the new controllers, while enthusiastically accepted first by aerospace designers for sophisticated high-performance supplies and later by major computer and instrumentation manufacturers, lacked the familiar pin-out of the earlier device. As a result it has not been possible until recently to easily upgrade the performance of an existing design by simply plugging in a more intelligent pin-forpin substitute.

The circuit to be described has been under development at Silicon General for more than two years, and represents an attempt to fit as much function as possible within the constraints of the original device pin-out. Designated the SG1524B, the device block diagram is shown in Figure 1.

2. FUNCTIONAL DESCRIPTION

A precision +5.00V reference trimmed to an initial \pm 1% accuracy provides a voltage standard for the regulation loop. It also powers most of the internal control circuitry, eliminating adverse effects due to fluctuating supply voltage. A high gain error amplifier compares the reference

voltage with the switchmode supply output voltage, and generates a PWM control voltage at Pin 9. This voltage is compared against a periodic linear ramp generated by the oscillator circuit. Oscillator frequency is determined by an external timing resistor and capacitor, R_T and C_T . The comparator output is a fixed-frequency, variable pulsewidth logic signal which passes through routing logic to one of the two high current output transistors if the Shutdown pin is LOW.

A current limit amplifier within the IC overrides the PWM control voltage when the voltage differential at the Current Limit Sense inputs reaches 200 mV. This built-in threshold permits direct sensing across an external current sampling resistor. On-chip undervoltage lockout circuitry protects the power semiconductors in the switchmode supply by guaranteeing orderly start-ups and shutdowns as supply voltage is switched on and off.

Each control section of this new PWM controller has been either redesigned for improved performance, or is a completely new function compared to the original SG1524 design. A detailed description of each section follows to highlight the major improvements.

2.1 Bandgap Reference Regulator

The precision reference uses the predictable base-emitter voltage of NPN transistors to generate the +5V reference voltage, rather than a zener diode^{1, 2}. The advantages of this design approach are: lower noise due to elimination of the shot noise associated with an avalanche device, low turn-on drift, better long term stability, and operation from a lower supply voltage. The primary disadvantages are that the bandgap requires more components, and thermal matching of key devices is necessary for realizing low thermal drift.



FIGURE 1. BLOCK DIAGRAM OF THE \$G1524B PULSE WIDTH MODULATOR.

	ZENER REFERENCE	BANDGAP REFERENCE
Minimum Supply Voltage	8V	7V
Output Noise Voltage	75 μVrms	25 μVrms
Long Term Stability	, 20 mV/ 1000 hrs	5 mV/ 1000 hrs
Turn-on Drift	5-35 mV	2 mV

TABLE 1. COMPARISON OF ZENER AND BANDGAP REFERENCE TYPICAL PARAMETERS

The ability of the PWM controller to be fully functional with a 7V supply enhances its usefulness in portable instrumentation applications, where sixcell Ni-Cad battery packs are frequently found, and a 1.16V cell voltage is defined as end-of-life before recharge.

2.2 Undervoltage Lockout

The undervoltage lockout circuitry prevents spurious turn-on commands to the external power transistors when the supply voltage to the integrated circuit is too low for proper operation. When the reference voltage is less than +4.5V, the output transistors are forced to an OFF or nonconducting state. Additionally, the output of the error amplifier is clamped to ground. When the supply voltage rises to +7V, the output drivers are enabled and the amplifier output is released. Since compensation capacitance is usually present at Pin 9, this provides a measure of built-in soft start.

During the power-up period of the controller, when the undervoltage lockout is active, bias current is freely supplied to all the internal control circuitry. This insures that all control functions have stabilized in the proper state when the turn-on voltage is reached, and it prevents the possibility of start-up glitches.

The lockout circuitry monitors the reference voltage rather than $+V_{IN}$ to allow the SG1524B to be used with +5V supplies in the same manner as the original SG1524. If the $+V_{IN}$ pin is connected to the V_{REF} pin and $+5V \pm 10\%$ is applied, the control chip will function normally. When the undervoltage sense circuitry monitors the $+V_{IN}$ pin, this type of operation is not possible due to the 2-3V drop across the internal regulator.

To provide jitter-free turn-on and turn-off points, the lockout circuitry has been designed with approximately 500mV of hysteresis. This provides rejection of 120Hz ripple on the $+V_{IN}$ line, and reduces capacitive filtering requirements on the controller supply voltage.

2.3 Error Amplifier

The error amplifier of the SG1524B was designed with three principle goals in mind: a commonmode range extending from $\pm 2.5V$ to $\pm V_{REF}$, excellent supply voltage and common-mode noise rejection characteristics, and a minimum voltage gain of 60 dB at $\pm 125^{\circ}$ C. Like its predecessor, it is a transconductance amplifier with a high-impedance output to permit external soft-start circuitry.





Input transistors Q1 and Q2 are connected as emitter-followers with their collectors tied to the +5V reference supply. This configuration provides the required common-mode range, even with +VIN connected to VREF for operation from a +5V supply. It also provides current gain to reduce input bias current, and produces a low impedance source to drive level shifters O3 and Q4. These PNP devices operate at a forced beta of 1.0, and are connected common-base to maximize frequency response. Input stage operating current is set up by the 100 μ A bias supply to the common base. Frequency response is further improved by the low impedance collector loads Q5 and Q7. These two devices are diode-connected and form the input sides of two precision 2-to-1 current mirrors, which provide additional current gain. The output current of Q6 provides the pull-down or sink current for the amplifier output. The collector current of Q8 is referenced to the +5V supply rail by the Wilson current mirror consisting of Q9, Q10, and Q11. The collector current of Q11 provides the pull-up or source current for the amplifier output.

It can be seen from the symmetry of the circuit that a differential input voltage is converted to an output current, with a maximum of $\pm 200\mu$ A

available. The open-loop voltage gain can be shown to be $^{\rm 3}$

$$A_V = gm R_L = I_S \frac{q}{kT} R_L = .001 R_L at +25^{\circ}C.$$

Since R_L is the parallel combination of the output impedances of Q6 and Q11, and is typically $4M\Omega$, an open-loop voltage gain of 72dB is obtained.

The circuit design of the output stage insures that the maximum positive output swing never exceeds +4.3V. This is important when considering loop recovery from momentary overloads which drive the PWM to maximum duty cycle. The peak value of the sawtooth oscillator waveform is +3.4V, and the error amplifier must slew from positive full scale to less than this voltage to reduce the duty cycle from maximum. Some error amplifier designs clamp the output voltage with a 6.3V zener diode, nearly tripling the recovery time from overload. Since all the voltage gain of the error amplifier takes place at the output pin, the amplifier can be easily frequency compensated at this node with shunt reactance to ground. The uncompensated amplifier exhibits an open loop pole at 350 Hz and a typical unity-gain bandwidth of 2 MHz.

2.4 Current Limit

The current limit amplifier has been redesigned to eliminate the two most common complaints about the original SG1524: limited input voltage range and slow response time. In the original design the \pm 1V common-mode range restricted current sensing to the supply return line only. In many systems, ground returns cannot be separated, making the current limit function unusable. Also, the internal frequency compensation provided freedom from oscillation at the expense of response time.



FIGURE 3. HIGH-GAIN CURRENT LIMIT AMPLIFIER.

In the new design, input transistors Q1 and Q2 allow common mode voltages as low as -0.3V over the operating temperature range, allowing sensing in the ground line for configurations that

require it. The upper limit is restrained only by the value of $+V_{IN}$, to which the level-shifter current sources I1 and I2 are referenced. The voltage drop across R2 creates a 200 mV offset voltage at the amplifier input which provides the current sense threshold. The positive 0.2%/° C temperature coefficient of R2 is balanced by a negative tempco for I2, effectively cancelling effects of temperature on the current sense threshold.

Since both the allowable common-mode and differential voltages are much greater with this design, higher current foldback ratios can be achieved compared to the maximum of 3 or 4 possible with the earlier part. Also, the bias currents are a factor of 10 lower, resulting in more consistent limiting thresholds from unitto-unit when foldback is employed. Because there is no internal compensation capacitor, stability in the current limit mode will depend on external components. Due to the controller architecture, in which the output of the current limit amplifier overrides the error amplifier, these external frequency compensation networks may either be shared with the error amplifier or optimized for the current limit amplifier. The two choices are shown in the figures. In either case, the designer now has the freedom to optimize bandwidth for his particular switcher configuration.



FIGURE 4. CURRENT LIMIT COMPENSATION IN COMMON WITH ERROR AMP.



FIGURE 5. CURRENT LIMIT WITH OPTIMIZED FREQUENCY COMPENSATION.

2.5 Oscillator

The sawtooth oscillator circuitry of the SG1524B incorporates the same design improvements recently applied to the SG1524. These result in greatly improved external drive and synchronization capability, together with reduced sawtooth undershoot at high frequencies. In the original SG1524 design, an external synchronization pulse applied to the OSC pin did not generate a self-sustaining discharge cycle. The extent of the discharge of CT depended on both the amplitude and duration of the external pulse. As a result, it was possible to generate erratic sawtooth waveforms with partial discharge cycles and pulse-to-pulse modulation of waveform endpoints. The frequent result was audible noise from subharmonics, transformer saturation, and destruction of the power transistors.

In the improved design, an external sync pulse which meets the minimum threshold requirements triggers a positive feedback circuit. This circuit drives the oscillator to end-of-discharge even if the external pulse is very narrow. Due to the feedback, there exists no in-between or quasisynchronized state; the oscillator switches smoothly between free-running and synchronized modes as the external pulse amplitude is varied through the trigger threshold. The positive feedback also effectively bootstraps the comparator gain, providing enhanced voltage swing and output current at Pin 3 to drive peripheral circuits. The improved oscillator design, together with a fast, DC-coupled toggle flip-flop, permits operation beyond 500 kHz. However, the limitations associated with single-transistor outputs put a practical upper limit of 400 kHz on the device.

2.6 Full Double-Pulse Suppression Logic

The PWM logic in the SG1524B insures that the output pulses always alternate from side to side, regardless of the action of the shutdown circuit. This is very important in push-pull switcher

configurations, where two pulses in succession on one side of the power transformer primary will cause core saturation and instantaneous failure of the power transistor.

The logic consists of two sections: a PWM latch circuit and a memory flip-flop. The latch allows only one pulse through per oscillator cycle. Once a PWM pulse is terminated, whether due to the normal PWM process or due to SHUTDOWN going high, the pulse cannot start again until the beginning of the next oscillator cycle. Pulse-by-pulse current limiting is easily accomplished now because of the latch feature and the completely digital (and therefore very fast) shutdown circuitry.

The memory flip-flop insures that output pulses always alternate from the output transistors. This is accomplished by generating a clock to the toggle flip-flop only if a PWM pulse was generated during the previous cycle. In the original 1524, the toggle flip-flop changes state with every oscillator pulse, irrespective of what the outputs are doing.

Figures 6 and 7 illustrate the difference in performance between two PWM control ICs, one with only a data latch and the other with the full double-pulse suppression logic described above. The triple-trace photos in each example show an alternating output pulse sequence interrupted by a SHUTDOWN command, followed a short time later by resumption of outputs from Emitters A and B. Oscillator frequency is 40 kHz for each device, so 20 kHz is obtained at the output transistors.



FIGURE 6. OUTPUT SEQUENCE WITHOUT DOUBLE PULSE SUPPRESSION.

In the first case, the PWM pulses are alternating can BABAB when a SHUTDOWN signal inhibits the outputs for five oscillator cycles. When output resumes, the output sequence begins BABAB....Two pulses have occurred in succession from Emitter B.

With the second control IC, the PWM pulses are again alternating BABAB when a SHUTDOWN

signal is received, again inhibiting output for five oscillator cycles. When SHUTDOWN is removed, output resumes, but with an ABABA...sequence. The potential double-pulse from Emitter B has been eliminated by the internal pulse-steering logic.



FIGURE 7. OUTPUT SEQUENCE WITH DOUBLE PULSE SUPPRESSION.

This side-by-side pulse-routing problem exists for any PWM control IC with push-pull architecture and a truly digital shutdown function. In the original 1524 design, recovery from shutdown was fairly slow since the error amplifier output was pulled to ground for turn-off. Turn-on was limited by the 100µA output current of the error amp, the internal compensation capacitor in the current limit circuitry, and any external frequency compensation components. This created an inherent soft-start characteristic. With digital shutdown, the error amp voltage is not immediately affected; the first pulse out after shutdown can be the same width as before shutdown, making pulse-routing logic an absolute necessity to guarantee the safety of the power switches.

2.7 Output Transistors

In response to requests for greater output drive capability, the output transistors were redesigned for both higher breakdown voltage and more current.

In a PWM controller with a single-transistor output structure, the load driven is frequently one end of a center-tapped transformer primary winding. Since the maximum collector voltage is $2 \times V_{CC}$, the absolute maximum rating of 40V for the earlier device restricted the supply voltage to 20V. Consideration given to the effects of transformer leakage reactance would reduce this voltage still further. The SG1524B output transistors carry BV_{CEX} ratings of 60V, high enough for use on a standard +28V supply bus.

Output device geometry was scaled up to allow reliable operation at continuous collector

currents of 100 mA. This represents a factor of two improvement over the earlier device, which was characterized only at 50mA. As a further aid to the designer, the data sheet for the new device specifies maximum saturation voltage at two continuous current levels: 10mA and 100mA. The maximum peak current capability of the output transistors is 200mA for 1μ S.

The anti-saturation clamp circuitry around the output transistors found in the earlier PWM controller has been retained in the SG1524B to enhance switching speed. Each output transistor is also guarded against excessive current by protective circuitry which limits the maximum continuous current to 150mA at +25°C.

3. DESIGN EXAMPLE

The functional usefulness of a new device is best demonstrated by study of an actual switcher design. The circuit described illustrates full control of a power supply with a single integrated circuit, resulting in reduction of overall cost and an increase in supply reliability through reduction of component count.

The circuit illustrated in Figure 8 is a push-pull, +28V to +5V converter operating at 50 kHz. The power supply is unique in that the only active component is the SG1524B regulating pulse width modulator; the only other semiconductors required are diodes.

The DC-coupled push-pull configuration was chosen because it is most sensitive to PWM controller anomalies which cause side-to-side imbalance. These include start-up problems such as output from only one driver until the toggle flip-flop begins to be correctly clocked by the oscillator. During normal operation, side-to-side imbalance of volt-second product due to unequal propagation delays in the IC can cause the onset of core saturation. Finally, as outlined earlier, when the digital Shutdown control is activated, double-pulse sequencing can drive the excursion of the transformer core flux past the saturation knee of the BH loop.

Capacitor C3 acts as a high-frequency bypass for the IC supply line, while C6 is the high current reservoir for the power stage. The oscillator is set for 100 kHz with C4 and R5. When divided by two by the action of the internal toggle flip-flop, this becomes 50 kHz at the power transformer. The +5V reference is filtered against high frequency noise pick-up by R2 and C1, and applied to the non-inverting input of the error amp. The inverting input is connected to the power supply output terminals to form the negative feedback loop required for regulation. R3 minimizes the effects of input offset bias current by equalizing the source impedance seen by each error amp input terminal. Closed loop stability is provided by frequency compensation components R4 and C2, using the common technique of cancelling one of the two poles of the LC output filter with a open-loop zero in the error amplifier.4

In the power section of the supply, the two output transistors are used to directly drive a center-tapped transformer. A snubber network consisting of C5 and R6 modifies the inductive



FIGURE 8. A SINGLE IC 50 kHz PUSH-PULL CONVERTER.

load line seen by each transistor. The transformer itself is wound on a small ferrite core; turns ratio is 3:1. Rectifier diodes D1 and D2 are Schottky junction devices to maximize efficiency at +5V output. Filtering is provided by L1, wound on a permalloy powder toroid, and C7. The improved common mode range of the current limit amp is used to good advantage here; current sensing is done directly in the output line. A foldback ratio of 7.5 to 1 is obtained with the given values of R7, R8, and R9. The divider formed by R7 and R8 applies a back-bias of 1.3 volts, or 6.5 times current limit threshold, when the supply output is at +5.0V. Peak output current before onset of current limiting is 200 mA. and short-circuit current is only 25 mA. Rapid turn-off of the control circuit is accomplished by closing SW1. R1 and Z1 limit the maximum voltage applied to the Shutdown terminal to less than +5V.

While capable of only limited output power due to thermal limitations of the 16 pin Cerdip package, the supply amply illustrates the controller ability to perform all the major control functions required both during start-up, normal regulation, and overload.

4. CONCLUSION

In the past it was often necessary to incorporate additional components around the 1524 pulsewidth modulator to enhance its capabilities, and to guard against various functional anomalies. Economically this was feasible due to the relative cost of the control device compared to the cost of the peripheral components.

With the occurrence of the usual price decline characteristic of most integrated circuits, the economic balance has shifted. Many users now pay more for the necessary support circuitry than for the 1524 itself.

The availability of the SG1524B now gives the designer another option. In many instances costly additional support components can be eliminated and a functionally superior device may be plugged directly into an existing design, with the benefit of simplicity, greater reliability, and reduced overall cost.

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Application Notes — SG1524/1525A/1526/1527A/1627/1629

POWER SUPPLY CIRCUITS HEAD FOR SIMPLICITY BY INTEGRATION

Stan Dendinger Advanced Product Development Silicon General, Inc. 11651 Monarch Street Garden Grove, California 92641

SUMMARY

The benefits obtained from switching power supplies have become universally recognized by power systems engineers in the past several years. However there has been a simultaneous realization that, too frequently, gains in efficiency and reductions in weight have been accompanied by an escalating component count and a decrease in reliability and predictability of performance. To effectively solve these problems, integrated circuit manufacturers have recently designed new products specifically for switchers. These devices offer the proven advantages of monolithic technology: compactness, accuracy, reproducibility, higher performance through reduction of parasitics, and the economies of mass production.

This paper reviews the circuit simplifications made possible by these specialized devices, as typified by the first practical switching regulator control chip, the SG1524 Pulse Width Modulator, and later by other circuits such as the ZN1066, the TL494A, and the MC3420. A second potential area of power supply simplification is the interface between the control circuit and the high power switching transistors. Two specialized driver circuits, the SG1627 and SG1629, are described which provide high-level turn-on and turn-off signals for efficient switching. Finally some second and third generation pulse width modulator designs will be discussed. These later devices, designated the SG1525/27 series and the SG1526, offer even higher levels of control function integration compared to earlier designs. The SG1526 in particular integrates a number of protective control features which substantially increase the reliability of the power semiconductors in "real world" switching power supplies.

HISTORICAL PERSPECTIVE

A basic pulse width modulated switching power supply requires only four control elements: a precision reference voltage, a ramp oscillator, an error amplifier, and a differential voltage comparator. Each of these elements has been available in integrated circuit form for years, with the well-established benefits of reduced physical size, greater reliability, and increased performance. In light of this background, the development of a single monolithic circuit for switching power supply control appears to be a logical progression.

One of the first devices available to power supply desigers was the SG1524 Pulse Width Modulator from Silicon General. This circuit, shown in Figure 1, contained all of the basic control elements required for a switching regulator. In addition to providing the four basic control elements, the device allowed for push-pull configurations by inclusion of a toggle flipflop and dual alternately-gated output transistors. Finally, provision was made for some abnormal power supply operating conditions. An analog current limit circuit and a digital shutdown control were included to provide protection against short circuits and other load faults.



FIGURE 1. SG1524 PULSE WIDTH MODULATOR BLOCK DIAGRAM

Despite this level of complexity, the device was easy to understand and was quite flexible. As a result, since its introduction in 1976, the SG1524 has been very widely accepted within the power supply industry, finding its way into a majority of new designs, including exotic applications in communications satellites and the space shuttle program.

POWER DRIVER INTEGRATION

As experience was gained in applying the SG1524, it became apparent that there was a gap between the output power capabilities of the control integrated circuit and the drive levels required by the power semiconductors. Two areas were identified within most supply configurations where specialized driver functions could be successfully implemented with monolithic technology.

An Integrated Source/Sink Driver

The first design is a dual 500mA totem-pole driver with externally programmable current sourcing. Both inverting and noninverting logic inputs are available, and may be driven by either an open-collector control circuit or (with a diode) by TTL logic. Connections to the high current output transistors are brought out separately, allowing maximum flexibility when interfacing with standard bipolar transistors, the new VMOS power FETs, and transformers.









<u>Power Bipolar Drive</u> is accomplished with the connection shown in Figure 3. R2 controls the magnitude of forward base drive, and is selected to develop a voltage drop of one VBE when the output Darlington pair is sourcing 350mA. At the same time R3 develops a 3.5 volt differential, which is stored by C1. During turn-off, sink transistor Q9 saturates, pulling the output terminal to ground. The emitter-base junction becomes reverse biased from a low impedance source, allowing stored base charge to be rapidly extracted.

<u>Power FET Drive</u> is possible with a minimum of external components. The source/sink capability of the SG1627, to-gether with its fast edge speeds, makes it an ideal driver for power MOSFET devices. Although MOSFETs have negligible DC gate current, input capacitances of 800—1000pF exist in the higher current units. Since this capacitance must be charged and discharged by 10 or 12 volts in 10 to 20 nano-seconds, high peak currents are required. At switching frequencies of 200 kHz, considerable dynamic power dissipation is required of the drive cicuit to obtain the high speed switching benefits of these devices.

In Figure 4, peak currents in the output stage are limited by R2, while R1 helps minimize power in the SG1627. With some power FETs, a 100 ohm resistor in series with the gate lead may also be necessary to eliminate device oscillations.



FIGURE 4. A SOURCE/SINK DRIVER PROVIDES THE PEAK CURRENTS REQUIRED BY POWER FET'S AT HIGH SWITCHING FREQUENCIES

<u>Transformer Drive</u> is the third interface area where an integrated power driver can eliminate components. Most bi-phase transformer drive circuits using grounded emitter transistors require additional components to reset the magnetic flux to zero every half cycle. This is necessary to insure that no net DC excitation is applied to the transformer primary over many cycles of operation, thereby avoiding core saturation. These additional components may include extra transformer windings, clamp diodes, and anti-phase driven clamp transistors. A much less complex circuit can be achieved with the SG1627, as shown in Figure 5.





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In this circuit the transformer primary is voltage-driven by the source/sink output structure of the SG1627. Core reset to zero occurs automatically during deadtime, when both ends of the primary winding are switched to ground. Resistors R₁ and R₂ serve as over-current protection for the driver in case of control malfunction or onset of core saturation due to load faults on the secondary. No center tap is required, resulting in elimination of winding balance problems.

An Integrated Floating Switch Driver

The second interface considered was that between the secondary winding of a drive transformer and the base-emitter junction of an NPN power transistor. This configuration is frequently found in off-line converters, where a half or full bridge design is chosen because of the high input supply voltage. In this case the design problem consisted of providing controlled forward base drive to the power device during the positive polarity of the secondary voltage, and a fast negative peak current for rapid switch-off during the negative portion of the cycle. No power other than that provided by the transformer secondary should be required, so that the power device can be floated above ground by several hundred volts.



FIGURE 6. SG1629 FLOATING SWITCH DRIVER BLOCK DIAGRAM

The circuit shown is a modification of a discrete design developed by Pete Wood while at TRW Semiconductors¹. During a positive cycle, base current flows from the drive transformer secondary winding through a source transistor which can be programmed for current limiting. A center tap on the secondary completes the circuit for returning base drive current. At the same time, external storage capacitor CS is charged to a negative value through the high current rectifier diode in the switch driver. When the secondary voltage is driven to zero, the rectifier diode becomes reverse biased. The resulting positive drive turns on the Darlington sink transistors, which reverse-biases the base-emitter junction of the power device through the storage capacitor. A large negative current spike results, minimizing the turn-off time and power loss in the switching transistor.



FIGURE 7. SG1629 FLOATING SWITCH DRIVER SCHEMATIC DIAGRAM

As the detailed schematic of the SG1629 indicates. in addition to the high current Darlington source and sink transistors the circuit also contains several gating options for the sink or turn-off section of the driver. Source transistors Q3-Q4 and sink transistors Q6-Q7 are designed to 2 amp collector currents. Base drive to the source is provided by R2, while Q5 provides current limiting. On the sink side of the circuit, base drive to Q6-Q7 is normally provided by a resistor connected to Pin 3. Q1 senses the polarity of the input voltage and gates the source transistor off between each drive current pulse. This action allows the external storage capacitor to be charged even at very low duty cycles, since the discharge current during the "off" portion of the drive cycle becomes negligible. The sink gate input is used when the risetime of base turn-on current is important, and transformer inductance is a significant limiting factor. Methods for using this feature are found in the SG1629 application note2.

Power Driver Summary

Two integrated power driver circuits designed specifically for use in switch-mode power supplies have been reviewed. These devices provide the necessary power gain between a complex low-power control circuit and high voltage, high current switching semiconductors, while offering greater performance in a reduced volume compared to discrete component designs. Monolithic technology will provide even higher levels of voltage and current handling capability in the future as soon as semiconductor packaging technolgy solves the problem of providing large pin-outs in a high power dissipation package.

A SECOND GENERATION PULSE WIDTH MODULATOR CONTROL CIRCUIT

As switch-mode power supplies gained in popularity, a demand was made by power supply design engineers for an integrated circuit that offered all of the functions of a control device and the interface capabilities of a power driver. The SG1525A series of pulse width modulators represents a combination control IC and power driver. The control section is based upon the time-proven architecture of the SG1524, while the output stage of this device combines many of the elements of the previously discussed 1627 power driver. At the same time, improvements were made within the architecture of the control chip to include even more functions than were originally available on the 1524.

The internal reference regulator on the chip is trimmed to an accuracy of ±1%, compared to the original ± 4%. Secondly, the chip now contains on-chip shutdown and soft start circuitry. The only external components required are an external timing capacitor. A third area of improvement is in the common mode range of the error amplifier. By designing the error amplifier so the common mode range now includes the 5.1V of the reference. a reference divider network is no longer necessary, thus eliminating two external resistors. The oscillator circuitry has been redesigned to make dead time control easier and multiple device synchronization easier. Finally, the output stage has been redesigned so that, instead of a single transistor which is periodically turned on for pulse width modulation, an output source/sink driver or totem-pole type design is used. Since this particular driver has the characteristic of low impedance in both the on and off states, it becomes much easier now to interface the control circuits with external power transistors including standard bipolar junction devices, the new power FETs, and also drive transformers.

This new family of regulating pulse width modulators is designated the SG1525A/1527A series of devices, and the device block diagram is illustrated in Figure 8.



FIGURE 8. BLOCK DIAGRAM OF A "SECOND GENERATION" PULSE WIDTH MODULATOR FAMILY: THE SG1525A/1527A SERIES

The trimmed reference regulator, which has an output voltage of 5.1V, not only acts as the reference terminal for the error amplifier control loop, but it acts as a power source for all the internal circuitry, with the exception of the error amplifier and the output drivers. The oscillator determines the basic operating frequency of the pulse width modulator circuit. An external R_T and C_T are the components that are fixed to set this frequency. Additionally, dead time is controlled by the insertion of a small amount of resistance between the discharge terminal (Pin 7) and the C_T terminal (Pin 5) on the oscillator. The oscillator circuit has two outputs: the ramp waveform, which is applied to the positive input of the pulse width modulation comparator, and a periodic positive-going pulse at the oscillator output pin which acts as the toggle signal for the flip-flop. It is also used as the deadtime control pulse for the output gating logic.

The totem-pole output drivers are designed to easily interface with either single ended or push-pull types of switching power supply configurations. There are two output polarities available with this series of pulse width modulators. In the 1525A series, the output gating is designed with NOR logic, which results in a positive-going output pulse during active time. The 1527A series uses OR logic, so that the active state is a low or ground state. This particular polarity of output is useful in certain types of proportional base drive circuits in which feedback from the power transformer is used to provide base current, thereby compensating for variations in transistor beta.



FIGURE 9. SG1525A/1527A SOFTSTART CIRCUIT

Soft Start Circuit

The equivalent of the SG1525A/1527A soft start circuitry is shown in Figure 9. An external capacitor CSOFT START provides the timing element for the soft start cycle. This capacitor is charged via a 50 micoramp current source internal to the chip. The P.W.M. comparator has two inverting inputs, and the more negative of the two voltages determines the duty cycle. During undervoltage conditions on the VIN line, current is forced through the two diodes in Q1's base circuit. A voltage of approximately 1 VBE appears across Q1's emitter resistor, resulting in a collector current of approximately 100 µA. Since the charging current available is only 50 µA, the soft start capacitor is held in a discharged state. Because the volatge at pin 8 is 0, the PWM comparator ignores the signal from the error amplifier, and zero duty cycle is obtained. When the controller supply rises to 8 volts the discharge current is turned off, and the voltage on pin 8 rises linearly, resulting in gradually increasing duty cycle. Eventually the capacitor charges up very close to the reference voltage and the duty cycle is controlled by the error amplifier. If the voltage on the shutdown pin is raised above ± 1.5 volts the capacitor is slowly discharged at the same rate it is normally charged.



SCHEMATIC DIAGRAM

^{VIN} ⁽¹⁾ ⁽¹⁾

Oscillator Description

The circuit for generation of the timing ramp waveform is shown in Figure 10. The timing capacitor C_T receives a constant charge current from the compound current mirror formed by Q1 and Q2. The R_T terminal voltage is two V_{BE} less than the reference voltage, so that a resistor tied from Pin 6 to ground sets up the charging current for C_T. Transistors Q5 through Q10 form a voltage comparator which constantly compares the voltage at C_T to either a +3.3V or +1V reference, depending on the state of the comparator. The timing capacitor C_T is discharged via the Darlington formed by Q3 and Q4.

When the voltage on C_T is less than +3.3V, the discharge network does not conduct and C_T receives a constant charge via the current mirror, resulting in a linearly increasing voltage. When the +3.3V trigger level is reached, the comparator changes state and turns on the discharge network. This rapidly removes charge from C_T so that the voltage falls towards +1V, at which time the comparator changes state again and another cycle begins. The discharge time of C_T is used to generate the blanking pulse at the oscillator output pin. The dead time or pulse width at the oscillator output pin may be increased from ti's minimum value of approximately 400 to 500 nanoseconds by a resistor between the discharge pin and Pin 5, which lengthens the discharge time of C_T during the second half of the oscillator cycle.

A positive pulse at the sync pin will initiate a discharge cycle in the oscillator. This pin then forms a convenient connection for synchronizing the IC to a frequency supplied by an external system clock.

Output Driver

A simplified schematic of the output gating and the power output stage of the 1525A is shown in Figure 11. Transistors Q1, Q2 and Q3, together with a 500 microamp current source, form a logical NOR gate where the pulse width modulation signal from the pulse width modulation comparator, the dead time pulse from the oscillator, and one side of the toggle flip-flop are combined. Q4 is an amplifier with active load which inverts the output signal from the NOR gate. Q5, in turn, acts as the phase-splitter transistor for the push-pull output. When Q5 is on, its emitter current drives the base of Q8, holding the output low. At the same time, the collector of Q5 is also low, thereby back-biasing Q6 and Q7, the output pull-up devices. When Q5 turns off, its collector voltage rises, turning on the output Darlington. At the same time, Q8 turns off and the output terminal is pulled up towards the VC supply. Diode D1 acts to protect the base emitter junction of the upper Darlington against reverse breakdown. D2 acts to provide extra base drive current to Q8 during turn off. If a capacitive load is present on the output terminal, D2 will turn on and the extra collector current of Q5 will then be routed to Q8 so that Q8 in turn will be turned on harder, thus discharging the output capacitance and enabling the output to fall rapidly to zero.

The source and sink transistors Q7 and Q8 in this driver are designed to provide more than 100mA of current handling capability. In most cases, the full current capability will not be used in a steady state condition to drive an external load but rather the peak current capability can be used to provide rapid charging of external capacitance loads, thereby providing very fast rise and fail times at the output of the driver.



I FIGURE 12. SG1525A/POWER FET TURN-ON WAVE FORMS



FIGURE 13. SG1525A/POWER FET TURN-OFF WAVE FORMS

Figures 12 and 13 illustrate the speed capabilities of the output drivers when driving power MOSFETs, in this case a pair of Siliconix VN64GA devices. The upper traces show the driver output voltage swing for a collector supply of +12 Volts. The lower waveforms are the 0-5 Amp drain currents of the FETs. Switching times of 100 nanoseconds were acheived by driving peak currents to 200mA with a 62 ohm resistor at the $+V_C$ terminal. Faster times can be obtained with the higher current SG1627 Power Driver.



FIGURE 14. SG1525A/1527A POWER FET DRIVE CAPABILITY

The ultimate frequency capabilities of the output drivers as a function of ambient temperature for a given VMOS load is shown in Figure 14. For this graph, a +V_C supply of 12 Volts was assumed. An effective power FET input capacitance of 1000 pF on each driver was also assumed. A thermocouple attached to the ceramic dual-in-line package allowed junction temperature to be calculated based on a worst case Θ_{JC} of 60°C/W and a Θ_{JA} of 100°C/W maximum.

For ambient temperatures below 90°C the maximum frequency allowable is determined by the maximum possible oscillator frequency of 400 kHz. Above 90°C operating frequency and dynamic power dissipation must be reduced to keep the junction temperature from exceeding +150°C. Different supply voltages, capacitive loads, and heat sinking will result in other temperature limits.

It will be noticed in comparing the block diagram of the SG1525A/1527A family to that of the SG1524 that there is no provision made directly for current limiting on the 1525A/1527A. The reason for this is that this chip is designed to interface with a new output supervisory circuit, the AF1543. This device has an extra comparator with adjustable offset which can be used for providing the current limit function in conjunction with the 1525A/1527A. Additionally, this particular chip has the capability for providing under and overvoltage protection for the remainder of the power supply.

A THIRD GENERATION SWITCHING POWER SUPPLY CONTROL CIRCUIT

- Supply operation to 40 volts
- Reference trimmed to ± 1%
- · Sawtooth oscillator with deadband control
- PWM comparator with hysteresis
- Undervoltage lockout
- Programmable soft start
- Wide error amp common mode range
- · Wide current limit common mode range
- · Two modes of digital current limiting
- Double pulse suppression logic
- Single pulse metering logic
- Symmetry correction capability
- TTL/CMOS compatible logic
- Dual 100mA source/sink output drivers

TABLE 1. DESIRABLE FEATURES OF A HIGH-PERFORMANCE PULSE WIDTH MODULATOR

An ideal circuit for switching power supplies should include not only the elements necessary for normal pulse modulation operation, but also the full range of abnormal operations. Ideally, the circuit should contain as many protective features as possible for the power semiconductors. If a table of parameters were constructed for such device, it would look much like that shown in Table 1. Analysis of the features in the table would show that most of the new features are control related and are therefore ideally suited for inclusion in an integrated circuit, where a great deal of complexity can be easily compressed into a very small area. Just such a device has been designed by Silicon General, and the block diagram of that device is shown in Figure 15.



FIGURE 15. SG1526 HIGH PERFORMANCE PULSE WIDTH MODULATOR BLOCK DIAGRAM

As can be seen, the four basic elements of the pulse modulator are present: a reference regulator, error amplifier, sawtooth oscillator, and a pulse width modulation comparator. Of particular interest are some new features in the block diagram: an undervoltage lockout, soft start circuitry, digital current limit comparator and digital signal processing logic between the pulse width modulation comparator and the output power drivers.

The operation of the circuit is as follows: An on-chip regulator trimmed to 1% is both reference voltage for the error amplifier, and also the stabilized power source for all the internal circuitry, with the exception of the error amplifier, the current limit comparator, and the output drivers.

The sawtooth oscillator is programmed for a specific frequency and deadband by values of R_T , C_T and R_D . The resulting ramp waveform is applied to one side of the pulse width modulation comparator, which has been designed with a very small amount of hysteresis to prevent oscillations at the comparison point. The other terminal of the PWM comparator is connected to the output of an error amplifier which has been designed with a common mode range that includes both ground and the 5V reference.

Also associated with the amplifier is on-chip soft start circuitry. This soft start circuitry is controlled not only by an external RESET terminal, but also by the undervoltage lockout circuitry. If the reference voltage should be less than the 5V required for normal linear operation of the control circuitry, the RESET terminal on the soft start is held low by the undervoltage lockout, thus preventing the soft start capacitor from charging. At the same time, the power output drivers of the device are inhibited, thus making it impossible for spurious output pulses to occur during undervoltage conditions.

The digital output of the pulse width modulation comparator is ANDed with the output of the current limit comparator. This provides very fast response to overcurrent conditions. The current limit comparator has a fixed input offset of 100mV plus a slight hysteresis of 20mV to eliminate indecision at the threshold point. The PWM signal from the AND gate is followed by three levels of pulse processing logic. It first passes through a metering flip-flop whose function is to allow only one output pulse per oscillator cycle, thus eliminating oscillations and permitting pulse-by-pulse current limiting. The second element is a memory flip-flop. This flip-flop is part of the double pulse suppression logic and prevents two pulses in succession from one output driver, independent of conditions on the SHUTDOWN terminat, RESET terminal or error amplifier inputs. Also included is a toggle flip-flop which alternately gates first one driver and then the other in the presence of a PWM signal.

The final elements in the block diagram are the source/sink output drivers, with a separate collector supply voltage terminal brought out for additional flexibility.

A simplified version of the undervoltage lockout circuitry is shown in Figure 16. The circuitry consists of a 1.2V bandgap reference and a voltage comparator which are fully operational for reference voltages greater than 2.1V. When the reference voltage is greater than 2.1V, the output transistor is turned on, inhibiting both power output drivers, It also holds the RESET line controlling the soft start circuitry in the low state, thus preventing the soft start capacitor from charging, and guaranteeing zero duty cycle.

Resistive divider R₁ and R₂ is scaled so that when the reference voltage reaches 4.5V the comparator changes state, thus releasing the soft start capacitor and also enabling the power drivers. Approximately 200mV hysteris is built into the comparator so that the transition from lockout to fully on is not accompanied by indecision and jitter.



FIGURE 16. THE UNDERVOLTAGE LOCKOUT CIRCUIT CONTAINS A BANDGAP REFERENCE AND COMPARATOR WHICH BECOMES ACTIVE AT V_{REF} = 3 V_{BE} \approx 2.1 VOLTS

Monitoring the reference voltage rather than the input terminal voltage has an additional benefit. With this particular configuration, this chip can operate on +5V by connecting the $+V_{IN}$ terminal to the VREFERENCE terminal and then regulating the input voltage between 4.5 and 5.5 volts. This is a desirable feature where other supply voltages must be generated from a regulated +5V source.



FIGURE 17. THE SG1526 OSCILLATOR PROVIDES DEADBAND CONTROL BY RATIOING THE CHARGING CURRENTS TO CT

A simplified schematic of the oscillator of the 1526 is shown in Figure 17. A new approach is taken for controlling dead time in the circuit. The principle of operation is similar to the 1524 and 1525 oscillator. A timing capacitor is charged via a constant current programmed by an external resistance RT. When the capacitor has charged linearly up to a nominal 3.2V, a voltage comparator changes state, thereby turning on a discharge network which reduces the capacitor voltage very rapidly to the +1V level. The distinctive difference between the oscillator in the 1525 and that in the 1526 is that the discharge network is a current source instead of a semi-saturating Darlington. In the 1526, the discharge circuit is formed by a compound current mirror, Q3, Q4 and Q5. The output current of this current mirror is ratioed to the current charging in CT by a ratio of 30:1. This results in a charge time to discharge time ratio of approximately 29:1 independent of the value of CT. This ratio can be modified to give longer dead times by insertion of a small amount of resistance from Pin 11 to ground. With this technique, dead times up to 50% or more are easily obtainable. This oscillator configuration has the advantage that the minimum dead time for the oscillator is now fixed at approximately 3% independently of the frequency of the circuit.

The remainder of the oscillator circuit functions similarly to that of the 1525. One notable exception is the TTL compatible buffer gate between the SYNC output pin and the remainder of the circuit. This enables the port to be bi-directional, driven either by open-collector TTL or by open-drain CMOS, or to itself drive other TTL or CMOS logic.



FIGURE 18. SG1526 PULSE PROCESSING LOGIC

Figure 18 contains a brief explanation of the pulse processing logic in the 1526. The logic consists of two specialized flipflops: a metering or data latch flip-flop, and a set/reset or memory flip-flop. The metering flip-flop is basically an asynchronous data latch which is enabled by a sync pulse from the oscillator during the beginning of every oscillator cycle. Once the metering flip-flop is enabled, a PWM signal may pass asynchronously through the device. However, once the signal is terminated for any reason, no new pulse can propagate through the data latch until a new sync pulse is received at the beginning of the next oscillator cycle. This feature allows each individual pulse to be terminated either by the action of the current limit comparator or by external circuitry which pulls the SHUT-DOWN pin low. This feature allows the SHUTDOWN pin to be a convenient input port for a strobe pulse from symmetry correction circuitry.

The function of the memory flip-flop is to generate the clock pulse for the toggle flip-flop, which alternately gates the two output power drivers. It operates as follows: Let us assume that the flip-flop begins operation in the reset state. When a sync pulse is received from the oscillator, the $\overline{\mathbf{Q}}$ terminal is then driven low, generating a clock pulse for the togole flip-flop. which then changes state. If a PWM signal is generated during this oscillator cycle, then the flip-flop is reset, thus enabling it to generate another clock at the beginning of the next oscillator cycle. If no pulse width modulation signal is generated because the duty cycle has gone to zero or SHUTDOWN has been pulled low, then the memory flip-flop will not be reset, and when the next sync pulse occurs, no clock will be generated. In this way, the output flip-flop is toggled only upon generation of pulse width modulation signals, thus rendering it impossible for two successive pulses to be obtained from one output driver.



FIGURE 19. TIMING DIAGRAM OF THE PULSE PROCESSING LOGIC OVER FOUR OSCILLATOR CYCLES

The operation of the metering logic in the 1526 is shown in more detail in the timing diagram in Figure 19. The top waveform, Waveform A, shows the \overline{SYNC} pulse train from the oscillator. This pulse tran defines four timing periods, T₁ through T₄, as shown at the bottom of the timing diagram. Waveform B represents the ramp signal from the master oscillator, while Waveform C represents the analog output signal from the error
amplifier. These two waveforms are differentially compared in the pulse width modulation comparator, whose output is shown as Waveform D. It can be seen that the error amplifier output voltage is just slightly less than the peak of the ramp signal from the oscillator, thus resulting in an output pulse which is approaching nearly full duty cycle. Waveform E is a SHUT-DOWN signal from the current limit comparator. Alternately, this line could also show a digital input signal from other control logic. The waveform at line F represents the ANDed output of the PWM comparator and the SHUTDOWN signal. This acts as the date input to the metering logic flip-flop, whose output is shown as Waveform G.

The first time frame, T1, illustrates a normal period of operation. The error amplifier calls for nearly full duty cycle; the SHUTDOWN pin stays high, and this output signal then passes unaltered through the metering logic flip-flop. During the second time frame, the SHUTDOWN pin is pulled low for several times during the active pulse period. This results in a series of pulses being applied to the data input of the metering logic flip-flop, but as can be shown in Waveform G, once the first pulse is terminated no other pulse can begin until the next oscillator cycle. During time frame T3, the SHUTDOWN pin is low, thus preventing any PWM signals from reaching the metering flip-flop. In the fourth time frame, the disturbance at the output of the error amplifier causes multiple ramp crossings, which generates multiple PWM signals during one oscillator cycle. These signals reah the data input of the metering flip-flop, but as before, once the first pulse is terminated, the remainder of the pulses cannot propagate through the device to the output drivers.



FIGURE 20. BASIC CONNECTIONS FOR A PUSH-PULL GROUNDED-EMITTER CONFIGURATION

The combination of source/sink drivers with a separate collector supply voltage terminal allows the output drivers to be easily interfaced with all the circuit configurations found in most switching power supplies. Figure 20 illustrates the connections for a common emitter push-pull configuration. In this circuit, the collector supply to the output source/sink drivers is tied to the supply voltage through R₁, which limits the voltage swing of each driver output, preventing emitter-base breakdown. During the turn off cycle, an additional spike of reverse base current is generated by the speed-up capacitor C₁ or C₂.



FIGURE 21. FOR SINGLE-ENDED CONFIGURATIONS THE V_C TERMINAL IS ALTERNATELY SWITCHED TO GROUND BY THE DRIVER PULL-UP TRANSISTORS

Buck-type converters are easily interfaced to the totempole output devices. For this mode of operation it is necessary only to ground the output terminals A and B, and drive the base of the switching device with the collector supply terminal. In this configuration, the upper Darlington transistors are alternately turned on and pull Pin 14 to ground, thus providing up to 100mA of current drive capability on alternate oscillator cycles.



FIGURE 22. LOW POWER TRANSFORMERS ARE DRIVEN DIRECTLY BY THE OUTPUT TERMINALS

The totem-pole outputs can also drive a transformer directly, as illustrated in Figure 22. Since each output driver exhibits a low impedance, no center tap winding is required on the transformer primary. In this example, the transformer drive capability is used to interface the control device with the power transistors in a half bridge configuration.

If an additional current drive capability beyond that available in the 1526 is necessary, it is very easy to interface the output totem-pole drivers with the 1627 dual 500mA driver circuit. This is shown in Figure 23.



FIGURE 23. THE TOTEM-POLE OUTPUTS OF THE SG1526 CAN BE INTERFACED TO THE SG1627 POWER DRIVER WITH A HIGH-SPEED SWITCHING DIODE

The logic threshold of the 1627 is a nominal +2V, while the sink current in the low state is about 1mA. A fast silicon switching diode such as a 1N914 can be used to provide a sink current path in the low state, while blocking excessive input current to the power driver during the control circuit's high state.



FIGURE 24. USING THE SG1526 IN A FLYBACK CONVERTER WITH CURRENT LIMITING

The ability of one control port of the 1526 to drive another control port enables a good deal of flexibility from the chip. The flyback converter in Figure 24 illustrates this point. Current limiting in a flyback converter is difficult because the overcurrent signal from the current sense resistor is always out of phase with the conduction of the principle power transistor. In this circuit, the output of the current limit comparator in the 1526 is used to re-trigger the soft start circuitry. By choosing the value of the soft start capacitor so that the recovery time of the soft start circuitry is of the order of one or two cycles, it is possible to provide current limiting with a minimal number of external components. This same technique can be used in a push-pull converter where it is desirable for the pulse width modulation signal to be turned off for multiple oscillator cycles rather than for a single cycle. This allows overstressed output semiconductors a cool-off period before returning to normal operation.

CONCLUSION

Several integrated circuits designed specifically for switchmode power supply control have been described. A brief review has been made of past approaches to the integration of switching power supply control and driver circuitry. A description of a newly available family of control/driver integrated circuits, the SG1525/1527 series, has been given. Finally, a sketch of a future high performance controller circuit, the SG1526, has been drawn.

The future of integrated circuits for switching power supplies clearly involves greater complexity in the control circuitry to account for all possible modes of supply operation. The benefits for the power supply designer will be greater performance and reliability from switchers with reduced component count and greater overall manufacturing economies.

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Application Notes — SG1542, 1543, 1544, 3523

OUTPUT SUPERVISORY CIRCUITS: A NEW FAMILY OF POWER SUPPLY CONTROL DEVICES

R. A. Mammano Edited by Stan Dendinger Manager, Advanced Product Development Silicon General, Inc.

ABSTRACT

This paper describes a series of new monolithic integrated circuits designed to perform all the functions necessary to monitor and control the outputs of sophisticated power supply systems. Beginning with a simple over-voltage sensing circuit, these devices range through more versatile and accurate single-function units, to all-inclusive devices which contain sensing circuits for both over and under-voltage conditions, current sensing, SCR crowbar firing, logic outputs, and an accurate independent reference generator. A description of the operation each of individual element is given together with several applications which demonstrate their utility.

Introduction

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Recent years have seen the introduction of many sophisticated integrated circuits for use in controlling the voltage regulation function of both linear and switching power supply systems. While these circuits have provided a high degree of performance with a side benefit of considerable increases in both reliability and cost savings, they have all addressed the basic function of maintaining the output voltage constant. Most power supply systems, however, require additional circuitry for monitoring satisfactory performance and providing protection in the event of a fault condition. These requirements have led to the development of a new class of power supply element — an Output Supervisory Control Circuit.

Supervisory Control Family Members

The first integrated circuit developed specifically as a power supply monitoring device was Motorola's MC3523 available also as an SG3523 from Silicon General. This device, which is packaged as an 8-pin minidip, was designed to sense an over-voltage condition, provide an adjustable time delay, and then fire a high-current SCR crowbar for power supply shutdown. An improved and interchangable device, the SG3523A, was later introduced to provide more tightly specified performance, greater threshold accuracy, and improved temperature stability. Block diagrams of these two devices are shown in Figure 1.

SG3523 OVER-VOLTAGE SENSING CIRCUIT



Figure 1. The SG3523 and 3523A contain an independent reference generator, an input comparator designed to initiate a setable time delay, and a second comparator which activates both a crowbar firing current and a low-level indication signal.

It was soon recognized that with the addition of a few more access points to this circuit, significant increases in versatility could be achieved. This led to the development of the SG1542 device shown in Figure 2. With 14 pins in this DIL package the following additional features could be offered:

- 1. Access to the reference generator's output so that one could take advantage of it's 1% accuracy and 50 ppm T.C.
- 2. Uncommitted inputs to the sensing comparator allowing use for either under or over-voltage sensing as well as the ability to set threshold levels below 2.6 volts
- 3. The addition of a logic level output active when the sensed voltage is within tolerance, aswell as the one which indicates out-of-tolerance.
- 4. A separate supply terminal for the high-current SCR trigger allowing greater utilization of this output.





Figure 2. The use of a 14-pin package for the SG1542 provides greater access to the circuit elements and thus greatly expanded versatility.

Finally, it was decided to build an all-encompassing device which would include both over and undervoltage sensing as well as a means for current limiting, all in one integrated circuit. This resulted in the 16-pin SG1543, the main subject of this paper. The circuitry of the SG3523, 3523A, and 1542 is equivalent to the OVP portion of the SG1543 and thus need not be described separately.

Before proceeding with a discussion of the SG1543. however, there is one more member of this family worth mentioning. The SG1544 is identical to the SG1543, but uses an 18-pin DIL package to keep the voltage-sensing comparator inputs uncommitted. This adds the ability to sense voltage levels below the reference voltage to the lengthy list of features offered by the SG1543. Now, on to a more complete description.

The SG1543 Output Supervisory Circuit

To fill the need for this output monitoring and controlling function, the SG1543 output supervisory circuit shown in Figure 3 was developed. This device contains an operational amplifier, a voltage reference circuit, several comparators, and a high-current SCR trigger circuit. The functions performed by this device include over-voltage and under-voltage sensing, current limiting, and provisions for triggering an external SCR crowbar shutdown. All the functions provide open collector outputs for maximum flexibility in interfacing with either the power supply or the system load and, although the SCR trigger is directly connected only to the over-voltage sensing circuit, it may be optionally activated by any of the other outputs or by an external shutdown command. The SCR trigger circuit also includes an optional latch with external reset capability. External capacitors may be used to accurately program the sensing circuits for a minimum time duration of fault before triggering.



SG1543 BLOCK DIAGRAM

OFFSET/COMP

Figure 3. The block diagram of the SG1543 Output Supervisory Circuit includes over-voltage and undervoltage sensing as well as the capability for current limiting and SCR crowbar triggering.

The SG1543 circuit may be powered by either the output voltage to be monitored or a separate bias voltage at any level between 4.5 and 40 volts with a standby current of less that 10mA.

This device is packaged in a standard 16-pin hermetically sealed ceramic package and is available in both commercial and military temperature ranges. Before describing in greater detail the overall functions that this device can perform, it is worth discussing the individual circuits which go into its makeup.

Voltage Reference Circuit

The precision 2.50V reference circuit of the SG1543 is shown in Figure 4. This regulator is based upon the well-known band gap reference circuit which has the capability of providing very stable performance over an input voltage range from as low as 4.5V to as high as 40V. The output is nominally set at 2.50V, but in addition, is trimmed to remove all effects of production manufacturing tolerances from the output voltage. In



PRECISION 2.50 VOLT REFERENCE

Figure 4. This precision 2.50 volt band-gap reference source is internally trimmed for $\pm 1\%$ accuracy in order to eliminate the need for adjustment potentiometers.

fact, this trimming not only adjusts the output voltage to within 1% of 2.50V, but in the process, as shown in Figure 5, also trims the temperature coefficient of output voltage to better than 50 parts per million per



CHANGE IN TEMPERATURE COEFFICIENT WITH REFERENCE VOLTAGE TRIM

Figure 5. As successive links are opened in the reference voltage trimming network, the output voltage increases and the temperature coefficient becomes less positive.

degree C. The trimming is performed at wafer probe by using controlled energy sources to blow fusable metal links which short out incremental values of resistance in the voltage setting network. These resistors are binarily coded so that three values give eight bits of resolution and allow trimming to better than ± 12 millivolts. With this accuracy, in all but the most precise applications, the need for adjustment or trimming potentiometers is effectively eliminated.

The output of this reference circuit is current limited for protection and will provide up to 10 milliamps of current for use as a reference for other functions that may be required along with the SG1543. In addition to stable temperature performance, this regulator also maintains its output voltage to within 10mV for all line and load changes. Additional benefits of the band gap reference circuit include low noise performance, instant turn-on, and a high degree of long-term stability.

Comparator Section

Over and under-voltage sensing circuits are identical with only the input polarity changed between them. The under-voltage circuit is shown schematically in Figure 6. This configuration is made up of two comparators in series, each referenced to 2.50 volts, with the delay terminal at their juncture. The first comparator activates a current source upon sensing an out-of-tolerance condition and that current is used to charge an externally selected capacitor to provide a delay. The second comparator then activates the output indicating circuit. The overall time delay from input sense to output indicate, with no external capacitor, is approximately 0.5 microsecond. By adding a capacitor at the delay terminal, the fault must

VOLTAGE SENSING COMPARATORS



Figure 6. Voltage level sensing is done with a high input impedance comparator with built-in hysteresis. When switched, the input comparator allows a constant current source to trigger the output comparator.

exist for an interval defined by the time it takes the voltage on the capacitor to charge from zero to 2.5V before the output comparator can switch. The charging current for this capacitor is a constant 250 microamps which provides for a delay of approximately 10 milliseconds per microfarad of capacitance. Since the comparator can discharge in excess of 10mA, the capacitor is reset in a fraction of its charge time.

The input comparator has PNP transistor inputs which provide both high input impedance with less than one microamp bias current, and a wide input voltage range which includes ground and goes to within 2V of the positive supply voltage. Because the input PNP operates as an emitter follower, the input impedance to that comparator remains high throughout the input range. To eliminate the tendency to oscillate at threshold, a hysteresis of approximately 25mV is built into the input comparator.

The output indicating transistor, Q18, is designed to sink 10mA of current with a saturation voltage of less than 0.4 volt. Its open collector allows several outputs to be connected together to provide a single indicating signal.

SCR Trigger Section

While the under-voltage sensing circuit has only the 10mA, or low current, open-collector output, the overvoltage section contains additionally, an SCR crowbar triggering circuit good for 200mA. This stage also includes provisions for remote activation of the output as well as a reset terminal. From the schematic shown in Figure 7, it can be seen that the output voltage comparator drives a PNP transistor, Q6, with two collectors, one of which drives the low-current, open collector indicating signal similar to the under-voltage



OVER-VOLTAGE CIRCUIT

Figure 7. Either the over-voltage output comparator or the remote activation terminal will energize both the SCR trigger and the O.V. indicating transistor. Connecting pins 4 and 2 form a latch.

circuit. The other collector of Q6 drives a darlington amplifier which will provide 200mA to activate an external high current SCR crowbar device. Note that these two outputs are complements of each other; i.e. when pin 4 switches to ground, pin 1 goes positive.

Since in many cases it is desired to activate the crowbar under other than over-voltage conditions, a remote activation circuit is also included. This consists of transistors Q1 through Q5 as shown in Figure 7. The functioning of this circuit is as follows: Q3 provides a controlled current source of approximately 300 microamps to saturate transistor Q4. With Q4 saturated, transistor Q5 is held in the off condition. When the remote activation terminal, pin 2, is grounded, it diverts the current away from the input of Q4, turning it off and turning Q5 on, which activates the output circuitry in the same manner as the overvoltage comparator.

An additional function of this circuit is to provide the capability to latch the outputs on after a fault is sensed, by externally connecting the over-voltage indicating terminal, pin 4, to the remote activation terminal, pin 2. With this configuration, an over-voltage condition which turns on Q10 will pull pin 2 to ground activating the remote activation signal which, in turn, holds the circuit in the on condition until the reset terminal is externally grounded, removing the latch and turning off the output. Thus, the user has the capability to either activate the high current output only as long as a fault condition exists, or to latch it on upon the occurrence of a fault requiring external action by an operator to reset the circuit to its initial condition. Thresholds for both remote activation and reset teminals are approximately 1.2 volts.

Current Sensing Amplifier

The amplifier in the SG1543 designated for current sensing actually has much wider application. It is basically a high-gain, non-compensated operational amplifier with an open collector output; i.e., pull-up on the output must be provided externally. From the schematic shown in Figure 8, it can be seen that this circuit also has a PNP front end which gives it a wide common-mode range extending from slightly below ground to within 2 volts of the supply voltage. With a pull-up resistor of $2k\Omega$, the open loop voltage gain is greater than 72dB with a unity gain bandwidth beyond 5MHz. When used as a comparator, the response time is less than 200 nanoseconds, and if linear amplification is required, external compensation may be added for stable performance over a wide frequency range or a unique frequency response.

The input to this amplifier is balanced for zero offset voltage but a fixed offset or threshold of up to 200mV

CURRENT-SENSING AMPLIFIER



Figure 8. PNP inputs give the current limit amplifier a common-mode input voltage range of from below ground to within 2 volts of the supply voltage.

may be incorporated by adding or subtracting current at the offset/compensation pin 12. For most current sensing applications the required threshold polarity calls for a positive voltage on the inverting input. This can be accomplished with a resistor, RT, to ground as shown in Figure 9.

CURRENT SENSE COMPENSATION



Figure 9. External components can be used with the current sense amplifier to establish an input offset or threshold, define the frequency response, and buffer the output.

Reducing the impedance at pin 12 also lowers the gain of the amplifier somewhat as shown in Figure 8. This fact allows pin 12 to do double-duty as a point to apply frequency compensation as well. Due to the excess phase shift of the internal PNP transistors, this amplifier requires compensation for stable closedloop, linear applications but this can be accomplished easily with either C1 to the output or C2 to ground as shown in Figures 9 and 10.

C.L. AMPLIFIER FREQUENCY RESPONSE



Figure 10. With 80dB gain and 5 MHz bandwidth, the current sense amplifier provides a wide dynamic response, even when modified with external passive components.

Diode D1 and resistor RC are used only if it is necessary to increase the frequency response by operating the output transistor at higher current and/or isolating the load from RC and C1 when the amplifier is off.

Applications

Figure 11 shows a typical application of the SG1543 as used to monitor a single power supply output voltage for both high and low voltage operation as well as current limiting. The data accompanying Figure 11 indicates how the values for the external components are selected. This circuit is driven from an external bias supply which must provide a standby current of 10mA maximum plus the activation current for the SCR trigger. The application in Figure 11 shows a single resistor divider string, R4, R5 and R6, which sets the thresholds for both the under and over-voltage activation levels. The external capacitors CD1 and CD2 are used to provide time delays before activation

SG1543 TYPICAL APPLICATION



Figure 11. This typical application for the SG1543 provides linear foldback current limiting as well as over and under-voltage protection.

of the output circuitry. The output of the comparators can be used for many different functions; in this case, they are shown driving indicators. They can also provide signals to the system under power to give information that an out-of-tolerance condition exists. Additionally, by the external connection between pin 2 and pin 4, a latch has been provided such that an overvoltage condition will activate and hold that control signal until positive reset action at pin 3 is performed.

In firing an SCR with supply voltages above 5 volts an external resistor, RG, is used on pin 1 to provide power dissipation limiting for the SG1543. While the SG1543 will provide up to 400mA of trigger current, the power limitation of the 16-pin dual-in-line package should be held to less than one watt.

In this application, current limiting is performed by sensing the current in the positive supply line with fold-back provided by the action of R2 and R3. A fixed threshold for the amplifier is set by R1 which is connected between pin 12 and ground.

Although the SG1543 could have been driven from the output voltage to be monitored, it would lose control when that output voltage fell to approximately 3V. This would, of course, preclude the use of the current limit function where short circuit protection must be provided.

The values for the external components used in conjunction with the SG1543 application of Figure 11 are determined as follows:

Current limit input threshold, Vth $\approx \frac{1000}{R1}$

Cs is determined by the current loop dynamics

Peak current to load, Ip
$$\cong \frac{Vth}{Rsc} + \frac{Vo}{Rsc} \left(\frac{R2}{R2 + R3}\right)$$

Short circuit current, Isc = $\frac{Vth}{Rsc}$

Low output voltage limit,
Vo (Low)=
$$\frac{2.5 (R4 + R5 + R6)}{R5 + R6}$$

High output voltage limit,
Vo (High) =
$$\frac{2.5 (R4 + R5 + R6)}{R6}$$

Voltage sensing delay, td = 10,000 Cd

SCR trigger power limiting resistor, Rg> $\frac{Vin - 5}{0.2}$

Current Sensing Options

It is important to remember that all the features of the

SG1543 apply equally to either linear or switching power supplies. Figure 12, for example, shows the current sensing amplifier in the SG1543 used to provide foldback current limiting for a linear regulator utilizing the SG723. To answer the question of why one would use the SG1543 for current limiting when that capability is built into the SG723, there are two important benefits: low sensing threshold voltage (whatever is selected vs. a fixed 700mV) and much higher gain for a very sharp transition from voltage to current feedback.



LINEAR FOLDBACK CURRENT LIMITING

Figure 12. The SG1543 is equally adaptable to either linear or switching supplies. The circuit above shows a substantially improved current limit function for a linear SG723 voltage regulator.

Output current limiting for a switching supply which gets its control from an SG1524 regulating pulse width modulator is shown in Figure 13. Here, foldback is not included but an optical coupler for isolation has been added. It should be noted that all the low-current outputs of the SG1543 are equally well suited for driving optical couplers.

DC CONVERTER WITH ISOLATED CURRENT LIMITING



Figure 13. Current limiting for a switching inverter is readily accomplished, even with a requirement for input-output isolation.

This last application suggests another use for the current sense amplifier completely disassociated with current. This is shown in Figure 14 where it is used in conjunction with the very excellent characteristic of the 2.50 volt reference contained within the SG1543 to provide an isolated voltage feedback signal. The SG1543's amplifier provides the gain and the overall loop compensation network, and drives a highfrequency opto-coupler which feeds into the unitygain configured error amplifier of the SG1524. A designer should recognize that there are many possible variations on this theme, including taking the error signal from the collector of the opto-coupler, feeding it into the output of the SG1524's error amplifier such that this amplifier provides a startup signal. Then the SG1543 may be powered directly from the output eliminating the need for an isolated bias supply.



Figure 14. The current sense amplifier can also be used in conjunction with the SG1543's reference to provide a stable, isolated voltage feedback signal.

One final possible use for the current limit amplifier is to provide complete shutdown of the power supply rather than linear voltage reduction upon sensing an over-current condition. This function is shown in Figure 15 where the current limit amplifier is used as a comparator with the output terminal connected to the remote activation terminal for the SCR trigger. In this case, sensing is done in the ground line. There is no offset added to the current limit amplifier but instead a threshold is provided by the action of R1 and R2 from the 2.50V reference signal. When an over-current condition is sensed and maintained for a period of time determined by a capacitor CD on pin 12, then the output transistor will conduct, activating the SCR trigger and shutting down the power supply.

OVERCURRENT SHUTDOWN



Figure 15. The current sense amplifier may also be used as a high-gain comparator to shut down the supply upon over-current.

Sensing Multiple Output Voltages

Many power supply systems have several output voltages which need to be monitored. This is easily done with the SG1543 because of the capability for remote activation and the availability of the reference voltage for use with external circuitry. A quad comparator like the SG139 which also has open collector outputs can be used to monitor several additional output voltages. As shown in Figure 16, the SG1543 is used to provide both over and under-voltage protection on a main positive supply. The additional comparators within the SG139 can be used to monitor either positive or negative supply voltages depending upon whether one uses the 2.50V signal or ground as the reference potential. The output collectors of each comparator are tied together to the remote activation terminal such that the operation of any single comparator in either the SG1543 or the SG139 will activate the SCR trigger shutdown circuit. Note that

SENSING MULTIPLE SUPPLY VOLTAGES





grounding the remote activation terminal also provides an output on the over-voltage indicating circuit; therefore, this output on pin 4 can be used as a master power supply-condition indicator which will provide a low signal if any output voltage that is being monitored is outside its allowable tolerance.

Under-Voltage Sensing

In addition to normal low-output voltage monitoring, the under-voltage sensing circuit has considerable possibilities in monitoring the input voltage to a power supply system. For example, in Figure 17, this circuit is used to measure the input DC voltage to an SG723 regulator and keep the output completely off whenever the input is lower than the minimum required for satisfactory operation of the SG723. This same protective feature, when applied to a switch-mode regulator, is even more important since it keeps the switching transistors off until the oscillator stabilizes.



UNDER VOLTAGE SHUTDOWN

Figure 17. In addition to output monitoring, the undervoltage circuit can be used to inhibit the output if the input voltage is too low for satisfactory performance.



Figure 18. The under-voltage sensing circuit can also be used to monitor the AC input voltage and provide a power failure signal before the power supply output voltage begins to fall.

As shown in Figure 18, the under-voltage circuit can be used to monitor the AC input voltage to a power supply. An isolation transformer and rectifier are used to provide a rectified AC signal to the input of the under-voltage comparator. The signal is compared with the 2.50V reference, activating the first stage of the comparator with each transition toward zero. With proper selection of the delay capacitor, no output is provided unless some number of input pulses are missing at which time the first comparator allows the charging of the capacitor to 2.50 volts which activates the output circuit. In this way, the under-voltage circuit provides an immediate indication of failure, even for one or two cycles. This provides an early warning indication that the power supply output voltage is going to drop while taking advantage of the holdup capability provided by normal electrolytic capacitor storage within the power supply system.

Like other parts of the SG1543, the under-voltage circuit is not limited to its primary function. Figure 19 demonstrates its use as an over-temperature indicator by using the well-defined temperature coefficient of a darlington transistor's VBE as a sensor. Divider R1-R2 establishes a fixed threshold equal to the 2N2723's VBE at the desired temperature limit. Below that limit, the transistor is off and RC back-biases the input to the U.V. sensor. Many other transistors could be used; however, the small case of the 2N2723 makes good thermal coupling relatively easy.



Figure 19. Another use of the under-voltage circuit is to provide an over-temperature indication using the $-4mV/^{\circ}C$ VBE tempco of the 2N2723 as a sensor.

By providing all of these diagnostic and protective features within one integrated circuit, a new class of control device has been generated to provide overall performance monitoring and control of sophisticated power supply systems. Thus, the SG1543 further enhances the inventory of building block components available to the power supply system designer providing new options in implementing increased performance at lower cost.



PROTECT YOUR SWITCHERS WITH DIGITAL CURRENT LIMITING

A New Current Sense Latch IC Provides Pulse-by-Pulse Current Control

By: Bob Mammano SILICON GENERAL, INC. 11651 Monarch Street Garden Grove, CA 92641

INTRODUCTION

Another new class of integrated circuits, designed specifically to ease the plight of the switch-mode power supply designer, has just been established with the introduction of the SG1549 Current Sense Latch IC. Although there have been many IC products developed over the past few years to provide simple methods of voltage control for switching supplies, the SG1549 is the first to specifically address and take a fresh approach to the problem of current control. Almost all existing PWM chips have included some type of circuit for current limiting, but these have all used the same techniques as linear regulators; that is, a current sense amplifier generates an error signal linearly proportional to load current which, after reaching an established threshold, takes command away from a voltage control amplifier. Thus, upon overload, the power supply switches from a voltage feedback loop to a separate current feedback path. Each loop must be stabilized separately and, because of the output filter, stable performance along with a reaction fast enough to protect the high-speed switching transistors is difficult to achieve. What is needed for optimum protection is a circuit which operates at the switching frequency and immediately turns off the main current-carrying switching transistors upon current overload. Turnoff must be rapid, without allowing the transistors any appreciable time in their linear operating region, and with no oscillation or multiple-pulsing.

A DIGITAL CURRENT LIMITER

The optimum approach to switch-mode current limiting is to treat each on-cycle as a separate problem. That is, pulse-by-pulse current limiting. This is implemented by a device monitoring current build-up each time the power supply's switching transistor conducts and, upon sensing an overcurrent condition, immediately turning the transistor off and holding it off for the duration of that normally on period. Such a circuit must have a latch, as once turn-off is achieved, the removal of the overcurrent signal would otherwise allow the transistor to return to conduction. Including a latch means a provision for reset must also be provided.

All of this and more is offered by the SG1549 Current Sense Latch IC. From the block diagram of this device, shown in Figure 1, it can be seen that the circuit includes a comparator with positive feedback, a means for establishing an input threshold of 100mV, a reset circuit, complementary outputs, and a high voltage level-shifting circuit. This device is designed to be completely compatible with many commonly-used Regulating PWM control IC's such as the SG1524, MC3420, and the TL494. Requiring only 2mA of supply current, the entire circuit can be operated from the reference voltage available with these chips, with reset accomplished by their clock output signals.



Figure 1. The SG1549 Current Sense Latch IC contains provision for sensing a current threshold over a wide voltage range. Complementary outputs and a latch with reset are also a part of this new protection circuit. Although obviously designed for use with switch-mode power supplies, the SG1549 has broader application as a general purpose, lowthreshold latch. A clock signal is not the only way to provide reset; that function may also be accomplished by any operation which will momentarily pull the reset pin high.

CIRCUIT OPERATION

For a detailed understanding of the operation of this device, refer to the schematic of Figure 2. With a +5 volt supply, a threshold reference is established by a current through R3. This current is mirrored by Q7 to provide a constant 200μ A through R11, thereby holding one input to the comparator at 100mV above ground. That same current is mirrored through Q4 to the floating threshold circuit of Q1-Q3, D1 and R1. This portion of the circuit will convert a differential voltage between pins 1 and 2 into an identical voltage across R2. It will do this accurately while allowing the absolute voltage on pins 1 and 2 to range from 2 to 40 volts with respect to ground.



Transistor Q17 also provides two outputs: a high-going signal on pin 6 which can source 2mA and an open-collector saturating transistor on pin 5 which can sink more than 10mA. With complementary outputs, a variety of shutdown options are offered. Typical delay times for the SG1549 are 180 nSec from the LO CM input and 300 nSec from HI CM to the outputs.

HIGH LINE SENSING

A very straightforward application of the SG1549 is its use for current sensing in the input line of a simple buck converter as shown in Figure 3. This switching regulator is shown implemented with the SG1524 PWM control IC and it can be seen that interfacing between these two chips couldn't be easier. The value for R_{SC} is determined by dividing the 100mV input threshold by the peak current desired. High frequency noise, or switching transients can usually be eliminated by a small capacitor between pins 3 and 4.



Figure 3. Using the SG1549 to sense input current to a simple buck converter and interface directly to a PWM control IC such as the SG1524.

Figure 2. The heart of the SG1549 is a high-speed comparator together with an input threshold level-shifting circuit.

Since the other input to the comparator is tied to pin 3, it can be seen that the comparator will switch when the voltage on pin 3 rises to 100mV, regardless of whether that voltage is applied to pin 3 directly or differentially between pins 1 and 2.

Once the comparator switches, positive feedback provided by Q17 and R14 will hold it latched until a reset signal, effected by raising pin 7 above 2 volts, momentarily increases the threshold, returning the circuit to its initial state. The current shutdown command can be coupled into the SG1524 by either connecting the HI-OUT, pin 6 to the SG1524's shutdown pin or, as shown here, using the LO-OUT pin to pull the compensation terminal low. In either case, activation of the current sense latch will tend to discharge the compensation capacitor, C_C which may cause slow recovery from pulse limiting. Keeping the value of C_C as small as possible within the requirements of voltage loop stability will minimize this effect; however, slow turn-on from current limit is often desirable and can be optimized by using the LO-OUT signal to discharge a soft-start network instead of coupling directly into the SG1524.

Where minimizing turn-off delay is important, the command from the SG1549 may be taken directly to the output stage of a switching regulator. A practical means of accomplishing this is shown in Figure 4 where the power switch consists of an SM625 15-amp hybrid circuit containing both the power switch and the commutating diode. This switch is driven by using the SG1524 to switch a constant current source formed by the 2N2222 transistor connected with its base to the 5 volt V_{REF} line through a 1k resistor. By connecting the LO-OUT terminal of the SG1549 to the base of the 2N2222, drive current to the output stage can be interrupted without the delays inherent in the SG1524.



Figure 4. A fully-protected, high performance, single-ended switching regulator is easily implemented with two IC's and a hybrid switch. Current control is direct to the power switch for fastest response.

LOW LINE SENSING

In many types of feed-forward or push-pull converters, current protection may be provided by sensing through an emitter resistor referenced to ground on the primary side of an output transformer. The fast-reacting SG1549 can easily sense secondary overload as reflected back to the primary and, additionally, provide protection from unbalanced transformer saturation. When using the LO CM inputs as shown in Figure 5, the HI CM inputs should be shorted together. While the LO CM inputs may be connected directly across a sense resistor, R_{SC} , a small low-pass filter, R1-C1, is often helpful in removing high frequency transients. It must be remembered that the 500 ohm input inpedance to the LO CM terminals will cause the use of R1 to increase the effective threshold; however, this also offers the possibility of an easily adjustable threshold by incorporating a potentiometer at the input to the SG1549.



Figure 5. When sensing emitter current, a small input filter is often useful in eliminating transients to the SG1549.

Coupling the current shutdown command back to the control circuit may be done in several ways as described above, but, again, the fastest approach is to go directly to the output switches. Figure 6 shows such an approach by adding two external shutdown transistors, Q1 and Q4. In this circuit, these transistors perform double-duty by the use of C2, R3 and R4 to generate a positive pulse when the main power switches, Q2 and Q3, are commanded off by the SG1524. Turn-off signals from either the PWM or the SG1549 are summed together through diodes D2 and D3 to Q1 and Q4.



Figure 6. Fastest turn-off response is achieved by taking the output of the SG1549 direct to the power switches through turn-off transistors, Q1 and Q4.

One problem often experienced with using pulse-by-pulse current limiting with a push-pull inverter is half-cycling caused by limiting on one period without full recovery in time for the next. A maximum duty-cycle clamp, formed by R1, R2 and D1 in Figure 6, minimizes this effect by holding the error amplifier out of saturation when the feedback voltage begins to fall. Another convenient way to tie the output of the SG1549 into the PWM control in higher power applications is by using the SG1627 Dual Interface Driver and connecting the LO-OUT terminal directly to the two non-inverting inputs of the SG1627 as shown in Figure 7. The N.I. inputs of the SG1627 will force the outputs off regardless of the commands on the inverting inputs, and do so within 100 nanoseconds.



Figure 7. An SG1627 provides both power gain for the voltage control signal as well as a high-speed interface for the SG1549's current protection.

And finally, keep in mind that the LO-OUT terminal of the SG1549 will easily drive most highspeed optical couplers should some type of isolation between current sense and shutdown control be required.

Applications Notes — SG1627/SG1629

POWER SWITCH DRIVERS: NEW IC INTERFACE BUILDING BLOCKS FOR SWITCHED-MODE CONVERTERS

> Bob Mammano Director, Advanced Development SILICON GENERAL, INC. Garden Grove, California

Abstract

This paper describes the characteristics and performance of two new integrated circuit products designed to interface between the control circuitry for switch mode converters and their high power output stages. The first device develops the high level turn-on and turn-off commands directly from the outputs of a low power P.W.M. control circuit while the second is designed as a floating switch to control a high current switching transistor directly from the secondary of a drive transformer.

INTRODUCTION

Recent years have seen significant developments by component suppliers which have resulted in the ready availability of many high performance power transistors and sophisticated control integrated circuits for switching power supply design. There existed a gap, however, between the control circuit and the power switching transistors where a considerable amount of circuitry was required to adequately condition and amplify the control signal in such a way as to provide the proper turn-on and turn-off commands to the power switch. This gap has now been filled with two new integrated power switch drivers, the SG1627 Dual Output Driver and the SG1629 High Current Floating Switch Driver.

SG1627 DUAL OUTPUT DRIVER

The SG1627 was designed to directly interface between low level control circuitry and the high current handling devices required in switching power supplies. As shown in Figure 1, this is a dual circuit containing both channels that are required for a push-pull system. It accepts the P.W.M. signals from a control circuit such as the SG1524 and provides the conditioning necessary to develop both turn-on and turn-off commands at currents up to 500mA. Its outputs can be used to directly control an external power transistor or to interface

with driver transformers for additional power amplification. Another feature of this circuit is the optional ability to provide a constant drive current.



FIGURE 1 – THE SG1627 DUAL OUTPUT DRIVER IS PACKAGED IN A 16-PIN CERDIP D.I.L. PACKAGE.

CIRCUIT DESCRIPTION

Figure 2 shows the schematic for one-half of an SG1627 dual output driver. It must be remembered that there are two identical circuits in each 16 pin dual-in-line package. The inputs to this circuit are switch closures to ground with both inverting and non-inverting logic configurations available. The input threshold level of both logic inputs is 2V, and the logic is powered by an internal voltage regulator so that input characteristics are unaffected by power supply voltage which can range from 5 to 30 volts.



The output sections of the SG1627 contain both source and sink transistors, each capable of 500mA, 30V operation. In addition, the source transistor has the capability of constant current operation by using an external sense resistor between the source emitter and the current sense terminals. The source transistor is in a darlington configuration which can easily deliver currents to 500mA under all operating conditions but at the cost, however, of a higher saturation voltage. The sink transistor is designed for very low saturation voltage: approximately 0.5 volts at 500mA. It does, however, need greater base drive to meet those high currents. This can be provided either by raising the supply voltage above 5V, or by adding a boost drive current through D6. The saturation characteristics of both source and sink are shown in Figures 3 and 4.





THE TOTEM-POLE OUTPUT CONFIGURATION

One of the simplest uses of the SG1627 is illustrated in Figure 5 where the output is configured to provide a constant 300mA turn-on command to an external switching transistor together with a high peak turn-off current. Note that the logic on the SG1627 is being driven directly from the 5V reference terminal of an SG1524 P.W.M. control I.C. The logic inputs are directly connected to the open collector output transistors of the SG1524 with no additional interfacing components. The output current of the SG1627 comes from the input voltage, which in this case is approximately 10V, but the use of R2 provides a constant source drive regardless of input voltage variations.



FIGURE 5 – IN A 300mA OUTPUT "TOTEM POLE" CONFIGURATION, THE SG1627 INTERFACES DIRECTLY WITH THE SG1524 REGULATING P.W.M. CONTROL CIRCUIT.

Resistor R3 is used to build up a voltage drop across capacitor C1. At turn-off, the energy stored in C1 provides both a negative voltage to the base of the power switching transistor and the boost drive current necessary to saturate the sink transistor during peak discharge currents of approximately 500mA. With this magnitude of reverse base current (Ib2), transistor turn-off is greatly accelerated.

There are two considerations to remember in this configuration. The first is that the maximum output voltage will be less than the value of Vcc because the source transistor operates as an emitter follower. With Vcc = 5 volts in this case, the peak output voltage is approximately 3 volts. The other consideration is power dissipation in the source transistor when using it in the constant current mode since it will absorb any excess voltage after current limiting.

The performance of this application is illustrated in Figure 6 which shows the base current into the external switching transistor. One can see both the constant drive current of about 300mA and the rapid, peak negative turn-off current in excess of 500mA. Note that the delays through the SG1627 are less than 50 nanoseconds making a very fast responding circuit.



200 ns/division FIGURE 6 – OUTPUT CURRENT TRANSFER FUNCTION

An alternate configuration shown in Figure 7 pictures the SG1627 with a higher value of supply voltage. This offers at least two advantages; first of all, it allows the output voltage swing to rise considerably higher remembering that the source as an emitter follower can rise to approximately 2V below the input supply voltage. The other benefit is in providing greater drive current for the sink transistor allowing 500mA saturation without the need for additional boost current. Because of the large supply voltage across the source transistor, power dissipation can be a problem. This probably means a reduced source current if current limiting is required, although the use of resistor R1 to absorb some of the voltage drop will reduce the power dissipation within the SG1627.



FIGURE 7 – HIGHER INPUT VOLTAGES CAN BE USED TO PROVIDE DRIVE FOR HIGHER SINK-TRANSISTOR CURRENTS

Recognizing the potential for package power limitations, it is important to consider the use of the SG1627 with various types of power boosting circuitry. Maximum flexibility for the use of external current boosting transistors is maintained by the uncommitted availability of both the collector and emitter terminals of both the source and sink transistors. Figure 8, for example, shows the use of an external PNP transistor to boost the source current to 1 amp. The use of the PNP transistor in this configuration still allows current sensing to be used for constant current operation. If constant current operation is not required, an NPN emitter follower booster could also be used. The use of a single boost transistor as shown in Figure 8 makes a powerful drive circuit as one can now drive one amp of turnon current into a switching power transistor and still have 500mA of turn-off current through the sink transistor.



FIGURE 8 – INCREASED SOURCE CURRENT WITH THE USE OF AN EXTERNAL BOOST TRANSISTOR

DUAL PHASE OUTPUTS

The SG1627 does not need to be committed to totem pole operation. The source and sink transistors can be separated and used independently for dual opposite-phased outputs. Figure 9 shows the operation with both source and sink transistor emitters grounded and each used as a common emitter amplifier driving an external load resistor. Figure 9 also shows the use of an external resistor R1 to provide additional drive current boost to the sink transistor. This will allow the sink transistor to provide full 500mA operation with only a 5 volt supply. The response characteristics of this type of configuration are shown in Figure 10, which pictures the response of both source and sink with 24 ohm load resistors to inputs at both the inverting and the non-inverting logic inputs. Note again the minimum delay of both outputs; less than 100 nanoseconds from input to output on both source and sink.



FIGURE 9 – SEPARATE DUAL-PHASE OUTPUTS WITH ADDITIONAL DRIVE CURRENT FOR 500mA SINK TRANSISTOR OPERATION



FIGURE 10 - SOURCE AND SINK RESPONSE CHARACTERISTICS

This use of the source and sink as separate outputs provides significant benefit for driving a transformer, as illustrated in Figure 11. In this example, the primary winding of the transformer is driven by the source transistor with its emitter grounded. Constant current operation is shown with the inclusion of the sense resistor, R2, but voltage switching could as easily be accomplished by merely shorting together the sense terminals. To provide greater efficiency in the magnetic design, a reset winding is added and shown being driven by the sink transistor. This ensures that the magnetic flux is reset to zero between each pulse. Of course, the sink transistor opens up every time the source transistor drives the primary winding.



An additional illustration of the versatility of the SG1627 is shown in Figure 12, where the non-inverting logic input is used to provide a positive guarantee that both sides of a push-pull inverter cannot be on at the same time. This circuit is shown using the inverting input as the primary drive path, which will force the source transistor to be on when the control circuit transistor is conducting. The non-inverting input is then diodecoupled to the opposite side of the inverter and senses saturation of the external power switch. If the collector of the opposite transistor is low, holding the non-inverting input low, then regardless of what happens at the inverting input terminal. the output source on that side cannot be turned on. The sink will remain on, holding the output low until a rising collector voltage on the opposite side removes the non-inverting input at which time the command signal will then come through the SG1627 and turn on the correct side. This circuit is particularly useful as a protection against cross-conduction of the output transistors during transient conditions at power-on or overload.



FIGURE 12 – SIMULTANEOUS CONDUCTION OF THE TWO OUTPUT TRANSISTORS IS PREVENTED BY GATING WITH THE NON-INVERTING INPUTS.

The above examples have been chosen to illustrate the versatility and performance of this new device designed to interface between a low level pulse width modulating control circuit and the high power switching transistors used in all modern-day switching power supply designs.

THE SG1629 HIGH CURRENT FLOATING SWITCH DRIVER

A second interface circuit to be discussed in this paper is the SG1629 illustrated in Figure 13. This device has been designed to provide an interface between a drive transformer secondary winding and a high power switching transistor, and again provide the proper signal conditioning to adequately deliver both turn-on and turn-off current into the base of that switching transistor. More importantly, its design is such that it requires no external power connection but develops all the power for

both turn-on and turn-off from the drive transformer and an external storage capacitor. With this capability, the SG1629 can be used in floating operation for bridge inverters at voltages in excess of 300V with respect to ground. This circuit also contains the capability for constant current drive operation with a similar type of current sensing circuit and an external current sensing resistor.



CIRCUIT OPERATION

The SG1629 functions with a center-tapped drive transformer secondary winding such that when a turn-on command is present and current is flowing in the upper half of the secondary winding through the source transistor and into the base of the power switching transistor, a current is also flowing in the lower portion of the transformer secondary through the high current rectifier to charge the external capacitor C_S to a negative voltage. When the drive command terminates, this negative voltage is used to turn on the sink transistor which then pulls a negative Ib2 current from the base of the switching power transistor down to the negative voltage on the capacitor providing again a high peak turn-off current to speed the response and minimize the power losses in the switching transistor. For maximum versatility, this circuit also contains several gating options.

In Figure 14, the schematic of the SG1629 shows two power darlington transistor structures, each capable of handling an excess of 2 amps of current: $\Omega 3/\Omega 4$ as the source, and $\Omega 6/\Omega 7$ forming the sink. Transistor $\Omega 5$ provides current sensing with feedback to provide constant current operation. The source transistor is turned on by conduction of drive current through resistor R2. The drive current for the source transistor is gated on and off through the action of $\Omega 1$ which senses the input voltage and provides a turn-off of the source transistor between each drive current pulse.



FIGURE 14 – THE SCHEMATIC OF THE SG1629. TRANSISTORS Q4 AND Q7 ARE DESIGNED FOR TWO-AMP OPERATION.

The darlington sink transistor has its input brought out as a separate sink drive terminal which gives the user several driving options. In addition, the sink driving current can be gated by the use of Q2, which has its own input terminal. The diodes D1 and D2 are high current rectifiers which provide the charging current for the external capacitor attached to the sink emitter terminal. The action of transistor Q1 to gate the source transistor insures that there is negligible discharge current (less than 10mA) from the external capacitor during the off periods of the circuit. This allows the capacitor to be charged with very narrow drive pulses separated by relatively long off periods.

The SG1629 is packaged in both a multi-pin TO-66 power package and an 8-pin minidip. Having no sensitive, low-current circuitry, this device can be operated with a maximum junction temperature of 175° C which, coupled with a low Θ 5C thermal resistance of 5° C/W, gives the TO-66 package a 3 Watt capability in free air and 10 Watts or more with some heat sinking. Because of the versatility of this device, it was felt that there may be applications for lower power requirements and thus the SG1629 will also be available in an 8-pin ceramic minidip package which, of course, has a power dissipation of only 800mW. With one pin less in the 8-pin minidip package, the sink gating function is sacrificed.

SG1629 APPLICATIONS

The use of the SG1629 can best be demonstrated in an application as shown in Figure 15 where two SG1629's are used to provide the drive signals for the power transistors in a 5 amp one-half bridge switching supply. The drive transformer is shown with 10 volt drive signals on the primary winding which, with a 2:1 transformer turns ratio, provides a 5V peak signal on each half of the secondary. When the drive command is present on one secondary, it is translated into a constant current through the source transistor by the use of the sense resistor, Rcs, which, in this case, provides a constant 700mA into the base of the external NPN transistor. At the same time, the 20 microfarad external capacitor is being charged with a current through the rectifier in the SG1629 and the lower half of the secondary winding. While this is occurring, the opposite phase signal is being applied to the lower SG1629 circuit which serves to further enhance the charge on its external capacitor while maintaining the power switch in the off state.



HALF-BRIDGE CONVERTER

When the drive command terminates, the voltage at both ends of the secondary winding goes to zero. Since there is approximately -4V at the emitter of the sink transistor while its base is being driven through the external drive resistor, RB, to zero volts, the sink transistor then immediately turns on and pulls a high current Ib2 pulse out of the external transistor and through the capacitor. This current, of course, only flows as long as it is available from the stored charge within the base of the external transistor as the source has been gated off. After that charge is depleted, the sink transistor remains on insuring a negative reverse voltage at the base of the switch transistor.

The performance of the SG1629 can be illustrated by the waveform photographs in Figures 16 through 18. In Figure 16, the command signal from one channel of the control circuitry and the waveform of the drive transformer primary voltage are shown. The voltage on the secondary winding, referenced to the centertap and the power transistor emitter, is pictured in Figure 17. Also shown in this photograph is the input voltage at the base of the external NPN transistor. Note that at the very first portion of this waveform, when the opposite side is on, there is an additional negative charge supplied to the capacitor so that we have a maximum reverse base-to-emitter voltage of close to -4V. During the off time, the action of the sink transistor maintains a negative voltage bias of approximately -3V on the base of the power transistor. When the drive command is given to turn on, the base voltage goes positive to the 0.7 or so volts necessary to turn it on and at turn-off, goes negative again. The important action is shown in Figure 18 which pictures the actual base current of the power transistor with a scale of one amp per division. Both the constant turn-on Ib1 of about % amp and the peak Ib2 of close to -2 amps can be seen along with the collector voltage waveform with a 5 amp resistive load. Remembering that the time base of all these waveform photographs is 5 microseconds per division, one can see approximately one microsecond delay between the turn-off signal at the base and the actual turn-off of the collector of the output transistor. Although this turn-off response is primarily a function of the transistor design, it is safe to say that any power switching transistor should perform faster with this form of base drive.









FIGURE 17 – THE BASE VOLTAGE DELIVERED TO THE EXTERNAL POWER SWITCHING TRANSISTOR BY THE SG1629





Note that one can also see in the collector waveform a soft knee at turn-on where the power transistor is not saturated instantaneously. This is partially because of the turn-on characteristics of the transistor and partially because of the finite rise time of base current through the driving circuitry. This rise time is primarily a function of the leakage inductance of the drive transformer which opposes a sudden change in current from zero to maximum value. It is an exercise in transformer design to configure the transformer to minimize to the greatest extent possible the leakage inductance. This can be done with a minimum number of turns and a maximum coupling between turns. In the illustration, a ferrite pot core of approximately 34" in diameter was used to configure the drive transformer. More will be said about turn-on rise time later, but first let's discuss one additional characteristic of concern in the turn-off circuitry: The operation with very narrow pulse command.

Since the charge on the external capacitor is developed during the turn-on command, narrow pulse widths accomplish the transfer of a minimum amount of energy. As the drive command pulse widths get narrower, there is a point where the voltage on the external capacitor begins to fall off. With the circuit components as shown earlier, this loss of Ib2 occurs at approximately 2 microsecond pulse widths. Figure 19 shows the base current and collector voltage waveforms at narrow pulse widths where the Ib2 has diminished from 2 amps down to approximately % of an amp. Further reductions in pulse width bring the Ib2 current ultimately to zero. This characteristic is, of course, a function of the time constants in the total circuit and some compromise or optimization can be achieved by appropriate selection of capacitor values and secondary drive voltages.

The above circuit incorporated constant current drive which is an advantage if the load current happens to be relatively constant but in many applications this is not the case. The SG1629



Time Base: $5 \,\mu$ Sec/DivisionUpper Trace:Transistor Base CurrentLower Trace:Collector Voltage with $R_1 = 2 \,\Omega$



may also be used to provide a base drive proportional to load demand by adding an anti-saturation clamp diode as shown in Figure 20. With the current sense terminals shorted, there are two V_{BE} voltage drops between the clamp and source emitter terminals. Therefore, the clamp diode D1 will hold the collector on voltage to approximately one diode drop above the base. This will keep the switching transistor right at the threshold of saturation, regardless of load current variations.



FIGURE 20 --- USE OF THE SG1629 IN A LOAD-DEPENDENT DRIVE CONFIGURATION

IMPROVING TURN-ON RESPONSE

In applications where maximizing base current rise time is important and secondary transformer inductance is a significant consideration, the use of the gating functions in the SG1629 can provide significant benefits. Figure 21 shows the addition of an external transistor Q1 to drive the sink transistor's gate circuit. To explain the operation of this circuit, note that the sink transistor's base drive is now being generated with RB connected to the common or center tap of the drive transformer secondary instead of the negative input terminal. This is essentially zero volts and since the emitter of the sink transistor



FIGURE 21 ~ IMPROVING BASE CURRENT TURN-ON RISE TIME

is attached to the capacitor which has a negative voltage on it, the sink transistor would normally be on continuously. Transistor Q1 is selected as a relatively slow non-gold-doped transistor which has a finite storage time. Its action is to turn the sink transistor off during the drive command signals, but to delay that off signal for some increment in time. Note that before the commencement of a drive command, the sink transistor is on by the action of RB. Transistor Q1 is also saturated by its base resistor being connected to the end of the transformer which is also at zero volts prior to the command signal.

When the drive command is initiated, current begins to build up in the secondary circuit and the first flow of current is through the source transistor, through the current limiting resistor, down through the sink transistor which is still conducting, and back to the negative terminal on the transformer secondary. The switching transistor is still back-biased while this occurs. Because the input to transistor Q1 is now at a negative voltage, it turns off, but since it has a finite storage time, that time is used to delay the rise of the input to the sink gate. Additional delay can be added with a small capacitor at the sink gate input terminal. When the input to the sink gate goes high, its output goes low, forcing the sink transistor to turn off. Since the source current is already flowing, turn-off of the sink diverts that current to the base of the output transistor producing an Ib1 rise time of less than 100 nanoseconds.

When the action is reversed at turn-off, there is negligible increase in delay between the turn-off signal and the actual turnon of the sink transistor. This is because Q1 is the only device with a long storage time and it is turning on so storage is not a factor. Another method of speeding up the rise time of current into the base is the use of some reactive components to differentiate the drive current signal. A simple approach is a capacitor by-pass around the current sense resistor, Rcs, providing an initial boost in turn-on current.

GETTING IT ALL TOGETHER

The overall simplifications which Silicon General has offered to the design of switch mode power converters can best be illustrated by Figure 22 which shows the total command signal flow from the feedback error information to the output of a high current half-bridge regulating inverter. The SG1524 was designed to provide all of a switching regulator's P.W.M. control signals with the only external components required being the divider resistors to interface with the error amplifier, the overall loop compensation network, and the resistor and capacitor to set the operating frequency. The SG1524 drives the SG1627 directly which, in turn, provides the signal conditioning to develop the drive and reset commands to an interstage drive transformer. The secondary windings of that drive transformer are directly coupled into a pair of SG1629 floating drivers which are then used to command the external 5 amp switching transistors which form the high power output stage of the power supply.

These circuits have all been designed to offer a maximum degree of flexibility while incorporating what would otherwise be a substantial amount of discrete circuitry.

Thus, all these new IC's greatly ease the design and manufacturing problems typically inherent in switching power supplies and, at the same time, provide greater repeatability and reliability at significantly reduced costs.



FIGURE 22 – THREE IC TYPES FORM A MAJOR PORTION OF THE CONTROL ELECTRONICS FOR A SWITCH-MODE HALF-BRIDGE CONVERTER.

Application Notes—SG3635

Use motor-drive IC to solve tricky design problems

An IC driver's logic-control features and high output capability suggest elegant ways to handle a variety of difficult-to-drive loads.

Jim Williams, Consultant, and Stan Dendinger, Silicon General Corp

You can use the SG3635 driver IC in a wide range of applications, ranging from a switched-mode motor-speed controller to a data-communications line driver. The device's input configuration simplifies interfacing between low-level circuitry (eg, a μ P or logic blocks) and the high-power load. And its output stage (see **box**, "Anatomy of a driver IC"), capable of driving 40V, 2A loads with peaks as high as 5A (including reactive loads), provides sinking and sourcing capability as well as commutation diodes.







Fig 1 shows one application of the device in a self-clocking switched-mode speed-control loop. The mechanically coupled tachometer detects the motor's speed; its output, scaled and filtered by the RC network, drives the 311 comparator, which compares the output with the speed-setting input and biases the SG3635 to complete the loop.

When the motor slows down, the SG3635's output switches on (**Fig 2**, trace A), forcing current into the motor (trace B) until the comparator's inputs balance. Under these conditions, the circuit oscillates in a controlled manner around the setpoint. The 10-k Ω , 0.1- μ F pair provides positive ac feedback to ensure clean transitions.

Control motor speed with minimum parts count

The 3.3-k Ω resistor from the comparator's offset pin to the 15V supply provides enough offset to prevent motor turn-on with a 0V speed setting. In this application the driver only sources current: The sink transistor is never enabled. You could turn the sink device on to dynamically brake the motor, but the motor's back EMF would cause considerable power dissipation. The back EMF appears after the initial inductive spike (clamped by the internal commutation diode), which appears when the IC's output switches LOW.

What about motor-reversing capability? Fig 3's single-supply circuit uses two SG3635s in a bridge configuration. The flip flop generates the necessary complementary instructions to the ICs' Enable inputs. In this example, the SG3635s' Pulse inputs are grounded; you could instead pulse-width-modulate



Anatomy of a driver IC

The nearby figure (a) shows the SG3635 driver IC's internal organization. The main consideration in the IC's design is to make logic-level/power-load interfacing as straightforward as possible. The logic-compatible Enable and Pulse inputs operate according to the truth table shown: Accepting drive from 74C Series circuits operating at 10V or more, they're compatible with all TTL forms except 54L. You can allow the inputs to float to the HIGH state, but you must force them to ground to produce a ZERO.

Negative supply voltages are permissible at the ground pin, but you must restrict the chip's total rail-to-rail voltage to 40V. The internal regulator stabilizes the IC against supply variations; the level-shift and interlock features provide proper drive levels and prevent simultaneous output-device conduction. The output sinks or sources 2A continuously (5A pk) with ±40V output swing; the commutating diodes handle 5A pk. Finally, the thermal-shutdown circuit disables the upper output device if chip temperature exceeds 160°C.

Why the interlock circuitry? It's important to prevent simultaneous conduction of a source/sink pair's devices (b). This condition usually

arises during switching, when the respective devices are interchanging OFF and ON states. During this interval, substantial



Providing logic-to-power-drive translation, the SG3635 (a) contains both lowand high-level circuitry. The interlock circuit-an important feature-allows only one power device to conduct at a time, thus avoiding transitional power-supply short circuits (b). An IC without the interlock can produce large current pulses (c) during switching. A test circuit (d) verifies the IC's interlock circuitry; (e) shows no common current flows in the output devices during switching.



IC's high-current output yields fast motor reversal



a mechanical scanner in either direction between a set of programmed limits. The driver IC's ground pin is biased at -15V, allowing the device's output to swing symmetrically about 0V.

The 5-k Ω pickoff potentiometer detects the scanner's position, then trips a pair of limit comparators; these comparators in turn bias the RS flip flop that controls the SG3635. To provide logic-level compatibility with the driver, the flip flop uses 0 and -15 supplies instead of the usual +15 and 0V configuration. This circuit forces the scanner to run continuously between the limits defined by the V_{LIMIT} inputs. You could control speed by summing pulse-width-modulated signals at the comparator inputs or by gating the SG3635's inputs.

Tackle nonmotor drive problems, too

You can also use the driver IC in applications other than motor control. Consider, for example, the problem of driving long cables at high data rates---a difficult task because of the rapid buildup of parasitic capacitance



data-communications cable having 0.1-µF capacitance. The driver transmits serial 100-kHz data to the receiving comparator.

Drive long cables with total data recovery

with increasing cable length. In a remote datamonitoring application, for instance, a 10,000-ft cable displays 0.1- μ F capacitance—a brutal load at high speed, making receiver-end data recovery difficult.

Fig 6's circuit provides the drive for this difficult load: The V/F converter presents a serial, 100-kHz square-wave data format to the SG3635. The driver's output (Fig 7, trace A)—somewhat distorted because of the load—drives the line. Trace B shows the IC's output current: The 5A peaks at the waveform's edges clearly reflect the heavy capacitance.

The square wave's distortion is relatively minor, allowing easy data recovery. The 311 comparator uses a simple RC network to set an adaptive amplitude threshold against which to compare the line output. Because the threshold is derived from the signal, power-supply shifts produce no undesirable effects.

In another nonmotor-related application, you can use the SG3635 in conjunction with a pH probe as a 3-mode controller (Fig 8). The FET op amp unloads the probe and routes the signal—via an RC filter—to the two comparators. The comparators, configured as a doubleended limit detector, bias the SG3635; the IC then drives valves that feed either acidic or basic solutions to the chemical vessel.

If pH is correct, both comparator's outputs remain HIGH and neither valve energizes: The appropriate LOW-switching comparator redresses eventual pH imbalance by turning the necessary valve on.



In a final example of the driver IC's versatility, consider its use as a power-transistor driver. Driving these devices at high speed requires active turn-off techniques to sweep charges from the base-emitter junction. Moreover, many high-voltage power transistors need negative base bias to guarantee breakdown ratings.

Assume, for example, the use of unipolar base drive







them to control motor speed.

Fig 3's circuit is a good test of the IC's peak current capabilities, because motors present a very difficult load during instantaneous reversal. Fig 4, trace A shows the motor current; traces B and C represent the SG3635's voltage outputs. The motor draws 200 mA in normal mode but requires more than 3A during a reversal because of the armature's stored energy.

Servoed motor makes position clear

In addition to controlling speed and direction, you can use the SG3635 in a simple circuit to control a shaft's position (**Fig 5**). In this configuration, the motor drives

Fig 4—Large peak-reversal current in Fig 3's motor is evident in trace A. Traces B and C show the drivers' output reversal; the outputs handle the 3A motor peaks cleanly.

supply current flows through both devices, effectively shorting the supplies. A common approach to alleviating the problem is to make the stage switch quickly, minimizing concurrent ON time.

The widely used 555 timer furnishes this simple solution. How-



ever, it still generates considerable supply glitches (c). Trace B shows the large supply-current spike the IC's output pair produces when switching (trace A). Such a current spike, in conjunction with a supply bus's impedance, can result in unacceptable system noise or device destruction.

The SG3635's interlock circuitry ensures complete turn-off of one output device before the other begins to turn on. This provision eliminatës supply shorts during switching, even when controlling high power. To verify this action, use the **figure**'s test circuit (d). Part (e), trace A shows one phase (Q) of the 74C74's output; trace B depicts the driver's output.

When Q switches LOW, the SG3635 unclamps its sink transistor, then allows the source device to turn on. The reverse holds true when Q switches HIGH. These intentional turn-on delays account for the 200-nsec output-timing skew. Note in trace C—the ground-pin-current—that no current ever flows directly through the source/sink pair.

Valve-control circuit maintains constant pH



turn-off speed more than sevenfold.

(Fig 9a) for a high-power 2N6308. Fig 10, trace A shows the transistor's base waveform; traces B and C display collector voltage and current, respectively. Because the base drive is unipolar, the collector turns off slowly: Voltage and current require about 1.5 μ sec to settle. What's more, the transistor dissipates considerable power during turnoff, increasing its vulnerability to secondary breakdown. Inductive loads (eg, flyback transformers) can exacerbate the situation.

The solution? Fig 9b's circuit uses an SG3635 to provide bipolar base drive, thereby shortening turn-off time. The 311 comparator shifts the TTL-command level to bias the driver's Enable input; shifting is necessary because the SG3635's ground pin is returned to -15V. The 25Ω resistor to ground limits the transistor's reverse bias. Traces D, E and F show the 2N6308's base voltage and collector voltage and current, respectively—you can see that collector turn-off time decreases to 200 nsec, greatly reducing the likelihood of secondary breakdown.

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SIMPLIFIED HIGH-EFFICIENCY MOTOR DRIVE SYSTEMS WITH NEW PWM INTEGRATED CIRCUITS

Stan Dendinger Manager, Applications Engineering SILICON GENERAL, INC. Garden Grove, California 92641

ABSTRACT

This paper describes a new pulse width modulator circuit designed specifically for DC motor control. It provides a bi-directional pulse train output in response to the magnitude and polarity of an analog error signal input. The device is useful as the control element in motor-driven servo systems for precision positioning and speed control, as well as in audio modulators and amplifiers using carrier frequencies to 350 kHz.

1. INTRODUCTION

Power management engineers have been aware for a number of years of the efficiency advantages of switching power supplies over linear designs. In response to growing production of switchers, the semiconductor industry has spawned a number of pulse width modulator (PWM) integrated circuits of varying degrees of complexity for the control of these power supplies.

Perceptive designers soon realized that the same efficiency advantages apply to motor control. Unfortunately, when they attempted to utilize existing PWM circuits, they found that the architecture was not optimized for motor control. So many auxiliary components had to be added to work around the restrictions of the PWM circuit that totally discrete designs were frequently found to be more economical.

The main difficulty has been that PWM controllers for switching power supplies were designed to be one quadrant power conditioners; i.e., the polarity of DC output voltage is fixed and proportional to a unipolar reference voltage. A second difficulty has been that power supply controllers attempt to produce an AC waveform of variable energy content, since power must be transferred through a high frequency transformer. This requires that PWM pulses alternate from side to side with a dual-driver architecture.

The requirements for PWM motor control are different: The integrated pulse train must have a DC component proportional to the magnitude of the applied reference voltage, and a polarity determined by the sign of the reference to accomplish bi-directional rotation. All of the necessary control elements for two quadrant operation are found in the PWM circuit to be described, which is designated the SG1731.

2. BLOCK DIAGRAM

The SG1731 contains a triangle waveform oscillator, a wideband operational amplifier for error voltage generation, a summing/scaling



network for level-shifting the oscillator waveform, externally-programmable PWM comparators, and dual ±100mA, ±32 volt totem pole drivers with commutation diodes for full bridge output drive. A TTL-compatible SHUTDOWN terminal forces the output drivers into a floating high-impedance state when driven LOW. Supply voltage to the circuit may be either from dual positive and negative supplies, or single-ended.

3. PULSE WIDTH MODULATION



FIGURE 2. DEADBAND OPERATION

Pulse width modulation occurs by adding an error voltage to the triangle waveform, attenuating the resulting signal by a factor of 2, and comparing it to threshold voltages +VT and -VT, which are applied to pins 1 and 8 respectively. Figure 2 illustrates the case for $V_{\Delta+} <+_{VT}$. When the error voltage is zero, no threshold crossings occur, and the output drivers remain in the LOW state. If the error voltage is sufficiently positive, the upper threshold will be periodically crossed by the shifted triangle waveform and output driver A will switch to the HIGH state. As the error voltage becomes larger, the duty cycle of driver A will linearly increase towards 100%. The same action occurs at output driver B for negative error voltages.

A motor connected across the full bridge formed by drivers A and B will receive a high frequency pulse train which, when integrated by the LR time constant of the armature, will result in a voltage drive proportional to the magnitude of the error signal. The polarity of the drive signal will be the same as the polarity of the error voltage.

With deadband operation, there is a small region around the null point of the servo loop where no power is applied to the motor. This conserves power, which may be desirable in some applications, but it also results in loss of both positioning accuracy and mechanical stiffness.



FIGURE 3. NON-DEADBAND OPERATION

The other possible mode of operation is shown in Figure 3, where $V_{\Delta+}$ -+ V_T . At the loop null point the motor still receives drive pulses, which provides resistance to armature movement by external forces. The integrated drive voltage is still zero when the error voltage is zero, since the drive pulses alternate in polarity with identical pulse widths at the null point.

This is the preferred mode of control in a missile fin actuator system where aerodynamic forces on the airfoil attempt to move the motor armature away from the null position. A second example where deadband operation is not desirable is a switching, or "Class D", audio amplifier. Crossover distortion would be unacceptable, and poor speaker damping would also result.

4. OSCILLATOR CIRCUIT



FIGURE 4. SG1731 OSCILLATOR SCHEMATIC

The triangle oscillator consists of two voltage comparators, a set/reset flip-flop, a bi-directional 500 μ A current source, and an external timing capacitor CT. A positive reference voltage applied to pin 2 (2V_A+) sets the peak value of the triangle, and a negative reference voltage at pin 7 (2V_A-) determines the valley of the triangle. Normally, the reference voltages are equal, so that a symmetrical waveform about ground results.

Circuit operation is as follows: Transistors Q6 and Q9 form the set/reset flip-flop. Assume that Q9 is conducting and Q6 is off. The collector voltage of Q9 will be low compared to that of Q6, resulting in Q7 conducting and Q8 being off. The current from the 500 μ A source will flow into CT and a positive voltage ramp will occur at pin 6. When the voltage exceeds $2V_{\Delta+}$, the comparator formed by Q1 through Q4 changes state, turning on Q5. This removes base drive from Q9 and the flip-flop will change state. The current-steering transistor pair Q7 and Q8 now switch the 1 mA discharge current source onto the CT bus. Since the 500 μ A charging source is still active, the net discharge current out of CT is the difference of the two sources, or 500 μ Å. Since monolithic construction allows close ratioing of current sources, the discharge rate will closely match the charge rate. When the voltage on C_T falls below $2V_{\Delta-}$, the comparator formed by Q11 through Q14 will reset the flip-flop and another charge cycle will begin. Since the values of the current sources are fixed at a nominal 500 μ A, the oscillator frequency may be calculated as follows:

For a given capacitance and current,

$$\frac{dV}{dt} = \frac{I}{C}$$
(1)

or

$$dt = \frac{C}{I} dV$$
 (2)

where

$$I = 500 \ \mu A = 5 \times 10^{-4} A$$

 $I = 500 \ \mu A = 5 \times 10^{-4} A$
 $I = \frac{1}{2} TOSC$ (assuming symmetry)
 $C = Variable$

Therefore

$$T_{OSC} = 2dt = \frac{2CdV}{5 \times 10^{-4}}$$
 (3)

The desired oscillator frequency can be obtained by first choosing a peak-to-peak voltage for the triangle waveform, and then selecting the proper value of C_T from Equation 3.



As a design aid, the solutions to Equation 3 over the recommended range of TOSC and VOSC are presented in graphical form in Figure 5. The lower limit on TOSC is 2.85 μ sec, corresponding to a maximum frequency of 350 kHz. The maximum value of VOSC, (2V Δ +)-(2V Δ -), is 10 volts peakto-peak for linear waveforms.

5. ERROR AMPLIFIER



The error amplifier is a high slew rate unit designed for low input offset voltage and bias current under equilibrium conditions. It consists of two gain sections, with frequency compensation for unity closed-loop gain stability in the second stage. The first stage is formed by transistors Q1 through Q12. When the differential input voltage is zero, the emitter voltages of Q2 and Q3 are equal, and the collector currents of Q5 and Q6 are equal to a small fraction of the collector current in Q4 and Q7. The value of current is set by current sources Q9 and Q10 and the two 5K emitter resistors. Transistors Q8, Q11 and Q12 form a compound current mirror which converts the full differential voltage gain of the input stage into a single-ended gain referred to -Vs. A Darlington gain stage formed by Q18 and Q20 provides the large voltage swing required for the amplifier output. When the differential input

voltage is not zero, that voltage appears across the 5K resistors of the input stage, increasing the operating current. Simultaneously this increased current is sensed by Q1, and current supply to the output stage is increased proportionally. Since more current is available to charge the 30 pF compensation capacitor, the amplifier output voltage slews at a much higher rate. When equilibrium is again reached, the bias currents return to their normal quiescent levels.



FIGURE 7. ERROR AMP POWER BANDWIDTH

As shown in Figure 7, the error amplifier is capable of excellent power bandwidth. Full output swing to 200 kHz is available, with slew rates exceeding 15 volts/microsecond. These dynamic characteristics allow application to audio modulation circuits with very low transient distortion.



The amplifier frequency-gain plot is a constant 6 dB/octave roll-off to unity gain, resulting both in unity gain stability and good transient response. Typical DC voltage gain is 110 dB into a 2K load, and unity gain crossover frequency is 1 megahertz.

6. OUTPUT DRIVERS



FIGURE 9. HALF-BRIDGE OUTPUT DRIVER SCHEMATIC

The output stage is a non-saturating quasicomplementary high current switch for efficient high frequency operation. Transistors Q3, Q4, Q5 and Q6 form a high voltage Schmitt trigger input stage. The positive feedback produces fast switching times and jitter-free pulse width modulation. Q7 and Q9 provide output current sourcing, and Q8, Q10 and Q11 provide current sinking. Commutation diodes D1 and D2 clamp inductive loads to the supply rails. Their current capability is the same as the output transistors: 200 mA peak.

7. TYPICAL APPLICATIONS 7.1 SIMPLE POSITION SERVO



FIGURE 10. A SIMPLE BATTERY-POWERED POSITION SERVO

A simple, low-voltage, battery-powered position servo is illustrated in Figure 10. A resistive divider network sets up the reference voltages for triangle waveform amplitude and PWM thresholds. Since the circuit is powered by battery, $V_{\Delta+}$ is designed to be less than $+V_T$ (deadband) to conserve power. The 9 volt DC motor is driven directly from the output drivers, and it in turn drives a position feedback potentiometer through a geartrain. The position feedback voltage is subtracted from the external position command voltage in the on-chip error amplifier. The difference between commanded position and actual position generates an error voltage which in turn generates a series of PWM pulses to the motor to correct the difference. Once null has been reached, no further power is applied to the motor until a new position command voltage is received, or the wiper is moved out of position by external forces.

7.2 HIGH TORQUE POSITION SERVO



FIGURE 11. HIGH TORQUE POSITION SERVO

Figure 11 illustrates a high power version of the previous position servo loop. The control circuit is powered from balanced positive and negative supply voltages, and the output drivers switch the load between ± 32 volt supply rails for maximum output power. Complementary emitter follower buffers on each output provide increased current gain and power handling capability.

7.3 MOTOR SPEED CONTROL



In Figure 12, a bi-directional motor speed control circuit is derived from the previous circuit by substituting a tachometer for the position pot in the motor feedback circuit. The external command voltage now represents a speed rather than a position, with direction of motor rotation a function of command voltage polarity. Magnetic tape drives are an example of this configuration, with the velocity feedback voltage frequently derived from an encoded bit pattern on the tape.

7.4 PWM AUDIO POWER AMPLIFIER



FIGURE 13. P.W.M. AUDIO POWER AMPLIFIER

A complete PWM power audio amplifier is illustrated in this last application. The circuit reconstructs an amplified version of the audio input voltage by deriving the feedback signal from the speaker voice coil. An oscillator frequency of 300 kHz was chosen to maintain a ratio of at least 15 to 1 between the carrier frequency and the highest modulation frequency (20 kHz).

Ratios of at least 10 to 1 are necessary for acceptable linearity, low distortion and good transient response. An LC output filter smoothes the pulse width modulated output to the speaker; its design is critical for low distortion. This circuit, consisting of one integrated circuit and four power transistors, can deliver 150 watts RMS of power into a 4 ohm load.

8. CONCLUSION

A new pulse width modulator integrated circuit designed for motor control has been described which includes all the circuitry necessary for implementing high efficiency bi-directional controllers. Inputs and outputs have been designed for maximum flexibility, allowing the device to be useful in a wide range of position and speed servo systems.

Application Notes—SG1731

Simplify feedback controllers with a 2-quadrant PWM IC

A 2-quadrant pulse-width-modulator IC eliminates many of the problems arising with unipolar devices in feedback-control applications.

Jim Williams, Consultant, and Stan Dendinger, Silicon General Corp

The SG1731 pulse-width-modulator (PWM) IC brings to motor controllers and similar applications the efficiency previously limited to switching-power-supply circuitry. As a result, you can use it to design motor-controller circuits having parts counts smaller than previously achievable.

Switching-power-supply PWM controllers are designed to be 1-quadrant power conditioners, furnishing a dc output voltage with fixed polarity and amplitude proportional to a unipolar reference voltage. Motor controllers, on the other hand, require an integrated pulse train with a dc component proportional to the magnitude of an applied reference voltage and polarity determined by the reference's sign. Otherwise, they can't produce bidirectional rotation.

In addition, the architecture of power-supply PWM ICs often proves inappropriate for motor-control tasks, requiring so many auxiliary circuits that totally discrete designs often prove more economical. PWM





Error voltage controls pulse-width modulation

power-supply controllers attempt to produce a variable-energy-content ac waveform, because power must be transferred via a high-frequency transformer. Unlike those from a PWM motor-control IC, the PWM pulses produced by these devices must alternate and are therefore produced by a dual-driver architecture.

Fig 1 shows the SG1731's structure. The device contains a triangle-waveform oscillator whose frequency is determined by an external capacitance at pin 6 and whose amplitude can be set through resistor or voltage programming at pins 2 and 7. The IC also contains a wide-band op amp for error-voltage generation, a summing/scaling network for level-shifting the oscillator waveform, externally programmable PWM comparators and dual ± 100 -mA continuous (± 200 -mA pk), $\pm 32V$ totem-pole drivers with commutation diodes for full-bridge output drive. Typical supply voltages are ± 15 V, although the device can function at values as low as ± 3.5 V. You can use dual- or single-polarity supply voltages. Pin 15, the Shutdown terminal, forces the output drivers into high-impedance states when LOW.

Pulse-width modulation occurs when an error voltage gets added to the triangle waveform, attenuating the resulting signal by a factor of two and comparing it with threshold voltages $+V_T$ and $-V_T$ (pins 1 and 8). Fig 2 illustrates the case for $V_{\Delta} < V_T$. When the error is 0V, no threshold crossings occur, and the output drivers remain at $-V_0$ (Fig 2a). As the error voltage goes positive, the upper threshold gets periodically crossed by the shifted waveform, and output driver A switches to $+V_0$ (Fig 2b). As the error voltage becomes larger, the duty cycle of driver A increases linearly toward 100%. The same action occurs at output B (Fig 2c) for negative error voltages.



Class D amplifiers for audio applications

Almost all amplifiers use some form of output pass element to deliver power to a load. Because the amplifier controls this pass element, and because the amount of power delivered to the load varies, dissipation is inevitable. And at high power, substantial dissipation losses place limits on packaging, power consumption and efficiency.

One form of amplifier, the Class D stage, largely circumvents these problems by using a switched-mode output stage to deliver power to the load. Because the amplifier's output is either ON or OFF, efficiency is higher than that of a linear stage, and heat dissipation is low. In **Fig A**, the output of such a stage is represented by a series of widthmodulated pulses whose powertime spectrum is related to the input signal.

In theory, this type of stage can serve in an efficient audio amplifier. And recently, designers have expressed a great deal of interest in developing such an amplifier. However, practical problems have made a workable switching design for audio difficult to achieve.

Historically, switched-modeamplifier designs called for complex circuitry and expensive output devices. Producing a pulse-width modulator that provides 2-quadrant response with high linearity and wide bandwidth was difficult. In addition, even if available, low-loss output switches that operated at high carrier frequencies were expensive, and the drive circuitry quite complex.

The introduction of power-FET devices has reduced design-cost and complexity problems in the output stage. But although such components make the job easier, designers still must deal with several issues to achieve optimum performance.

One unpleasant surprise is the combination of the high-frequency



Fig A—A switched-mode PWM Class D amplifier coupled to an FET output stage provides efficient operation.

carrier and the FETs' input capacitance. The FET gate drive (**Fig B**, trace A) causes the current drawn through the input capacitances (trace B) to peak at 400 mA on both edges as the FETs switch. Although the FETs have a high impedance at dc, the high carrier frequency required for audio calls for substantial average gate current. This requirement in turn calls for some form of preceding driver.

A more serious problem centers on filtering the carrier at the load (a speaker in audio applications). Filter design is complicated by the uncertain characteristics of the lead wire and speaker that connect to the amplifier. Even if these parameters are fixed by specification, the speaker's reactive nature complicates the design.

Even assuming the filter can be built, the waveform across the speaker is well out of the phase with the input because of carrierinduced phase shift as well as filter phase shift. As a result, closing a feedback loop from the load proves difficult. It might be possible to use a complementary phase-shift network to correct for this shortcoming, but the design of this type of an audio-grade compensation scheme is difficult. Without feedback, the problem goes away, but nonlinearities in



400-mA pk gate current when the FETs switch (trace B). Trace A is the gate drive signal; trace C, the FETs' source lines.

the pulse-width modulator then contribute to output distortion.

Finally, the high-frequency harmonics in the switching stage pose a difficult RFI-suppression problem. The same fast switching that yields efficiency and widerange audio bandwidth also qualifies as a potential broadband radio transmitter and must be suppressed. This need mandates careful layout, expensive and complex packaging and RFI suppression on both power and speaker connections.
No motor power required with deadband operation

A motor connected across the full bridge formed by drivers A and B receives a high-frequency pulse train. When integrated by the armature's L/R time constant, this pulse train results in a voltage drive proportional to the error signal's magnitude. Drive-signal and errorvoltage polarities are identical.

With this deadband operation, no motor power gets applied in a small region around the servo loop's null point. Although this action conserves power (desirable in some applications), it results in a loss of both positioning accuracy and mechanical stiffness. Deadband operation is also not desirable in switching (Class D) audio amplifiers. There, crossover distortion is unacceptable, and poor speaker damping results (see **box**, "Class D amplifiers for audio applications").

The other SG1731 mode of operation is shown in Fig 3, where $V_{\Delta} > V_{T}$. At the loop null point, the motor receives drive pulses that resist externally produced armature movement. The integrated drive voltage is 0V with no error voltage (Fig 3a) because the drive pulses alternate in polarity and have identical widths at the null point. Figs 3b and 3c show the effects of error voltages on the oscillator signal. This is the preferred control mode in a missile-finactuator system, for example, where aerodynamic forces on the airfoil attempt to move the motor armature away from the null position.

You can configure the SG1731 as a bidirectional motor-speed controller as shown in **Fig 4**. The motor specified runs directly from the device's outputs, and the tachometer produces an output directly proportional to the motor's speed and direction. This high-level signal gets divided down and filtered by the discrete components associated with the tachometer, then applied to the 1731's error-amplifier input. The 1731 internally compares this signal with the speed-control input's value and provides output drive of the appropriate phase and magnitude, completing a speed-control loop. Set the comparator voltages for nondeadband operation. The lowest rotation speed depends on the motor's friction characteristics.

Instantaneous-direction-reversing applications might require an optional current-limiting circuit rather than $\pm 15V$ applied directly to pins 11 and 14. At the time of direction reversing, the motor draws peak currents that could damage the 1731's output drivers. Q_i's ability



Fig 4—In this bidirectional motor-speed controller, the tachometer provides feedback while the current-limiting circuit protects the outputs from surge currents.

Extend control capability with high-current drivers

to supply current is controlled by Q_2 's state, which in turn depends on the voltage across the 4Ω currentsensing resistor. If the motor current exceeds 200 to 250 mA, Q_2 turns on and Q_1 shuts off.

Another bidirectional speed-control loop appears in **Fig 5.** Here, SG1635 drivers control higher motor power and eliminate the need for a speed-monitoring tachometer; instead, back EMF produced by the motor serves as a feedback signal. This arrangement entails some increase in circuit complexity but eliminates the tachometer's cost.

The circuit's basic servo mode is similar to that of Fig 4. The 311 comparator (IC₁) senses the polarity of the input command signal. Its output goes to the 1635s via a diode and inverter, allowing both 1635s to be OFF, neither sinking nor sourcing current, when the 1731 is not producing output pulses. Fig 6 shows the circuit waveforms. When either 1731 output is HIGH, the other output is LOW, and the motor is driven. When both outputs are LOW, the 1635s are OFF and the motor is electrically floating.

The motor's inductive turn-off spike gets damped by the 1635s' internal diodes. After turn-off, the waveform







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Eliminate servo hunting with long time constants

returns to a dc level determined by the back EMF of the undriven motor, now functioning as a tachometer. This level gets differentially picked off by the 301A op amp (IC₃), whose output feeds a switched synchronous filter. This filter, composed of the FET and the 100-k $\Omega/0.01$ -µF combination, samples the back-EMF value during the motor's powered interval.

A 311 (IC₂) gates the FET switch synchronously with the 1731's output. The diode-RC network feeding IC₂ allows either output to actuate the filter. The 10-k Ω / 0.02- μ F network's decay time length (Fig 6, trace D) ensures that the FET drive (trace E) remains OFF until well after the inductive spike has settled out.

The pure dc filter output feeds back to the 1731's error amplifier to complete the speed-control loop. The zener-diode bridge clamps all inputs above approximately $\pm 10V$; otherwise the 1731's outputs would saturate at dc and the switched feedback loop would never operate.

Another SG1731 application appears in Fig 7. Here, two 1731s bidirectionally control the speed and shaft position of a printed-circuit-type motor. The shaft position gets sensed at the output of a geardown transmission. Slave the 1731s together to avoid producing frequency beating from separate oscillators; take the triangle waveform of SG1731_A through a 301A follower and use the output to drive the capacitor pin of SG1731_B. This is an effective way to slave 1731s together because the follower's low-impedance output overrides whatever state the unbiased internal oscillator of SG1731_B might take. Control the shaft position by sensing it with a potentiometer that feeds a signal back to SG1731_A. This signal then gets compared with the Position input, and the outputs of SG1731_A drive the shaft to the position required to balance the error amplifier's inputs.

 $SG1731_B$ functions in a speed-control loop similar to that described in **Fig 4**. It controls speed by using its output pins, via a diode OR gate, to pulse-widthmodulate $SG1731_A$'s Shutdown pin. The 311 comparator prevents either $SG1731_B$ output from going LOW on a dc basis by synchronously gating signals into the device's output comparators, forcing the appropriate output HIGH.



Fig 7—In this bidirectional motor-speed-controller/positioner application, SG1731_A acts as a position servo, while SG1731_B controls speed.



Motors adapt easily to Class D operation, speakers don't

Consider SG1731_A to be a position servo; $SG1731_B$ controls how quickly the position is acquired. Deadzone control results from voltage-modulating SG1731_B's comparator thresholds.

Fan-temperature control safeguards instruments

You can also use a 1731 to control a fan motor's speed, regulating instrument temperature and extending fan life (Fig 8). At least one oscilloscope manufacturer uses this approach, and it has also found use in several military applications.

When power is applied, the thermistor, located near the fan, has a high resistive value. This condition unbalances the amplifier-driven bridge, sending pin 12 LOW. Q_1 and the fan motor are off. But as the instrument warms, thermistor resistance decreases, producing PWM signals at pin 12 and turning Q_1 and the fan motor on.

The $100-\mu$ F capacitor determines the time constant across the error amplifier; a short time constant produces audibly annoying hunting in the servo. The 50Ω resistor limits motor current, and the 1N4002 diode dampens motor spikes. The SG1731 can function in nonmotor applications, too. The freezing point of water serves as a reference point for the calibration of various types of temperature sensors, such as platinum RTDs and thermocouples. In such applications, an ice slurry in a Styrofoam container or a Dewar bottle is usually used to achieve the 0°C condition. Although inexpensive, this approach requires constant ice replenishment and water removal and tends to be messy. As an alternative, you can use the SG1731 to provide 2-quadrant control for a Peltier-junction-type thermoelectric cooler.

Current flow in a Peltier device cools one side of the junction and heats the other; reversing the applied current causes the cold side of the junction to heat and the hot side to cool. Commercial devices use a large number of junctions to achieve high thermal capacity and are about the size of a postage stamp. They are optimized for one direction of current flow but can work both ways.

Fig 9's circuit capitalizes on this characteristic to achieve a very precise temperature reference that cools to 0° C and then settles out very quickly. Most thermal control loops settle slowly because energy can only be



Temperature reference is bidirectional



removed (as in a refrigerator) or added (as in a crystal oven). But because the Peltier device is thermodynamically bidirectional, it's an ideal choice for use in a low-temperature servo.

When power is applied, the platinum sensor (at a high resistive value) unbalances the bridge and causes the AD524 instrumentation amplifier to saturate negatively. This action turns the 1731 and its 1635 drivers on, resulting in current flow through the Peltier device in the cooling direction. When the temperature reaches 0° C, the 1731 tends to cut off, causing loop overshoot. However, the heat-pump reversal in the Peltier device forces short thermal settling times.

The 100-k Ω potentiometer adjusts loop gain; the 1- μ F capacitor sets bandwidth. The 100-k Ω resistors and the 0.01- μ F capacitor across the instrumentation amplifier filter out the fast chopping noise the platinum sensor, a wirewound device, picks up.

If you use the resistance decade shown, you can control the junction at any desired temperature around 0° C. For an ideal 1000 Ω sensor at 0° C, the **table** values shown in **Fig 9** apply. You can substitute the actual 0° C value for the platinum sensor used, biasing all values by the difference between the sensor resistance at 0° C and 1000 Ω . The bidirectional thermal control and high loop gain produce very rapid response to any shift in temperature setpoint, plus high stability.

Finally, the SG1731's 2-quadrant capability allows its use as a switched-mode (Class D) power amplifier. Motors and other devices that can integrate the time-power spectrum of a Class D amplifier output are obvious loads. The design can also serve audio applications but requires careful attention to output filtering to achieve acceptable distortion levels.

Fig 10 shows the 1731 set up to deliver high power to a 10Ω load via complementary power FETs. The device's output stage swings $\pm 25V$, providing a 10V enhancement for turning on the FETs. The active 1731 outputs are ideal for driving power FETs because they can both source and sink the relatively high gate currents caused by the FETs' input capacitances. Fig 11 shows the waveforms associated with this circuit.

Package Outlines



Package Outlines



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		Silicon General	NSC	Signetics	Fairchild	Motorola	ті	RCA	AMD	Raytheon	Sprague
	Plastic DIP 8-Lead 14,16 and 18 Lead	M	N	V A B	T P	P	P N	E	PC PC	N DN DP MP	M
	TO-220	Р	т	U	U	Т	кс				т
	Low Temperature Glass Hermetic Flat-Pack	F	w		F	F	w		FM		J
ф.	TO-66 3 Lead 5 Lead 9 Lead	R			Р	R				R TK	
ţ 🗖	Glass/Metal Flat-Pack	F	F	Q	F	F	F S	к	F	J F Q	
TT ©	TO-5, TO-39, TO-96, TO-99, TO-100 and TO-101	т	н	T K L DB	н	G	L	S* V1**	н	т	D K
	Ceramic DIP 8-Lead Ceramic DIP 14,16 and 18 Lead	J	J	F	D	U	J			DC DD	R
	TO-3 (Steel)	к	к			<u> </u>		к		к	
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140 McCormick Ave. Costa Mesa, CA 92626 (714) 549-8401 Diplomat/Westates Elec.

9787 Aero Dr. San Diego, CA 92123 (619) 292-5693

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Jaco Electronics 145 Oser Ave. Hauppauge, L.I., NY 11787 (516) 273-5500 TWX: 510-227-6232

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Milgray 57 Monroe Ave. Pittsford, NY 14534 (716) 385-9330

OHIO Milgray Electronics, Inc. 6155 Rockside Road Cleveland, OH 44131 (216) 447-1520

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PENNSYLVANIA (Contact Factory)

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 Quality Components

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 Austin, TX 78758

 (512) 835-0220

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 4257 Kellway Cir.

 Addison, TX 75001

 (214) 387-4949

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NORWAY Henaco

Trondheimsveien 436 Ammerud Oslo, Norway Tel: 02-645040 Telex: 16716 HENACN

PUERTO RICO

M. Anderson Co., Inc. Suite 18 3rd Floor Edifisio El Monte Hall Hato Ray, P.R. 00918 Tel: (809) 751-2026 Telex: 345 0531

REPUBLIC OF CHINA Heim Engineering & Trading 9FL, 143, HSIN YI RD, SEC 4 Taipei, Taiwan, R.O.C. Tel: (02) 781-0003 Telex: 28204

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SPAIN Amitron S.A. Loecheo LE 6 Madrid 8, Spain Tel: 2485863 Telex: 45550

SWEDEN Svensk Teleindustri AB

Box 502 S-16205 Vallingby 5 Sweden Tel: 08-380320 Telex: 13033

SWITZERLAND Kontron Electronics Bernerstr Sud 169 8048 Zurich Switzerland Tel: 01 4354111

UNITED KINGDOM

Telex: 58836

Power Technology Ltd. Bulton Rd. Buiton Rd. Reading, Berkshire, RG20LT England Tel: (734) 866 766 Telex: 847203

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3630 Enterprize St. San Diego, CA 92138 Tel: (619) 224-3291 Telex: 69-7966

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SILICON GENEPAL

CUSTOM CIRCUITS CAPABILITY

Silicon General designs and produces standard and custom integrated circuits in high volume. The full complement of logic elements can be integrated with operational amplifiers, comparators and power drivers to produce low cost, high performance system design. Over 500 logic gates may be integrated with power drivers and linear circuits.

Short Design Cycles are possible. Silicon General has the basic building block devices and logic elements in its CAD data base. Often prototypes, based on metal mask changes to existing standard products, can be delivered within twelve weeks. Other designs may require 20 to 40 weeks.

Unit Cost is directly related to chip size, package and volume. A minimum volume order is required. Silicon General's engineering staff will work with the customer's engineers to develop the most cost effective design for the total system.

The Specification for a custom device should be well defined. Silicon General's engineers will work with the customer to develop a solid specification.

PACKAGING

DIP to 40 pins (ceramic or plastic) Power SIP (12 and 15 pins) TO-3 TO-39 TO-66 TO-96 TO-99 TO-100 TO-101 TO-220 Flatpack Leadless chip carrier Custom Silicon General sells dice.

TYPICAL CUSTOM DESIGN SCHEDULE

Task	Time in Weeks	Responsibility		
Define Specification		Shared		
Circuit Design	2 to 10	Silicon General		
Breadboard Construction	2 to 8	Silicon General		
Breadboard Approval	2 to 4	Customer		
Circuit Layout	2 to 8	Silicon General		
Prototype Build	3 to 8	Silicon General		
Prototype Approval	3 to 4	Customer		
Production Volume	12 to 16	Silicon General		

Integrated Component Capability

Power Transistors	Sourcing — to 4A at 60V				
	Sinking — to 4A at 60V				
······································	(Several Power Transistors may be combined on a single chip).				
Transistors	NPN — Beta to 300				
	BV _{CES} to 120V				
	ft to 500 MHz				
	PNP — Beta to 40				
	BVCES to 100V				
	ft to 4 mHz				
Diodes	Small Signal — BV = 7.0V				
	Zener 5.7 to 7.0 ±0.3V				
·····	Large Signal — BV = 100V at 4A				
Resistors	0.1 to 2M Ohms (±20%)				
	(Ratios within less than 1% are possible)				
Capacitors	0.05 pF to 300 pF				
inear Circuit Elements	Operational Amplifiers				
	Regulators				
	Comparators				
	Oscillators				
	Power Amplifiers				
	Custom				
ogic Circuit Elements	Standard Gates: AND, NAND, OR, NOR, XOR, etc				
	Flip/flops and Latches				
	One Shots				
	Shift Registers				
	Custom				
	(Standard bipolar gates with propagation delays of 10 nS per gate and I2L gates of 100 nS per gate)				





IC Solutions for Power Management

11651 Monarch Street Garden Grove, California 92641 Telephone: (714) 892-5531 TWX: 910-598-1804 TELEX: 69-2411